



1Gb DDR3L SDRAM

Revision 0.1

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Contents

DDR3L Sync DRAM Features	12
Functional Block Diagrams	13
Ball Assignments and Descriptions	15
Package Dimensions	17
State Diagram	19
Ball Descriptions	20
Functional Description	24
Industrial Temperatures	24
General Notes	24
Electrical Specifications	25
Absolute Ratings	25
Input / Output Capacitance	26
Thermal Characteristics	27
Electrical Specifications – I DD Specifications and Conditions	29
Electrical Characteristics – IDD Specifications	39
Electrical Specifications – DC and AC	40
DC Operating Conditions	40
Input Operating Conditions	40
AC Overshoot/Undershoot Specification	44
Slew Rate Definitions for Single-Ended Input Signals	47
Slew Rate Definitions for Differential Input Signals	49
ODT Characteristics	50
ODT Resistors	51
ODT Sensitivity	52
ODT Timing Definitions	52
Output Driver Impedance	56
34 Ohm Output Driver Impedance	56
34 Ohm Driver	57
34 Ohm Output Driver Sensitivity	58
Alternative 40 Ohm Driver	58
40 Ohm Output Driver Sensitivity	59
Output Characteristics and Operating Conditions	60
Reference Output Load	63
Slew Rate Definitions for Single-Ended Output Signals	64
Slew Rate Definitions for Differential Output Signals	65
Speed Bin Tables	66
Electrical Characteristics and AC Operating Conditions	70
Command and Address Setup, Hold, and Derating	88
Data Setup, Hold, and Derating	95
Commands – Truth Tables	103

Contents

Commands -----	106
DESELECT -----	106
NO OPERATION -----	106
ZQ CALIBRATION LONG -----	106
ZQ CALIBRATION SHORT -----	106
ACTIVATE -----	106
READ -----	106
WRITE -----	107
PRECHARGE -----	108
REFRESH -----	108
SELF REFRESH -----	109
DLL Disable Mode -----	110
Input Clock Frequency Change -----	114
Write Leveling -----	116
Write Leveling Procedure -----	118
Write Leveling Mode Exit Procedure -----	120
Initialization -----	121
Voltage Initialization / Change -----	123
VDD Voltage Switching -----	124
Mode Registers -----	125
Mode Register 0 (MR0) -----	125
Burst Length -----	126
Burst Type -----	127
DLL RESET -----	127
Write Recovery -----	128
Precharge Power-Down (Precharge PD) -----	128
CAS Latency (CL) -----	129
Mode Register 1 (MR1) -----	130
DLL Enable/DLL Disable -----	130
Output Drive Strength -----	131
OUTPUT ENABLE/DISABLE -----	131
TDQS Enable -----	131
On-Die Termination -----	131
WRITE LEVELING -----	132
POSTED CAS ADDITIVE Latency -----	132
Mode Register 2 (MR2) -----	133
CAS Write Latency (CWL) -----	133
AUTO SELF REFRESH (ASR) -----	134
SELF REFRESH TEMPERATURE (SRT) -----	134
SRT vs. ASR -----	134
DYNAMIC ODT -----	134

Contents

Mode Register 3 (MR3)	135
MULTIPURPOSE REGISTER (MPR)	135
MPR Functional Description	136
MPR Register Address Definitions and Bursting Order	137
MPR Read Predefined Pattern	142
MODE REGISTER SET (MRS) Command	142
ZQ CALIBRATION Operation	143
ACTIVATE Operation	144
READ Operation	145
WRITE Operation	156
DQ Input Timing	164
PRECHARGE Operation	165
SELF REFRESH Operation	165
Extended Temperature Usage	167
Power-Down Mode	168
RESET Operation	176
On-Die Termination (ODT)	177
Functional Representation of ODT	177
Nominal ODT	177
Dynamic ODT	179
Dynamic ODT Special Use Case	179
Functional Description	179
Synchronous ODT Mode	185
ODT Latency and Posted ODT	185
Timing Parameters	185
ODT Off During READs	188
Asynchronous ODT Mode	190
Synchronous to Asynchronous ODT Mode Transition (Power-Down Entry)	192
Asynchronous to Synchronous ODT Mode Transition (Power-Down Exit)	194
Asynchronous to Synchronous ODT Mode Transition (Short CKE Pulse)	196
Selection Guide	198
Part Numbering System	199

List of Table

Table 1: Absolute Maximum Ratings	25
Table 2: DDR3L Input/Output Capacitance	26
Table 3: Thermal Characteristics	27
Table 4: DDR3L Timing Parameters Used for IDD Measurements – Clock Units	29
Table 5: DDR3L IDD0 Measurement Loop	30
Table 6: DDR3L IDD1 Measurement Loop	31
Table 7: DDR3L IDD Measurement Conditions for Power-Down Currents	32
Table 8: DDR3L IDD2N and IDD3N Measurement Loop	33
Table 9: DDR3L IDD2NT Measurement Loop	33
Table 10: DDR3L IDD4R Measurement Loop	34
Table 11: DDR3L IDD4W Measurement Loop	35
Table 12: DDR3L IDD5B Measurement Loop	36
Table 13: DDR3L IDD Measurement Conditions for IDD6, IDD6ET, and IDD8	37
Table 14: DDR3L IDD7 Measurement Loop	38
Table 15: IDD Maximum Limits	39
Table 16: DDR3L 1.35V DC Electrical Characteristics and Operating Conditions	40
Table 17: DDR3L 1.35V DC Electrical Characteristics and Input Conditions	40
Table 18: DDR3L 1.35V Input Switching Conditions	40
Table 19: DDR3L 1.35V Differential Input Operating Conditions (CK, CK# and DQS, DQS#)	42
Table 20: DDR3L 1.35V Control and Address Pins	44
Table 21: DDR3L 1.35V Clock, Data, Strobe, and Mask Pins	44
Table 22: DDR3L 1.35V Allowed Time Before Ringback (tDVAC) for CK - CK# and DQS - DQS#	46
Table 23: Single-Ended Input Slew Rate Definition	47
Table 24: DDR3L 1.35V Differential Input Slew Rate Definition	49
Table 25: On-Die Termination DC Electrical Characteristics	50
Table 26: 1.35V RTT Effective Impedances	51
Table 27: ODT Sensitivity Definition	52
Table 28: ODT Temperature and Voltage Sensitivity	52
Table 29: ODT Timing Definitions	53
Table 30: DDR3L 1.35V Reference Settings for ODT Timing Measurements	56
Table 31: DDR3L 34 Ohm Driver Impedance Characteristics	56
Table 32: DDR3L 34 Ohm Driver Pull-Up and Pull-Down Impedance Calculations	57
Table 33: DDR3L 34 Ohm Driver IOH/IOL Characteristics: VDD = VDDQ = 1.35V	57
Table 34: DDR3L 34 Ohm Driver IOH/IOL Characteristics: VDD = VDDQ = 1.45V	57
Table 35: DDR3L 34 Ohm Driver IOH/IOL Characteristics: VDD = VDDQ = 1.283V	57
Table 36: DDR3L 34 Ohm Output Driver Sensitivity Definition	58
Table 37: DDR3L 34 Ohm Output Driver Voltage and Temperature Sensitivity	58
Table 38: DDR3L 40 Ohm Driver Impedance Characteristics	58
Table 39: DDR3L 40 Ohm Output Driver Sensitivity Definition	59
Table 40: 40 Ohm Output Driver Voltage and Temperature Sensitivity	59
Table 41: DDR3L Single-Ended Output Driver Characteristics	61

List of Table

Table 42: DDR3L Differential Output Driver Characteristics -----	61
Table 43: DDR3L Differential Output Driver Characteristics VOX(AC) -----	61
Table 44: Single-Ended Output Slew Rate Definition -----	64
Table 45: Differential Output Slew Rate Definition -----	65
Table 46: DDR3L-1066 Speed Bins -----	66
Table 47: DDR3L-1333 Speed Bins -----	67
Table 48: DDR3L-1600 Speed Bins -----	68
Table 49: DDR3L-1866 Speed Bins -----	69
Table 50: Electrical Characteristics and AC Operating Conditions -----	70
Table 51: Electrical Characteristics and AC Operating Conditions for Speed Extensions -----	79
Table 52: DDR3L Command and Address Setup and Hold Values Referenced – AC/DC-Based -----	88
Table 53: DDR3L 800 / 1066 / 1333 / 1600 Derating Values for tIS/tIH – AC160/DC90-Based -----	89
Table 54: DDR3L 800 / 1066 / 1333 / 1600 Derating Values for tIS/tIH – AC135/DC90-Based -----	89
Table 55: DDR3L 1866 Derating Values for tIS/tIH – AC125/DC90-Based -----	90
Table 56: DDR3L Minimum Required Time tVAC Above VIH(AC) or Below VIL(AC) for Valid Transition -----	90
Table 57: DDR3L Data Setup and Hold Values at 1 V/ns (DQS, DQS# at 2 V/ns) – AC/DC-Based -----	95
Table 58: DDR3L Derating Values for tDS/tDH – AC160/DC90-Based -----	95
Table 59: DDR3L Derating Values for tDS/tDH – AC135/DC100-Based -----	96
Table 60: DDR3L Derating Values for tDS/tDH – AC130/DC100-Based at 2V/ns -----	97
Table 61: DDR3L Minimum Required Time tVAC Above VIH(AC) (Below VIL(AC)) for Valid DQ Transition -----	98
Table 62: Truth Table – Command -----	103
Table 63: Truth Table – CKE -----	105
Table 64: READ Command Summary -----	107
Table 65: WRITE Command Summary -----	107
Table 66: READ Electrical Characteristics, DLL Disable Mode -----	113
Table 67: Write Leveling Matrix -----	117
Table 68: Burst Order -----	128
Table 69: MPR Functional Description of MR3 Bits -----	136
Table 70: MPR Readouts and Burst Order Bit Mapping -----	137
Table 71: Self Refresh Temperature and Auto Self Refresh Description -----	167
Table 72: Self Refresh Mode Summary -----	167
Table 73: Command to Power-Down Entry Parameters -----	168
Table 74: Power-Down Modes -----	169
Table 75: Truth Table – ODT (Nominal) -----	178
Table 76: ODT Parameters -----	178
Table 77: Write Leveling with Dynamic ODT Special Case -----	179
Table 78: Dynamic ODT Specific Parameters -----	180
Table 79: Mode Registers for RTT,nom -----	180
Table 80: Mode Registers for RTT(WR) -----	181
Table 81: Timing Diagrams for Dynamic ODT -----	181

List of Table

Table 82: Synchronous ODT Parameters	186
Table 83: Asynchronous ODT Timing Parameters for All Speed Bins	191
Table 84: ODT Parameters for Power-Down (DLL Off) Entry and Exit Transition Period	193

List of Figure

Figure 1: Thermal Measurement Point	28
Figure 2: DDR3L 1.35V Input Signal	43
Figure 3: Overshoot	44
Figure 4: Undershoot	44
Figure 5: VIX for Differential Signals	45
Figure 6: Single-Ended Requirements for Differential Signals	45
Figure 7: Definition of Differential AC-Swing and tDVAC	46
Figure 8: Nominal Slew Rate Definition for Single-Ended Input Signals	48
Figure 9: DDR3L 1.35V Nominal Differential Input Slew Rate Definition for DQS, DQS# and CK, CK#	49
Figure 10: ODT Levels and I-V Characteristics	50
Figure 11: ODT Timing Reference Load	52
Figure 12: tAON and tAOF Definitions	54
Figure 13: tAONPD and tAOFPD Definitions	54
Figure 14: tADC Definition	55
Figure 15: Output Driver	56
Figure 16: DQ Output Signal	62
Figure 17: Differential Output Signal	63
Figure 18: Reference Output Load for AC Timing and Output Slew Rate	63
Figure 19: Nominal Slew Rate Definition for Single-Ended Output Signals	64
Figure 20: Nominal Differential Output Slew Rate Definition for DQS, DQS#	65
Figure 21: Nominal Slew Rate and tVAC for tIS (Command and Address – Clock)	91
Figure 22: Nominal Slew Rate for tIH (Command and Address – Clock)	92
Figure 23: Tangent Line for tIS (Command and Address – Clock)	93
Figure 24: Tangent Line for tIH (Command and Address – Clock)	94
Figure 25: Nominal Slew Rate and tVAC for tDS (DQ – Strobe)	99
Figure 26: Nominal Slew Rate for tDH (DQ – Strobe)	100
Figure 27: Tangent Line for tDS (DQ – Strobe)	101
Figure 28: Tangent Line for tDH (DQ – Strobe)	102
Figure 29: Refresh Mode	109
Figure 30: DLL Enable Mode to DLL Disable Mode	111
Figure 31: DLL Disable Mode to DLL Enable Mode	112
Figure 32: DLL Disable tDQCK	113
Figure 33: Change Frequency During Precharge Power-Down	115
Figure 34: Write Leveling Concept	116
Figure 35: Write Leveling Sequence	119
Figure 36: Write Leveling Exit Procedure	120
Figure 37: Initialization Sequence	122
Figure 38: VDD Voltage Switching	124
Figure 39: MRS to MRS Command Timing (tMRD)	125
Figure 40: MRS to nonMRS Command Timing (tMOD)	126
Figure 41: Mode Register 0 (MR0) Definitions	127

List of Figure

Figure 42: READ Latency	129
Figure 43: Mode Register 1 (MR1) Definition	130
Figure 44: READ Latency (AL = 5, CL = 6)	132
Figure 45: Mode Register 2 (MR2) Definition	133
Figure 46: CAS Write Latency	133
Figure 47: Mode Register 3 (MR3) Definition	135
Figure 48: Multipurpose Register (MPR) Block Diagram	136
Figure 49: MPR System Read Calibration with BL8: Fixed Burst Order Single Readout	138
Figure 50: MPR System Read Calibration with BL8: Fixed Burst Order, Back-to-Back Readout	139
Figure 51: MPR System Read Calibration with BC4: Lower Nibble, Then Upper Nibble	140
Figure 52: MPR System Read Calibration with BC4: Upper Nibble, Then Lower Nibble	141
Figure 53: ZQ CALIBRATION Timing (ZQCL and ZQCS)	143
Figure 54: Example: Meeting tRRD (MIN) and tRCD (MIN)	144
Figure 55: Example: tFAW	144
Figure 56: READ Latency	145
Figure 57: Consecutive READ Bursts (BL8)	147
Figure 58: Consecutive READ Bursts (BC4)	147
Figure 59: Nonconsecutive READ Bursts	148
Figure 60: READ (BL8) to WRITE (BL8)	148
Figure 61: READ (BC4) to WRITE (BC4) OTF	149
Figure 62: READ to PRECHARGE (BL8)	149
Figure 63: READ to PRECHARGE (BC4)	150
Figure 64: READ to PRECHARGE (AL = 5, CL = 6)	150
Figure 65: READ with Auto Precharge (AL = 4, CL = 6)	150
Figure 66: Data Output Timing – tDQSQ and Data Valid Window	152
Figure 67: Data Strobe Timing – READs	153
Figure 68: Method for Calculating tLZ and tHZ	154
Figure 69: tRPRE Timing	154
Figure 70: tRPST Timing	155
Figure 71: tWPRE Timing	157
Figure 72: tWPST Timing	157
Figure 73: WRITE Burst	158
Figure 74: Consecutive WRITE (BL8) to WRITE (BL8)	159
Figure 75: Consecutive WRITE (BC4) to WRITE (BC4) via OTF	159
Figure 76: Nonconsecutive WRITE to WRITE	160
Figure 77: WRITE (BL8) to READ (BL8)	160
Figure 78: WRITE to READ (BC4 Mode Register Setting)	161
Figure 79: WRITE (BC4 OTF) to READ (BC4 OTF)	162
Figure 80: WRITE (BL8) to PRECHARGE	163
Figure 81: WRITE (BC4 Mode Register Setting) to PRECHARGE	163
Figure 82: WRITE (BC4 OTF) to PRECHARGE	164

List of Figure

Figure 83: Data Input Timing	164
Figure 84: Self Refresh Entry/Exit Timing	155
Figure 85: Active Power-Down Entry and Exit	170
Figure 86: Precharge Power-Down (Fast-Exit Mode) Entry and Exit	170
Figure 87: Precharge Power-Down (Slow-Exit Mode) Entry and Exit	171
Figure 88: Power-Down Entry After READ or READ with Auto Precharge (RDAP)	171
Figure 89: Power-Down Entry After WRITE	172
Figure 90: Power-Down Entry After WRITE with Auto Precharge (WRAP)	172
Figure 91: REFRESH to Power-Down Entry	173
Figure 92: ACTIVATE to Power-Down Entry	173
Figure 93: PRECHARGE to Power-Down Entry	174
Figure 94: MRS Command to Power-Down Entry	174
Figure 95: Power-Down Exit to Refresh to Power-Down Entry	175
Figure 96: RESET Sequence	176
Figure 97: On-Die Termination	177
Figure 98: Dynamic ODT: ODT Asserted Before and After the WRITE, BC4	182
Figure 99: Dynamic ODT: Without WRITE Command	182
Figure 100: Dynamic ODT: ODT Pin Asserted Together with WRITE Command for 6 Clock Cycles, BL8	183
Figure 101: Dynamic ODT: ODT Pin Asserted with WRITE Command for 6 Clock Cycles, BC4	184
Figure 102: Dynamic ODT: ODT Pin Asserted with WRITE Command for 4 Clock Cycles, BC4	184
Figure 103: Synchronous ODT	186
Figure 104: Synchronous ODT (BC4)	187
Figure 105: ODT During READs	189
Figure 106: Asynchronous ODT Timing with Fast ODT Transition	191
Figure 107: Synchronous to Asynchronous Transition During Precharge Power-Down (DLL Off) Entry	193
Figure 108: Asynchronous to Synchronous Transition During Precharge Power-Down (DLL Off) Exit	195
Figure 109: Transition Period for Short CKE LOW Cycles with Entry and Exit Period Overlapping	197
Figure 110: Transition Period for Short CKE HIGH Cycles with Entry and Exit Period Overlapping	197

DDR3L Sync DRAM Features

• Functionality

- VDD/VDDQ = 1.35V (1.283V to 1.45V)
- Backward compatible to VDD = VDDQ = 1.5V $\pm$ 0.075V
- 8n-bit prefetch DDR architecture
- Differential clock inputs (CK, CK#)
- 8 internal banks
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Programmable CAS (READ) latency (CL)
- Programmable CAS additive latency (AL)
- Programmable CAS (WRITE) latency (CWL)
- Fixed burst length (BL) of 8 and burst chop (BC) of 4 (via the mode register set [MRS])
- Selectable BC4 or BL8 on-the-fly (OTF)
- Self refresh mode
- Tc of 0°C to +95°C
 - 64ms, 8192 cycle refresh at 0°C to +85°C
 - 32ms at 85°C to +95°C
- Self refresh temperature (SRT)

- Automatic self refresh (ASR)
- Write leveling
- Multipurpose register
- Output driver calibration

• Configuration

- 64 Meg X 16 (8 Meg X 16 X 8 Banks).
- 128 Meg X 8 (16 Meg X 8 X 8 Banks)
- 256 Meg X 4 (32 Meg X 4 X 8 Banks)

• Timing – Cycle time

- 1.07ns @ CL = 13 (-9M)
- 1.25ns @ CL = 11 (-8K)
- 1.50ns @ CL = 9 (-6H)
- 1.87ns @ CL = 7 (-5F)

• Operating Temperature Ranges

- Commercial (0°C to +95°C)
- Industrial (-40°C to +95°C)

Key Timing Parameters

Speed Grade	Data Rate (MT/s)	Target ^t RCD- ^t RP-CL	^t RCD (ns)	^t RP (ns)	CL (ns)	Notes
-9M	1866	13-13-13	13.91	13.91	13.91	1, 2, 3
-8K	1600	11-11-11	13.75	13.75	13.75	1, 2
-6H	1333	9-9-9	13.5	13.5	13.5	1
-5F	1066	7-7-7	13.1	13.1	13.1	

Notes : 1. Backward compatible to 1066, CL = 7.
 2. Backward compatible to 1333, CL = 9.
 3. Backward compatible to 1600, CL = 11.

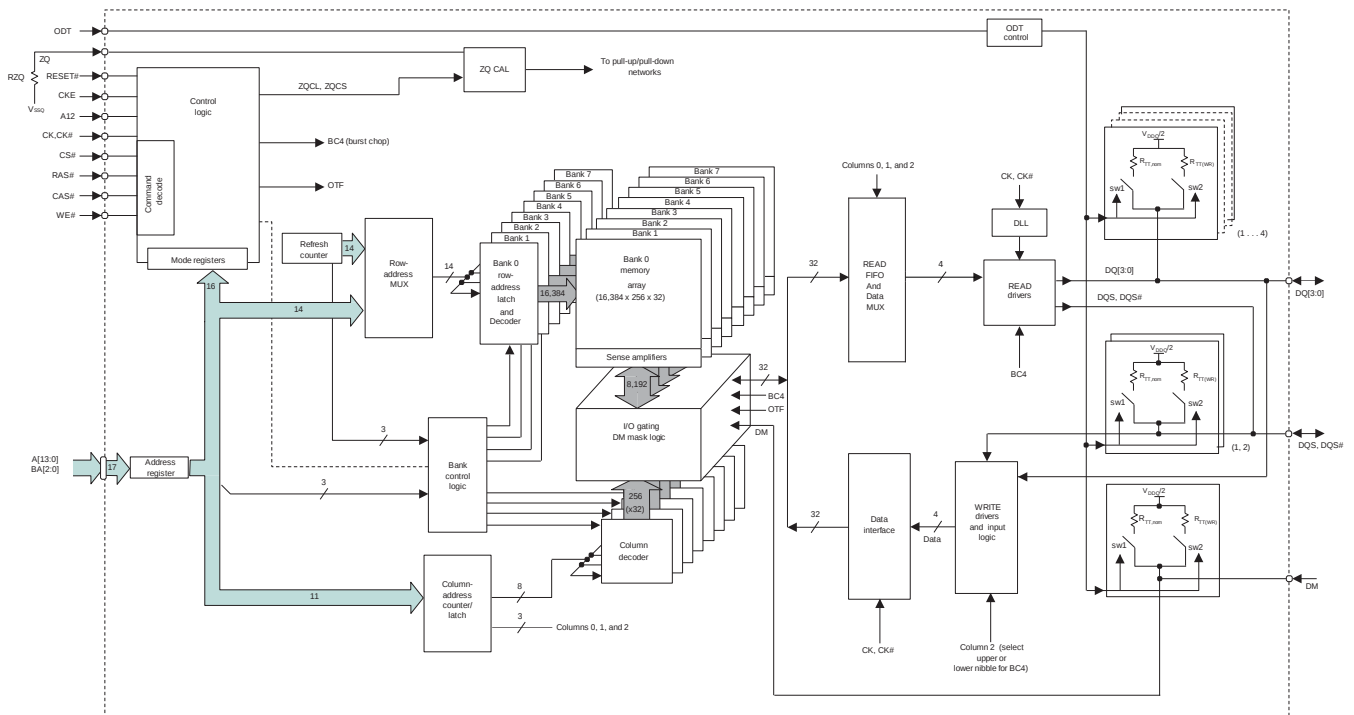
Addressing

Parameter	256 Meg x 4	128 Meg x 8	64 Meg x 16
Configuration	32 Meg x 4 x 8 banks	16 Meg x 8 x 8 banks	8 Meg x 16 x 8 banks
Refresh count	8K	8K	8K
Row addressing	16K (A[13:0])	16K (A[13:0])	8K (A[12:0])
Bank addressing	8 (BA[2:0])	8 (BA[2:0])	8 (BA[2:0])
Column addressing	2K (A[11, 9:0])	1K (A[9:0])	1K (A[9:0])
Page Size	1KB	1KB	2KB

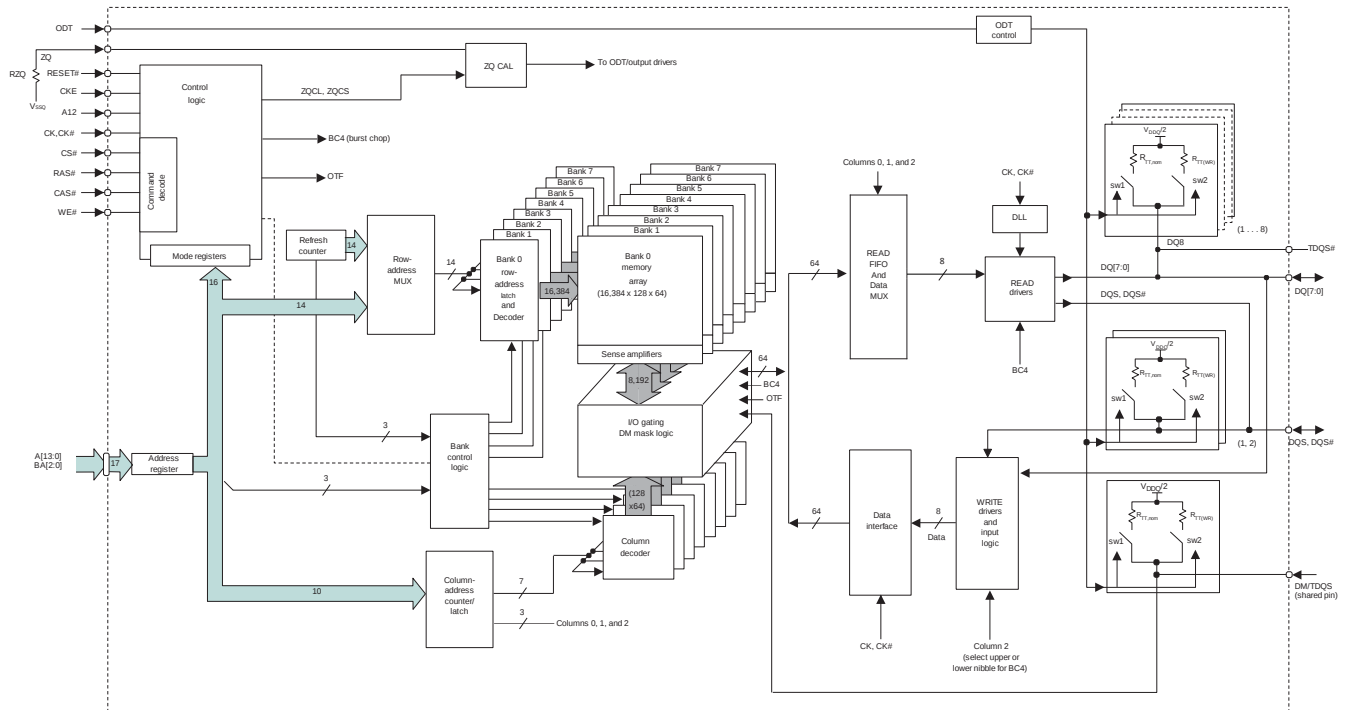
Functional Block Diagrams

DDR3L SDRAM is a high-speed, CMOS dynamic random access memory. It is internally configured as an 8-bank DRAM.

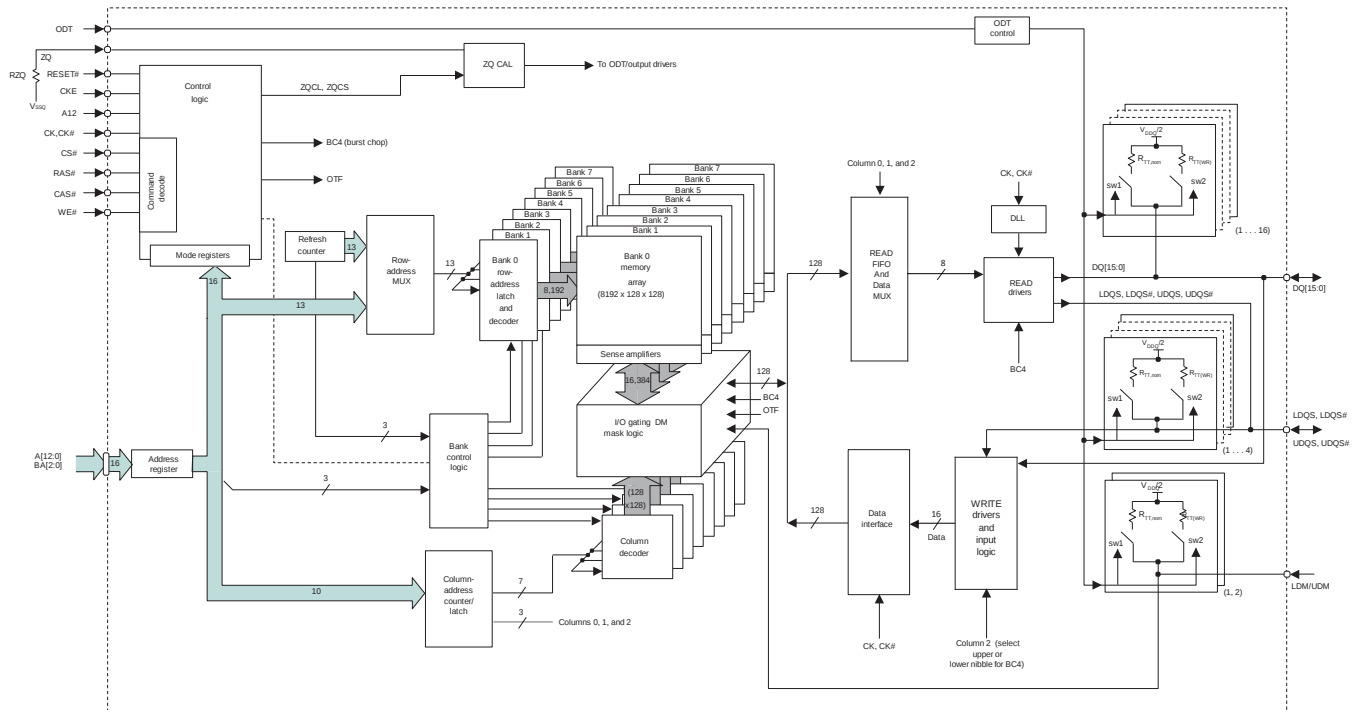
256 Meg x 4 Functional Block Diagram



128 Meg x 8 Functional Block Diagram



64 Meg x 16 Functional Block Diagram



Ball Assignments and Descriptions

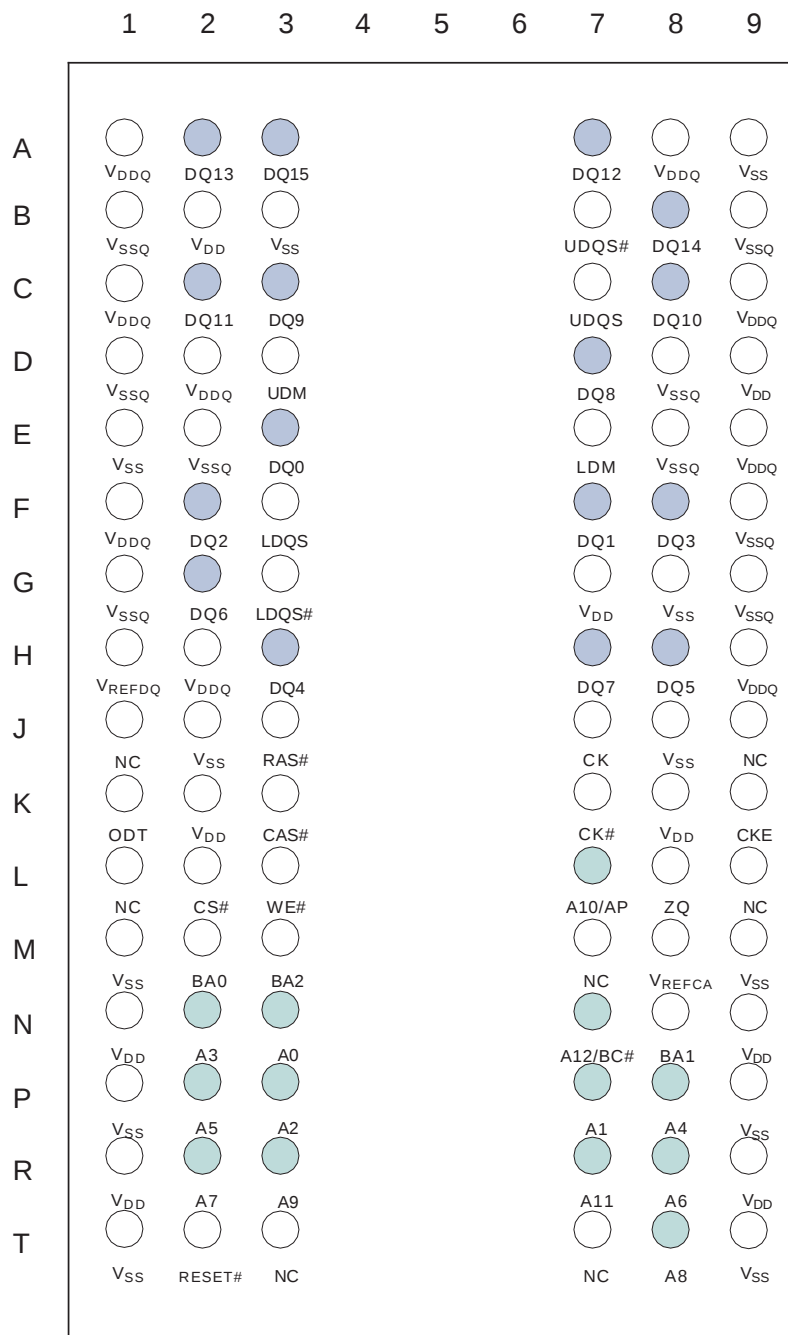
78-Ball FBGA – x4, x8 (Top View)

	1	2	3	4	5	6	7	8	9
A	 V _{SS}	 V _{DD}	 NC				 NF, NF/TDQS#	 V _{SS}	 V _{DD}
B	 V _{SS}	 V _{SSQ}	 DQ0				 DM, DM/TDQS	 V _{SSQ}	 V _{DDQ}
C	 V _{DDQ}	 DQ2	 DQS				 DQ1	 DQ3	 V _{SSQ}
D	 V _{SSQ}	 NF, DQ6	 DQS#				 V _{DD}	 V _{SS}	 V _{SSQ}
E	 V _{REFDQ}	 V _{DDQ}	 NF, DQ4				 NF, DQ7	 NF, DQ5	 V _{DDQ}
F	 NC	 V _{SS}	 RAS#				 CK	 V _{SS}	 NC
G	 ODT	 V _{DD}	 CAS#				 CK#	 V _{DD}	 CKE
H	 NC	 CS#	 WE#				 A10/AP	 ZQ	 NC
J	 V _{SS}	 BA0	 BA2				 NC	 V _{REFCA}	 V _{SS}
K	 V _{DD}	 A3	 A0				 A12/BC#	 BA1	 V _{DD}
L	 V _{SS}	 A5	 A2				 A1	 A4	 V _{SS}
M	 V _{DD}	 A7	 A9				 A11	 A6	 V _{DD}
N	 V _{SS}	 RESET#	 A13				 NC	 A8	 V _{SS}

Notes : 1. Ball descriptions listed in Table(page 20) are listed as “x4, x8” if unique; otherwise, x4 and x8 are the same.

2. A comma separates the configuration; a slash defines a selectable function.

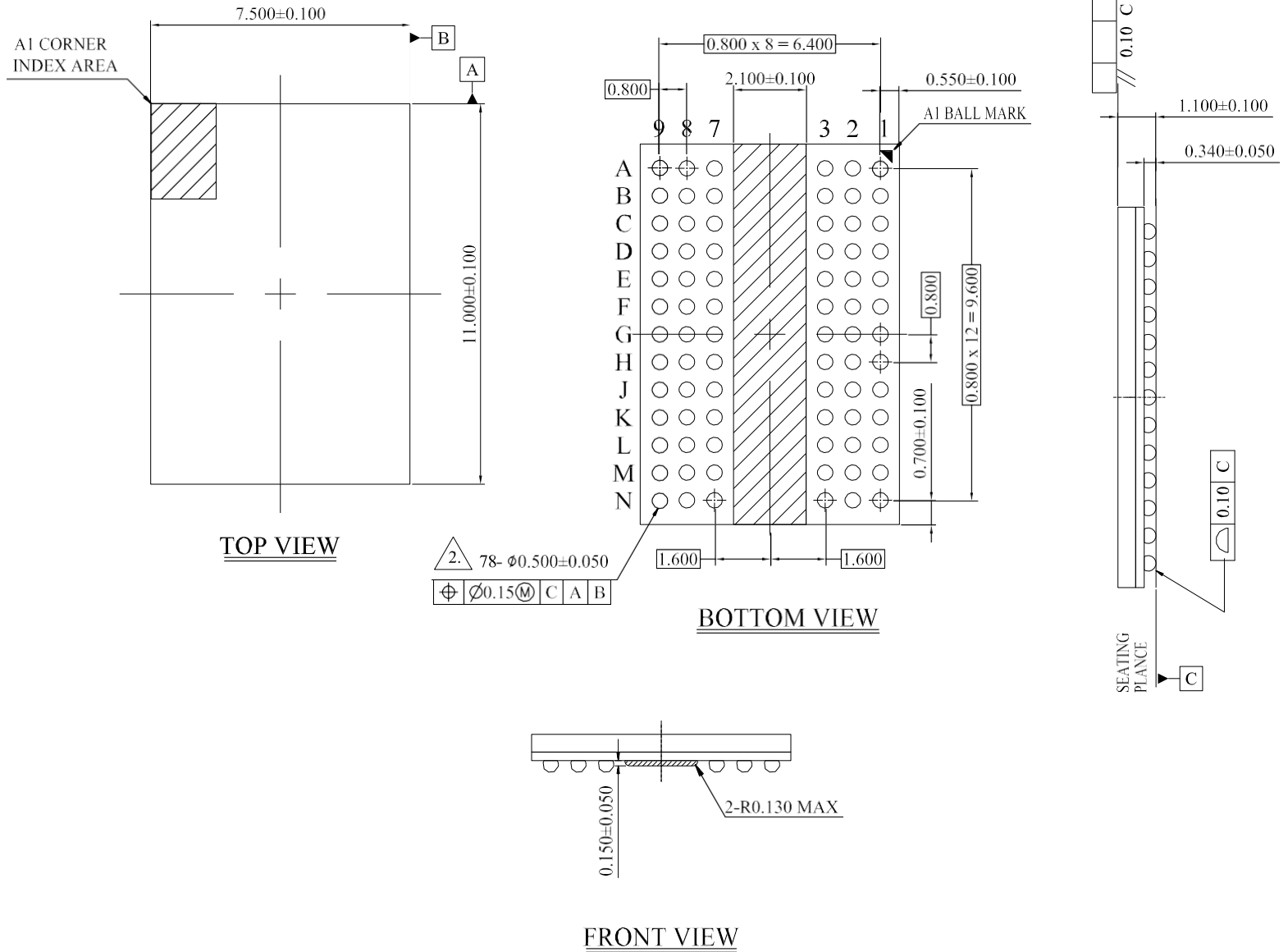
Example A7 = NF, NF/TDQS#. NF applies to the x4 configuration only. NF/TDQS# applies to the x8 configuration only selectable between NF or TDQS# via MRS (symbols are defined in Ball description).

96-Ball FBGA – x16 (Top View)


Notes : 1. Ball descriptions listed in Table (page 22).

Package Dimensions

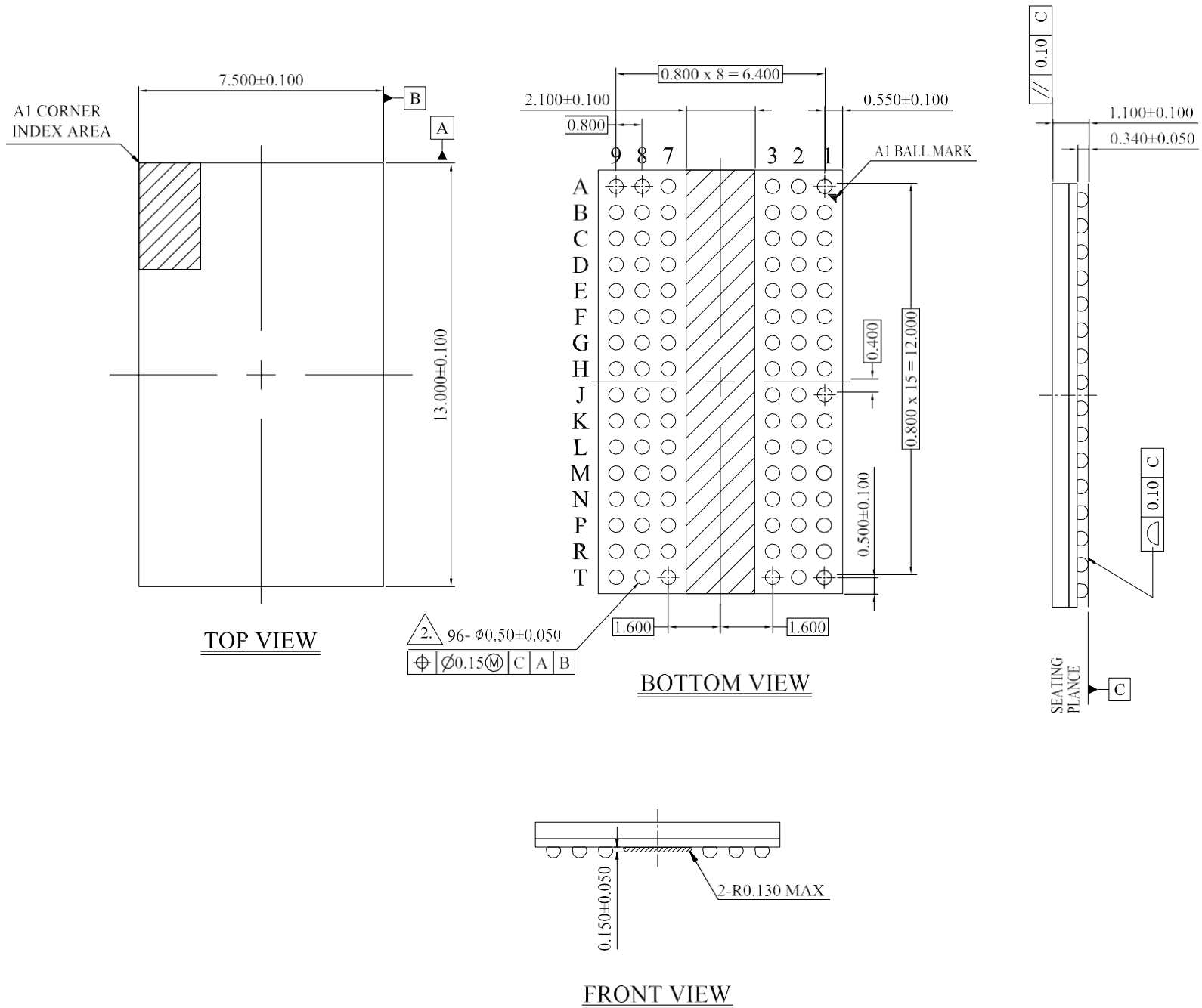
78-Ball FBGA – x4, x8



Notes : 1. All dimensions are in millimeters.

②. Post-Reflow solder ball Diameters. (Pre-Reflow Diameter : Ø0.45 ± 0.2)

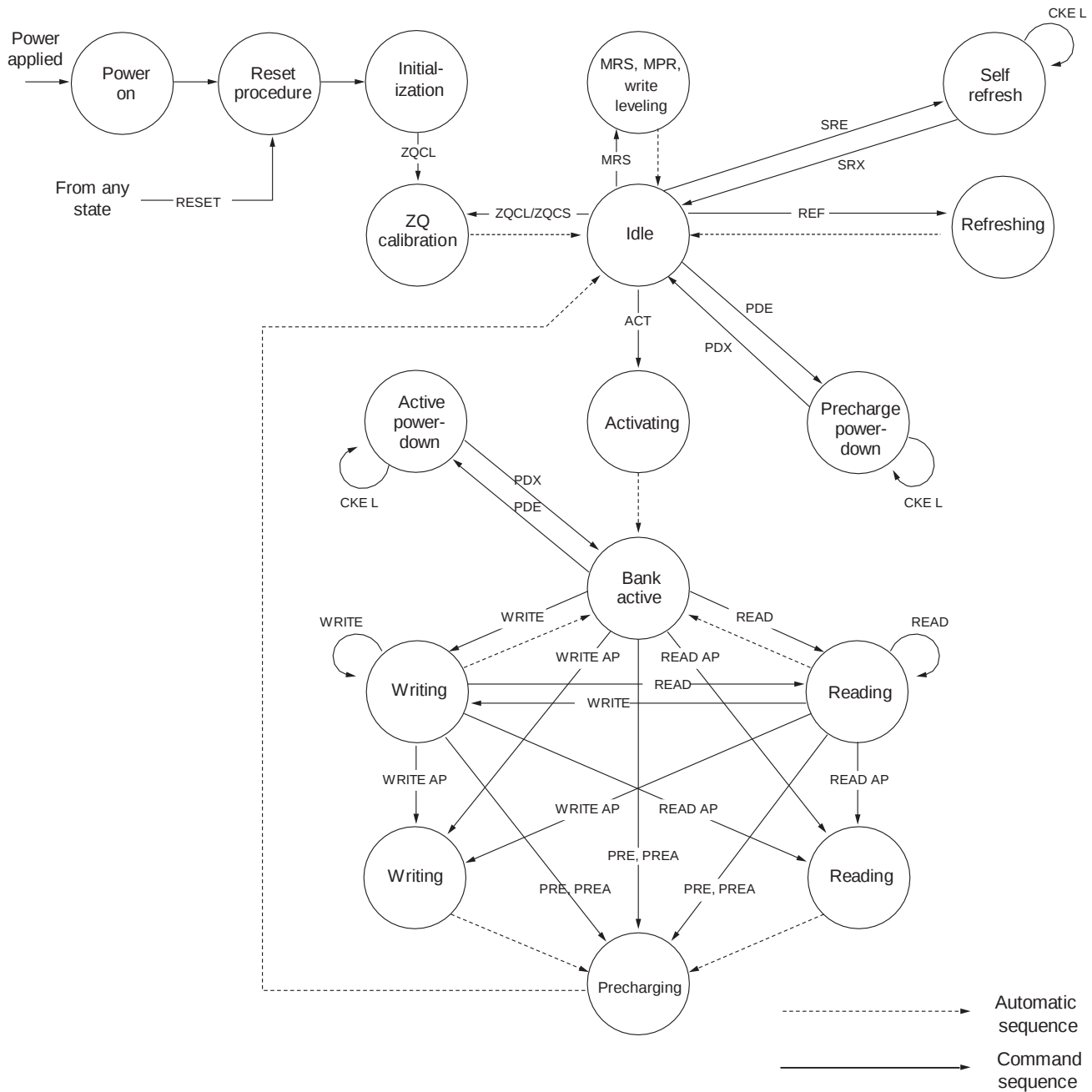
96-Ball FBGA – x16



Notes : 1. All dimensions are in millimeters.

②. Post-Reflow solder ball Diameters. (Pre-Reflow Diameter : Ø0.45 ± 0.2)

Simplified Bus Interface State Diagram



ACT = Activate
 MPR = Multipurpose register
 MRS = Mode register set
 PDE = Power-down entry
 PDX = Power-down exit
 PRE = Precharge

PREA = Precharge all
 READ = RD, RDS4, RDS8
 READ AP = RDAP, RDAPS4, RDAPS8
 REF = Refresh
 RESET = Start reset procedure
 SRE = Self refresh entry

SRX = Self refresh exit
 WRITE = WR, WRS4, WRS8
 WRITE AP = WRAP, WRAPS4, WRAPS8
 ZQCL = ZQ long calibration
 ZQCS = ZQ short calibration

78-Ball FBGA – x4, x8 Ball Descriptions

Symbol	Type	Description
A13, A12/BC# A10/AP, A[9:0]	Input	Address inputs : Provide the row address for ACTIVATE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one bank (A10 LOW, bank selected by BA[2:0]) or all banks (A10 HIGH). The address inputs also provide the op-code during a LOAD MODE command. Address inputs are referenced to VREFCA. A12/BC#: When enabled in the mode register (MR), A12 is sampled during READ and WRITE commands to determine whether burst chop (on-the-fly) will be performed (HIGH=BL8 or no burst chop, LOW=BC4).
BA [2:0]	Input	Bank address inputs : BA[2:0] define the bank to which an ACTIVATE, READ, WRITE, or PRECHARGE command is being applied. BA[2:0] define which mode register (MR0, MR1, MR2, or MR3) is loaded during the LOAD MODE command. BA[2:0] are referenced to VREFCA.
CK, CK#	Input	Clock : CK and CK# are differential clock inputs. All control and address input signals are sampled on the crossing of the positive edge of CK and the negative edge of CK#. Output data strobe (DQS, DQS#) is referenced to the crossings of CK and CK#.
CKE	Input	Clock enable : CKE enables (registered HIGH) and disables (registered LOW) internal circuitry and clocks on the DRAM. The specific circuitry that is enabled / disabled is dependent upon the DDR3L SDRAM configuration and operating mode. Taking CKE LOW provides PRECHARGE POWER-DOWN and SELF REFRESH operations (all banks idle), or active power-down (row active in any bank). CKE is synchronous for power-down entry and exit and for self refresh entry. CKE is asynchronous for self refresh exit. Input buffers (excluding CK, CK#, CKE, RESET#, and ODT) are disabled during POWER-DOWN. Input buffers (excluding CKE and RESET#) are disabled during SELF REFRESH. CKE is referenced to VREFCA.
CS#	Input	Chip select : CS# enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when CS# is registered HIGH. CS# provides for external rank selection on systems with multiple ranks. CS# is considered part of the command code. CS# is referenced to VREFCA.
DM	Input	Input data mask : DM is an input mask signal for write data. Input data is masked when DM is sampled HIGH along with the input data during a write access. Although the DM ball is input-only, the DM loading is designed to match that of the DQ and DQS balls. DM is referenced to VREFDQ. DM has an optional use as TDQS on the x8.
ODT	Input	On-die termination : ODT enables (registered HIGH) and disables (registered LOW) termination resistance internal to the DDR3L SDRAM. When enabled in normal operation, ODT is only applied to each of the following balls: DQ[7:0], DQS, DQS#, and DM for the x8; DQ[3:0], DQS, DQS#, and DM for the x4. The ODT input is ignored if disabled via the LOAD MODE command. ODT is referenced to VREFCA.
RAS#, CAS#, WE#	Input	Command inputs : RAS#, CAS#, and WE# (along with CS#) define the command being entered and are referenced to VREFCA.
RESET#	Input	Reset : RESET# is an active LOW CMOS input referenced to VSS. The RESET# input receiver is a CMOS input defined as a rail-to-rail signal with DC HIGH $\geq 0.8 \times VDD$ and DC LOW $\leq 0.2 \times VDDQ$. RESET# assertion and desertion are asynchronous.
DQ[3:0]	I/O	Data input/output : Bidirectional data bus for the x4 configuration. DQ[3:0] are referenced to VREFDQ.
DQ[7:0]	I/O	Data input/output : Bidirectional data bus for the x8 configuration. DQ[7:0] are referenced to VREFDQ.

78-Ball FBGA – x4, x8 Ball Descriptions (Continued)

Symbol	Type	Description
DQS, DQS#	I/O	Data strobe: Output with read data. Edge-aligned with read data. Input with write data. Center-aligned to write data.
TDQS, TDQS#	Output	Termination data strobe: Applies to the x8 configuration only. When TDQS is enabled, DM is disabled, and the TDQS and TDQS# balls provide termination resistance.
VDD	Supply	Power supply : 1.35V, 1.283V to 1.45V operational; compatible with 1.5V operation.
VDDQ	Supply	DQ power supply: 1.35V, 1.283V to 1.45V operational; compatible with 1.5V operation.
VREFCA	Supply	Reference voltage for control, command, and address: VREFCA must be maintained at all times (including self refresh) for proper device operation.
VREFDQ	Supply	Reference voltage for data: VREFDQ must be maintained at all times (excluding self refresh) for proper device operation.
VSS	Supply	Ground.
VSSQ	Supply	DQ ground: Isolated on the device for improved noise immunity.
ZQ	Reference	External reference ball for output drive calibration: This ball is tied to an external 240Ω resistor (RZQ), which is tied to VSSQ.
NC	–	No connect: These balls should be left unconnected (the ball has no connection to the DRAM or to other balls).
NF	–	No function: When configured as a x4 device, these balls are NF. When configured as a x8 device, these balls are defined as TDQS#, DQ[7:4].

96-Ball FBGA – x16 Ball Descriptions

Symbol	Type	Description
A12/BC#, A10/AP, A[9:0]	Input	Address inputs : Provide the row address for ACTIVATE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one bank (A10 LOW, bank selected by BA[2:0]) or all banks (A10 HIGH). The address inputs also provide the op-code during a LOAD MODE command. Address inputs are referenced to VREFCA. A12/BC#: When enabled in the mode register (MR), A12 is sampled during READ and WRITE commands to determine whether burst chop (on-the-fly) will be performed (HIGH=BL8 or no burst chop, LOW=BC4).
BA [2:0]	Input	Bank address inputs : BA[2:0] define the bank to which an ACTIVATE, READ, WRITE, or PRECHARGE command is being applied. BA[2:0] define which mode register (MR0, MR1, MR2, or MR3) is loaded during the LOAD MODE command. BA[2:0] are referenced to VREFCA.
CK, CK#	Input	Clock : CK and CK# are differential clock inputs. All control and address input signals are sampled on the crossing of the positive edge of CK and the negative edge of CK#. Output data strobe (DQS, DQS#) is referenced to the crossings of CK and CK#.
CKE	Input	Clock enable : CKE enables (registered HIGH) and disables (registered LOW) internal circuitry and clocks on the DRAM. The specific circuitry that is enabled /disabled is dependent upon the DDR3L SDRAM configuration and operating mode. Taking CKE LOW provides PRECHARGE POWER-DOWN and SELF REFRESH operations (all banks idle), or active power-down (row active in any bank). CKE is synchronous for power-down entry and exit and for self refresh entry. CKE is asynchronous for self refresh exit. Input buffers (excluding CK, CK#, CKE, RESET#, and ODT) are disabled during POWER-DOWN. Input buffers (excluding CKE and RESET#) are disabled during SELF REFRESH. CKE is referenced to VREFCA.
CS#	Input	Chip select : CS# enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when CS# is registered HIGH. CS# provides for external rank selection on systems with multiple ranks. CS# is considered part of the command code. CS# is referenced to VREFCA.
LDM	Input	Input data mask : LDM is a lower-byte, input mask signal for write data. Lower-byte input data is masked when LDM is sampled HIGH along with the input data during a write access. Although the LDM ball is input-only, the LDM loading is designed to match that of the DQ and DQS balls. LDM is referenced to VREFDQ.
ODT	Input	On-die termination : ODT enables (registered HIGH) and disables (registered LOW) termination resistance internal to the DDR3L SDRAM. When enabled in normal operation, ODT is only applied to each of the following balls: DQ[15:0], LDQS, LDQS#, UDQS, UDQS#, LDM, and UDM for the x16; DQ0[7:0], DQS, DQS#, DM /TDQS, and NF/TDQS# (when TDQS is enabled) for the x8; DQ[3:0], DQS, DQS#, and DM for the x4. The ODT input is ignored if disabled via the LOAD MODE command. ODT is referenced to VREFCA.
RAS#, CAS#, WE#	Input	Command inputs : RAS#, CAS#, and WE# (along with CS#) define the command being entered and are referenced to VREFCA.
RESET#	Input	Reset : RESET# is an active LOW CMOS input referenced to VSS. The RESET# input receiver is a CMOS input defined as a rail-to-rail signal with DC HIGH $\geq 0.8 \times VDD$ and DC LOW $\leq 0.2 \times VDDQ$. RESET# assertion and desertion are asynchronous..

96-Ball FBGA – x16 Ball Descriptions

Symbol	Type	Description
UDM	input	Input data mask : UDM is an upper-byte, input mask signal for write data. Upper byte input data is masked when UDM is sampled HIGH along with that input data during a WRITE access. Although the UDM ball is input-only, the UDM loading is designed to match that of the DQ and DQS balls. UDM is referenced to VREFDQ.
DQ[7:0]	I/O	Data input/output : Lower byte of bidirectional data bus for the x16 configuration. DQ[7:0] are referenced to VREFDQ.
DQ[15:8]	I/O	Data input/output : Upper byte of bidirectional data bus for the x16 configuration. DQ[15:8] are referenced to VREFDQ.
LDQS, LDQS#	I/O	Lower byte data strobe : Output with read data. Edge-aligned with read data. Input with write data. Center-aligned to write data.
UDQS, UDQS#	I/O	Upper byte data strobe : Output with read data. Edge-aligned with read data. Input with write data. DQS is center-aligned to write data..
VDD	Supply	Power supply : 1.35V, 1.283V to 1.45V.
VDDQ	Supply	DQ power supply : 1.35V, 1.283V to 1.45V.
VREFCA	Supply	Reference voltage for control, command, and address : VREFCA must be maintained at all times (including self refresh) for proper device operation.
VREFDQ	Supply	Reference voltage for data : VREFDQ must be maintained at all times (excluding self refresh) for proper device operation.
VSS	Supply	Ground.
VSSQ	Supply	DQ ground : Isolated on the device for improved noise immunity.
ZQ	Reference	External reference ball for output drive calibration : This ball is tied to an external 240Ω resistor (RZQ), which is tied to VSSQ.
NC	–	No connect : These balls should be left unconnected (the ball has no connection to the DRAM or to other balls).

Functional Description

DDR3L SDRAM uses a double data rate architecture to achieve high-speed operation.

The double data rate architecture is an $8n$ -prefetch architecture with an interface designed to transfer two data words per clock cycle at the I/O pins. A single read or write operation for the DDR3L SDRAM effectively consists of a single $8n$ -bit-wide, four-clock-cycle data transfer at the internal DRAM core and eight corresponding n -bit-wide, one-half-clock-cycle data transfers at the I/O pins.

The differential data strobe (DQS, DQS#) is transmitted externally, along with data, for use in data capture at the DDR3L SDRAM input receiver. DQS is center-aligned with data for WRITES. The read data is transmitted by the DDR3L SDRAM and edge-aligned to the data strobes.

The DDR3LSDRAM operates from a differential clock (CK and CK#). The crossing of CK going HIGH and CK# going LOW is referred to as the positive edge of CK. Control, command, and address signals are registered at every positive edge of CK. Input data is registered on the first rising edge of DQS after the WRITE preamble, and output data is referenced on the first rising edge of DQS after the READ preamble.

Read and write accesses to the DDR3LSDRAM are burst-oriented. Accesses start at a selected location and continue for a programmed number of locations in a programmed sequence. Accesses begin with the registration of an ACTIVATE command, which is then followed by a READ or WRITE command. The address bits registered coincident with the ACTIVATE command are used to select the bank and row to be accessed. The address bits registered coincident with the READ or WRITE commands are used to select the bank and the starting column location for the burst access.

The device uses a READ and WRITE BL8 and BC4. An auto precharge function may be enabled to provide a self-timed row precharge that is initiated at the end of the burst access.

As with standard DDR SDRAM, the pipelined, multibank architecture of DDR3LSDRAM allows for concurrent operation, thereby providing high bandwidth by hiding row precharge and activation time.

A self refresh mode is provided, along with a power-saving, power-down mode.

Industrial Temperature

The industrial temperature (IT) device requires that the case temperature not exceed -40°C or 95°C . JEDEC specifications require the refresh rate to double when TC exceeds 85°C ; this also requires use of the high-temperature self refresh option. Additionally, ODT resistance and the input/output impedance must be derated when TC is $< 0^{\circ}\text{C}$ or $> 95^{\circ}\text{C}$.

General Notes

- The functionality and the timing specifications discussed in this data sheet are for the DLL enable mode of operation (normal operation).
- Throughout this data sheet, various figures and text refer to DQs as "DQ." DQ is to be interpreted as any and all DQ collectively, unless specifically stated otherwise.
- The terms "DQS" and "CK" found throughout this data sheet are to be interpreted as DQS, DQS# and CK, CK# respectively, unless specifically stated otherwise.
- Complete functionality may be described throughout the document; any page or diagram may have been simplified to convey a topic and may not be inclusive of all requirements.
- Any specific requirement takes precedence over a general statement.
- Any functionality not specifically stated is considered undefined, illegal, and not supported, and can result in unknown operation.

- Row addressing is denoted as A[n:0]. For example, 1Gb: $n = 12$ (x16); 1Gb: $n = 13$ (x4, x8); 2Gb: $n = 13$ (x16) and 2Gb: $n = 14$ (x4, x8); 4Gb: $n = 14$ (x16); and 4Gb: $n = 15$ (x4, x8).
- Dynamic ODT has a special use case: when DDR3L devices are architected for use in a single rank memory array, the ODT ball can be wired HIGH rather than routed.
Refer to the Dynamic ODT Special Use Case section.
- A x16 device's DQ bus is comprised of two bytes. If only one of the bytes needs to be used, use the lower byte for data transfers and terminate the upper byte as noted :
 - Connect UDQS to ground via 1k Ω * resistor.
 - Connect UDQS# to VDD via 1k Ω * resistor.
 - Connect UDM to VDD via 1k Ω * resistor.
 - Connect DQ[15:8] individually to either VSS, VDD, or VREF via 1k Ω resistors,* or float DQ[15:8].

* If ODT is used, 1k Ω resistor should be changed to 4x that of the selected ODT.

Electrical Specifications

Absolute Ratings

Stresses greater than those listed in Table 1 may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may adversely affect reliability.

Table 1 : Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit	Notes
V _{DD}	V _{DD} supply voltage relative to V _{SS}	−0.4	1.975	V	1
V _{DDQ}	V _{DD} supply voltage relative to V _{SSQ}	−0.4	1.975	V	
V _{IN} , V _{OUT}	Voltage on any pin relative to V _{SS}	−0.4	1.975	V	
T _C	Operating case temperature - Commercial	0	95	°C	2, 3
	Operating case temperature - Industrial	−40	95	°C	2, 3
	Operating case temperature - Automotive	−40	105	°C	2, 3
T _{STG}	Storage temperature	−55	150	°C	

Notes : 1. VDD and VDDQ must be within 300mV of each other at all times, and VREF must not be greater than $0.6 \times VDDQ$.

When VDD and VDDQ are <500mV, VREF can be ≤ 300 mV.

2. MAX operating case temperature. TC is measured in the center of the package.

3. Device functionality is not guaranteed if the DRAM device exceeds the maximum TC during operation.

Input / Output Capacitance

Table 2 : DDR3L Input / Output Capacitance

Note 1 applies to the entire table

Capacitance Parameters	Symbol	800		1066		1333		1600		1866		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
CK and CK#	C _{CK}	0.8	1.6	0.8	1.6	0.8	1.4	0.8	1.4	0.8	1.3	pF	
ΔC: CK to CK#	C _{DCK}	0	0.15	0	0.15	0	0.15	0	0.15	0	0.15	pF	
Single-end I/O : DQ, DM	C _{IO}	1.5	3	1.5	2.7	1.5	2.5	1.5	2.3	1.5	2.2	pF	2
Differential I/O : DQS, DQS#, TDQS, TDQS#	C _{IO}	1.5	3	1.5	2.7	1.5	2.5	1.5	2.3	1.5	2.2	pF	3
ΔC: DQS to DQS#, TDQS, TDQS#	C _{DDQS}	0	0.2	0	0.2	0	0.15	0	0.15	0	0.15	pF	3
ΔC: DQ to DQS	C _{DIO}	-0.5	0.3	-0.5	0.3	-0.5	0.3	-0.5	0.3	-0.5	0.3	pF	4
Inputs(CTRL, CMD, ADDR)	C _I	0.75	1.4	0.75	1.35	0.75	1.3	0.75	1.3	0.75	1.2	pF	5
ΔC: CTRL to CK	C _{DI_CTRL}	-0.5	0.3	-0.5	0.3	-0.4	0.2	-0.4	0.2	-0.4	0.2	pF	6
ΔC: CMD_ADDR to CK	C _{DI_CMD_ADDR}	-0.5	0.5	-0.5	0.5	-0.4	0.4	-0.4	0.4	-0.4	0.4	pF	7
ZQ pin capacitance	C _{ZQ}	–	3.0	–	3.0	–	3.0	–	3.0	–	3.0	pF	
Reset pin capacitance	C _{RE}	–	3.0	–	3.0	–	3.0	–	3.0	–	3.0	pF	

Note : 1. VDD = 1.5V ±0.075mV, VDDQ = VDD, VREF = VSS, f = 100 MHz, TC = 25°C. VOUT(DC) = 0.5 × VDDQ, VOUT = 0.1V (peak-to-peak).

2. DM input is grouped with I/O pins, reflecting the fact that they are matched in loading.

3. Includes TDQS, TDQS#. CDDQS is for DQS vs. DQS# and TDQS vs. TDQS# separately.

4. CDIO = CIO(DQ) - 0.5 × (CIO(DQS) + CIO(DQS#)).

5. Excludes CK, CK#, CTRL = ODT, CS#, and CKE; CMD = RAS#, CAS#, and WE#; ADDR = A[n:0], BA[2:0].

6. CDI_CTRL = CI(CTRL) - 0.5 × (CCK(CK) + CCK(CK#)).

7. CDI_CMD_ADDR = CI(CMD_ADDR) - 0.5 × (CCK(CK) + CCK(CK#)).

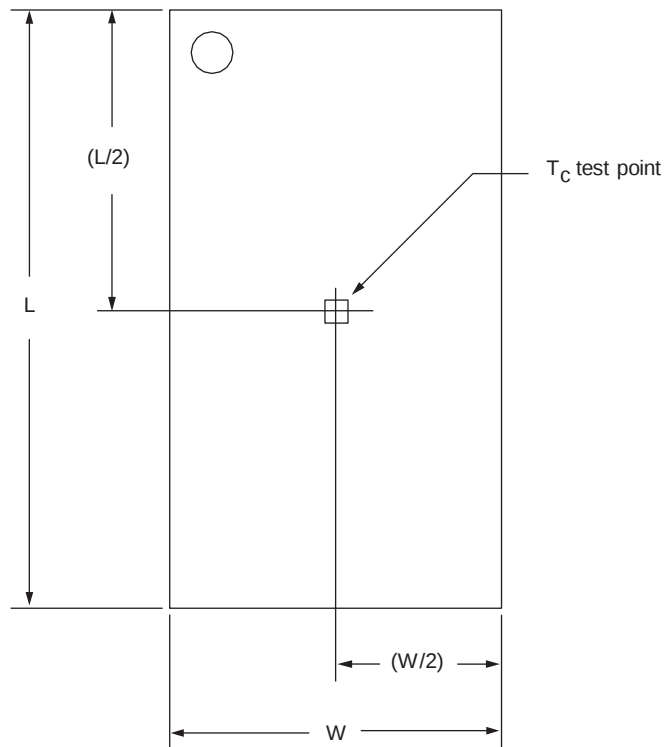
Thermal Characteristics

Table 3 : Thermal Characteristics

Parameter/Condition		Value	Units	Symbol	Notes
Operating case temperature – Commercial		0 to +85	°C	T _C	1, 2, 3
		0 to +95	°C	T _C	1, 2, 3, 4
Operating case temperature – Industrial		–40 to +85	°C	T _C	1, 2, 3
		–40 to +95	°C	T _C	1, 2, 3, 4
Operating case temperature – Automotive		–40 to +85	°C	T _C	1, 2, 3
		–40 to +105	°C	T _C	1, 2, 3, 4
Junction-to-case (TOP)	78-ball	-	°C/W	Θ _{JC}	5
	96-ball	-			

- Notes :
1. MAX operating case temperature. TC is measured in the center of the package.
 2. A thermal solution must be designed to ensure the DRAM device does not exceed the maximum TC during operation.
 3. Device functionality is not guaranteed if the DRAM device exceeds the maximum TC during operation.
 4. If TC exceeds 85°C, the DRAM must be refreshed externally at 2x refresh, which is a 3.9μs interval refresh rate.
The use of SRT or ASR must be enabled.
 5. The thermal resistance data is based off of a number of samples from multiple lots and should be viewed as a typical number.

Figure 1 : Thermal Measurement Point



Electrical Specifications – IDD Specifications and Conditions

Within the following IDD measurement tables, the following definitions and conditions are used, unless stated otherwise :

- LOW: $V_{IN} \leq V_{IL(AC)max}$; HIGH: $V_{IN} \geq V_{IH(AC)min}$.
- Midlevel: Inputs are $V_{REF} = V_{DD}/2$.
- RON set to $R_{ZQ}/7$ (34 Ω).
- $R_{TT,nom}$ set to $R_{ZQ}/6$ (40 Ω).
- $R_{TT(WR)}$ set to $R_{ZQ}/2$ (120 Ω).
- QOFF is enabled in MR1.
- ODT is enabled in MR1 ($R_{TT,nom}$) and MR2 ($R_{TT(WR)}$).
- TDQS is disabled in MR1.
- External DQ/DQS/DM load resistor is 25 Ω to $V_{DDQ}/2$.
- Burst lengths are BL8 fixed.
- AL equals 0 (except in IDD7).
- IDD specifications are tested after the device is properly initialized.
- Input slew rate is specified by AC parametric test conditions.
- ASR is disabled.
- Read burst type uses nibble sequential (MR0[3] = 0).
- Loop patterns must be executed at least once before current measurements begin.

Table 4 : DDR3L Timing Parameters Used for IDD Measurements – Clock Units

I _{DD} Parameter		DDR3 -800		DDR3 -1066		DDR3 -1333		DDR3 -1600		DDR3 -1866	Unit
		5-5-5	6-6-6	7-7-7	8-8-8	9-9-9	10-10-10	10-10-10	11-11-11	13-13-13	
t _{CK} (MIN) I _{DD}		2.5		1.875		1.5		1.25		1.071	ns
CL I _{DD}		5	6	7	8	9	10	10	11	13	CK
t _{RCD} (MIN) I _{DD}		5	6	7	8	9	10	10	11	13	CK
t _{RC} (MIN) I _{DD}		20	21	27	28	33	34	38	39	45	CK
t _{RAS} (MIN) I _{DD}		15	15	20	20	24	24	28	28	32	CK
t _{RP} (MIN)		5	6	7	8	9	10	10	11	13	CK
t _{FAW}	x4, x8	16	16	20	20	20	20	24	24	26	CK
	x16	20	20	27	27	30	30	32	32	33	CK
t _{RRD} I _{DD}	x4, x8	4	4	4	4	4	4	5	5	5	CK
	x16	4	4	6	6	5	5	6	6	6	CK
t _{RFC}	1Gb	44	44	59	59	74	74	88	88	103	CK
	2Gb	64	64	86	86	107	107	128	128	150	CK
	4Gb	104	104	139	139	174	174	208	208	243	CK
	8Gb	140	140	187	187	234	234	280	280	328	CK

Table 5 : DDR3L IDD0 Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data
Toggling	Static HIGH	0	0	ACT	0	0	1	1	0	0	0	0	0	0	0	–
			1	D	1	0	0	0	0	0	0	0	0	0	0	–
			2	D	1	0	0	0	0	0	0	0	0	0	0	–
			3	D#	1	1	1	1	0	0	0	0	0	0	0	–
			4	D#	1	1	1	1	0	0	0	0	0	0	0	–
			Repeat cycles 1 through 4 until $nRAS - 1$; truncate if needed													
			$nRAS$	PRE	0	0	1	0	0	0	0	0	0	0	0	–
			Repeat cycles 1 through 4 until $nRC - 1$; truncate if needed													
			nRC	ACT	0	0	1	1	0	0	0	0	0	F	0	–
			$nRC + 1$	D	1	0	0	0	0	0	0	0	0	F	0	–
			$nRC + 2$	D	1	0	0	0	0	0	0	0	0	F	0	–
			$nRC + 3$	D#	1	1	1	1	0	0	0	0	0	F	0	–
			$nRC + 4$	D#	1	1	1	1	0	0	0	0	0	F	0	–
			Repeat cycles $nRC + 1$ through $nRC + 4$ until $nRC - 1 + nRAS - 1$; truncate if needed													
			$nRC + nRAS$	PRE	0	0	1	0	0	0	0	0	0	F	0	–
			Repeat cycles $nRC + 1$ through $nRC + 4$ until $2 \times RC - 1$; truncate if needed													
		1	$2 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 1												
		2	$4 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 2												
		3	$6 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 3												
		4	$8 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 4												
		5	$10 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 5												
		6	$12 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 6												
		7	$14 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 7												

Note : 1. DQ, DQS, DQS# are midlevel.
 2. DM is LOW.
 3. Only selected bank (single) active.

Table 6 : DDR3L IDD1 Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data ²
Toggling	Static HIGH	0	0	ACT	0	0	1	1	0	0	0	0	0	0	0	–
			1	D	1	0	0	0	0	0	0	0	0	0	0	–
			2	D	1	0	0	0	0	0	0	0	0	0	0	–
			3	D#	1	1	1	1	0	0	0	0	0	0	0	–
			4	D#	1	1	1	1	0	0	0	0	0	0	0	–
			Repeat cycles 1 through 4 until $nRCD - 1$; truncate if needed													
			$nRCD$	RD	0	1	0	1	0	0	0	0	0	0	0	00000000
			Repeat cycles 1 through 4 until $nRAS - 1$; truncate if needed													
			$nRAS$	PRE	0	0	1	0	0	0	0	0	0	0	0	–
			Repeat cycles 1 through 4 until $nRC - 1$; truncate if needed													
			nRC	ACT	0	0	1	1	0	0	0	0	0	F	0	–
			$nRC + 1$	D	1	0	0	0	0	0	0	0	0	F	0	–
			$nRC + 2$	D	1	0	0	0	0	0	0	0	0	F	0	–
			$nRC + 3$	D#	1	1	1	1	0	0	0	0	0	F	0	–
			$nRC + 4$	D#	1	1	1	1	0	0	0	0	0	F	0	–
			Repeat cycles $nRC + 1$ through $nRC + 4$ until $nRC + nRCD - 1$; truncate if needed													
			$nRC + nRCD$	RD	0	1	0	1	0	0	0	0	0	F	0	00110011
			Repeat cycles $nRC + 1$ through $nRC + 4$ until $nRC + nRAS - 1$; truncate if needed													
			$nRC + nRAS$	PRE	0	0	1	0	0	0	0	0	0	F	0	–
			Repeat cycle $nRC + 1$ through $nRC + 4$ until $2 \times nRC - 1$; truncate if needed													
		1	$2 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 1												
		2	$4 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 2												
		3	$6 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 3												
		4	$8 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 4												
		5	$10 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 5												
		6	$12 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 6												
		7	$14 \times nRC$	Repeat sub-loop 0, use BA[2:0] = 7												

- Notes :
1. DQ, DQS, DQS# are midlevel unless driven as required by the RD command.
 2. DM is LOW.
 3. Burst sequence is driven on each DQ signal by the RD command.
 4. Only selected bank (single) active.

Table 7 : DDR3L IDD Measurement Conditions for Power-Down Currents

Name	I _{DD2P0} Precharge Power-Down Current (Slow Exit) ¹	I _{DD2P1} Precharge Power-Down Current (Fast Exit) ¹	I _{DD2Q} Precharge Quiet Standby Current	I _{DD3P} Active Power-Down Current
Timing pattern	N/A	N/A	N/A	N/A
CKE	LOW	LOW	HIGH	LOW
External clock	Toggling	Toggling	Toggling	Toggling
t _{CK}	t _{CK} (MIN) I _{DD}	t _{CK} (MIN) I _{DD}	t _{CK} (MIN) I _{DD}	t _{CK} (MIN) I _{DD}
t _{RC}	N/A	N/A	N/A	N/A
t _{RAS}	N/A	N/A	N/A	N/A
t _{RCD}	N/A	N/A	N/A	N/A
t _{RRD}	N/A	N/A	N/A	N/A
t _{RC}	N/A	N/A	N/A	N/A
CL	N/A	N/A	N/A	N/A
AL	N/A	N/A	N/A	N/A
CS#	HIGH	HIGH	HIGH	HIGH
Command inputs	LOW	LOW	LOW	LOW
Row/column addr	LOW	LOW	LOW	LOW
Bank addresses	LOW	LOW	LOW	LOW
DM	LOW	LOW	LOW	LOW
Data I/O	Midlevel	Midlevel	Midlevel	Midlevel
Output buffer DQ, DQS	Enabled	Enabled	Enabled	Enabled
ODT ²	Enabled, off	Enabled, off	Enabled, off	Enabled, off
Burst length	8	8	8	8
Active banks	None	None	None	All
Idle banks	All	All	All	None
Special notes	N/A	N/A	N/A	N/A

Notes : 1. MR0[12] defines DLL on/off behavior during precharge power-down only; DLL on (fast exit, MR0[12] = 1) and DLL off (slow exit, MR0[12] = 0).

2. “Enabled, off” means the MR bits are enabled, but the signal is LOW.

Table 8 : DDR3L IDD2N and IDD3N Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data
Toggling	Static HIGH	0	0	D	1	0	0	0	0	0	0	0	0	0	0	–
			1	D	1	0	0	0	0	0	0	0	0	0	0	–
			2	D#	1	1	1	1	0	0	0	0	0	F	0	–
			3	D#	1	1	1	1	0	0	0	0	0	F	0	–
		1	4–7	Repeat sub-loop 0, use BA[2:0] = 1												
		2	8–11	Repeat sub-loop 0, use BA[2:0] = 2												
		3	12–15	Repeat sub-loop 0, use BA[2:0] = 3												
		4	16–19	Repeat sub-loop 0, use BA[2:0] = 4												
		5	20–23	Repeat sub-loop 0, use BA[2:0] = 5												
		6	24–27	Repeat sub-loop 0, use BA[2:0] = 6												
		7	28–31	Repeat sub-loop 0, use BA[2:0] = 7												

Notes : 1. DQ, DQS, DQS# are midlevel.
 2. DM is LOW.
 3. All banks closed during IDD2N; all banks open during IDD3N.

Table 9 : DDR3L IDD2NT Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data
Toggling	Static HIGH	0	0	D	1	0	0	0	0	0	0	0	0	0	0	–
			1	D	1	0	0	0	0	0	0	0	0	0	0	–
			2	D#	1	1	1	1	0	0	0	0	0	F	0	–
			3	D#	1	1	1	1	0	0	0	0	0	F	0	–
		1	4–7	Repeat sub-loop 0, use BA[2:0] = 1; ODT = 0												
		2	8–11	Repeat sub-loop 0, use BA[2:0] = 2; ODT = 1												
		3	12–15	Repeat sub-loop 0, use BA[2:0] = 3; ODT = 1												
		4	16–19	Repeat sub-loop 0, use BA[2:0] = 4; ODT = 0												
		5	20–23	Repeat sub-loop 0, use BA[2:0] = 5; ODT = 0												
		6	24–27	Repeat sub-loop 0, use BA[2:0] = 6; ODT = 1												
		7	28–31	Repeat sub-loop 0, use BA[2:0] = 7; ODT = 1												

Notes : 1. DQ, DQS, DQS# are midlevel.
 2. DM is LOW.
 3. All banks closed.

Table 10 : DDR3L IDD4R Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data ³
Toggling	Static HIGH	0	0	RD	0	1	0	1	0	0	0	0	0	0	0	00000000
			1	D	1	0	0	0	0	0	0	0	0	0	0	–
			2	D#	1	1	1	1	0	0	0	0	0	0	0	–
			3	D#	1	1	1	1	0	0	0	0	0	0	0	–
			4	RD	0	1	0	1	0	0	0	0	0	F	0	00110011
			5	D	1	0	0	0	0	0	0	0	0	F	0	–
			6	D#	1	1	1	1	0	0	0	0	0	F	0	–
			7	D#	1	1	1	1	0	0	0	0	0	F	0	–
		1	8–15	Repeat sub-loop 0, use BA[2:0] = 1												
		2	16–23	Repeat sub-loop 0, use BA[2:0] = 2												
		3	24–31	Repeat sub-loop 0, use BA[2:0] = 3												
		4	32–39	Repeat sub-loop 0, use BA[2:0] = 4												
		5	40–47	Repeat sub-loop 0, use BA[2:0] = 5												
		6	48–55	Repeat sub-loop 0, use BA[2:0] = 6												
		7	56–63	Repeat sub-loop 0, use BA[2:0] = 7												

- Notes :
1. DQ, DQS, DQS# are midlevel when not driving in burst sequence.
 2. DM is LOW.
 3. Burst sequence is driven on each DQ signal by the RD command.
 4. All banks open.

Table 11 : DDR3L IDD4W Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data ⁴
Toggling	Static HIGH	0	0	WR	0	1	0	0	1	0	0	0	0	0	0	00000000
			1	D	1	0	0	0	1	0	0	0	0	0	0	–
			2	D#	1	1	1	1	1	0	0	0	0	0	0	–
			3	D#	1	1	1	1	1	0	0	0	0	0	0	–
			4	WR	0	1	0	0	1	0	0	0	0	F	0	00110011
			5	D	1	0	0	0	1	0	0	0	0	F	0	–
			6	D#	1	1	1	1	1	0	0	0	0	F	0	–
			7	D#	1	1	1	1	1	0	0	0	0	F	0	–
		1	8–15	Repeat sub-loop 0, use BA[2:0] = 1												
		2	16–23	Repeat sub-loop 0, use BA[2:0] = 2												
		3	24–31	Repeat sub-loop 0, use BA[2:0] = 3												
		4	32–39	Repeat sub-loop 0, use BA[2:0] = 4												
		5	40–47	Repeat sub-loop 0, use BA[2:0] = 5												
		6	48–55	Repeat sub-loop 0, use BA[2:0] = 6												
		7	56–63	Repeat sub-loop 0, use BA[2:0] = 7												

Notes : 1. DQ, DQS, DQS# are midlevel when not driving in burst sequence.
2. DM is LOW.
3. Burst sequence is driven on each DQ signal by the WR command.
4. All banks open.

Table 12 : DDR3L IDD5B Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data
Toggling	Static HIGH	0	0	REF	0	0	0	1	0	0	0	0	0	0	0	—
		1a	1	D	1	0	0	0	0	0	0	0	0	0	0	—
			2	D	1	0	0	0	0	0	0	0	0	0	0	—
			3	D#	1	1	1	1	0	0	0	0	0	F	0	—
			4	D#	1	1	1	1	0	0	0	0	0	F	0	—
		1b	5–8	Repeat sub-loop 1a, use BA[2:0] = 1												
		1c	9–12	Repeat sub-loop 1a, use BA[2:0] = 2												
		1d	13–16	Repeat sub-loop 1a, use BA[2:0] = 3												
		1e	17–20	Repeat sub-loop 1a, use BA[2:0] = 4												
		1f	21–24	Repeat sub-loop 1a, use BA[2:0] = 5												
		1g	25–28	Repeat sub-loop 1a, use BA[2:0] = 6												
		1h	29–32	Repeat sub-loop 1a, use BA[2:0] = 7												
		2	33– n RFC - 1	Repeat sub-loop 1a through 1h until n RFC - 1; truncate if needed												

Notes : 1. DQ, DQS, DQS# are midlevel.
2. DM is LOW.

Table 13 : DDR3L IDD Measurement Conditions for IDD6, IDD6ET, and IDD8

I_{DD} Test	I_{DD6}: Self Refresh Current Normal Temperature Range T_C = 0°C to +85°C	I_{DD6ET}: Self Refresh Current Extended Temperature Range T_C = 0°C to +95°C	I_{DD8}: Reset²
CKE	LOW	LOW	Midlevel
External clock	Off, CK and CK# = LOW	Off, CK and CK# = LOW	Midlevel
t _{CK}	N/A	N/A	N/A
t _{RC}	N/A	N/A	N/A
t _{RAS}	N/A	N/A	N/A
t _{RCD}	N/A	N/A	N/A
t _{RRD}	N/A	N/A	N/A
t _{RC}	N/A	N/A	N/A
CL	N/A	N/A	N/A
AL	N/A	N/A	N/A
CS#	Midlevel	Midlevel	Midlevel
Command inputs	Midlevel	Midlevel	Midlevel
Row/column addresses	Midlevel	Midlevel	Midlevel
Bank addresses	Midlevel	Midlevel	Midlevel
Data I/O	Midlevel	Midlevel	Midlevel
Output buffer DQ, DQS	Enabled	Enabled	Midlevel
ODT ¹	Enabled, midlevel	Enabled, midlevel	Midlevel
Burst length	N/A	N/A	N/A
Active banks	N/A	N/A	None
Idle banks	N/A	N/A	All
SRT	Disabled (normal)	Enabled (extended)	N/A
ASR	Disabled	Disabled	N/A

Notes : 1. "Enabled, midlevel" means the MR command is enabled, but the signal is midlevel.

2. During a cold boot RESET (initialization), current reading is valid after power is stable and RESET has been LOW for 1ms; During a warm boot RESET (while operating), current reading is valid after RESET has been LOW for 200ns + tRFC.

Table 14 : DDR3L IDD7 Measurement Loop

CK, CK#	CKE	Sub-Loop	Cycle Number	Command	CS#	RAS#	CAS#	WE#	ODT	BA[2:0]	A[15:11]	A[10]	A[9:7]	A[6:3]	A[2:0]	Data ³
Toggling	Static HIGH	0	0	ACT	0	0	1	1	0	0	0	0	0	0	0	–
			1	RDA	0	1	0	1	0	0	0	1	0	0	0	00000000
			2	D	1	0	0	0	0	0	0	0	0	0	0	–
			3	Repeat cycle 2 until $nRRD - 1$												
		1	$nRRD$	ACT	0	0	1	1	0	1	0	0	0	F	0	–
			$nRRD + 1$	RDA	0	1	0	1	0	1	0	1	0	F	0	00110011
			$nRRD + 2$	D	1	0	0	0	0	1	0	0	0	F	0	–
			$nRRD + 3$	Repeat cycle $nRRD + 2$ until $2 \times nRRD - 1$												
		2	$2 \times nRRD$	Repeat sub-loop 0, use BA[2:0] = 2												
		3	$3 \times nRRD$	Repeat sub-loop 1, use BA[2:0] = 3												
		4	$4 \times nRRD$	D	1	0	0	0	0	3	0	0	0	F	0	–
			$4 \times nRRD + 1$	Repeat cycle $4 \times nRRD$ until $nFAW - 1$, if needed												
		5	$nFAW$	Repeat sub-loop 0, use BA[2:0] = 4												
		6	$nFAW + nRRD$	Repeat sub-loop 1, use BA[2:0] = 5												
		7	$nFAW + 2 \times nRRD$	Repeat sub-loop 0, use BA[2:0] = 6												
		8	$nFAW + 3 \times nRRD$	Repeat sub-loop 1, use BA[2:0] = 7												
		9	$nFAW + 4 \times nRRD$	D	1	0	0	0	0	7	0	0	0	F	0	–
			$nFAW + 4 \times nRRD + 1$	Repeat cycle $nFAW + 4 \times nRRD$ until $2 \times nFAW - 1$, if needed												
		10	$2 \times nFAW$	ACT	0	0	1	1	0	0	0	0	0	F	0	–
			$2 \times nFAW + 1$	RDA	0	1	0	1	0	0	0	1	0	F	0	00110011
			$2 \times nFAW + 2$	D	1	0	0	0	0	0	0	0	0	F	0	–
			$2 \times nFAW + 3$	Repeat cycle $2 \times nFAW + 2$ until $2 \times nFAW + nRRD - 1$												
		11	$2 \times nFAW + nRRD$	ACT	0	0	1	1	0	1	0	0	0	0	0	–
			$2 \times nFAW + nRRD + 1$	RDA	0	1	0	1	0	1	0	1	0	0	0	00000000
			$2 \times nFAW + nRRD + 2$	D	1	0	0	0	0	1	0	0	0	0	0	–
			$2 \times nFAW + nRRD + 3$	Repeat cycle $2 \times nFAW + nRRD + 2$ until $2 \times nFAW + 2 \times nRRD - 1$												
		12	$2 \times nFAW + 2 \times nRRD$	Repeat sub-loop 10, use BA[2:0] = 2												
		13	$2 \times nFAW + 3 \times nRRD$	Repeat sub-loop 11, use BA[2:0] = 3												
		14	$2 \times nFAW + 4 \times nRRD$	D	1	0	0	0	0	3	0	0	0	0	0	–
			$2 \times nFAW + 4 \times nRRD + 1$	Repeat cycle $2 \times nFAW + 4 \times nRRD$ until $3 \times nFAW - 1$, if needed												
		15	$3 \times nFAW$	Repeat sub-loop 10, use BA[2:0] = 4												
		16	$3 \times nFAW + nRRD$	Repeat sub-loop 11, use BA[2:0] = 5												
		17	$3 \times nFAW + 2 \times nRRD$	Repeat sub-loop 10, use BA[2:0] = 6												
		18	$3 \times nFAW + 3 \times nRRD$	Repeat sub-loop 11, use BA[2:0] = 7												
		19	$3 \times nFAW + 4 \times nRRD$	D	1	0	0	0	0	7	0	0	0	0	0	–
			$3 \times nFAW + 4 \times nRRD + 1$	Repeat cycle $3 \times nFAW + 4 \times nRRD$ until $4 \times nFAW - 1$, if needed												

- Notes : 1. DQ, DQS, DQS# are midlevel unless driven as required by the RD command.
 2. DM is LOW.
 3. Burst sequence is driven on each DQ signal by the RD command.
 4. AL = CL-1.

Electrical Characteristics – IDD Specifications

Table 15 : IDD Maximum Limits

Speed Bin			DDR3 -1600	DDR3 -1866	Units	Notes
Parameter	Symbol	Width				
Operating current 0: One bank ACTIVATE-to-RECHARGE	IDD0	X16	105	115	mA	1, 2
Operating current 1: One bank ACTIVATE-to-READ to-PRECHARGE	IDD1	X16	120	130	mA	1, 2
Precharge power-down current; Slow exit	IDD2PD (slow)	All	14	14	mA	1, 2
Precharge power-down current; Fast exit	IDD2P1 (fast)	All	35	40	mA	1, 2
Precharge quiet standby Current	IDD2Q	All	65	70	mA	1, 2
Precharge standby current	IDD2N	All	70	75	mA	1, 2
Precharge standby ODT current	IDD2NT	X16	70	80	mA	1, 2
Active power-down current	IDD3P	All	60	65	mA	1, 2
Active standby current	IDD3N	X16	125	140	mA	1, 2
Burst read operating current	IDD4R	X16	180	200	mA	1, 2
Burst write operating current	IDD4W	X16	220	240	mA	1, 2
Burst refresh current	IDD5B	All	150	155	mA	1, 2
Room temperature self refresh	IDD6	All	11	11	mA	1, 2, 3
Extended temperature self refresh	IDD6ET	All	12	12	mA	1, 4
All banks interleaved read current	IDD7	X16	200	215	mA	1, 2
Reset current	IDD8	All	11	11	mA	1, 2

Notes : 1. TC = 85°C; SRT and ASR are disabled.

2. Enabling ASR could increase IDD_x by up to an additional 2mA.

3. Restricted to TC (MAX) = 85°C.

4. TC = 85°C; ASR and ODT are disabled; SRT is enabled.

5. The IDD values must be derated (increased) on IT-option and AT-option devices when operated outside of the range 0°C ≤ TC ≤ +85°C :

- When TC < 0°C: IDD2P0, IDD2P1 and IDD3P must be derated by 4%; IDD4R and IDD4W must be derated by 2%; and IDD6 and IDD7 must be derated by 7%.

- When TC > 85°C: IDD0, IDD1, IDD2N, IDD2NT, IDD2Q, IDD3N, IDD3P, IDD4R, IDD4W, and IDD5B must be derated by 2%; IDD2Px must be derated by 30%.

Electrical Specifications – DC and AC

DC Operating Conditions

Table 16 : DDR3L 1.35V DC Electrical Characteristics and Operating Conditions

All voltages are referenced to VSS

Parameter/Condition	Symbol	Min	Nom	Max	Unit	Notes
Supply voltage	V_{DD}	1.283	1.35	1.45	V	1-7
I/O supply voltage	V_{DDQ}	1.283	1.35	1.45	V	1-7
Input leakage current Any input $0V \leq V_{IN} \leq V_{DD}$, V_{REF} pin $0V \leq V_{IN} \leq 1.1V$ (All other pins not under test = 0V)	I_I	-2	-	2	μA	
V_{REF} supply leakage current $V_{REFDQ} = V_{DD}/2$ or $V_{REFCA} = V_{DD}/2$ (All other pins not under test = 0V)	I_{VREF}	-1	-	1	μA	8, 9

- Notes :
1. VDD and VDDQ must track one another. VDDQ must be $\leq V_{DD}$. VSS = VSSQ.
 2. VDD and VDDQ may include AC noise of $\pm 50mV$ (250 kHz to 20 MHz) in addition to the DC (0 Hz to 250 kHz) specifications. VDD and VDDQ must be at same level for valid AC timing parameters.
 3. Maximum DC value may not be greater than 1.425V. The DC value is the linear average of VDD/VDDQ(t) over a very long period of time (for example, 1 second).
 4. Under these supply voltages, the device operates to this DDR3L specification.
 5. If the maximum limit is exceeded, input levels shall be governed by DDR3L specifications.
 6. Under 1.5V operation, this DDR3L device operates in accordance with the DDR3L specifications under the same speed timings as defined for this device.
 7. Once initialized for DDR3L operation, DDR3L operation may only be used if the device is in reset while VDD and VDDQ are changed for DDR3L operation (see VDD Voltage Switching).
 8. The minimum limit requirement is for testing purposes. The leakage current on the VREF pin should be minimal.
 9. VREF (see Table 17).

Input Operating Conditions

Table 17 : DDR3L 1.35V DC Electrical Characteristics and Input Conditions

All voltages are referenced to VSS

Parameter/Condition	Symbol	Min	Nom	Max	Unit	Notes
V_{IN} low; DC/commands/address busses	V_{IL}	V_{SS}	n/a	See Table 18	V	
V_{IN} high; DC/commands/address busses	V_{IH}	See Table 18	n/a	V_{DD}	V	
Input reference voltage command/address bus	$V_{REFCA}(DC)$	$0.49 \times V_{DD}$	$0.5 \times V_{DD}$	$0.51 \times V_{DD}$	V	1, 2
I/O reference voltage DQ bus	$V_{REFDQ}(DC)$	$0.49 \times V_{DD}$	$0.5 \times V_{DD}$	$0.51 \times V_{DD}$	V	2, 3
I/O reference voltage DQ bus in SELF REFRESH	$V_{REFDQ}(SR)$	V_{SS}	$0.5 \times V_{DD}$	V_{DD}	V	4
Command/address termination voltage (system level, not direct DRAM input)	V_{TT}	-	$0.5 \times V_{DDQ}$	-	V	5

- Notes :
1. VREFCA(DC) is expected to be approximately $0.5 \times V_{DD}$ and to track variations in the DC level. Externally generated peak noise (non-common mode) on VREFCA may not exceed $\pm 1\% \times V_{DD}$ around the VREFCA(DC) value. Peak-to-peak AC noise on VREFCA should not exceed $\pm 2\%$ of VREFCA(DC).
 2. DC values are determined to be less than 20 MHz in frequency. DRAM must meet specifications if the DRAM induces additional AC noise greater than 20 MHz in frequency.

3. VREFDQ(DC) is expected to be approximately $0.5 \times VDD$ and to track variations in the DC level. Externally generated peak noise(non-common mode) on VREFDQ may not exceed $\pm 1\% \times VDD$ around the VREFDQ(DC) value. Peak-to-peak AC noise on VREFDQ should not exceed $\pm 2\%$ of VREFDQ(DC).
4. VREFDQ(DC) may transition to VREFDQ(SR) and back to VREFDQ(DC) when in SELF REFRESH, within restrictions outlined in the SELF REFRESH section.
5. VTT is not applied directly to the device. VTT is a system supply for signal termination resistors. Minimum and maximum values are system-dependent.

Table 18 : DDR3L 1.35V Input Switching Conditions – Command and Address

Parameter/Condition	Symbol	DDR3L-800/1066	DDR3L-1333/1600	DDR3L-1866	Unit
Command and Address					
Input high AC voltage: Logic 1	V _{IH} (AC160)min ⁵	160	160	–	mV
	V _{IH} (AC135)min ⁵	135	135	135	
	V _{IH} (AC125)min ⁵	–	–	125	
Input high DC voltage: Logic 1	V _{IH} (DC90)min	90	90	90	
Input low DC voltage: Logic 0	V _{IL} (DC90)max	– 90	– 90	– 90	
Input low AC voltage: Logic 0	V _{IL} (AC125)max ⁵	–	–	–125	
	V _{IL} (AC135)max ⁵	–135	–135	–135	
	V _{IL} (AC160)max ⁵	–160	–160	–	
DQ and DM					
Input high AC voltage: Logic 1	V _{IH} (AC160)min ⁵	160	160	–	mV
	V _{IH} (AC135)min ⁵	135	135	135	
	V _{IH} (AC125)min ⁵	–	–	130	
Input high DC voltage: Logic 1	V _{IH} (DC90)min	90	90	90	
Input low DC voltage: Logic 0	V _{IL} (DC90)max	– 90	– 90	– 90	
Input low AC voltage: Logic 0	V _{IL} (AC125)max ⁵	–	–	–130	
	V _{IL} (AC135)max ⁵	–135	–135	–135	
	V _{IL} (AC160)max ⁵	–160	–160	–	

- Notes :
1. All voltages are referenced to V_{REF} . V_{REF} is V_{REFCA} for control, command, and address. All slew rates and setup/hold times are specified at the DRAM ball. V_{REF} is V_{REFDQ} for DQ and DM inputs.
 2. Input setup timing parameters (tIS and tDS) are referenced at $V_{IL(AC)} / V_{IH(AC)}$, not $V_{REF(DC)}$.
 3. Input hold timing parameters (tIH and tDH) are referenced at $V_{IL(DC)} / V_{IH(DC)}$, not $V_{REF(DC)}$.
 4. Single-ended input slew rate = 1 V/ns; maximum input voltage swing under test is 900mV (peak-to-peak).
 5. When two $V_{IH(AC)}$ values (and two corresponding $V_{IL(AC)}$ values) are listed for a specific speed bin, the user may choose either value for the input AC level. Whichever value is used, the associated setup time for that AC level must also be used. Additionally, one $V_{IH(AC)}$ value may be used for address/command inputs and the other $V_{IH(AC)}$ value may be used for data inputs.

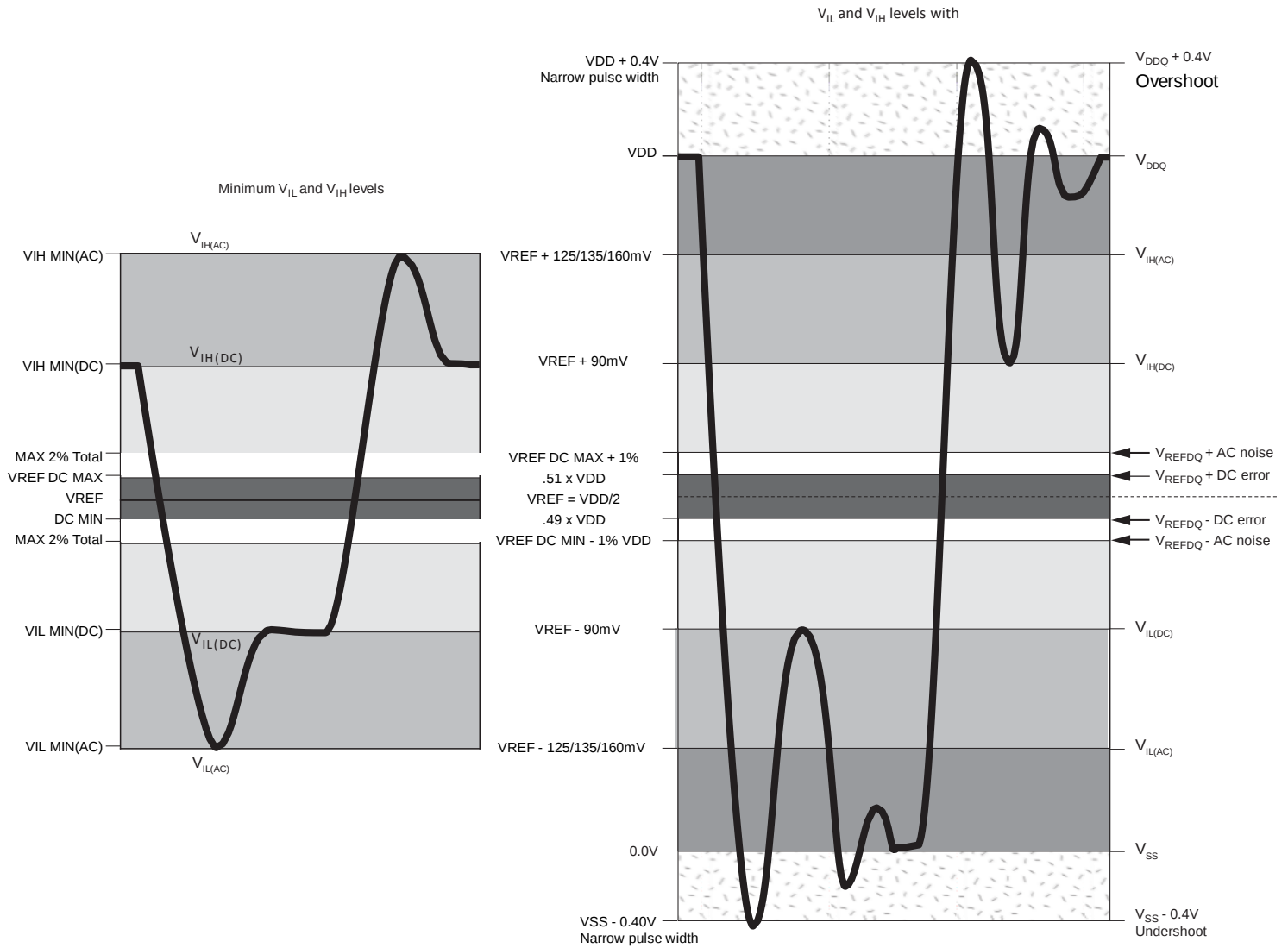
For example, for DDR3-800, two input AC levels are defined: $V_{IH(AC160),min}$ and $V_{IH(AC135),min}$ (corresponding $V_{IL(AC160),min}$ and $V_{IL(AC135),min}$). For DDR3-800, the address/command inputs must use either $V_{IH(AC160),min}$ with tIS(AC160) of 210ps or $V_{IH(AC150),min}$ with tIS(AC135) of 365ps; independently, the data inputs must use either $V_{IH(AC160),min}$ with tDS(AC160) of 75ps or $V_{IH(AC150),min}$ with tDS(AC150) of 125ps.

Table 19 : DDR3L 1.35V Differential Input Operating Conditions (CK, CK# and DQS, DQS#)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Differential input voltage logic high - slew	$V_{IH,diff(AC)slew}$	180	N/A	mV	4
Differential input voltage logic low - slew	$V_{IL,diff(AC)slew}$	n/a	-180	mV	4
Differential input voltage logic high	$V_{IH,diff(AC)}$	$2 \times (V_{IH(AC)} - V_{REF})$	V_{DD}/V_{DDQ}	mV	5
Differential input voltage logic low	$V_{IL,diff(AC)}$	V_{SS}/V_{SSQ}	$2 \times (V_{IL(AC)} - V_{REF})$	mV	6
Differential input crossing voltage relative to $V_{DD}/2$ for DQS, DQS#; CK, CK#	V_{IX}	$V_{REF(DC)} - 150$	$V_{REF(DC)} + 150$	mV	5,7,9
Differential input crossing voltage relative to $V_{DD}/2$ for CK, CK#	$V_{IX(175)}$	$V_{REF(DC)} - 175$	$V_{REF(DC)} + 175$	mV	5,7-9
Single-ended high level for strobes	V_{SEH}	$V_{DDQ}/2 + 160$	V_{DDQ}	mV	5
Single-ended high level for CK, CK#		$V_{DD}/2 + 160$	V_{DD}	mV	5
Single-ended low level for strobes	V_{SEL}	V_{SSQ}	$V_{DDQ}/2 - 160$	mV	6
Single-ended low level for CK, CK#		V_{SS}	$V_{DD}/2 - 160$	mV	6

- Notes :
1. Clock is referenced to VDD and VSS. Data strobe is referenced to VDDQ and VSSQ.
 2. Reference is $V_{REFCA(DC)}$ for clock and $V_{REFDQ(DC)}$ for strobe.
 3. Differential input slew rate = 2 V/ns
 4. Defines slew rate reference points, relative to input crossing voltages.
 5. Minimum DC limit is relative to single-ended signals; overshoot specifications are applicable.
 6. Maximum DC limit is relative to single-ended signals; undershoot specifications are applicable.
 7. The typical value of $V_{IX(AC)}$ is expected to be about $0.5 \times V_{DD}$ of the transmitting device, and $V_{IX(AC)}$ is expected to track variations in VDD. $V_{IX(AC)}$ indicates the voltage at which differential input signals must cross.
 8. The V_{IX} extended range ($\pm 175mV$) is allowed only for the clock; this V_{IX} extended range is only allowed when the following conditions are met: The single-ended input signals are monotonic, have the single-ended swing V_{SEL} , V_{SEH} of at least $V_{DD}/2 \pm 250mV$, and the differential slew rate of CK, CK# is greater than 3 V/ns.
 9. V_{IX} must provide 25mV (single-ended) of the voltages separation.

Figure 2 : DDR3L 1.35V Input Signal



Notes : 1. Numbers in diagrams reflect nominal values.

DDR3L 1.35V AC Overshoot/Undershoot Specification

Table 20 : DDR3L Control and Address Pins

Parameter	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866
Maximum peak amplitude allowed for overshoot area (see Figure 3)	0.4V	0.4V	0.4V	0.4V	0.4V
Maximum peak amplitude allowed for undershoot area (see Figure 4)	0.4V	0.4V	0.4V	0.4V	0.4V
Maximum overshoot area above V_{DD} (see Figure 3)	0.67 Vns	0.5 Vns	0.4 Vns	0.33 Vns	0.28 Vns
Maximum undershoot area below V_{SS} (see Figure 4)	0.67 Vns	0.5 Vns	0.4 Vns	0.33 Vns	0.28 Vns

Table 21 : Clock, Data, Strobe, and Mask Pins

Parameter	DDR3-800	DDR3-1066	DDR3-1333	DDR3-1600	DDR3-1866
Maximum peak amplitude allowed for overshoot area (see Figure 3)	0.4V	0.4V	0.4V	0.4V	0.4V
Maximum peak amplitude allowed for undershoot area (see Figure 4)	0.4V	0.4V	0.4V	0.4V	0.4V
Maximum overshoot area above V_{DD}/V_{DDQ} (see Figure 3)	0.25 Vns	0.19 Vns	0.15 Vns	0.13 Vns	0.11 Vns
Maximum undershoot area below V_{SS}/V_{SSQ} (see Figure 4)	0.25 Vns	0.19 Vns	0.15 Vns	0.13 Vns	0.11 Vns

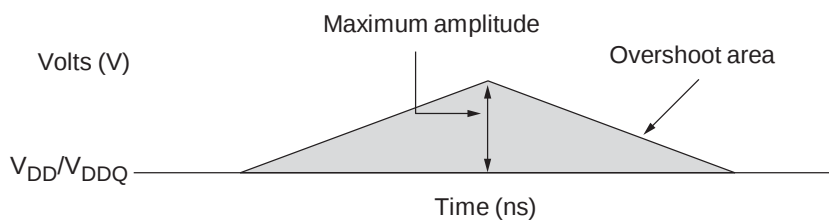
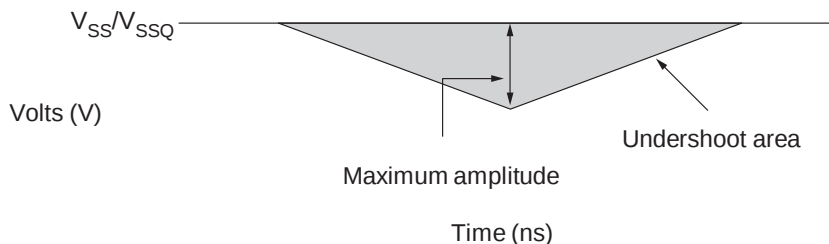
Figure 3 : Overshoot

Figure 4 : Undershoot


Figure 5 : V_{IX} for Differential Signals

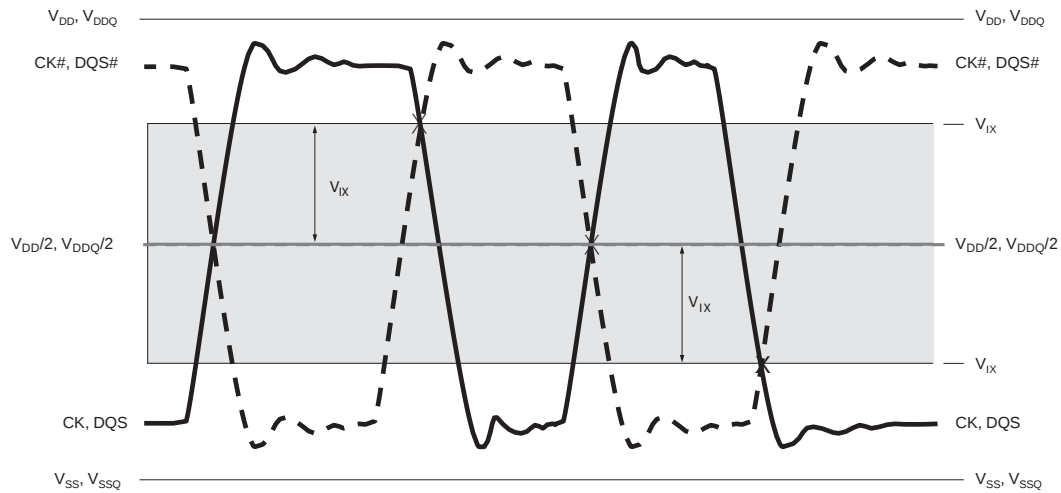


Figure 6 : Single-Ended Requirements for Differential Signals

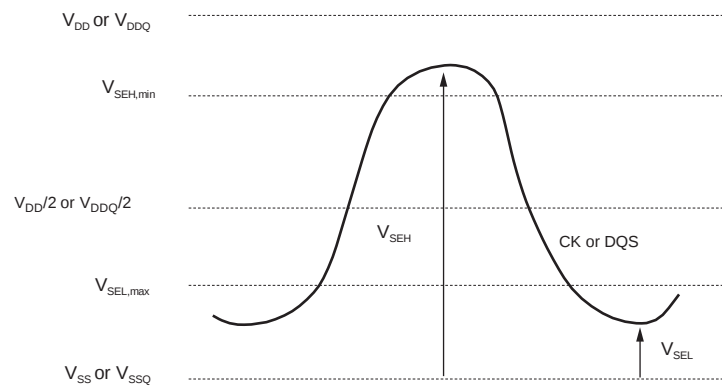


Figure 7 : Definition of Differential AC-Swing and tDVAC

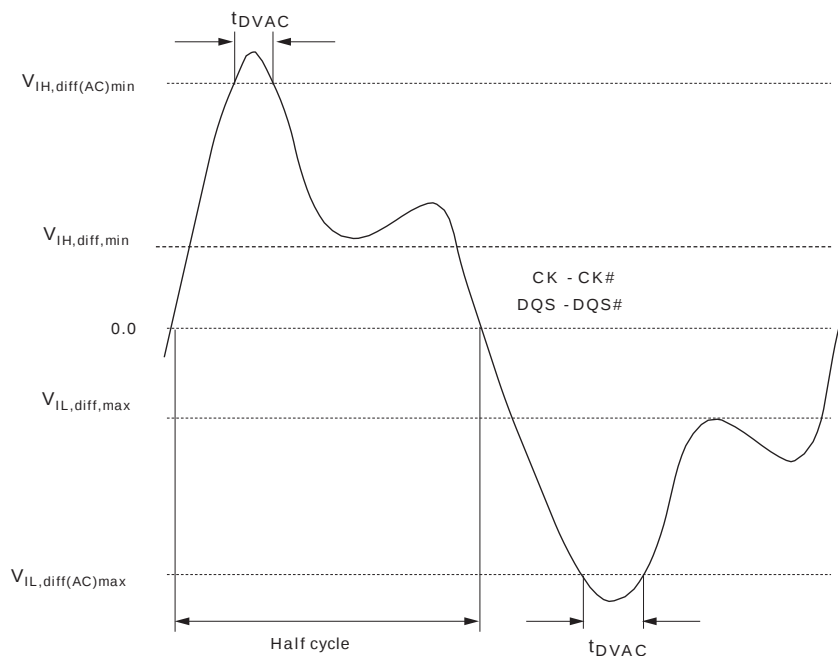


Table 22 : DDR3L 1.35V - Minimum Required Time tDVAC for CK/CK#, DQS/DQS# Differential for AC Ringback

Slew Rate (V/ns)	DDR3L-800/1066/1333/1600		DDR3L-1866		
	tDVAC at 320mV (ps)	tDVAC at 270mV (ps)	tDVAC at 270mV (ps)	tDVAC at 250mV (ps)	tDVAC at 260mV (ps)
>4.0	189	201	163	168	176
4.0	189	201	163	168	176
3.0	162	179	140	147	154
2.0	109	134	95	105	111
1.9	91	119	80	91	97
1.6	69	100	62	74	78
1.4	40	76	37	52	55
1.2	Note 1	44	5	22	24
1.0	Note 1				
<1.0	Note 1				

Note: 1. Rising input signal shall become equal to or greater than VIH(AC) level and Falling input signal shall become equal to or less than VIL(AC) level.

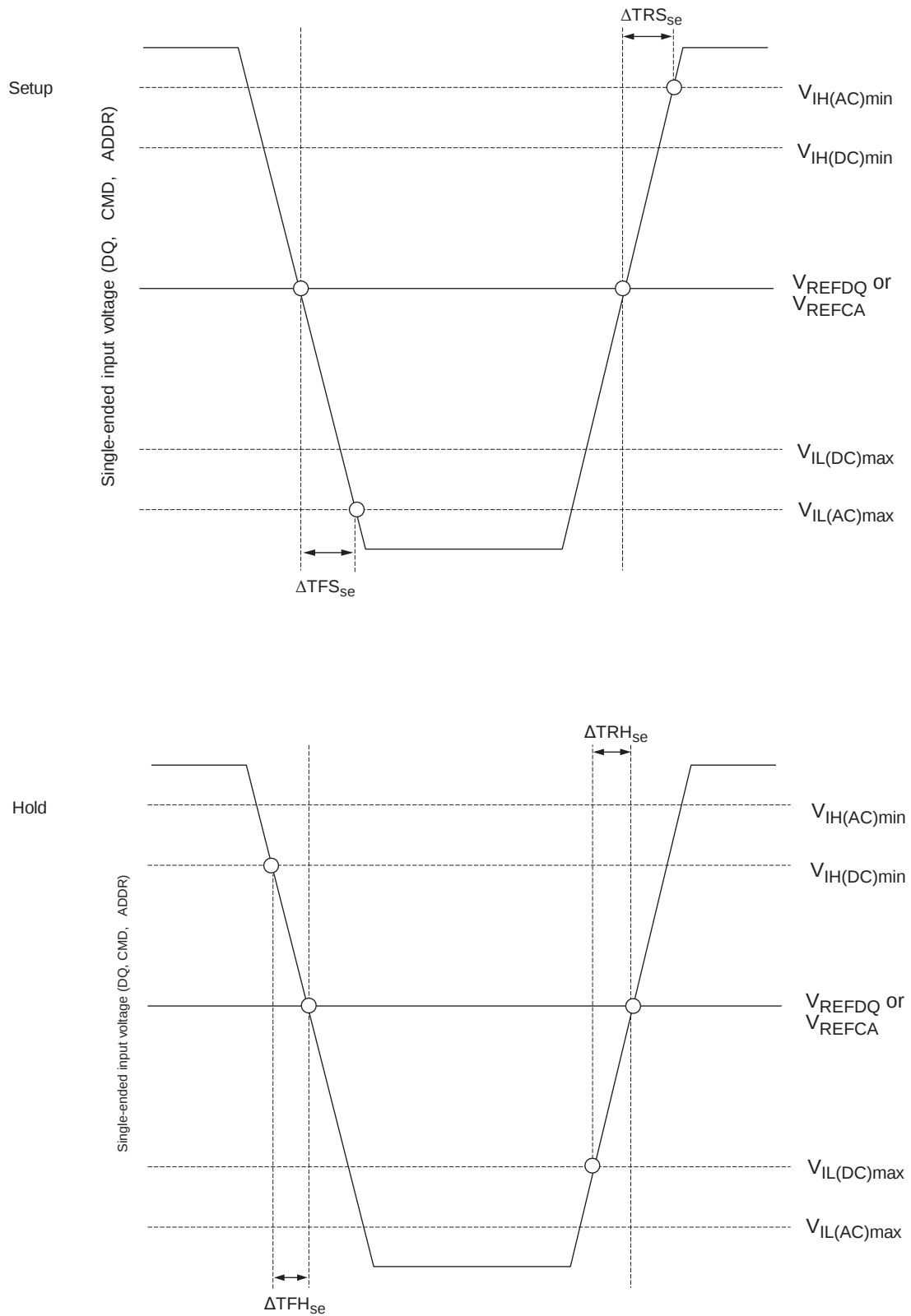
DDR3L 1.35V Slew Rate Definitions for Single-Ended Input Signals

Setup (tIS and tDS) nominal slew rate for a rising signal is defined as the slew rate between the last crossing of VREF and the first crossing of VIH(AC)min. Setup (tIS and tDS) nominal slew rate for a falling signal is defined as the slew rate between the last crossing of VREF and the first crossing of VIL(AC)max. Hold (tIH and tDH) nominal slew rate for a rising signal is defined as the slew rate between the last crossing of VIL(DC)max and the first crossing of VREF. Hold (tIH and tDH) nominal slew rate for a falling signal is defined as the slew rate between the last crossing of VIH(DC)min and the first crossing of VREF.

Table 23 : Single-Ended Input Slew Rate Definition

Input Slew Rates (Linear Signals)		Measured		Calculation
Input	Edge	From	To	
Setup	Rising	VREF	VIH(AC)min	$\frac{V_{IH(AC),min} - V_{REF}}{\Delta TRS_{se}}$
	Falling	VREF	VIL(AC)max	$\frac{V_{REF} - V_{IL(AC),max}}{\Delta TFS_{se}}$
Hold	Rising	VIL(DC)max	VREF	$\frac{V_{REF} - V_{IL(DC),max}}{\Delta TFH_{se}}$
	Falling	VIH(DC)min	VREF	$\frac{V_{IH(DC),min} - V_{REF}}{\Delta TRSH_{se}}$

Figure 8 : Nominal Slew Rate Definition for Single-Ended Input Signals



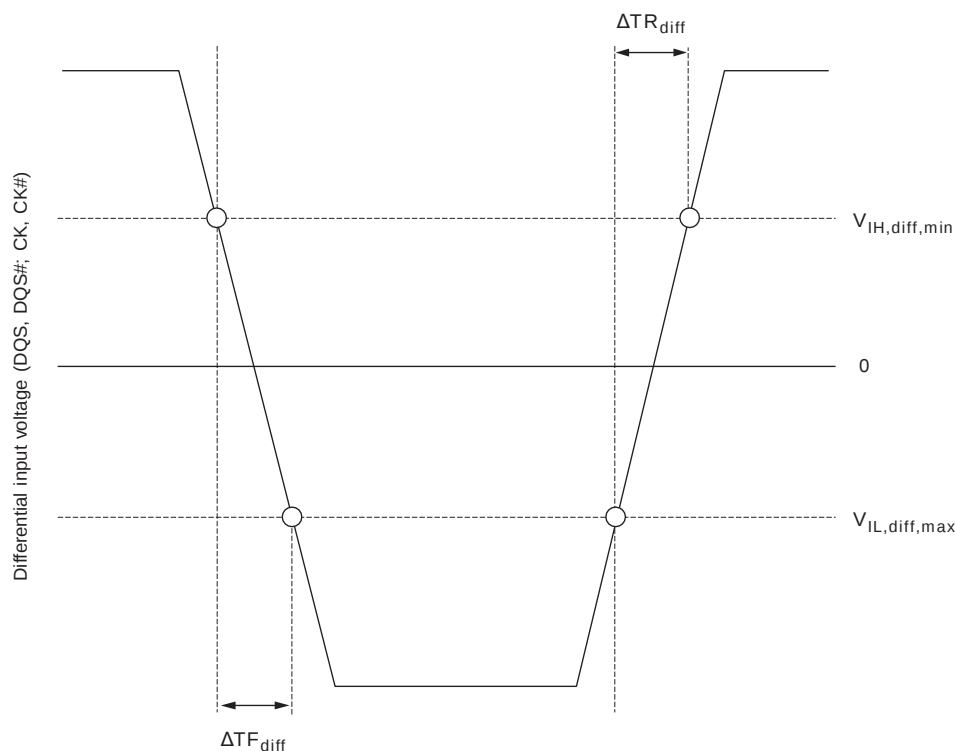
DDR3L 1.35V Slew Rate Definitions for Differential Input Signals

Input slew rate for differential signals (CK, CK# and DQS, DQS#) are defined and measured. The nominal slew rate for a rising signal is defined as the slew rate between $V_{IL,diff,max}$ and $V_{IH,diff,min}$. The nominal slew rate for a falling signal is defined as the slew rate between $V_{IH,diff,min}$ and $V_{IL,diff,max}$.

Table 24 : DDR3L 1.35V Differential Input Slew Rate Definition

Differential Input Slew Rates (Linear Signals)		Measured		Calculation
Input	Edge	From	To	
CK and DQS reference	Rising	$V_{IL,diff,max}$	$V_{IH,diff,min}$	$\frac{V_{IH,diff,min} - V_{IL,diff,max}}{\Delta T_{R,diff}}$
	Falling	$V_{IH,diff,min}$	$V_{IL,diff,max}$	$\frac{V_{IH,diff,min} - V_{IL,diff,max}}{\Delta T_{F,diff}}$

Figure 9 : DDR3L 1.35V Nominal Differential Input Slew Rate Definition for DQS, DQS# and CK, CK#



ODT Characteristics

The ODT effective resistance R_{TT} is defined by MR1[9, 6, and 2]. ODT is applied to the DQ, DM, DQS, DQS#, and TDQS, TDQS# balls (x8 devices only). The ODT target values and a functional representation are listed in Table 25 and Table 26 .

The individual pull-up and pull-down resistors ($R_{TT(PU)}$) and ($R_{TT(PD)}$) are defined as follows:

- $R_{TT(PU)} = (V_{DDQ} - V_{OUT})/|I_{OUT}|$, under the condition that $R_{TT(PD)}$ is turned off
- $R_{TT(PD)} = (V_{OUT})/|I_{OUT}|$, under the condition that $R_{TT(PU)}$ is turned off

Figure 10 : ODT Levels and I-V Characteristics

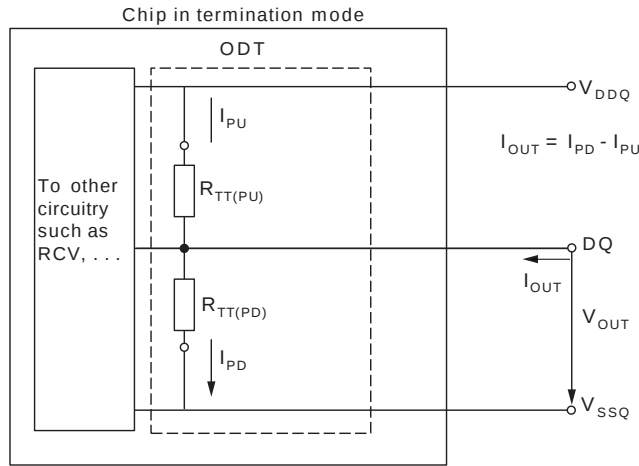


Table 25 : On-Die Termination DC Electrical Characteristics

Parameter/Condition	Symbol	Min	Nom	Max	Unit	Notes
R_{TT} effective impedance	$R_{TT(EFF)}$	See Table 26				1, 2
Deviation of VM with respect to $V_{DDQ}/2$	ΔVM	-5		5	%	1, 2, 3

- Notes :
1. Tolerance limits are applicable after proper ZQ calibration has been performed at a stable temperature and voltage ($V_{DDQ} = V_{DD}$, $V_{SSQ} = V_{SS}$). Refer to ODT Sensitivity if either the temperature or voltage changes after calibration.
 2. Measurement definition for R_{TT} : Apply $V_{IH}(AC)$ to pin under test and measure current $I[V_{IH}(AC)]$, then apply $V_{IL}(AC)$ to pin under test and measure current $I[V_{IL}(AC)]$: $R_{TT} = (V_{IH}(AC) - V_{IL}(AC)) / (I[V_{IH}(AC)] - I[V_{IL}(AC)])$
 3. Measure voltage (VM) at the tested pin with no load : $\Delta VM = ((2 \times VM) / V_{DDQ} - 1) \times 100$
 4. For IT and AT devices, the minimum values are derated by 6% when the device operates between $-40^{\circ}C$ and $0^{\circ}C$ (TC).

1.35V ODT Resistors

Table 26 provides an overview of the ODT DC electrical characteristics. The values provided are not specification requirements; however, they can be used as design guidelines to indicate what R_{TT} is targeted to provide:

- R_{TT} 120 Ω is made up of $R_{TT120(PD240)}$ and $R_{TT120(PU240)}$
- R_{TT} 60 Ω is made up of $R_{TT60(PD120)}$ and $R_{TT60(PU120)}$
- R_{TT} 40 Ω is made up of $R_{TT40(PD80)}$ and $R_{TT40(PU80)}$
- R_{TT} 30 Ω is made up of $R_{TT30(PD60)}$ and $R_{TT30(PU60)}$
- R_{TT} 20 Ω is made up of $R_{TT20(PD40)}$ and $R_{TT20(PU40)}$

Table 26 : 1.35V R_{TT} Effective Impedances

MR1 [9, 6, 2]	R _{TT}	Resistor	V _{OUT}	Min	Nom	Max	Unit
0, 1, 0	120Ω	R _{TT120} (PD240)	0.2 × V _{DDQ}	0.6	1.0	1.15	RZQ/1
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/1
			0.8 × V _{DDQ}	0.9	1.0	1.45	RZQ/1
		R _{TT120} (PU240)	0.2 × V _{DDQ}	0.9	1.0	1.45	RZQ/1
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/1
			0.8 × V _{DDQ}	0.6	1.0	1.15	RZQ/1
	120Ω		V _{IL(AC)} to V _{IH(AC)}	0.9	1.0	1.65	RZQ/2
0, 0, 1	60Ω	R _{TT60} (PD120)	0.2 × V _{DDQ}	0.6	1.0	1.15	RZQ/2
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/2
			0.8 × V _{DDQ}	0.9	1.0	1.45	RZQ/2
		R _{TT60} (PU120)	0.2 × V _{DDQ}	0.9	1.0	1.45	RZQ/2
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/2
			0.8 × V _{DDQ}	0.6	1.0	1.15	RZQ/2
	60Ω		V _{IL(AC)} to V _{IH(AC)}	0.9	1.0	1.65	RZQ/4
0, 1, 1	40Ω	R _{TT40} (PD80)	0.2 × V _{DDQ}	0.6	1.0	1.15	RZQ/3
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/3
			0.8 × V _{DDQ}	0.9	1.0	1.45	RZQ/3
		R _{TT40} (PU80)	0.2 × V _{DDQ}	0.9	1.0	1.45	RZQ/3
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/3
			0.8 × V _{DDQ}	0.6	1.0	1.15	RZQ/3
	40Ω		V _{IL(AC)} to V _{IH(AC)}	0.9	1.0	1.65	RZQ/6
1, 0, 1	30Ω	R _{TT30} (PD60)	0.2 × V _{DDQ}	0.6	1.0	1.15	RZQ/4
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/4
			0.8 × V _{DDQ}	0.9	1.0	1.45	RZQ/4
		R _{TT30} (PU60)	0.2 × V _{DDQ}	0.9	1.0	1.45	RZQ/4
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/4
			0.8 × V _{DDQ}	0.6	1.0	1.15	RZQ/4
	30Ω		V _{IL(AC)} to V _{IH(AC)}	0.9	1.0	1.65	RZQ/8

MR1 [9, 6, 2]	R _{TT}	Resistor	V _{OUT}	Min	Nom	Max	Unit
1, 0, 0	20Ω	R _{TT20(PD40)}	0.2 × V _{DDQ}	0.6	1.0	1.15	RZQ/6
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/6
			0.8 × V _{DDQ}	0.9	1.0	1.45	RZQ/6
		R _{TT20(PU40)}	0.2 × V _{DDQ}	0.9	1.0	1.45	RZQ/6
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/6
			0.8 × V _{DDQ}	0.6	1.0	1.15	RZQ/6
	20Ω	V _{IL(AC)} to V _{IH(AC)}	0.9	1.0	1.65	RZQ/12	

Symbol	Min	Max	Unit
R_{TT}	$0.9 - dR_{TT}dT \times DT - dR_{TT}dV \times DV $	$1.6 + dR_{TT}dT \times DT + dR_{TT}dV \times DV $	RZQ/(2, 4, 6, 8, 12)

Change	Min	Max	Unit
dR _{TT} dT	0	1.5	%/°C
dR _{TT} dV	0	0.15	%/mV

Table 29 : ODT Timing Definitions

Symbol	Begin Point Definition	End Point Definition	Figure
t_{AON}	Rising edge of CK - CK# defined by the end point of ODTLon	Extrapolated point at V_{SSQ}	Figure 12
t_{AOF}	Rising edge of CK - CK# defined by the end point of ODTLoff	Extrapolated point at $V_{RTT,nom}$	Figure 12
t_{AONPD}	Rising edge of CK - CK# with ODT first being registered HIGH	Extrapolated point at V_{SSQ}	Figure 13
t_{AOFPD}	Rising edge of CK - CK# with ODT first being registered LOW	Extrapolated point at $V_{RTT,nom}$	Figure 13
t_{ADC}	Rising edge of CK - CK# defined by the end point of ODTLcnw, ODTLcwn4, or ODTLcwn8	Extrapolated points at $V_{RTT(WR)}$ and $V_{RTT,nom}$	Figure 14

Table 30 : DDR3L(1.35V) Reference Settings for ODT Timing Measurements

Measured Parameter	$R_{TT,nom}$ Setting	$R_{TT(WR)}$ Setting	V_{SW1}	V_{SW2}
t_{AON}	RZQ/4 (60 Ω)	N/A	50mV	100mV
	RZQ/12 (20 Ω)	N/A	100mV	200mV
t_{AOF}	RZQ/4 (60 Ω)	N/A	50mV	100mV
	RZQ/12 (20 Ω)	N/A	100mV	200mV
t_{AONPD}	RZQ/4 (60 Ω)	N/A	50mV	100mV
	RZQ/12 (20 Ω)	N/A	100mV	200mV
t_{AOFPD}	RZQ/4 (60 Ω)	N/A	50mV	100mV
	RZQ/12 (20 Ω)	N/A	100mV	200mV
t_{ADC}	RZQ/12 (20 Ω)	RZQ/2 (120 Ω)	200mV	250mV

Figure 12 : tAON and tAOF Definitions

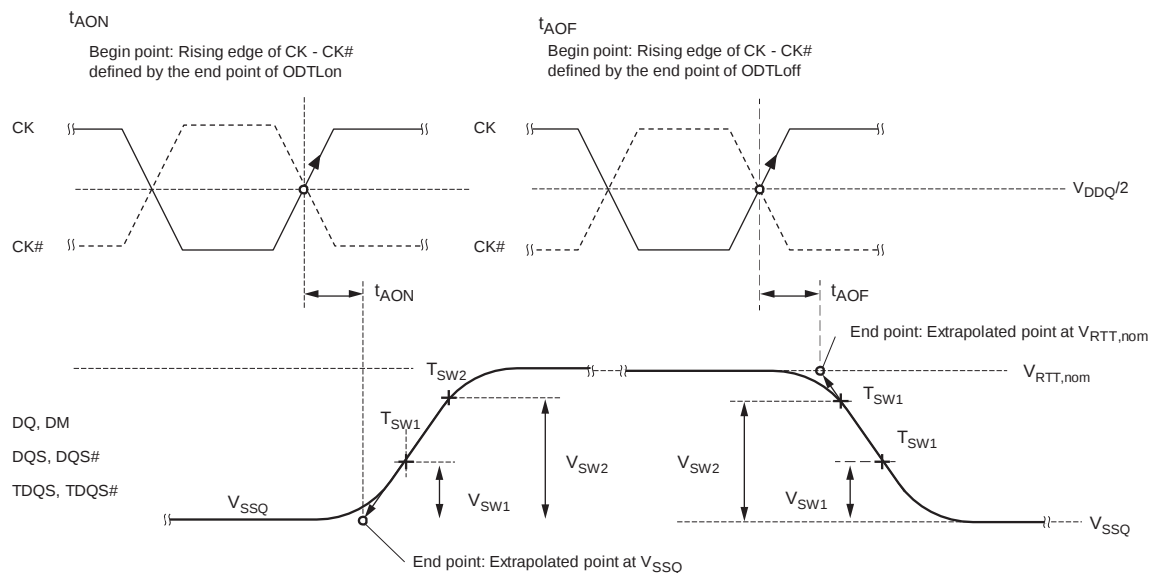


Figure 13 : tAONPD and tAOFPD Definitions

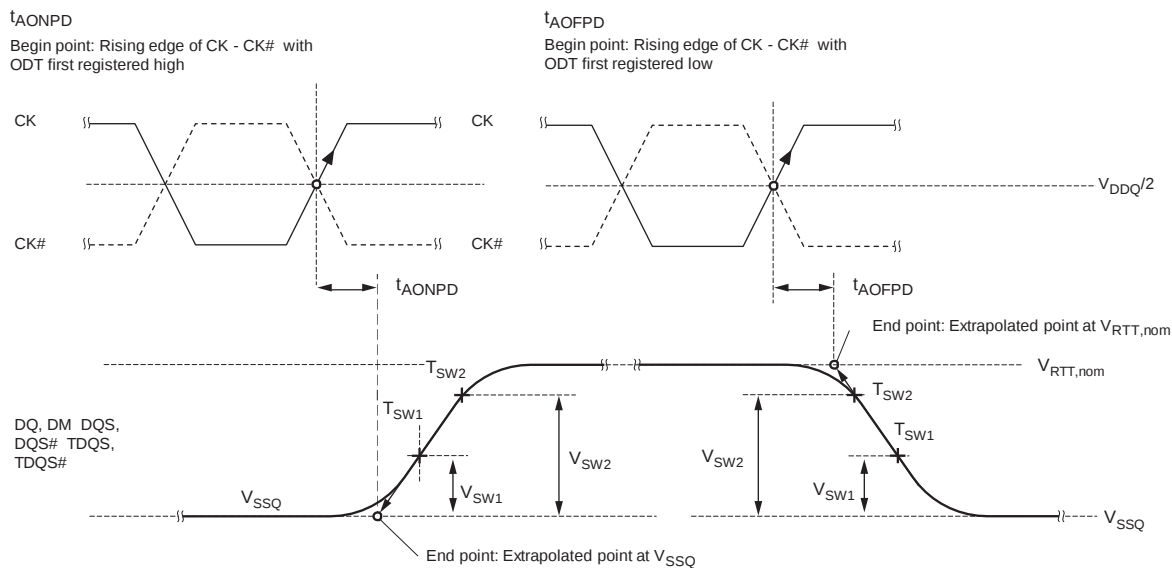
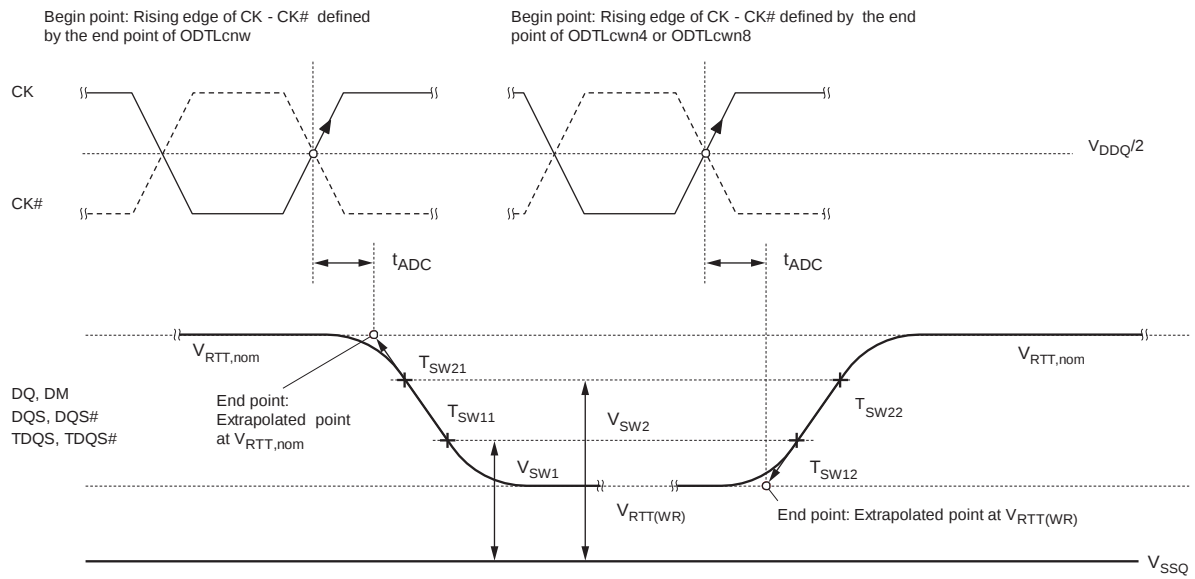


Figure 14 : t_{ADC} Definition



Output Driver Impedance

The output driver impedance is selected by MR1[5,1] during initialization. The selected value is able to maintain the tight tolerances specified if proper ZQ calibration is performed. Output specifications refer to the default output driver unless specifically stated otherwise. A functional representation of the output buffer is shown below.

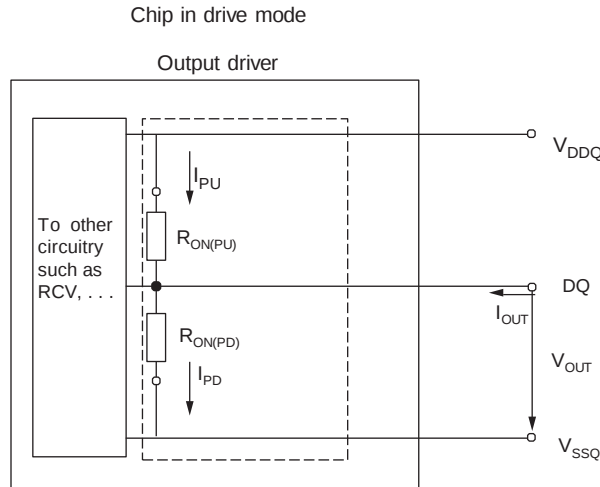
The output driver impedance RON is defined by the value of the external reference resistor RZQ as follows:

- $RON,x = RZQ/y$ (with $RZQ = 240\Omega \pm 1\%$; $x=34\Omega$ or 40Ω with $y = 7$ or 6 , respectively)

The individual pull-up and pull-down resistors RON(PU) and RON(PD) are defined as follows:

- $RON(PU) = (VDDQ - VOUT)/|IOUT|$, when RON(PD) is turned off
- $RON(PD) = (VOUT)/|IOUT|$, when RON(PU) is turned off

Figure 15 : Output Driver



34 Ohm Output Driver Impedance

The 34Ω driver (MR1[5, 1] = 01) is the default driver. Unless otherwise stated, all timings and specifications listed herein apply to the 34Ω driver only. Its impedance RON is defined by the value of the external reference resistor RZQ as follows: $RON34 = RZQ/7$ (with nominal $RZQ = 240\Omega \pm 1\%$) and is actually $34.3\Omega \pm 1\%$.

Table 31 : DDR3L 34 Ohm Driver Impedance Characteristics

MR1[5,1]	R _{ON}	Resistor	V _{OUT}	Min	Nom	Max	Unit
0,1	34.3Ω	R _{ON34} (PD)	0.2 x V _{DDQ}	0.6	1.0	1.15	RZQ/7
			0.5 x V _{DDQ}	0.9	1.0	1.15	RZQ/7
			0.8 x V _{DDQ}	0.9	1.0	1.45	RZQ/7
		R _{ON34} (PU)	0.2 x V _{DDQ}	0.9	1.0	1.45	RZQ/7
			0.5 x V _{DDQ}	0.9	1.0	1.15	RZQ/7
			0.8 x V _{DDQ}	0.6	1.0	1.15	RZQ/7
Pull-up/pull-down mismatch (MM _{PUPD})		V _{IL} (AC) to V _{IH} (AC)	−10%	N/A	10	%	

- Notes:
1. Tolerance limits assume RZQ of $240\Omega \pm 1\%$ and are applicable after proper ZQ calibration has been performed at a stable temperature and voltage: $VDDQ = VDD$; $VSSQ = VSS$). Refer to 34 Ohm Output Driver Sensitivity if either the temperature or the voltage changes after calibration.
 2. Measurement definition for mismatch between pull-up and pull-down (MMPUPD). Measure both RON(PU) and RON(PD) at $0.5 \times VDDQ$: $MMPUPD = ((RON(PU) - RON(PD)) / RON,nom) \times 100$
 3. For IT and AT (1Gb only) devices, the minimum values are derated by 6% when the device operates between -40°C and 0°C (TC). A larger maximum limit will result in slightly lower minimum currents.

DDR3L 34 Ohm Driver

The 34Ω driver's current range has been calculated and summarized in Table 33 VDD=1.35V, Table 34 for VDD =1.45V, and Table 35 for VDD=1.283V. The individual pull-up and pull-down resistors RON34(PD) and RON34(PU) are defined as follows:

- RON34(PD) = (VOUT)/|IOUT|; RON34(PU) is turned off
- RON34(PU) = (VDDQ - VOUT)/|IOUT|; RON34(PD) is turned off

Table 32 : DDR3L 34 Ohm Driver Pull-Up and Pull-Down Impedance Calculations

RON				Min	Nom	Max	Unit
RZQ = 240Ω±1%				237.6	240	242.4	Ω
RZQ/7 = (240Ω±1%)/7				33.9	34.3	34.6	Ω
MR1[5,1]	RON	Resistor	VOUT	Min	Nom	Max	Unit
0, 1	34.3Ω	RON34(PD)	0.2 × VDDQ	20.4	34.3	38.1	Ω
			0.5 × VDDQ	30.5	34.3	38.1	Ω
			0.8 × VDDQ	30.5	34.3	48.5	Ω
		RON34(PU)	0.2 × VDDQ	30.5	34.3	48.5	Ω
			0.5 × VDDQ	30.5	34.3	38.1	Ω
			0.8 × VDDQ	20.4	34.3	38.1	Ω

Table 33 : DDR3L 34 Ohm Driver IOH/IOL Characteristics: VDD = VDDQ = 1.35V

MR1[5,1]	RON	Resistor	VOUT	Max	Nom	Min	Unit
0, 1	34.3Ω	RON34(PD)	IOL @ 0.2 × VDDQ	13.3	7.9	7.1	mA
			IOL @ 0.5 × VDDQ	22.1	19.7	17.7	mA
			IOL @ 0.8 × VDDQ	35.4	31.5	22.3	mA
		RON34(PU)	IOH @ 0.2 × VDDQ	35.4	31.5	22.3	mA
			IOH @ 0.5 × VDDQ	22.1	19.7	17.7	mA
			IOH @ 0.8 × VDDQ	13.3	7.9	7.1	mA

Table 34 : DDR3L 34 Ohm Driver IOH/IOL Characteristics: VDD = VDDQ = 1.45V

MR1[5,1]	RON	Resistor	VOUT	Max	Nom	Min	Unit
0, 1	34.3Ω	RON34(PD)	IOL @ 0.2 × VDDQ	14.2	8.5	7.6	mA
			IOL @ 0.5 × VDDQ	23.7	21.1	19.0	mA
			IOL @ 0.8 × VDDQ	38.0	33.8	23.9	mA
		RON34(PU)	IOH @ 0.2 × VDDQ	38.0	33.8	23.9	mA
			IOH @ 0.5 × VDDQ	23.7	21.1	19.0	mA
			IOH @ 0.8 × VDDQ	14.2	8.5	7.6	mA

Table 35 : DDR3L 34 Ohm Driver IOH/IOL Characteristics: VDD = VDDQ = 1.283V

MR1[5,1]	RON	Resistor	VOUT	Max	Nom	Min	Unit
0, 1	34.3Ω	RON34(PD)	IOL @ 0.2 × VDDQ	12.6	7.5	6.7	mA
			IOL @ 0.5 × VDDQ	21.0	18.7	16.8	mA
			IOL @ 0.8 × VDDQ	33.6	29.9	21.2	mA
		RON34(PU)	IOH @ 0.2 × VDDQ	33.6	29.9	21.2	mA
			IOH @ 0.5 × VDDQ	21.0	18.7	16.8	mA
			IOH @ 0.8 × VDDQ	12.6	7.5	6.7	mA

DDR3L 34 Ohm Output Driver Sensitivity

If either the temperature or the voltage changes after ZQ calibration, then the tolerance limits listed in Table 31 can be expected to widen according to Table 36 and Table 37.

Table 36 : DDR3L 34 Ohm Output Driver Sensitivity Definition

Symbol	Min	Max	Unit
$R_{ON(PD)} @ 0.2 \times V_{DDQ}$	$0.6 - dR_{ONdTL} \times \Delta T - dR_{ONdVL} \times \Delta V $	$1.1 + dR_{ONdTL} \times \Delta T + dR_{ONdVL} \times \Delta V $	RZQ/7
$R_{ON(PD)} @ 0.5 \times V_{DDQ}$	$0.9 - dR_{ONdTM} \times \Delta T - dR_{ONdVM} \times \Delta V $	$1.1 + dR_{ONdTM} \times \Delta T + dR_{ONdVM} \times \Delta V $	RZQ/7
$R_{ON(PD)} @ 0.8 \times V_{DDQ}$	$0.9 - dR_{ONdTH} \times \Delta T - dR_{ONdVH} \times \Delta V $	$1.4 + dR_{ONdTH} \times \Delta T + dR_{ONdVH} \times \Delta V $	RZQ/7
$R_{ON(PU)} @ 0.2 \times V_{DDQ}$	$0.9 - dR_{ONdTL} \times \Delta T - dR_{ONdVL} \times \Delta V $	$1.4 + dR_{ONdTL} \times \Delta T + dR_{ONdVL} \times \Delta V $	RZQ/7
$R_{ON(PU)} @ 0.5 \times V_{DDQ}$	$0.9 - dR_{ONdTM} \times \Delta T - dR_{ONdVM} \times \Delta V $	$1.1 + dR_{ONdTM} \times \Delta T + dR_{ONdVM} \times \Delta V $	RZQ/7
$R_{ON(PU)} @ 0.8 \times V_{DDQ}$	$0.6 - dR_{ONdTH} \times \Delta T - dR_{ONdVH} \times \Delta V $	$1.1 + dR_{ONdTH} \times \Delta T + dR_{ONdVH} \times \Delta V $	RZQ/7

Note : 1. $\Delta T = T - T(@CALIBRATION)$, $\Delta V = V_{DDQ} - V_{DDQ}(@CALIBRATION)$; and $V_{DD} = V_{DDQ}$.

Table 37 : DDR3L 34 Ohm Output Driver Voltage and Temperature Sensitivity

Change	Min	Max	Unit
dR_{ONdTM}	0	1.5	%/°C
dR_{ONdVM}	0	0.13	%/mV
dR_{ONdTL}	0	1.5	%/°C
dR_{ONdVL}	0	0.13	%/mV
dR_{ONdTH}	0	1.5	%/°C
dR_{ONdVH}	0	0.13	%/mV

DDR3L Alternative 40 Ohm Driver

Table 38 : 40 Ohm Driver Impedance Characteristics

MR1[5,1]	R _{ON}	Resistor	V _{OUT}	Min	Nom	Max	Unit
0,0	40Ω	R _{ON40(PD)}	0.2 × V _{DDQ}	0.6	1.0	1.15	RZQ/6
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/6
			0.8 × V _{DDQ}	0.9	1.0	1.45	RZQ/6
		R _{ON40(PU)}	0.2 × V _{DDQ}	0.9	1.0	1.45	RZQ/6
			0.5 × V _{DDQ}	0.9	1.0	1.15	RZQ/6
			0.8 × V _{DDQ}	0.6	1.0	1.15	RZQ/6
Pull-up/pull-down mismatch (MM _{PUPD})			0.5 × V _{DDQ}	−10%	n/a	10	%

- Notes :
1. Tolerance limits assume RZQ of 240 $\Omega \pm 1\%$ and are applicable after proper ZQ calibration has been performed at a stable temperature and voltage ($V_{DDQ} = V_{DD}$; $V_{SSQ} = V_{SS}$). Refer to 40 Ohm Output Driver Sensitivity if either the temperature or the voltage changes after calibration.
 2. Measurement definition for mismatch between pull-up and pull-down (MMPUPD). Measure both $R_{ON(PU)}$ and $R_{ON(PD)}$ at $0.5 \times V_{DDQ}$: $MMPUPD = (R_{ON(PU)} - R_{ON(PD)}) / R_{ON,nom} \times 100$
 3. For IT and AT (1Gb only) devices, the minimum values are derated by 6% when the device operates between -40°C and 0°C (TC). A larger maximum limit will result in slightly lower minimum currents.

DDR3L 40 Ohm Output Driver Sensitivity

If either the temperature or the voltage changes after I/O calibration, then the tolerance limits listed in Table 38 can be expected to widen according to Table 39 and Table 40.

Table 39 : 40 Ohm Output Driver Sensitivity Definition

Symbol	Min	Max	Unit
$R_{ON(PD)} @ 0.2 \times V_{DDQ}$	$0.6 - dR_{ONdTL} \times \Delta T - dR_{ONdVL} \times \Delta V $	$1.1 + dR_{ONdTL} \times \Delta T + dR_{ONdVL} \times \Delta V $	RZQ/6
$R_{ON(PD)} @ 0.5 \times V_{DDQ}$	$0.9 - dR_{ONdTM} \times \Delta T - dR_{ONdVM} \times \Delta V $	$1.1 + dR_{ONdTM} \times \Delta T + dR_{ONdVM} \times \Delta V $	RZQ/6
$R_{ON(PD)} @ 0.8 \times V_{DDQ}$	$0.9 - dR_{ONdTH} \times \Delta T - dR_{ONdVH} \times \Delta V $	$1.4 + dR_{ONdTH} \times \Delta T + dR_{ONdVH} \times \Delta V $	RZQ/6
$R_{ON(PU)} @ 0.2 \times V_{DDQ}$	$0.9 - dR_{ONdTL} \times \Delta T - dR_{ONdVL} \times \Delta V $	$1.4 + dR_{ONdTL} \times \Delta T + dR_{ONdVL} \times \Delta V $	RZQ/6
$R_{ON(PU)} @ 0.5 \times V_{DDQ}$	$0.9 - dR_{ONdTM} \times \Delta T - dR_{ONdVM} \times \Delta V $	$1.1 + dR_{ONdTM} \times \Delta T + dR_{ONdVM} \times \Delta V $	RZQ/6
$R_{ON(PU)} @ 0.8 \times V_{DDQ}$	$0.6 - dR_{ONdTH} \times \Delta T - dR_{ONdVH} \times \Delta V $	$1.1 + dR_{ONdTH} \times \Delta T + dR_{ONdVH} \times \Delta V $	RZQ/6

Note: 1. $\Delta T = T - T(@CALIBRATION)$, $\Delta V = V_{DDQ} - V_{DDQ}(@CALIBRATION)$; and $V_{DD} = V_{DDQ}$.

Table 40 : 40 Ohm Output Driver Voltage and Temperature Sensitivity

Change	Min	Max	Unit
dR_{ONdTM}	0	1.5	%/°C
dR_{ONdVM}	0	0.15	%/mV
dR_{ONdTL}	0	1.5	%/°C
dR_{ONdVL}	0	0.15	%/mV
dR_{ONdTH}	0	1.5	%/°C
dR_{ONdVH}	0	0.15	%/mV

Output Characteristics and Operating Conditions

Table 41 : DDR3L Single-Ended Output Driver Characteristics

All voltages are referenced to VSS

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output leakage current: DQ are disabled; $0V \leq V_{OUT} \leq V_{DDQ}$; ODT is disabled; ODT is HIGH	I_{OZ}	-5	5	μA	1
Output slew rate: Single-ended; For rising and falling edges, measure between $V_{OL(AC)} = V_{REF} - 0.09 \times V_{DDQ}$ and $V_{OH(AC)} = V_{REF} + 0.09 \times V_{DDQ}$	SRQ_{se}	1.75	6	V/ns	1, 2, 3, 4
Single-ended DC high-level output voltage	$V_{OH(DC)}$	$0.8 \times V_{DDQ}$		V	1, 2, 5
Single-ended DC mid-point level output voltage	$V_{OM(DC)}$	$0.5 \times V_{DDQ}$		V	1, 2, 5
Single-ended DC low-level output voltage	$V_{OL(DC)}$	$0.2 \times V_{DDQ}$		V	1, 2, 5
Single-ended AC high-level output voltage	$V_{OH(AC)}$	$V_{TT} + 0.1 \times V_{DDQ}$		V	1, 2, 3, 6
Single-ended AC low-level output voltage	$V_{OL(AC)}$	$V_{TT} - 0.1 \times V_{DDQ}$		V	1, 2, 3, 6
Delta R_{ON} between pull-up and pull-down for DQ/DQS	MM_{PUPD}	-10	10	%	1, 7
Test load for AC timing and output slew rates	Output to V_{TT} ($V_{DDQ}/2$) via 25 Ω resistor				3

Notes : 1. RZQ of 240 $\Omega \pm 1\%$ with RZQ/7 enabled (default 34 Ω driver) and is applicable after proper ZQ calibration has been performed at a stable temperature and voltage ($V_{DDQ}=V_{DD}$; $V_{SSQ}=V_{SS}$).

2. $V_{TT} = V_{DDQ}/2$.

3. See Figure 18 for the test load configuration.

4. The 6 V/ns maximum is applicable for a single DQ signal when it is switching either from HIGH to LOW or LOW to HIGH while the remaining DQ signals in the same byte lane are either all static or all switching in the opposite direction. For all other DQ signal switching combinations, the maximum limit of 6 V/ns is reduced to 5 V/ns.

5. See Figure 15 for IV curve linearity. Do not use AC test load.

6. See Table 44 for output slew rate.

7. See Figure 15 for additional information.

8. See Figure 16 for an example of a single-ended output signal.

Table 42 : DDR3L Differential Output Driver Characteristics

All voltages are referenced to VSS

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output leakage current: DQ are disabled; $0V \leq V_{OUT} \leq V_{DDQ}$; ODT is disabled; ODT is HIGH	I_{OZ}	-5	5	μA	1
Output slew rate: Differential; For rising and falling edges, measure between $V_{OL,diff(AC)} = -0.2 \times V_{DDQ}$ and $V_{OH,diff(AC)} = +0.2 \times V_{DDQ}$	SRQ_{diff}	3.5	12	V/ns	1
Output differential cross-point voltage	$V_{OX(AC)}$	$V_{REF} - 150$	$V_{REF} + 150$	mV	1, 2, 3
Differential high-level output voltage	$V_{OH,diff(AC)}$	$+0.2 \times V_{DDQ}$		V	1, 4
Differential low-level output voltage	$V_{OL,diff(AC)}$	$-0.2 \times V_{DDQ}$		V	1, 4
Delta R_{ON} between pull-up and pull-down for DQ/DQS	MM_{PUPD}	-10	10	%	1, 5
Test load for AC timing and output slew rates	Output to V_{TT} ($V_{DDQ}/2$) via 25 Ω resistor				3

- Notes :
1. RZQ of 240 $\Omega \pm 1\%$ with RZQ/7 enabled (default 34 Ω driver) and is applicable after proper ZQ calibration has been performed at a stable temperature and voltage ($V_{DDQ} = V_{DD}$; $V_{SSQ} = V_{SS}$).
 2. $V_{REF} = V_{DDQ}/2$; slew rate @ 5 V/ns, interpolate for faster slew rate.
 3. See Figure 18 for the test load configuration.
 4. See Table 45 for the output slew rate.
 5. See Table 31 for additional information.
 6. See Figure 17 for an example of a differential output signal.

Table 43 : DDR3L Differential Output Driver Characteristics $V_{OX(AC)}$

All voltages are referenced to VSS

Parameter/Condition	Symbol		DDR3L- 800/1066/1333 DQS/DQS# Differential Slew Rate									Unit
			3.5V/ns	4V/ns	5V/ns	6V/ns	7V/ns	8V/ns	9V/ns	10V/ns	12V/ns	
Output differential crosspoint voltage	$V_{OX(AC)}$	Max	+115	+130	+135	+195	+205	+205	+205	+205	+205	mV
		Min	-115	-130	-135	-195	-205	-205	-205	-205	-205	mV
Parameter/Condition	Symbol		DDR3L-1600/1866 DQS/DQS# Differential Slew Rate									Unit
			3.5V/ns	4V/ns	5V/ns	6V/ns	7V/ns	8V/ns	9V/ns	10V/ns	12V/ns	
Output differential crosspoint voltage	$V_{OX(AC)}$	Max	+90	+105	+135	+155	+180	+205	+205	+205	+205	mV
		Min	-90	-105	-135	-155	-180	-205	-205	-205	-205	mV

- Note :
1. RZQ of 240 $\Omega \pm 1\%$ with RZQ/7 enabled (default 34 Ω driver) and is applicable after proper ZQ calibration has been performed at a stable temperature and voltage ($V_{DDQ} = V_{DD}$; $V_{SSQ} = V_{SS}$).
 2. See Figure 18 for the test load configuration.
 3. See Figure 17 for an example of a differential output signal.
 4. For a differential slew rate between the list values, the $V_{OX(AC)}$ value may be obtained by linear interpolation.

Figure 16 : DQ Output Signal

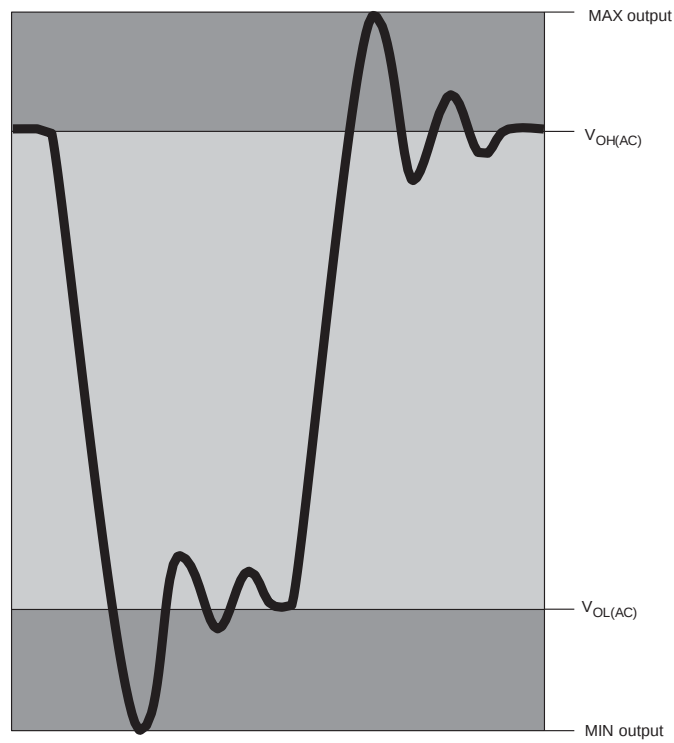
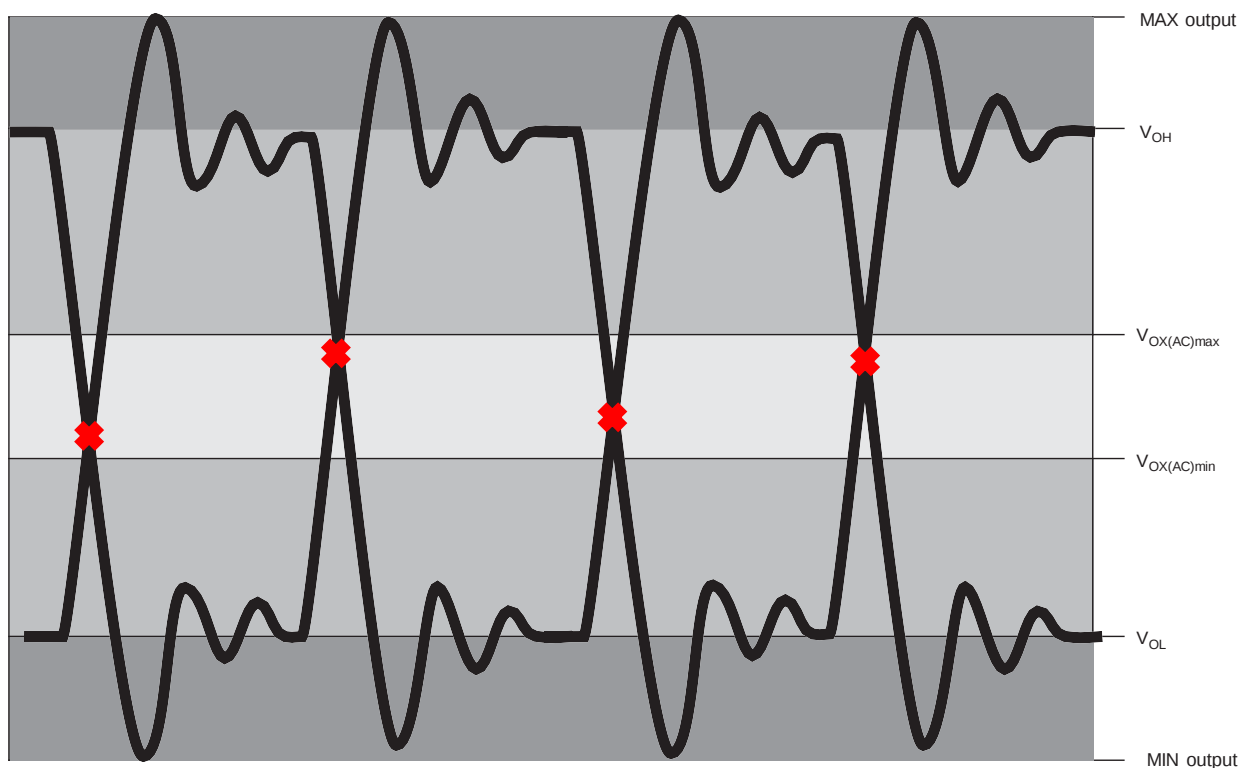


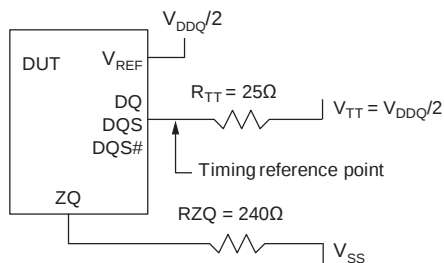
Figure 17 : Differential Output Signal



Reference Output Load

Figure 18 represents the effective reference load of 25Ω used in defining the relevant device AC timing parameters (except ODT reference timing) as well as the output slew rate measurements. It is not intended to be a precise representation of a particular system environment or a depiction of the actual load presented by a production tester. System designers should use IBIS or other simulation tools to correlate the timing reference load to a system environment.

Figure 18 : Reference Output Load for AC Timing and Output Slew Rate



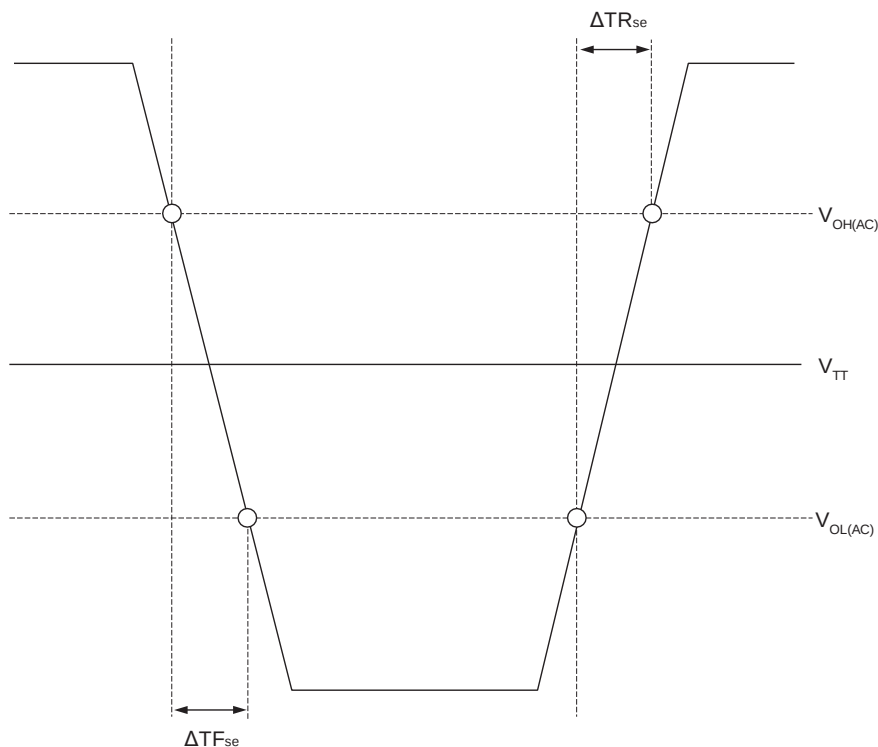
Slew Rate Definitions for Single-Ended Output Signals

The single-ended output driver is summarized in Table 41. With the reference load for timing measurements, the output slew rate for falling and rising edges is defined and measured between $V_{OL(AC)}$ and $V_{OH(AC)}$ for single-ended signals.

Table 44 : Single-Ended Output Slew Rate Definition

Single-Ended Output Slew Rates (Linear Signals)		Measured		Calculation
Output	Edge	From	To	
DQ	Rising	$V_{OL(AC)}$	$V_{OH(AC)}$	$\frac{V_{OH(AC)} - V_{OL(AC)}}{\Delta T_{Rse}}$
	Falling	$V_{OH(AC)}$	$V_{OL(AC)}$	$\frac{V_{OH(AC)} - V_{OL(AC)}}{\Delta T_{Fse}}$

Figure 19 : Nominal Slew Rate Definition for Single-Ended Output Signals



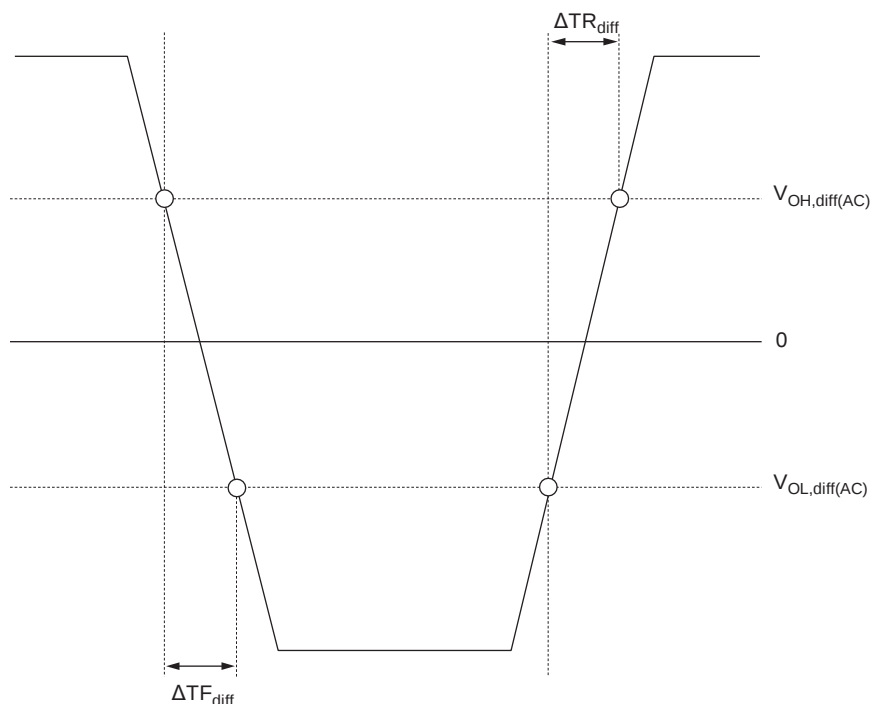
Slew Rate Definitions for Differential Output Signals

The differential output driver is summarized in Table 42. With the reference load for timing measurements, the output slew rate for falling and rising edges is defined and measured between VOL(AC) and VOH(AC) for differential signals.

Table 45 : Single-Ended Output Slew Rate Definition

Differential Output Slew Rates (Linear Signals)		Measured		Calculation
Output	Edge	From	To	
DQS, DQS#	Rising	$V_{OL,diff(AC)}$	$V_{OH,diff(AC)}$	$\frac{V_{OH,diff(AC)} - V_{OL,diff(AC)}}{\Delta TR_{diff}}$
	Falling	$V_{OH,diff(AC)}$	$V_{OL,diff(AC)}$	$\frac{V_{OH,diff(AC)} - V_{OL,diff(AC)}}{\Delta TF_{diff}}$

Figure 20 : Nominal Differential Output Slew Rate Definition for DQS, DQS#



Speed Bin Tables

Table 46 : DDR3L-1066 Speed Bins

DDR3-1066 Speed Bin			-5F		-5G		Unit	Notes
CL- ^t RCD- ^t RP			7-7-7		8-8-8			
Parameter	Symbol	Min	Max	Min	Max			
Internal READ command to first data	^t AA	13.125	–	15	–	ns		
ACTIVATE to internal READ or WRITE delay time	^t RCD	13.125	–	15	–	ns		
PRECHARGE command period	^t RP	13.125	–	15	–	ns		
ACTIVATE-to-ACTIVATE or REFRESH command period	^t RC	50.625	–	52.5	–	ns		
ACTIVATE-to-PRECHARGE command period	^t RAS	37.5	9 x ^t REFI	37.5	9 x ^t REFI	ns	1	
CL = 5	CWL = 5	^t CK (AVG)	3.0	3.3	3.0	3.3	ns	2
	CWL = 6	^t CK (AVG)	Reserved		Reserved		ns	3
CL = 6	CWL = 5	^t CK (AVG)	2.5	3.3	2.5	3.3	ns	2
	CWL = 6	^t CK (AVG)	Reserved		Reserved		ns	3
CL = 7	CWL = 5	^t CK (AVG)	Reserved		Reserved		ns	3
	CWL = 6	^t CK (AVG)	1.875	<2.5	Reserved		ns	2,3
CL = 8	CWL = 5	^t CK (AVG)	Reserved		Reserved		ns	3
	CWL = 6	^t CK (AVG)	1.875	<2.5	1.875	<2.5	ns	2
Supported CL settings			5, 6, 7, 8		5, 6, 8		CK	
Supported CWL settings			5, 6		5, 6		CK	

Notes : 1. ^tREFI depends on T_{OPER} .

2. The CL and CWL settings result in ^tCK requirements. When making a selection ^tCK, both CL and CWL requirement settings need to be fulfilled.

3. Reserved settings are not allowed.

Table 47 : DDR3-1333 Speed Bins

DDR3-1333 Speed Bin			-6H ¹		-6J ²		Unit	Notes
CL- ^t RCD- ^t RP			9-9-9		10-10-10			
Parameter	Symbol	Min	Max	Min	Max			
Internal READ command to first data	^t AA	13.5	–	15	–	ns		
ACTIVATE to internal READ or WRITE delay time	^t RCD	13.5	–	15	–	ns		
PRECHARGE command period	^t RP	13.5	–	15	–	ns		
ACTIVATE-to-ACTIVATE or REFRESH command period	^t RC	49.5	–	51	–	ns		
ACTIVATE-to-PRECHARGE command period	^t RAS	36	9 x ^t REFI	36	9 x ^t REFI	ns	3	
CL = 5	CWL = 5	^t CK (AVG)	3.0	3.3	3.0	3.3	ns	4
	CWL = 6, 7	^t CK (AVG)	Reserved		Reserved		ns	5
CL = 6	CWL = 5	^t CK (AVG)	2.5	3.3	2.5	3.3	ns	4
	CWL = 6	^t CK (AVG)	Reserved		Reserved		ns	5
	CWL = 7	^t CK (AVG)	Reserved		Reserved		ns	5
CL = 7	CWL = 5	^t CK (AVG)	Reserved		Reserved		ns	5
	CWL = 6	^t CK (AVG)	1.875	<2.5	Reserved		ns	4,5
	CWL = 7	^t CK (AVG)	Reserved		Reserved		ns	5
CL = 8	CWL = 5	^t CK (AVG)	Reserved		Reserved		ns	5
	CWL = 6	^t CK (AVG)	1.875	<2.5	1.875	<2.5	ns	4
	CWL = 7	^t CK (AVG)	Reserved		Reserved		ns	5
CL = 9	CWL = 5, 6	^t CK (AVG)	Reserved		Reserved		ns	5
	CWL = 7	^t CK (AVG)	1.5	<1.875	Reserved		ns	4,5
CL = 10	CWL = 5, 6	^t CK (AVG)	Reserved		Reserved		ns	5
	CWL = 7	^t CK (AVG)	1.5	<1.875	1.5	<1.875	ns	4
Supported CL settings			5, 6, 7, 8, 9, 10		5, 6, 8, 10		CK	
Supported CWL settings			5, 6, 7		5, 6, 7		CK	

- Notes :
1. The -6H speed grade is backward compatible with 1066, CL = 7 (-5F).
 2. The -6J speed grade is backward compatible with 1066, CL = 8 (-5G).
 3. ^tREFI depends on T_{OPER} .
 4. The CL and CWL settings result in ^tCK requirements. When making a selection of ^tCK, both CL and CWL requirement settings need to be fulfilled.
 5. Reserved settings are not allowed

Table 48 : DDR3-1600 Speed Bins

DDR3-1600 Speed Bin			-8K ¹		Unit	Notes
CL- ^t RCD- ^t RP			11-11-11			
Parameter	Symbol	Min	Max			
Internal READ command to first data	^t AA	13.75	–		ns	
ACTIVATE to internal READ or WRITE delay time	^t RCD	13.75	–		ns	
PRECHARGE command period	^t RP	13.75	–		ns	
ACTIVATE-to-ACTIVATE or REFRESH command period	^t RC	48.75	–		ns	
ACTIVATE-to-PRECHARGE command period	^t RAS	35	9 x ^t REFI		ns	2
CL = 5	CWL = 5	^t CK (AVG)	3.0	3.3	ns	3
	CWL = 6, 7, 8	^t CK (AVG)	Reserved		ns	4
CL = 6	CWL = 5	^t CK (AVG)	2.5	3.3	ns	3
	CWL = 6	^t CK (AVG)	Reserved		ns	4
	CWL = 7, 8	^t CK (AVG)	Reserved		ns	4
CL = 7	CWL = 5	^t CK (AVG)	Reserved		ns	4
	CWL = 6	^t CK (AVG)	1.875	<2.5	ns	3
	CWL = 7	^t CK (AVG)	Reserved		ns	4
	CWL = 8	^t CK (AVG)	Reserved		ns	4
CL = 8	CWL = 5	^t CK (AVG)	Reserved		ns	4
	CWL = 6	^t CK (AVG)	1.875	<2.5	ns	3
	CWL = 7	^t CK (AVG)	Reserved		ns	4
	CWL = 8	^t CK (AVG)	Reserved		ns	4
CL = 9	CWL = 5, 6	^t CK (AVG)	Reserved		ns	4
	CWL = 7	^t CK (AVG)	1.5	<1.875	ns	3
	CWL = 8	^t CK (AVG)	Reserved		ns	4
CL = 10	CWL = 5, 6	^t CK (AVG)	Reserved		ns	4
	CWL = 7	^t CK (AVG)	1.5	<1.875	ns	3
	CWL = 8	^t CK (AVG)	Reserved		ns	4
CL = 11	CWL = 5, 6, 7	^t CK (AVG)	Reserved		ns	4
	CWL = 8	^t CK (AVG)	1.25	<1.5	ns	3
Supported CL settings			5, 6, 7, 8, 9, 10, 11		CK	
Supported CWL settings			5, 6, 7, 8		CK	

- Notes :
1. The -8K speed grade is backward compatible with 1333, CL = 9 (-6H) and 1066, CL = 7 (-6J).
 2. . ^tREFI depends on T_{OPER} .
 3. The CL and CWL settings result in ^tCK requirements. When making a selection of ^tCK , both CL and CWL requirement settings need to be fulfilled.
 4. Reserved settings are not allowed.

Table 49 : DDR3-1866 Speed Bins

DDR3-1866 Speed Bin			-9M ¹		Unit	Notes
CL-'RCD-'RP			13-13-13			
Parameter	Symbol	Min	Max			
Internal READ command to first data	tAA	13.91	20			
ACTIVATE to internal READ or WRITE delay time	tRCD	13.91	–	ns		
PRECHARGE command period	tRP	13.91	–	ns		
ACTIVATE-to-ACTIVATE or REFRESH command period	tRC	47.91	–	ns		
ACTIVATE-to-PRECHARGE command period	tRAS	34	9 x tREFI	ns	2	
CL = 5	CWL = 5	tCK (AVG)	3.0	3.3	ns	3
	CWL = 6, 7, 8, 9	tCK (AVG)	Reserved		ns	4
CL = 6	CWL = 5	tCK (AVG)	2.5	3.3	ns	3
	CWL = 6, 7, 8, 9	tCK (AVG)	Reserved		ns	4
CL = 7	CWL = 5, 7, 8, 9	tCK (AVG)	Reserved		ns	4
	CWL = 6	tCK (AVG)	1.875	<2.5	ns	3
CL = 8	CWL = 5, 8, 9	tCK (AVG)	Reserved		ns	4
	CWL = 6	tCK (AVG)	1.875	<2.5	ns	3
	CWL = 7	tCK (AVG)	Reserved		ns	4
CL = 9	CWL = 5, 6, 8, 9	tCK (AVG)	Reserved		ns	4
	CWL = 7	tCK (AVG)	1.5	<1.875	ns	3
CL = 10	CWL = 5, 6, 9	tCK (AVG)	Reserved		ns	4
	CWL = 7	tCK (AVG)	1.5	<1.875	ns	3
	CWL = 8	tCK (AVG)	Reserved		ns	4
CL = 11	CWL = 5, 6, 7	tCK (AVG)	Reserved		ns	4
	CWL = 8	tCK (AVG)	1.25	<1.5	ns	3
	CWL = 9	tCK (AVG)	Reserved		ns	4
CL = 12	CWL = 5, 6, 7, 8	tCK (AVG)	Reserved		ns	4
	CWL = 9	tCK (AVG)	Reserved		ns	4
CL = 13	CWL = 5, 6, 7, 8	tCK (AVG)	Reserved		ns	4
	CWL = 9	tCK (AVG)	1.07	<1.25	ns	3
Supported CL settings			5, 6, 7, 8, 9, 10, 11, 13		CK	
Supported CWL settings			5, 6, 7, 8, 9		CK	

Notes : 1. The -9M speed grade is backward compatible with 1600, CL = 11 (-8K); 1333, CL = 9 (-6H); and 1066, CL = 7 (-5F).

2. ^tREFI depends on T_{OPER} .

3. The CL and CWL settings result in ^tCK requirements. When making a selection of ^tCK, both CL and CWL requirement settings need to be fulfilled.

4. Reserved settings are not allowed.

Electrical Characteristics and AC Operating Conditions

Table 50 : Electrical Characteristics and AC Operating Conditions

Notes 1–8 apply to the entire table

Parameter		Symbol	Clock Timing								Unit	Notes
			DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600			
			Min	Max	Min	Max	Min	Max	Min	Max		
Clock period average: DLL disable mode		t_{CK} (DLL_DIS)	8	7800	8	7800	8	7800	8	7800	ns	9, 42
			8	3900	8	3900	8	3900	8	3900	ns	42
Clock period average: DLL enable mode		t_{CK} (AVG)	See Speed Bin Tables for t_{CK} range allowed								ns	10, 11
High pulse width average Low pulse width average		t_{CH} (AVG)	0.47	0.53	0.47	0.53	0.47	0.53	0.47	0.53	CK	12
		t_{CL} (AVG)	0.5	0.53	0.47	0.53	0.47	0.53	0.47	0.53	CK	12
Clock period jitter		t_{JITper}	-100	100	-90	90	-80	80	-70	70	ps	13
		$t_{JITper,lck}$	-90	90	-80	80	-70	70	-60	60	ps	13
Clock absolute period		t_{CK} (ABS)	MIN = t_{CK} (AVG) MIN + t_{JITper} MIN; MAX = t_{CK} (AVG) MAX + t_{JITper} MAX								ps	
Clock absolute high pulse width		t_{CH} (ABS)	0.43	-	0.43	-	0.43	-	0.43	-	t_{CK} (AVG)	14
Clock absolute low pulse width		t_{CL} (ABS)	0.43	-	0.43	-	0.43	-	0.43	-	t_{CK} (AVG)	15
Cycle-to-cycle jitter		t_{JITcc}	200		180		160		140		ps	16
		$t_{JITcc,lck}$	180		160		140		120		ps	16
Cumulative error across		$t_{ERR2per}$	-147	147	-132	132	-118	118	-103	103	ps	17
		$t_{ERR3per}$	-175	175	-157	157	-140	140	-122	122	ps	17
		$t_{ERR4per}$	-194	194	-175	175	-155	155	-136	136	ps	17
		$t_{ERR5per}$	-209	209	-188	188	-168	168	-147	147	ps	17
		$t_{ERR6per}$	-222	222	-200	200	-177	177	-155	155	ps	17
		$t_{ERR7per}$	-232	232	-209	209	-186	186	-163	163	ps	17
		$t_{ERR8per}$	-241	241	-217	217	-193	193	-169	169	ps	17
		$t_{ERR9per}$	-249	249	-224	224	-200	200	-175	175	ps	17
		$t_{ERR10per}$	-257	257	-231	231	-205	205	-180	180	ps	17
		$t_{ERR11per}$	-263	263	-237	237	-210	210	-184	184	ps	17
		$t_{ERR12per}$	-269	269	-242	242	-215	215	-188	188	ps	17
		$n = 13, 14 \dots 49, 50$ cycles		$t_{ERRnper}$	$t_{ERRnper}$ MIN = $(1 + 0.68\ln[n]) \times t_{JITper}$ MIN $t_{ERRnper}$ MAX = $(1 + 0.68\ln[n]) \times t_{JITper}$ MAX							

Table 50 : Electrical Characteristics and AC Operating Conditions (Continued)

Notes 1–8 apply to the entire table

Parameter		Symbol	DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600		Unit	Notes
			Min	Max	Min	Max	Min	Max	Min	Max		
DQ Input Timing												
Data setup time to DQS, DQS#	Base (specification)	'DS (AC160)	90	–	40	–	–	–	–	–	ps	18,19,44
	VREF @ 1 V/ns		250	–	200	–	–	–	–	–	ps	19,20
Data setup time to DQS, DQS#	Base (specification)	'DS (AC135)	140	–	90	–	45	–	25	–	ps	18, 19
	VREF @ 1 V/ns		275	–	250	–	180	–	160	–	ps	19, 20
Data hold time from DQS, DQS#	Base (specification)	'DH (DC90)	160	–	110	–	75	–	45	–	ps	18, 19
	VREF @ 1 V/ns		250	–	200	–	165	–	145	–	ps	19, 20
Minimum data pulse width			600	–	490	–	400	–	360	–	ps	41
DQ Output Timing												
DQS, DQS# to DQ skew, per access		'DQSQ	–	200	–	150	–	125	–	100	ps	
DQ output hold time from DQS, DQS#		'QH	0.38	–	0.38	–	0.38	–	0.38	–	CK (AVG)	21
DQ Low-Z time from CK, CK#		'LZDQ	–800	400	–600	300	–500	250	–450	225	ps	22, 23
DQ High-Z time from CK, CK#		'HZDQ	–	400	–	300	–	250	–	225	ps	22, 23
DQ Strobe Input Timing												
DQS, DQS# rising to CK, CK# rising		'DQSS	–0.25	0.25	–0.25	0.25	–0.25	0.25	–0.27	0.27	CK	25
DQS, DQS# differential input low pulse width		'DQSL	0.45		0.5	0.55	0.45	0.55	0.45	0.55	CK	
DQS, DQS# differential input high pulse width		'DQSH	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	CK	
DQS, DQS# falling setup to CK, CK# rising		'DSS	0.2	–	0.2	–	0.2	–	0.18	–	CK	25
DQS, DQS# falling hold from CK, CK# rising		'DSH	0.2	–	0.2	–	0.2	–	0.18	–	CK	25
DQS, DQS# differential WRITE preamble		'WPRE	0.9	–	0.9	–	0.9	–	0.9	–	CK	
DQS, DQS# differential WRITE postamble		'WPST	0.3	–	0.3	–	0.3	–	0.3	–	CK	
DQ Strobe Output Timing												
DQS, DQS# rising to/from rising CK, CK#		'DQSCK	–400	400	–300	300	–255	255	–225	225	ps	23
DQS, DQS# rising to/from rising CK, CK# when DLL is disabled		'DQSCK (DLL_DIS)	1	10	1	10	1	10	1	10	ns	26

Table 50 : Electrical Characteristics and AC Operating Conditions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
DQS, DQS# differential output high time	^t QSH	0.38	–	0.38	–	0.40	–	0.40	–	CK	21
DQS, DQS# differential output low time	^t QSL	0.38	–	0.38	–	0.40	–	0.40	–	CK	21
DQS, DQS# Low-Z time (RL - 1)	^t LZDQS	–800	400	–600	300	–500	250	–450	225	ps	22, 23
DQS, DQS# High-Z time (RL + BL/2)	^t HZDQS	–	400	–	300	–	250	–	225	ps	22, 23
DQS, DQS# differential READ preamble	^t RPRE	0.9	Note 24	0.9	Note 24	0.9	Note 24	0.9	Note 24	CK	23, 24
DQS, DQS# differential READ postamble	^t RPST	0.3	Note 27	0.3	Note 27	0.3	Note 27	0.3	Note 27	CK	23, 27
Command and Address Timing											
DLL locking time	^t DLLK	512	–	512	–	512	–	512	–	CK	28
CTRL, CMD, ADDR setup to CK,CK#	Base (specification)	215	–	140	–	80	–	60	–	ps	29, 30, 44
	V _{REF} @ 1 V/ns	375	–	300	–	240	–	220	–	ps	20, 30
CTRL, CMD, ADDR setup to CK,CK#	Base (specification)	365	–	290	–	205	–	185	–	ps	29, 30, 44
	V _{REF} @ 1 V/ns	500	–	425	–	340	–	320	–	ps	20, 30
CTRL, CMD, ADDR hold from CK,CK#	Base (specification)	285	–	210	–	150	–	130	–	ps	29, 30
	V _{REF} @ 1 V/ns	375	–	300	–	240	–	220	–	ps	20, 30
Minimum CTRL, CMD, ADDR pulse width	^t IPW	900	–	780	–	620	–	560	–	ps	41
ACTIVATE to internal READ or WRITE delay	^t RCD	See Speed Bin Tables for ^t RCD									
PRECHARGE command period	^t RP	See Speed Bin for ^t RP									
ACTIVATE-to-PRECHARGE command period	^t RAS	See Speed Bin Tables for ^t RAS									
ACTIVATE-to-ACTIVATE command period	^t RC	See Speed Bin Tables for ^t RC									
ACTIVATE-to-ACTIVATE minimum command period	^t RRD	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 7.5ns	MIN = greater of 4CK or 6ns	MIN = greater of 4CK or 6ns	MIN = greater of 4CK or 6ns	MIN = greater of 4CK or 6ns	MIN = greater of 4CK or 6ns	CK	31
		MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	MIN = greater of 4CK or 10ns	CK	31
Four ACTIVATE windows	^t FAW	40	–	37.5	–	30	–	30	–	ns	31
		50	–	50	–	45	–	40	–	ns	31
Write recovery time	^t WR	MIN = 15ns; MAX = n/a									
Delay from start of internal WRITE transaction to internal READ command	^t WTR	MIN = greater of 4CK or 7.5ns; MAX = n/a									

Table 50 : Electrical Characteristics and AC Operating Conditions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600		Unit	Notes	
		Min	Max	Min	Max	Min	Max	Min	Max			
READ-to-PRECHARGE time	t _{RTP}	MIN = greater of 4CK or 7.5ns; MAX = n/a									CK	31, 32
CAS#-to-CAS# command delay	t _{CCD}	MIN = 4CK; MAX = n/a									CK	
Auto precharge write recovery + precharge time	t _{DAL}	MIN = WR + t _{RP} /CK (AVG); MAX = n/a									CK	
MODE REGISTER SET command cycle time	t _{MRD}	MIN = 4CK; MAX = n/a									CK	
MODE REGISTER SET command update delay	t _{MOD}	MIN = greater of 12CK or 15ns; MAX = n/a									CK	
MULTIPURPOSE REGISTER READ burst end to mode register set for multipurpose register exit	t _{MPRR}	MIN = 1CK; MAX = n/a									CK	
Calibration Timing												
ZQCL command: Long calibration time	POWER-UP and RE-SET operation	t _{ZQinit}	512	–	512	–	512	–	512	–	CK	
	Normal operation	t _{ZQoper}	256	–	256	–	256	–	256	–	CK	
ZQCS command: Short calibration time	t _{ZQCS}	64	–	–	64	–	64	–	64	–	CK	
Initialization and Reset Timing												
Exit reset from CKE HIGH to a valid command	t _{XPR}	MIN = greater of 5CK or t _{RFC} + 10ns; MAX = n/a									CK	
Begin power supply ramp to power supplies stable	t _{VDDPR}	MIN = n/a; MAX = 200									ms	
RESET# LOW to power supplies stable	t _{RPS}	MIN = 0; MAX = 200									ms	
RESET# LOW to I/O and R _{TT} High-Z	t _{IOZ}	MIN = n/a; MAX = 20									ns	35
Refresh Timing												
REFRESH-to-ACTIVATE or REFRESH command period	t _{RFC} – 1Gb	MIN = 110; MAX = 70,200									ns	
	t _{RFC} – 2Gb	MIN = 160; MAX = 70,200									ns	
	t _{RFC} – 4Gb	MIN = 260; MAX = 70,200									ns	
	t _{RFC} – 8Gb	MIN = 350; MAX = 70,200									ns	
Maximum refresh period	T _C ≤ 85°C	64 (1X)									ms	36
	T _C > 85°C	32 (2X)									ms	36
Maximum average periodic refresh	T _C ≤ 85°C	7.8 (64ms/8192)									μs	36
	T _C > 85°C	3.9 (32ms/8192)									μs	36
Self Refresh Timing												

Table 50 : Electrical Characteristics and AC Operating Conditions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600		Unit	Notes	
		Min	Max	Min	Max	Min	Max	Min	Max			
Exit self refresh to commands not requiring a locked DLL	'XS	MIN = greater of 5CK or 'RFC + 10ns; MAX = n/a									CK	
Exit self refresh to commands requiring a locked DLL	'XSDLL	MIN = 'DLLK (MIN); MAX = n/a									CK	28
Minimum CKE low pulse width for self re-fresh entry to self refresh exit timing	'CKESR	MIN = 'CKE (MIN) + CK; MAX = n/a									CK	
Valid clocks after self refresh entry or power-down entry	'CKSRE	MIN = greater of 5CK or 10ns; MAX = n/a									CK	
Valid clocks before self refresh exit, power-down exit, or reset exit	'CKSRX	MIN = greater of 5CK or 10ns; MAX = n/a									CK	
Power-Down Timing												
CKE MIN pulse width	'CKE (MIN)	Greater of 3CK or 7.5ns	Greater of 3CK or 5.625ns	Greater of 3CK or 5.625ns	Greater of 3CK or 5.625ns	Greater of 3CK or 5ns	CK					
Command pass disable delay	'CPDED	MIN = 1; MAX = n/a									CK	
Power-down entry to power-down exit timing	'PD	MIN = 'CKE (MIN); MAX = 9 * tREFI									CK	
Begin power-down period prior to CKE registered HIGH	'ANPD	WL - 1CK									CK	
Power-down entry period: ODT either synchronous or asynchronous	PDE	Greater of 'ANPD or 'RFC - REFRESH command to CKE LOW time									CK	
Power-down exit period: ODT either synchronous or asynchronous	PDX	'ANPD + 'XPDLL									CK	
Power-Down Entry Minimum Timing												
ACTIVATE command to power-down entry	'ACTPDEN	MIN = 1									CK	
PRECHARGE/PRECHARGE ALL command to power-down entry	'PRPDEN	MIN = 1									CK	
REFRESH command to power-down entry	'REFPDEN	MIN = 1									CK	37
MRS command to power-down entry	'MRSPDEN	MIN = 'MOD (MIN)									CK	
READ/READ with auto precharge command to power-down entry	'RDPDEN	MIN = RL + 4 + 1									CK	
WRITE command to power-down entry	'WRPDEN	MIN = WL + 4 + 'WR/'CK (AVG)									CK	
	'WRPDEN	MIN = WL + 2 + tWR/tCK (AVG)									CK	

Table 50 : Electrical Characteristics and AC Operating Conditions (Continued)

Notes 1–8 apply to the entire table

Parameter		Symbol	DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600		Unit	Notes		
			Min	Max	Min	Max	Min	Max	Min	Max				
WRITE with auto precharge command to power-down entry	BL8 (OTF, MRS) BC4OTF	^t WRAP-DEN	MIN = WL + 4 + WR + 1										CK	
	BC4MRS	^t WRAP-DEN	MIN = WL + 2 + WR + 1										CK	
Power-Down Exit Timing														
DLL on, any valid command, or DLL off to commands not requiring locked DLL		^t XP	MIN = greater of 3CK or 7.5ns; MAX = n/a		MIN = greater of 3CK or 7.5ns; MAX = n/a		MIN = greater of 3CK or 6ns; MAX = n/a				CK			
Precharge power-down with DLL off to commands requiring a locked DLL		^t XPDLL	MIN = greater of 10CK or 24ns; MAX = n/a										CK	28
ODT Timing														
R _{TT} synchronous turn-on delay		ODTLon	CWL + AL - 2CK										CK	38
R _{TT} synchronous turn-off delay		ODTLoff	CWL + AL - 2CK										CK	40
R _{TT} turn-on from ODTL on reference		^t AON	-400	400	-300	300	-250	250	-225	225	ps	23, 38		
R _{TT} turn-off from ODTL off reference		^t AOF	0.3	0.7	0.3	0.7	0.3	0.7	0.3	0.7	CK	39, 40		
Asynchronous R _{TT} turn-on delay (power-down with DLL off)		^t AONPD	MIN = 2; MAX = 8.5										ns	38
Asynchronous R _{TT} turn-off delay (power-down with DLL off)		^t AOFPD	MIN = 2; MAX = 8.5										ns	40
ODT HIGH time with WRITE command and BL8		ODTH8	MIN = 6; MAX = n/a										CK	
ODT HIGH time without WRITE command or with WRITE command and BC4		ODTH4	MIN = 4; MAX = n/a										CK	
Dynamic ODT Timing														
R _{TT, nom} to R _{TT(WR)} change skew		ODTLcnw	WL - 2CK										CK	
R _{TT(WR)} to R _{TT, nom} change skew - BC4		ODTLcwn4	4CK + ODTLoff										CK	
R _{TT(WR)} to R _{TT, nom} change skew - BL8		ODTLcwn8	6CK + ODTLoff										CK	
R _{TT} dynamic change skew		^t ADC	0.3	0.7	0.3	0.7	0.3	0.7	0.3	0.7	CK	39		
Write Leveling Timing														
First DQS, DQS# rising edge		^t WLMRD	40	-	40	-	40	-	40	-	CK			
DQS, DQS# delay		^t WLDQSEN	25	-	25	-	25	-	25	-	CK			
Write leveling setup from rising CK, CK# crossing to rising DQS, DQS# crossing		^t WLS	325	-	245	-	195	-	165	-	ps			

Table 50 : Electrical Characteristics and AC Operating Conditions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-800		DDR3-1066		DDR3-1333		DDR3-1600		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Write leveling hold from rising DQS, DQS# crossing to rising CK, CK# crossing	t_{WLH}	325	–	245	–	195	–	165	–	ps	
Write leveling output delay	t_{WLO}	0	9	0	9	0	9	0	7.5	ns	
Write leveling output error	t_{WLOE}	0	2	0	2	0	2	0	2	ns	

- Notes :
1. AC timing parameters are valid from specified T_C MIN to T_C MAX values.
 2. All voltages are referenced to VSS.
 3. Output timings are only valid for R_{ON34} output buffer selection.
 4. The unit tCK (AVG) represents the actual tCK (AVG) of the input clock under operation.
The unit CK represents one clock cycle of the input clock, counting the actual clock edges.
 5. AC timing and I_{DD} tests may use a V_{IL} -to- V_{IH} swing of up to 900mV in the test environment, but input timing is still referenced to V_{REF} (except tIS, tIH, tDS, and tDH use the AC/DC trip points and CK, CK# and DQS, DQS# use their crossing points). The minimum slew rate for the input signals used to test the device is 1 V/ns for single-ended inputs and 2 V/ns for differential inputs in the range between $V_{IL(AC)}$ and $V_{IH(AC)}$.
 6. All timings that use time-based values (ns, μ s, ms) should use tCK (AVG) to determine the correct number of clocks (Table50 uses CK or tCK [AVG] interchangeably). In the case of noninteger results, all minimum limits are to be rounded up to the nearest whole integer, and all maximum limits are to be rounded down to the nearest whole integer.
 7. Strobe or DQS_{diff} refers to the DQS and DQS# differential crossing point when DQS is the rising edge. Clock or CK refers to the CK and CK# differential crossing point when CK is the rising edge.
 8. This output load is used for all AC timing (except ODT reference timing) and slew rates. The actual test load may be different. The output signal voltage reference point is VDDQ/2 for single-ended signals and the crossing point for differential signals (see Figure 17).
 9. When operating in DLL disable mode, Dosilicon does not warrant compliance with normal mode timings or functionality.
 10. The clock's tCK (AVG) is the average clock over any 200 consecutive clocks and tCK (AVG) MIN is the smallest clock rate allowed, with the exception of a deviation due to clock jitter. Input clock jitter is allowed provided it does not exceed values specified and must be of a random Gaussian distribution in nature.
 11. Spread spectrum is not included in the jitter specification values. However, the input clock can accommodate spread spectrum at a sweep rate in the range of 20–60 kHz with an additional 1% of tCK (AVG) as a long-term jitter component; however, the spread spectrum may not use a clock rate below tCK (AVG) MIN.
 12. The clock's tCH (AVG) and tCL (AVG) are the average half clock period over any 200 consecutive clocks and is the smallest clock half period allowed, with the exception of a deviation due to clock jitter. Input clock jitter is allowed provided it does not exceed values specified and must be of a random Gaussian distribution in nature.
 13. The period jitter (tJITper) is the maximum deviation in the clock period from the average or nominal clock. It is allowed in either the positive or negative direction.
 14. tCH (ABS) is the absolute instantaneous clock high pulse width as measured from one rising edge to the following falling edge.
 15. tCL (ABS) is the absolute instantaneous clock low pulse width as measured from one falling edge to the following rising edge.
 16. The cycle-to-cycle jitter tJITcc is the amount the clock period can deviate from one cycle to the next. It is important to keep cycle-to-cycle jitter at a minimum during the DLL locking time.
 17. The cumulative jitter error tERRnper, where n is the number of clocks between 2 and 50, is the amount of clock time allowed to accumulate consecutively away from the average clock over n number of clock cycles.
 18. tDS (base) and tDH (base) values are for a single-ended 1 V/ns slew rate DQs and 2 V/ns slew rate differential DQS, DQS#.
 19. These parameters are measured from a data signal (DM, DQ0, DQ1, and so forth) transition edge to its respective data strobe signal (DQS, DQS#) crossing.
 20. The setup and hold times are listed converting the base specification values (to which derating tables apply) to V_{REF} when the slew rate is 1 V/ns. These values, with a slew rate of 1 V/ns, are for reference only.
 21. When the device is operated with input clock jitter, this parameter needs to be derated by the actual tJITper (larger of tJITper (MIN) or tJITper (MAX) of the input clock (output deratings are relative to the SDRAM input clock).
 22. Single-ended signal parameter.
 23. The DRAM output timing is aligned to the nominal or average clock. Most output parameters must be derated by the actual jitter error when input clock jitter is present, even when within specification. This results in each parameter becoming larger. The following parameters are required to be derated by subtracting tERR10per (MAX): tDQSCK (MIN), tLZDQS (MIN), tLZDQ (MIN), and tAON (MIN). The following parameters are required to be derated by subtracting tERR10per (MIN) : tDQSCK (MAX), tHZ (MAX), tLZDQS (MAX), tLZDQ (MAX), and tAON (MAX). The parameter tRPRE(MIN) is derated by subtracting tJITper (MAX), while tRPRE (MAX) is derated by subtracting tJITper (MIN).
 24. The maximum preamble is bound by tLZDQS (MAX).

25. These parameters are measured from a data strobe signal (DQS, DQS#) crossing to its respective clock signal (CK, CK#) crossing. The specification values are not affected by the amount of clock jitter applied, as these are relative to the clock signal crossing. These parameters should be met whether clock jitter is present.
26. The tDQSCK (DLL_DIS) parameter begins CL + AL - 1 cycles after the READ command.
27. The maximum postamble is bound by tHZDQS (MAX).
28. Commands requiring a locked DLL are: READ (and RDAP) and synchronous ODT commands. In addition, after any change of latency tXPDLL, timing must be met.
29. tIS (base) and tIH (base) values are for a single-ended 1 V/ns control/command/address slew rate and 2 V/ns CK, CK# differential slew rate.
30. These parameters are measured from a command/address signal transition edge to its respective clock (CK, CK#) signal crossing. The specification values are not affected by the amount of clock jitter applied as the setup and hold times are relative to the clock signal crossing that latches the command/address. These parameters should be met whether clock jitter is present.
31. For these parameters, the DDR3L SDRAM device supports $tnPARAM (nCK) = RU(tPARAM [ns]/tCK[AVG] [ns])$, assuming all input clock jitter specifications are satisfied. For example, the device will support $tnRP (nCK)=RU(tRP/tCK [AVG])$ if all input clock jitter specifications are met. This means that for DDR3-800 6-6-6, of which $tRP = 5ns$, the device will support $tnRP = RU(tRP/tCK[AVG]) = 6$ as long as the input clock jitter specifications are met. That is, the PRECHARGE command at T0 and the ACTIVATE command at T0 + 6 are valid even if six clocks are less than 15ns due to input clock jitter.
32. During READs and WRITEs with auto precharge, the DDR3L SDRAM will hold off the internal PRECHARGE command until tRAS (MIN) has been satisfied.
33. When operating in DLL disable mode, the greater of 4CK or 15ns is satisfied for tWR.
34. The start of the write recovery time is defined as follows:
 - For BL8 (fixed by MRS or OTF): Rising clock edge four clock cycles after WL
 - For BC4 (OTF): Rising clock edge four clock cycles after WL
 - For BC4 (fixed by MRS): Rising clock edge two clock cycles after WL
35. RESET# should be LOW as soon as power starts to ramp to ensure the outputs are in High-Z. Until RESET# is LOW, the outputs are at risk of driving and could result in excessive current, depending on bus activity.
36. The refresh period is 64ms when TC is less than or equal to 85°C. This equates to an average refresh rate of 7.8125μs. However, nine REFRESH commands should be asserted at least once every 70.3μs. When TC is greater than 85°C, the refresh period is 32ms.
37. Although CKE is allowed to be registered LOW after a REFRESH command when tREFPDEN (MIN) is satisfied, there are cases where additional time such as tXPDLL (MIN) is required.
38. ODT turn-on time MIN is when the device leaves High-Z and ODT resistance begins to turn on. ODT turn-on time maximum is when the ODT resistance is fully on. The ODT reference load is shown in Figure 11. Designs that were created prior to JEDEC tightening the maximum limit from 9ns to 8.5ns will be allowed to have a 9ns maximum.
39. Half-clock output parameters must be derated by the actual tERR10per and tJITdy when input clock jitter is present. This results in each parameter becoming larger. The parameters tADC (MIN) and tAOF (MIN) are each required to be derated by subtracting both tERR10per (MAX) and tJITdy (MAX). The parameters tADC (MAX) and tAOF (MAX) are required to be derated by subtracting both tERR10per (MAX) and tJITdy (MAX).
40. ODT turn-off time minimum is when the device starts to turn off ODT resistance. ODT turn-off time maximum is when the DRAM buffer is in High-Z. The ODT reference load is shown in Figure 11. This output load is used for ODT timings (see Figure 18).
41. Pulse width of a input signal is defined as the width between the first crossing of $V_{REF(DC)}$ and the consecutive crossing of $V_{REF(DC)}$.
42. Should the clock rate be larger than tRFC (MIN), an AUTO REFRESH command should have at least one NOP command between it and another AUTO REFRESH command. Additionally, if the clock rate is slower than 40ns(25 MHz), all REFRESH commands should be followed by a PRECHARGE ALL command.
43. DRAM devices should be evenly addressed when being accessed. Disproportionate accesses to a particular row address may result in a reduction of REFRESH characteristics or product lifetime.
44. When two $V_{IH(AC)}$ values (and two corresponding $V_{IL(AC)}$ values) are listed for a specific speed bin, the user may choose either value for the input AC level. Whichever value is used, the associated setup time for that AC level must also be used. Additionally, one $V_{IH(AC)}$ value may be used for address/command inputs and the other $V_{IH(AC)}$ value may be used for data inputs. For example, for DDR3-800, two input AC levels are defined : $V_{IH(AC175),min}$ and $V_{IH(AC150),min}$ (corresponding $V_{IL(AC175),min}$ and $V_{IL(AC150),min}$. For DDR3-800, the address/ command inputs must use either $V_{IH(AC175),min}$ with tIS(AC175) of 200ps or $V_{IH(150),min}$ with tIS(AC150) of 350ps; independently, the data inputs must use either $V_{IH(AC175),min}$ with tDS(AC175) of 75ps or $V_{IH(AC150),min}$ with tDS(AC150) of 125ps.

Electrical Characteristics and AC Operating Conditions

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-1866		Unit	Notes
		Min	Max		
Clock Timing					
Clock period average : DLL disable mode	T _c = 0°C to 85°C	t'CK	8	7800	ns
	T _c = >85°C to 95°C	(DLL_DIS)	8	3900	ns
Clock period average: DLL enable mode		t'CK (AVG)	See Speed Bin Tables for t'CK range allowed		ns
High pulse width average		t'CH (AVG)	0.47	0.53	CK
Low pulse width average		t'CL (AVG)	0.47	0.53	CK
Clock period jitter	DLL locked	t'JITper	−60	60	ps
	DLL locking	t'JITper,lck	−50	50	ps
Clock absolute period		t'CK (ABS)	MIN = t'CK (AVG) MIN + t'JITper MIN; MAX =tCK (AVG) MAX +tJITper MAX		ps
Clock absolute high pulse width		t'CH (ABS)	0.43	−	t'CK(AVG)
Clock absolute low pulse width		t'CL (ABS)	0.43	−	t'CK(AVG)
Cycle-to-cycle jitter	DLL locked	t'JTcc	120		ps
	DLL locking	t'JTcc,lck	100		ps

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions (Continued)

Notes 1–8 apply to the entire table

Parameter		Symbol	DDR3-1866		Unit	Notes
			Min	Max		
Cumulative error across	2 cycles	t'ERR2per	–88	88	ps	17
	3 cycles	t'ERR3per	–105	105	ps	17
	4 cycles	t'ERR4per	–117	117	ps	17
	5 cycles	t'ERR5per	–126	126	ps	17
	6 cycles	t'ERR6per	–133	133	ps	17
	7 cycles	t'ERR7per	–139	139	ps	17
	8 cycles	t'ERR8per	–145	145	ps	17
	9 cycles	t'ERR9per	–150	150	ps	17
	10 cycles	t'ERR10per	–154	154	ps	17
	11 cycles	t'ERR11per	–158	158	ps	17
	12 cycles	t'ERR12per	–161	161	ps	17
	$n = 13, 14 \dots 49, 50$ cycles	t'ERRnper	t'ERRnper MIN = (1 + 0.68ln[n]) × tJITper MIN t'ERRnper MAX = (1 + 0.68ln[n]) × tJITper MAX		ps	17
DQ Input Timing						
Data setup time to DQS, DQS#	Base (specification) @ 2 V/ns	tDS (AC130)	70	–	ps	18, 19
	VREF @ 2 V/ns		135	–	ps	19, 20
Data hold time from DQS, DQS#	Base (specification) @ 2 V/ns	tDH (DC90)	75	–	ps	18, 19
	VREF @ 2 V/ns		110	–	ps	19, 20
Minimum data pulse width		tDIPW	320	–	ps	41
DQ Output Timing						
DQS, DQS# to DQ skew, per access		tDQSQ	–	85	ps	
DQ output hold time from DQS, DQS#		tQH	0.38	–	tCK (AVG)	21
DQ Low-Z time from CK, CK#		tLZDQ	–390	195	ps	22, 23
DQ High-Z time from CK, CK#		tHZDQ	–	195	ps	22, 23
DQ Strobe Input Timing						
DQS, DQS# rising to CK, CK# rising		tDQSS	–0.27	0.27	CK	25

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-1866		Unit	Notes
		Min	Max		
DQS, DQS# differential input low pulse width	'DQSL	0.45	0.55	CK	
DQS, DQS# differential input high pulse width	'DQSH	0.45	0.55	CK	
DQS, DQS# falling setup to CK, CK# rising	'DSS	0.18	–	CK	25
DQS, DQS# falling hold from CK, CK# rising	'DSH	0.18	–	CK	25
DQS, DQS# differential WRITE preamble	'WPRE	0.9	–	CK	
DQS, DQS# differential WRITE postamble	'WPST	0.3	–	CK	
DQ Strobe Output Timing					
DQS, DQS# rising to/from rising CK, CK#	'DQCK	–195	195	ps	23
DQS, DQS# rising to/from rising CK, CK# when DLL is disabled	'DQCK(DLL_DIS)	1	10	ns	26
DQS, DQS# differential output high time	'QSH	0.4	–	CK	21
DQS, DQS# differential output low time	'QSL	0.4	–	CK	21
DQS, DQS# Low-Z time (RL - 1)	'LZDQS	–390	195	ps	22, 23
DQS, DQS# High-Z time (RL + BL/2)	'HZDQS	–	195	ps	22, 23
DQS, DQS# differential READ preamble	'RPRE	0.9	Note 24	CK	23, 24
DQS, DQS# differential READ postamble	'RPST	0.3	Note 27	CK	23, 27
Command and Address Timing					
DLL locking time	'DLLK	512	–	CK	28
CTRL, CMD, ADDR setup to CK, CK#	Base (specification)	'tS (AC135)	–	ps	29, 30, 44
	V _{REF} @ 1 V/ns		–	ps	20, 30
CTRL, CMD, ADDR setup to CK, CK#	Base (specification)	'tS (AC125)	–	ps	29, 30, 44
	V _{REF} @ 1 V/ns		–	ps	20, 30
CTRL, CMD, ADDR hold from CK, CK#	Base (specification)	'tH (DC90)	–	ps	29, 30
	V _{REF} @ 1 V/ns		–	ps	20, 30
Minimum CTRL, CMD, ADDR pulse width	'IPW	535	–	ps	41
ACTIVATE to internal READ or WRITE delay	'RCD	See Speed Bin Tables for tRCD			31
PRECHARGE command period	'RP	See Speed Bin Tables for tRP			31
ACTIVATE-to-PRECHARGE command period	'RAS	See Speed Bin Tables for tRAS			31, 32

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-1866		Unit	Notes
		Min	Max		
ACTIVATE-to-ACTIVATE command period	^t RC	See Speed Bin Tables for ^t RC		ns	31, 43
ACTIVATE to minimum command period	^t RRD	MIN = greater of 4CK or 5ns		CK	31
		MIN = greater of 4CK or 6ns		CK	31
Four ACTIVATE windows	^t FAW	27	–	ns	31
		35	–	ns	31
Write recovery time	^t WR	MIN = 15ns; MAX = n/a		ns	31, 32, 33
Delay from start of internal WRITE transaction to internal READ command	^t WTR	MIN = greater of 4CK or 7.5ns; MAX = n/a		CK	31, 34
READ-to-PRECHARGE time	^t RTP	MIN = greater of 4CK or 7.5ns; MAX = n/a		CK	31, 32
CAS#-to-CAS# command delay	^t CCD	MIN = 4CK; MAX = n/a		CK	
Auto precharge write recovery + precharge time	^t DAL	MIN = WR + ^t RP/CK (AVG); MAX = n/a		CK	
MODE REGISTER SET command cycle time	^t MRD	MIN = 4CK; MAX = n/a		CK	
MODE REGISTER SET command update delay	^t MOD	MIN = greater of 12CK or 15ns; MAX = n/a		CK	
MULTIPURPOSE REGISTER READ burst end to mode register set for multipurpose register exit	^t MPRR	MIN = 1CK; MAX = n/a		CK	
Calibration Timing					
ZQCL command: Long calibration time	POWER-UP and RE-SET operation	MIN = n/a MAX = max(512nCK, 640ns)		CK	
	Normal operation	MIN = n/a MAX = max(256nCK, 320ns)		CK	
ZQCS command: Short calibration time	^t ZQCS	MIN = n/a MAX = max(64nCK, 80ns)		CK	
Initialization and Reset Timing					
Exit reset from CKE HIGH to a valid command	^t XPR	MIN = greater of 5CK or ^t RFC + 10ns; MAX = n/a		CK	
Begin power supply ramp to power supplies stable	^t VDDPR	MIN = n/a; MAX = 200		ms	
RESET# LOW to power supplies stable	^t RPS	MIN = 0; MAX = 200		ms	
RESET# LOW to I/O and R _{TT} High-Z	^t IOZ	MIN = n/a; MAX = 20		ns	35

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-1866		Unit	Notes
		Min	Max		
Refresh Timing					
REFRESH-to-ACTIVATE or REFRESH command period	'RFC – 1Gb	MIN = 110; MAX = 70,200		ns	
	'RFC – 2Gb	MIN = 160; MAX = 70,200		ns	
	'RFC – 4Gb	MIN = 260; MAX = 70,200		ns	
	'RFC – 8Gb	MIN = 350; MAX = 70,200		ns	
Maximum refresh period	–	T _C ≤ 85°C	64 (1X)	ms	36
		T _C > 85°C	32 (2X)	ms	36
Maximum average periodic refresh	'REFI	T _C ≤ 85°C	7.8 (64ms/8192)	µs	36
		T _C > 85°C	3.9 (32ms/8192)	µs	36
Self Refresh Timing					
Exit self refresh to commands not requiring a locked DLL	'XS	MIN = greater of 5CK or 'RFC + 10ns; MAX = n/a		CK	
Exit self refresh to commands requiring a locked DLL	'XSDLL	MIN = 'DLLK (MIN); MAX = n/a		CK	28
Minimum CKE low pulse width for self refresh entry to self refresh exit timing	'CKESR	MIN = 'CKE (MIN) + CK; MAX = n/a		CK	
Valid clocks after self refresh entry or power-down entry	'CKSRE	MIN = greater of 5CK or 10ns; MAX = n/a		CK	
Valid clocks before self refresh exit, power-down exit, or reset exit	'CKSRX	MIN = greater of 5CK or 10ns; MAX = n/a		CK	
Power-Down Timing					
CKE MIN pulse width	'CKE (MIN)	Greater of 3CK or 5ns		CK	
Command pass disable delay	'CPDED	MIN = 2; MAX = n/a		CK	
Power-down entry to power-down exit timing	'PD	MIN = 'CKE (MIN); MAX = 9 * tREFI		CK	
Begin power-down period prior to CKE registered HIGH	'ANPD	WL - 1CK		CK	
Power-down entry period: ODT either synchronous or asynchronous	PDE	Greater of 'ANPD or 'RFC - REFRESH command to CKE LOW time		CK	
Power-down exit period: ODT either synchronous or asynchronous	PDX	'ANPD + 'XPDLL		CK	

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-1866		Unit	Notes
		Min	Max		
Power-Down Entry Minimum Timing					
ACTIVATE command to power-down entry	'ACTPDEN	MIN = 2		CK	
PRECHARGE/PRECHARGE ALL command to power-down entry	'PRPDEN	MIN = 2		CK	
REFRESH command to power-down entry	'REFPDEN	MIN = 2		CK	37
MRS command to power-down entry	'MRSPDEN	MIN = tMOD (MIN)		CK	
READ/READ with auto precharge command to power-down entry	'RDPDEN	MIN = RL + 4 + 1		CK	
WRITE command to power-down entry	'WRPDEN	MIN = WL + 4 + tWR/tCK (AVG)		CK	
	'WRPDEN	MIN = WL + 2 + tWR/tCK (AVG)		CK	
WRITE with auto pre-charge command to power-down entry	'WRAP-DEN	MIN = WL + 4 + WR + 1		CK	
	'WRAP-DEN	MIN = WL + 2 + WR + 1		CK	
Power-Down Exit Timing					
DLL on, any valid command, or DLL off to commands not requiring locked DLL	'XP	MIN = greater of 3CK or 6ns; MAX = n/a		CK	
Precharge power-down with DLL off to commands requiring a locked DLL	'XPDLL	MIN = greater of 10CK or 24ns; MAX = n/a		CK	28
ODT Timing					
R _{TT} synchronous turn-on delay	ODTL on	CWL + AL - 2CK		CK	38
R _{TT} synchronous turn-off delay	ODTL off	CWL + AL - 2CK		CK	40
R _{TT} turn-on from ODTL on reference	'AON	-195	195	ps	23, 38
R _{TT} turn-off from ODTL off reference	'AOF	0.3	0.7	CK	39, 40
Asynchronous R _{TT} turn-on delay (power-down with DLL off)	'AONPD	MIN = 2; MAX = 8.5		ns	38
Asynchronous R _{TT} turn-off delay (power-down with DLL off)	'AOFPD	MIN = 2; MAX = 8.5		ns	40
ODT HIGH time with WRITE command and BL8	ODTH8	MIN = 6; MAX = n/a		CK	

Table 51 : Electrical Characteristics and AC Operating Conditions for Speed Extensions (Continued)

Notes 1–8 apply to the entire table

Parameter	Symbol	DDR3-1866		Unit	Notes
		Min	Max		
ODT HIGH time without WRITE command or with WRITE command and BC4	ODTH4	MIN = 4; MAX = n/a		CK	
Dynamic ODT Timing					
$R_{TT, nom}$ -to- $R_{TT(WR)}$ change skew	ODTLcnw	WL - 2CK		CK	
$R_{TT(WR)}$ -to- $R_{TT, nom}$ change skew - BC4	ODTLcwn4	4CK + ODTLoff		CK	
$R_{TT(WR)}$ -to- $R_{TT, nom}$ change skew - BL8	ODTLcwn8	6CK + ODTLoff		CK	
R_{TT} dynamic change skew	^t ADC	0.3	0.7	CK	39
Write Leveling Timing					
First DQS, DQS# rising edge	^t WLMRD	40	–	CK	
DQS, DQS# delay	^t WLDQSEN	25	–	CK	
Write leveling setup from rising CK, CK# crossing to rising DQS, DQS# crossing	^t WLS	140	–	ps	
Write leveling hold from rising DQS, DQS# crossing to rising CK, CK# crossing	^t WLH	140	–	ps	
Write leveling output delay	^t WLO	0	7.5	ns	
Write leveling output error	^t WLOE	0	2	ns	

- Notes :
1. AC timing parameters are valid from specified T_C MIN to T_C MAX values.
 2. All voltages are referenced to VSS.
 3. Output timings are only valid for R_{ON34} output buffer selection.
 4. The unit tCK (AVG) represents the actual tCK (AVG) of the input clock under operation.
The unit CK represents one clock cycle of the input clock, counting the actual clock edges.
 5. AC timing and I_{DD} tests may use a V_{IL} -to- V_{IH} swing of up to 900mV in the test environment, but input timing is still referenced to V_{REF} (except tIS, tIH, tDS, and tDH use the AC/DC trip points and CK, CK# and DQS, DQS# use their crossing points). The minimum slew rate for the input signals used to test the device is 1 V/ns for single-ended inputs and 2 V/ns for differential inputs in the range between $V_{IL(AC)}$ and $V_{IH(AC)}$.
 6. All timings that use time-based values (ns, μ s, ms) should use tCK (AVG) to determine the correct number of clocks (Table51 uses CK or tCK [AVG] interchangeably). In the case of noninteger results, all minimum limits are to be rounded up to the nearest whole integer, and all maximum limits are to be rounded down to the nearest whole integer.
 7. Strobe or DQS_{diff} refers to the DQS and DQS# differential crossing point when DQS is the rising edge. Clock or CK refers to the CK and CK# differential crossing point when CK is the rising edge.
 8. This output load is used for all AC timing (except ODT reference timing) and slew rates. The actual test load may be different. The output signal voltage reference point is VDDQ/2 for single-ended signals and the crossing point for differential signals (see Figure 17).
 9. When operating in DLL disable mode, Dosilicon does not warrant compliance with normal mode timings or functionality.
 10. The clock's tCK (AVG) is the average clock over any 200 consecutive clocks and tCK (AVG) MIN is the smallest clock rate allowed, with the exception of a deviation due to clock jitter. Input clock jitter is allowed provided it does not exceed values specified and must be of a random Gaussian distribution in nature.
 11. Spread spectrum is not included in the jitter specification values. However, the input clock can accommodate spread spectrum at a sweep rate in the range of 20–60 kHz with an additional 1% of tCK (AVG) as a long-term jitter component; however, the spread spectrum may not use a clock rate below tCK (AVG) MIN.
 12. The clock's tCH (AVG) and tCL (AVG) are the average half clock period over any 200 consecutive clocks and is the smallest clock half period allowed, with the exception of a deviation due to clock jitter. Input clock jitter is allowed provided it does not exceed values specified and must be of a random Gaussian distribution in nature.
 13. The period jitter (tJITper) is the maximum deviation in the clock period from the average or nominal clock. It is allowed in either the positive or negative direction.
 14. tCH (ABS) is the absolute instantaneous clock high pulse width as measured from one rising edge to the following falling edge.
 15. tCL (ABS) is the absolute instantaneous clock low pulse width as measured from one falling edge to the following rising edge.
 16. The cycle-to-cycle jitter tJITcc is the amount the clock period can deviate from one cycle to the next. It is important to keep cycle-to-cycle jitter at a minimum during the DLL locking time.
 17. The cumulative jitter error tERRnper, where n is the number of clocks between 2 and 50, is the amount of clock time allowed to accumulate consecutively away from the average clock over n number of clock cycles.
 18. tDS (base) and tDH (base) values are for a single-ended 1 V/ns slew rate DQs and 2 V/ns slew rate differential DQS, DQS#.
 19. These parameters are measured from a data signal (DM, DQ0, DQ1, and so forth) transition edge to its respective data strobe signal (DQS, DQS#) crossing.
 20. The setup and hold times are listed converting the base specification values (to which derating tables apply) to VREF when the slew rate is 1 V/ns. These values, with a slew rate of 1 V/ns, are for reference only.
 21. When the device is operated with input clock jitter, this parameter needs to be derated by the actual tJITper (larger of tJITper (MIN) or tJITper (MAX) of the input clock (output deratings are relative to the SDRAM input clock).
 22. Single-ended signal parameter.
 23. The DRAM output timing is aligned to the nominal or average clock. Most output parameters must be derated by the actual jitter error when input clock jitter is present, even when within specification. This results in each parameter becoming larger. The following parameters are required to be derated by subtracting tERR10per (MAX): tDQSCK (MIN), tLZDQS (MIN), tLZDQ (MIN), and tAON (MIN). The following parameters are required to be derated by subtracting tERR10per (MIN) : tDQSCK (MAX), tHZ (MAX), tLZDQS (MAX), tLZDQ (MAX), and tAON (MAX). The parameter tRPRE(MIN) is derated by subtracting tJITper (MAX), while tRPRE (MAX) is derated by subtracting tJITper (MIN).
 24. The maximum preamble is bound by tLZDQS (MAX).

25. These parameters are measured from a data strobe signal (DQS, DQS#) crossing to its respective clock signal (CK, CK#) crossing. The specification values are not affected by the amount of clock jitter applied, as these are relative to the clock signal crossing. These parameters should be met whether clock jitter is present.
26. The tDQSCK (DLL_DIS) parameter begins CL + AL - 1 cycles after the READ command.
27. The maximum postamble is bound by tHZDQS (MAX).
28. Commands requiring a locked DLL are: READ (and RDAP) and synchronous ODT commands. In addition, after any change of latency tXPDLL, timing must be met.
29. tIS (base) and tIH (base) values are for a single-ended 1 V/ns control/command/address slew rate and 2 V/ns CK, CK# differential slew rate.
30. These parameters are measured from a command/address signal transition edge to its respective clock (CK, CK#) signal crossing. The specification values are not affected by the amount of clock jitter applied as the setup and hold times are relative to the clock signal crossing that latches the command/address. These parameters should be met whether clock jitter is present.
31. For these parameters, the DDR3L SDRAM device supports $tnPARAM (nCK) = RU(tPARAM [ns]/tCK[AVG] [ns])$, assuming all input clock jitter specifications are satisfied. For example, the device will support $tnRP (nCK)=RU(tRP/tCK [AVG])$ if all input clock jitter specifications are met. This means that for DDR3-800 6-6-6, of which $tRP = 5ns$, the device will support $tnRP = RU(tRP/tCK[AVG]) = 6$ as long as the input clock jitter specifications are met. That is, the PRECHARGE command at T0 and the ACTIVATE command at T0 + 6 are valid even if six clocks are less than 15ns due to input clock jitter.
32. During READs and WRITEs with auto precharge, the DDR3L SDRAM will hold off the internal PRECHARGE command until tRAS (MIN) has been satisfied.
33. When operating in DLL disable mode, the greater of 4CK or 15ns is satisfied for tWR.
34. The start of the write recovery time is defined as follows:
 - For BL8 (fixed by MRS or OTF): Rising clock edge four clock cycles after WL
 - For BC4 (OTF): Rising clock edge four clock cycles after WL
 - For BC4 (fixed by MRS): Rising clock edge two clock cycles after WL
35. RESET# should be LOW as soon as power starts to ramp to ensure the outputs are in High-Z. Until RESET# is LOW, the outputs are at risk of driving and could result in excessive current, depending on bus activity.
36. The refresh period is 64ms when TC is less than or equal to 85°C. This equates to an average refresh rate of 7.8125µs. However, nine REFRESH commands should be asserted at least once every 70.3µs. When TC is greater than 85°C, the refresh period is 32ms.
37. Although CKE is allowed to be registered LOW after a REFRESH command when tREFPDEN (MIN) is satisfied, there are cases where additional time such as tXPDLL (MIN) is required.
38. ODT turn-on time MIN is when the device leaves High-Z and ODT resistance begins to turn on. ODT turn-on time maximum is when the ODT resistance is fully on. The ODT reference load is shown in Figure 11. Designs that were created prior to JEDEC tightening the maximum limit from 9ns to 8.5ns will be allowed to have a 9ns maximum.
39. Half-clock output parameters must be derated by the actual tERR10per and tJITdty when input clock jitter is present. This results in each parameter becoming larger. The parameters tADC (MIN) and tAOF (MIN) are each required to be derated by subtracting both tERR10per (MAX) and tJITdty (MAX). The parameters tADC (MAX) and tAOF (MAX) are required to be derated by subtracting both tERR10per (MAX) and tJITdty (MAX).
40. ODT turn-off time minimum is when the device starts to turn off ODT resistance. ODT turn-off time maximum is when the DRAM buffer is in High-Z. The ODT reference load is shown in Figure 11. This output load is used for ODT timings (see Figure 18).
41. Pulse width of a input signal is defined as the width between the first crossing of $V_{REF(DC)}$ and the consecutive crossing of $V_{REF(DC)}$.
42. Should the clock rate be larger than tRFC (MIN), an AUTO REFRESH command should have at least one NOP command between it and another AUTO REFRESH command. Additionally, if the clock rate is slower than 40ns(25 MHz), all REFRESH commands should be followed by a PRECHARGE ALL command.
43. DRAM devices should be evenly addressed when being accessed. Disproportionate accesses to a particular row address may result in a reduction of REFRESH characteristics or product lifetime.
44. When two $V_{IH(AC)}$ values (and two corresponding $V_{IL(AC)}$ values) are listed for a specific speed bin, the user may choose either value for the input AC level. Whichever value is used, the associated setup time for that AC level must also be used. Additionally, one $V_{IH(AC)}$ value may be used for address/command inputs and the other $V_{IH(AC)}$ value may be used for data inputs. For example, for DDR3-800, two input AC levels are defined : $V_{IH(AC175),min}$ and $V_{IH(AC150),min}$ (corresponding $V_{IL(AC175),min}$ and $V_{IL(AC150),min}$. For DDR3-800, the address/ command inputs must use either $V_{IH(AC175),min}$ with tIS(AC175) of 200ps or $V_{IH(150),min}$ with tIS(AC150) of 350ps; independently, the data inputs must use either $V_{IH(AC175),min}$ with tDS(AC175) of 75ps or $V_{IH(AC150),min}$ with tDS(AC150) of 125ps.

Command and Address Setup, Hold, and Derating

The total tIS (setup time) and tIH (hold time) required is calculated by adding the data sheet tIS (base) and tIH (base) values (see Table 52; values come from Table 50 to the ΔtIS and ΔtIH derating values (see Table 53 and Table 54), respectively.

Example: $tIS(\text{total setup time}) = tIS(\text{base}) + \Delta tIS$. For a valid transition, the input signal has to remain above/below $V_{IH(AC)}/V_{IL(AC)}$ for some time $tVAC$ (see Table 54).

Although the total setup time for slow slew rates might be negative (for example, a valid input signal will not have reached $V_{IH(AC)}/V_{IL(AC)}$ at the time of the rising clock transition), a valid input signal is still required to complete the transition and to reach $V_{IH(AC)}/V_{IL(AC)}$ (see Figure 2) for input signal requirements). For slew rates that fall between the values listed in Table 54 and Table 57, the derating values may be obtained by linear interpolation.

Setup (tIS) nominal slew rate for a rising signal is defined as the slew rate between the last crossing of $V_{REF(DC)}$ and the first crossing of $V_{IH(AC)min}$. Setup (tIS) nominal slew rate for a falling signal is defined as the slew rate between the last crossing of $V_{REF(DC)}$ and the first crossing of $V_{IL(AC)max}$. If the actual signal is always earlier than the nominal slew rate line between the shaded $V_{REF(DC)}$ -to-AC region, use the nominal slew rate for derating value (see Figure 21). If the actual signal is later than the nominal slew rate line anywhere between the shaded $V_{REF(DC)}$ -to-AC region, the slew rate of a tangent line to the actual signal from the AC level to the DC level is used for derating value (see Figure 23).

Hold (tIH) nominal slew rate for a rising signal is defined as the slew rate between the last crossing of $V_{IL(DC)max}$ and the first crossing of $V_{REF(DC)}$. Hold (tIH) nominal slew rate for a falling signal is defined as the slew rate between the last crossing of $V_{IH(DC)min}$ and the first crossing of $V_{REF(DC)}$. If the actual signal is always later than the nominal slew rate line between the shaded DC-to- $V_{REF(DC)}$ region, use the nominal slew rate for derating value (see Figure 22). If the actual signal is earlier than the nominal slew rate line anywhere between the shaded DC-to- $V_{REF(DC)}$ region, the slew rate of a tangent line to the actual signal from the DC level to the $V_{REF(DC)}$ level is used for derating value (see Figure 24).

Table 52 : Command and Address Setup and Hold Values Referenced – AC/DC-Based

Symbol	800	1066	1333	1600	1866	Unit	Reference
$tIS(\text{base, AC160})$	215	140	80	60	–	ps	$V_{IH(AC)}/V_{IL(AC)}$
$tIS(\text{base, AC135})$	365	290	205	185	65	ps	$V_{IH(AC)}/V_{IL(AC)}$
$tIS(\text{base, AC125})$	–	–	–	–	150	ps	$V_{IH(AC)}/V_{IL(AC)}$
$tIH(\text{base, DC90})$	285	210	150	130	110	ps	$V_{IH(DC)}/V_{IL(DC)}$

Table 53 : DDR3L-800/1066/1333/1600 Derating Values t_{IS}/t_{IH} – AC160/DC90-Based

$\Delta t_{IS}, \Delta t_{IH}$ Derating (ps) – AC/DC-Based																
CMD/ ADDR Slew Rate V/ns	CK, CK# Differential Slew Rate															
	4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}
2.0	80	45	80	45	80	45	88	53	96	61	104	69	112	79	120	95
1.5	53	30	53	30	53	30	61	38	69	46	77	54	85	64	93	80
1.0	0	0	0	0	0	0	8	8	16	16	24	24	32	34	40	50
0.9	-1	-3	-1	-3	-1	-3	7	5	15	13	23	21	31	31	39	47
0.8	-3	-8	-3	-8	-3	-8	5	1	13	9	21	17	29	27	37	43
0.7	-5	-13	-5	-13	-5	-13	3	-5	11	3	19	11	27	21	35	37
0.6	-8	-20	-8	-20	-8	-20	0	-12	8	-4	16	4	24	14	32	30
0.5	-20	-30	-20	-30	-20	-30	-12	-22	-4	-14	4	-6	12	4	20	20
0.4	-40	-45	-40	-45	-40	-45	-32	-37	-24	-29	-16	-21	-8	-11	0	5

Table 54 : DDR3L-800/1066/1333/1600 Derating Values for t_{IS}/t_{IH} – AC135/DC90-Based

$\Delta t_{IS}, \Delta t_{IH}$ Derating (ps) – AC/DC-Based																
CMD/ ADDR Slew Rate V/ns	CK, CK# Differential Slew Rate															
	4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}	Δt_{IS}	Δt_{IH}
2.0	68	45	68	45	68	45	76	53	84	61	92	69	100	79	108	95
1.5	45	30	45	30	45	30	53	38	61	46	69	54	77	64	85	80
1.0	0	0	0	0	0	0	8	8	16	16	24	24	32	34	40	50
0.9	2	-3	2	-3	2	-3	10	5	18	13	26	21	34	31	42	47
0.8	3	-8	3	-8	3	-8	11	1	19	9	27	17	35	27	43	43
0.7	6	-13	6	-13	6	-13	14	-5	22	3	30	11	38	21	46	37
0.6	9	-20	9	-20	9	-20	17	-12	25	-4	33	4	41	14	49	30
0.5	5	-30	5	-30	5	-30	13	-22	21	-14	29	-6	37	4	45	20
0.4	-3	-45	-3	-45	-3	-45	6	-37	14	-29	22	-21	30	-11	38	5

Table 55 : DDR3L-1866 Derating Values for tIS/tIH – AC125/DC90-Based

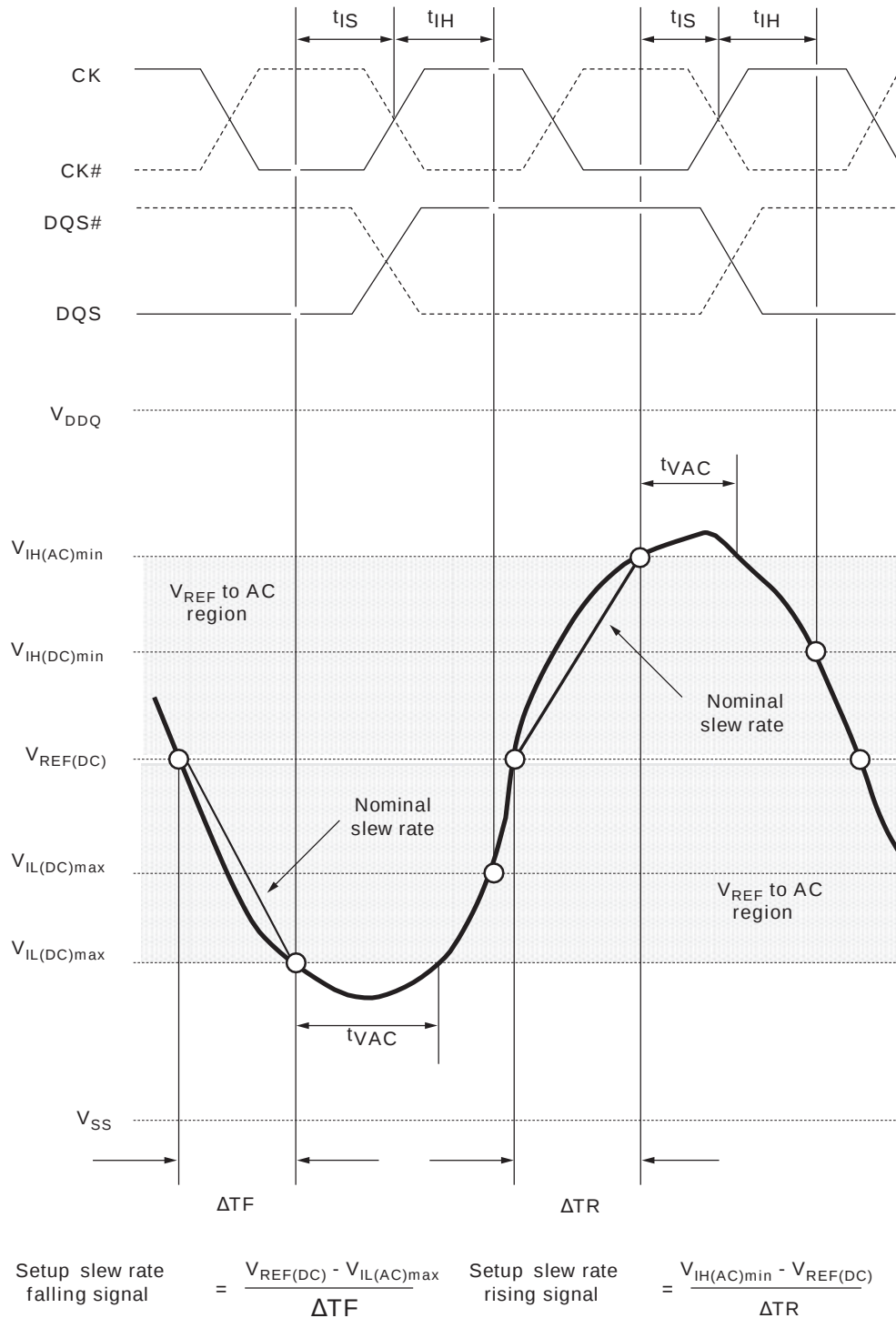
$\Delta^{\text{I}}\text{S}, \Delta^{\text{I}}\text{H}$ Derating (ps) – AC/DC-Based																
CMD/ ADDR Slew Rate V/ns	CK, CK# Differential Slew Rate															
	4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$	$\Delta^{\text{I}}\text{S}$	$\Delta^{\text{I}}\text{H}$
2.0	63	45	63	45	63	45	71	53	79	61	87	69	95	79	103	95
1.5	42	30	42	30	42	30	50	38	58	46	66	54	74	64	82	80
1.0	0	0	0	0	0	0	8	8	16	16	24	24	32	34	40	50
0.9	3	-3	3	-3	3	-3	11	5	19	13	27	21	35	31	43	47
0.8	6	-8	6	-8	6	-8	14	1	22	9	30	17	38	27	46	43
0.7	10	-13	10	-13	10	-13	18	-5	26	3	34	11	42	21	50	37
0.6	16	-20	16	-20	16	-20	24	-12	32	-4	40	4	48	14	56	30
0.5	15	-30	15	-30	15	-30	23	-22	31	-14	39	-6	47	4	55	20
0.4	13	-45	13	-45	13	-45	21	-37	29	-29	37	-21	45	-11	53	5

Table 56 : DDR3L Minimum Required Time tVAC Above VIH(AC) (Below VIL[AC]) for Valid ADD/CMD Transition

Slew Rate (V/ns)	DDR3L-800/1066/1333/1600		DDR3L-1866	
	tVAC at 160mV (ps)	tVAC at 135mV (ps)	tVAC at 135mV (ps)	tVAC at 125mV (ps)
>2.0	200	213	200	205
2.0	200	213	200	205
1.5	173	190	178	184
1.0	120	145	133	143
0.9	102	130	118	129
0.8	80	111	99	111
0.7	51	87	75	89
0.6	13	55	43	59
0.5	Note 1	10	Note 1	18
<0.5	Note 1	10	Note 1	18

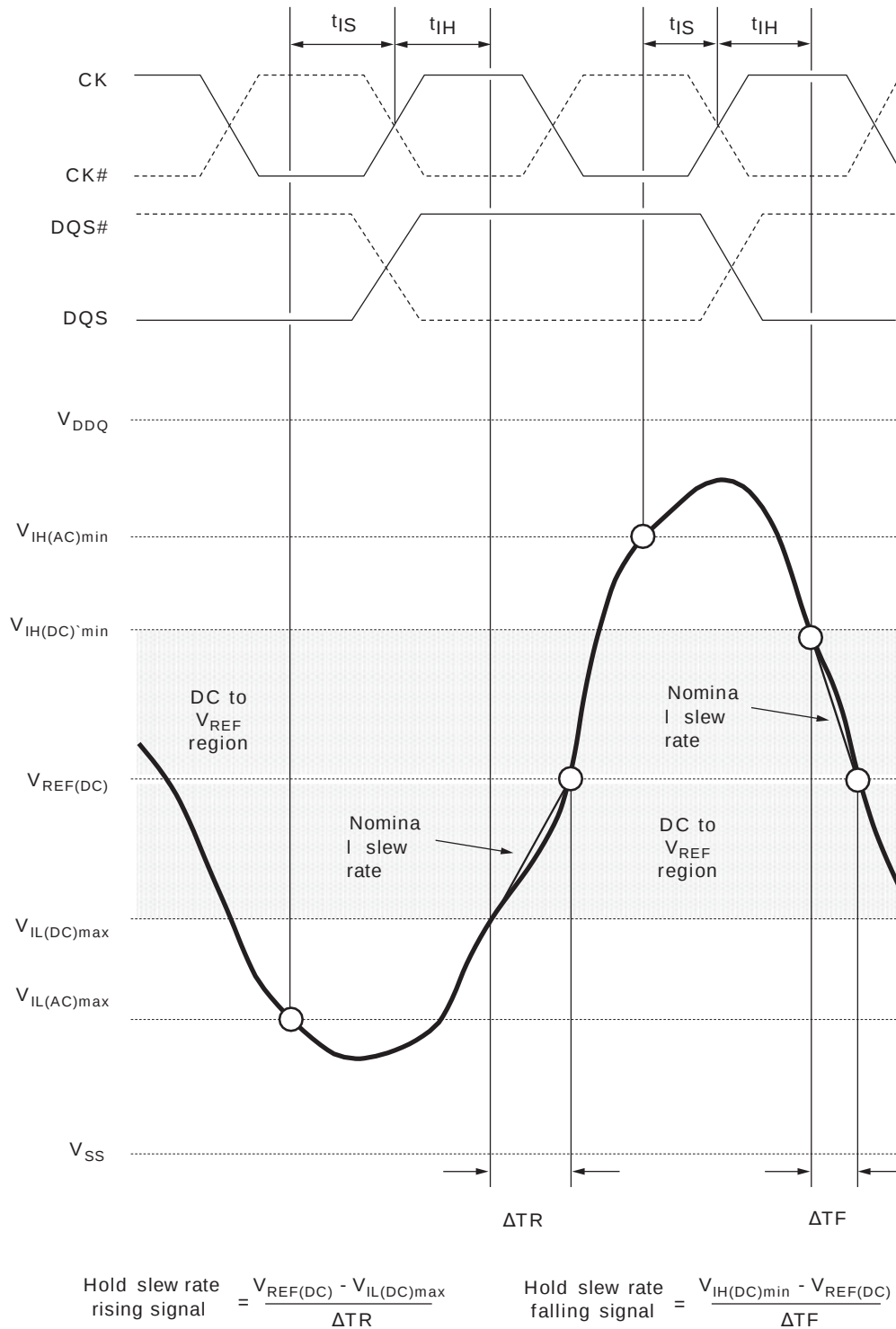
Note : 1. Rising input signal shall become equal to or greater than VIH(ac) level and Falling input signal shall become equal to or less than VIL(ac) level.

Figure 21 : Nominal Slew Rate and tVAC for tIS (Command and Address – Clock)



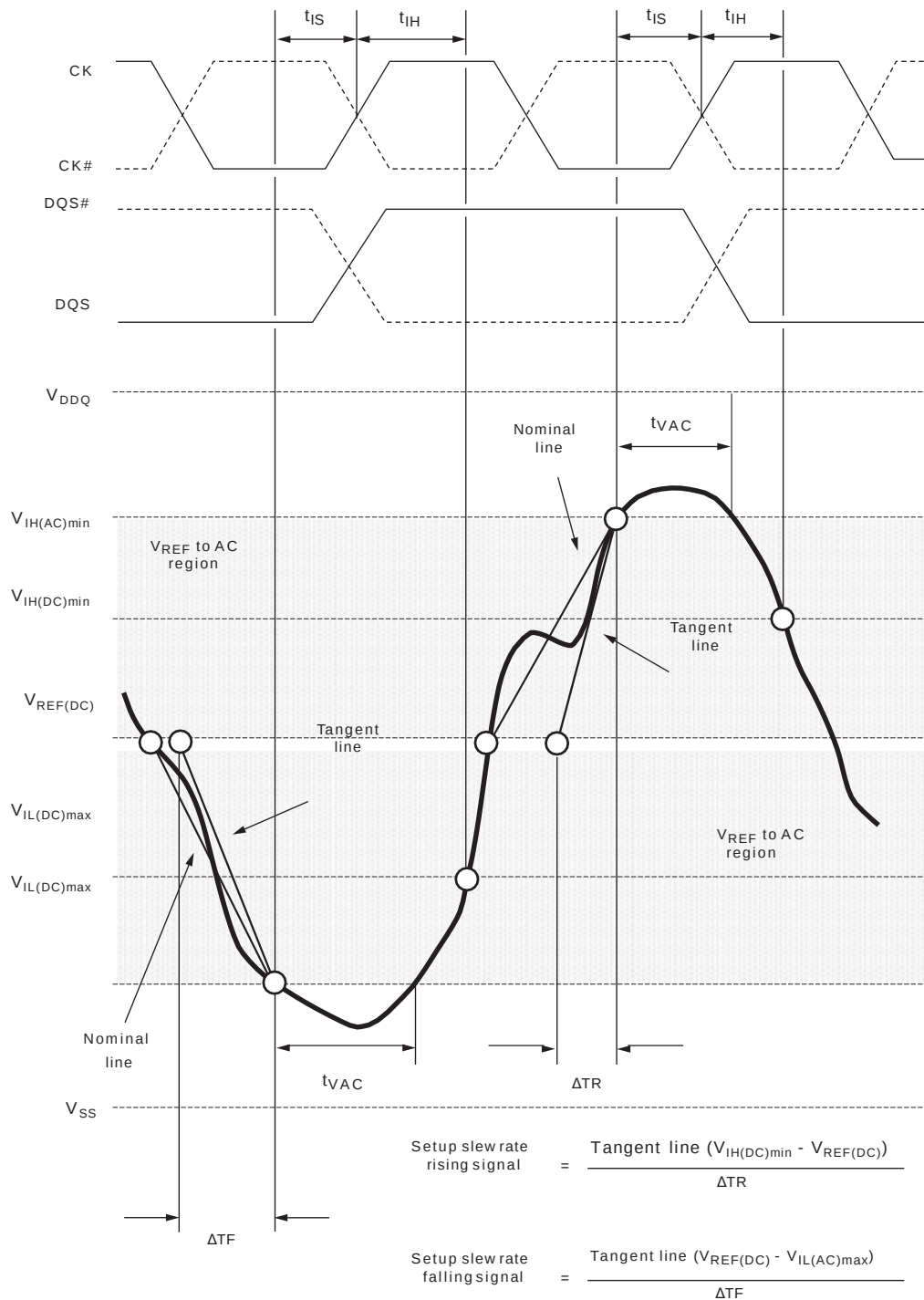
Note : 1. The clock and the strobe are drawn on different time scales.

Figure 22 : Nominal Slew Rate for t_{IH} (Command and Address – Clock)



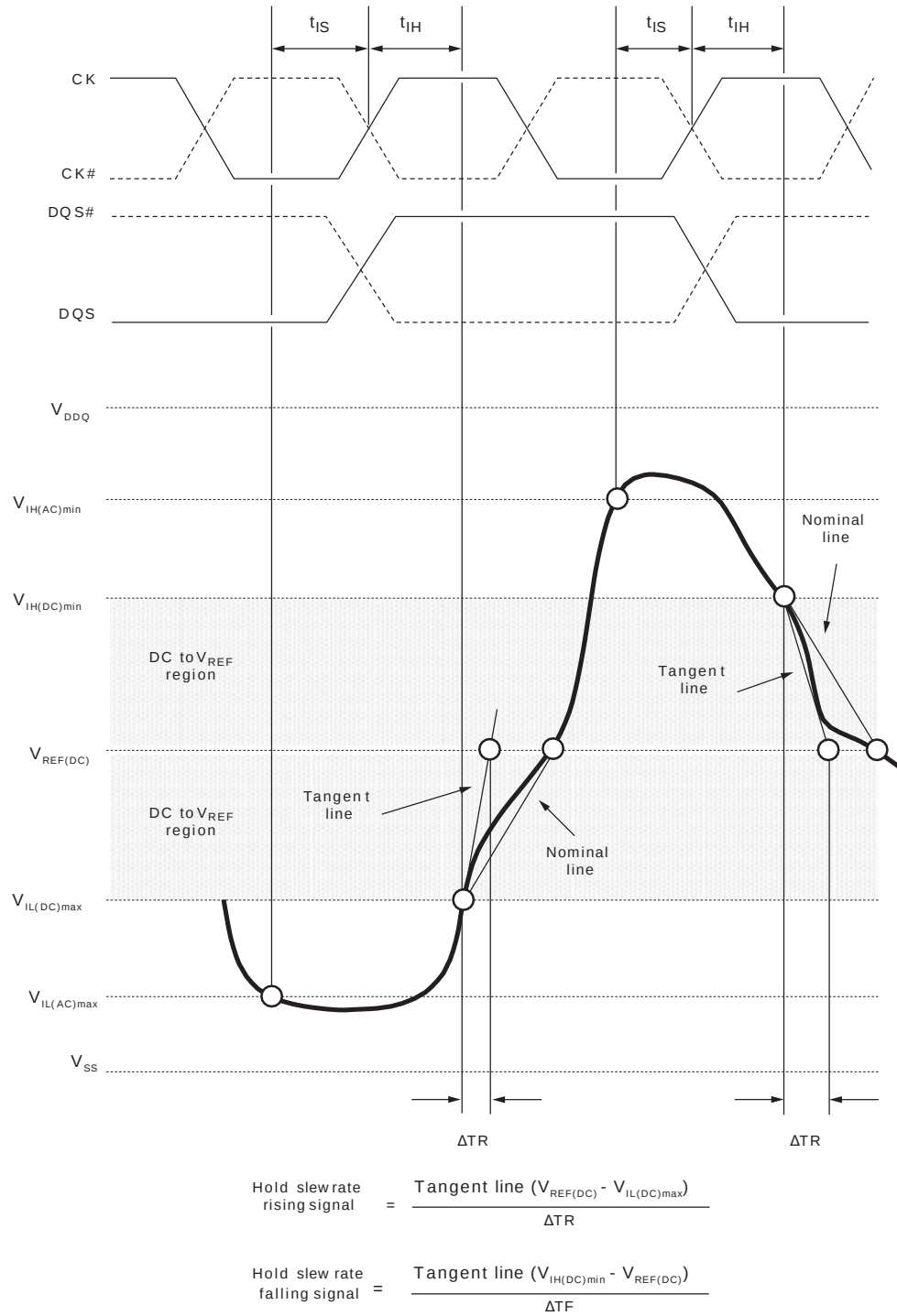
Note : 1. The clock and the strobe are drawn on different time scales.

Figure 23 : Tangent Line for tIS (Command and Address – Clock)



Note: 1. The clock and the strobe are drawn on different time scales.

Figure 24 : Tangent Line for tIH (Command and Address – Clock)



Note : 1. The clock and the strobe are drawn on different time scales.

Data Setup, Hold, and Derating

The total tDS (setup time) and tDH (hold time) required is calculated by adding the data sheet tDS (base) and tDH (base) values (see Table 57; values come from Table 50) to the ΔtDS and ΔtDH derating values (see Table 58), Table 59) or Table 64) respectively. Example : tDS (total setup time) = tDS (base) + ΔtDS . For a valid transition, the input signal has to remain above/below VIH(AC)/VIL(AC) for some time tVAC(see Table 61).

Although the total setup time for slow slew rates might be negative (for example, a valid input signal will not have reached VIH(AC)/VIL(AC) at the time of the rising clock transition), a valid input signal is still required to complete the transition and to reach VIH/VIL(AC). For slew rates that fall between the values listed in Table 58, Table 59 or Table 59, the derating values may be obtained by linear interpolation.

Setup (tDS) nominal slew rate for a rising signal is defined as the slew rate between the last crossing of VREF(DC) and the first crossing of VIH(AC)min. Setup (tDS) nominal slew rate for a falling signal is defined as the slew rate between the last crossing of VREF(DC) and the first crossing of VIL(AC)max. If the actual signal is always earlier than the nominal slew rate line between the shaded VREF(DC)-to-AC region, use the nominal slew rate for derating value (see Figure 25). If the actual signal is later than the nominal slew rate line anywhere between the shaded VREF(DC)-to-AC region, the slew rate of a tangent line to the actual signal from the AC level to the DC level is used for derating value (see Figure 27).

Hold (tDH) nominal slew rate for a rising signal is defined as the slew rate between the last crossing of VIL(DC)max and the first crossing of VREF(DC). Hold (tDH) nominal slew rate for a falling signal is defined as the slew rate between the last crossing of VIH(DC)min and the first crossing of VREF(DC). If the actual signal is always later than the nominal slew rate line between the shaded DC-to-VREF(DC) region, use the nominal slew rate for derating value (see Figure 26). If the actual signal is earlier than the nominal slew rate line anywhere between the shaded DC-to-VREF(DC) region, the slew rate of a tangent line to the actual signal from the DC-to-VREF(DC) region is used for derating value (see Figure 28).

Table 57 : DDR3L Data Setup and Hold Values at 1 V/ns (DQS, DQS# at 2 V/ns) – AC/DC-Based

Symbol	800	1066	1333	1600	1866	Unit	Reference
tDS (base) AC160	90	40	-	-	-	ps	VIH(AC)/VIL(AC)
tDS (base) AC135	140	90	45	25	-	ps	
tDS (base) AC130	-	-	-	-	70	ps	
tDH (base) DC90	160	110	75	55	-	ps	
tDH (base) DC90	-	-	-	-	75	ps	
Slew Rate Referenced	1	1	1	1	2	V/ns	

Table 58 : DDR3L Derating Values for tDS/tDH – AC160/DC90-Based

Shaded cells indicate slew rate combinations not supported

$\Delta tDS, \Delta tDH$ Derating (ps) – AC/DC-Based																
DQ Slew Rate V/ns	DQS, DQS# Differential Slew Rate															
	4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH	ΔtDS	ΔtDH
2.0	80	45	80	45	80	45										
1.5	53	30	53	30	53	30	61	38								
1.0	0	0	0	0	0	0	8	8	16	16						
0.9			-1	-3	-1	-3	7	5	15	13	23	21				
0.8					-3	-8	5	1	13	9	21	17	29	27		
0.7							-3	-5	11	3	19	11	27	21	35	37
0.6									8	-4	16	4	24	14	32	30
0.5											4	-6	12	4	20	20
0.4													-8	-11	0	5

Table 59 : DDR3L Derating Values for tDS/tDH – AC135/DC100-Based

Shaded cells indicate slew rate combinations not supported

$\Delta^t\text{DS}, \Delta^t\text{DH}$ Derating (ps) – AC/DC-Based																
DQ Slew Rate V/ns	DQS, DQS# Differential Slew Rate															
	4.0 V/ns		3.0 V/ns		2.0 V/ns		1.8 V/ns		1.6 V/ns		1.4 V/ns		1.2 V/ns		1.0 V/ns	
	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$	$\Delta^t\text{DS}$	$\Delta^t\text{DH}$
2.0	68	45	68	45	68	45										
1.5	45	30	45	30	45	30	53	38								
1.0	0	0	0	0	0	0	8	8	16	16						
0.9			2	-3	2	-3	10	5	18	13	26	21				
0.8					3	-8	11	1	19	9	27	17	35	27		
0.7							14	-5	22	3	30	11	38	21	46	37
0.6									25	-4	33	4	41	14	49	30
0.5											39	-6	37	4	45	20
0.4													30	-11	38	5

Table 60 : Derating Values for tDS/tDH – AC135/DC100-Based at 2V/ns

Shaded cells indicate slew rate combinations not supported

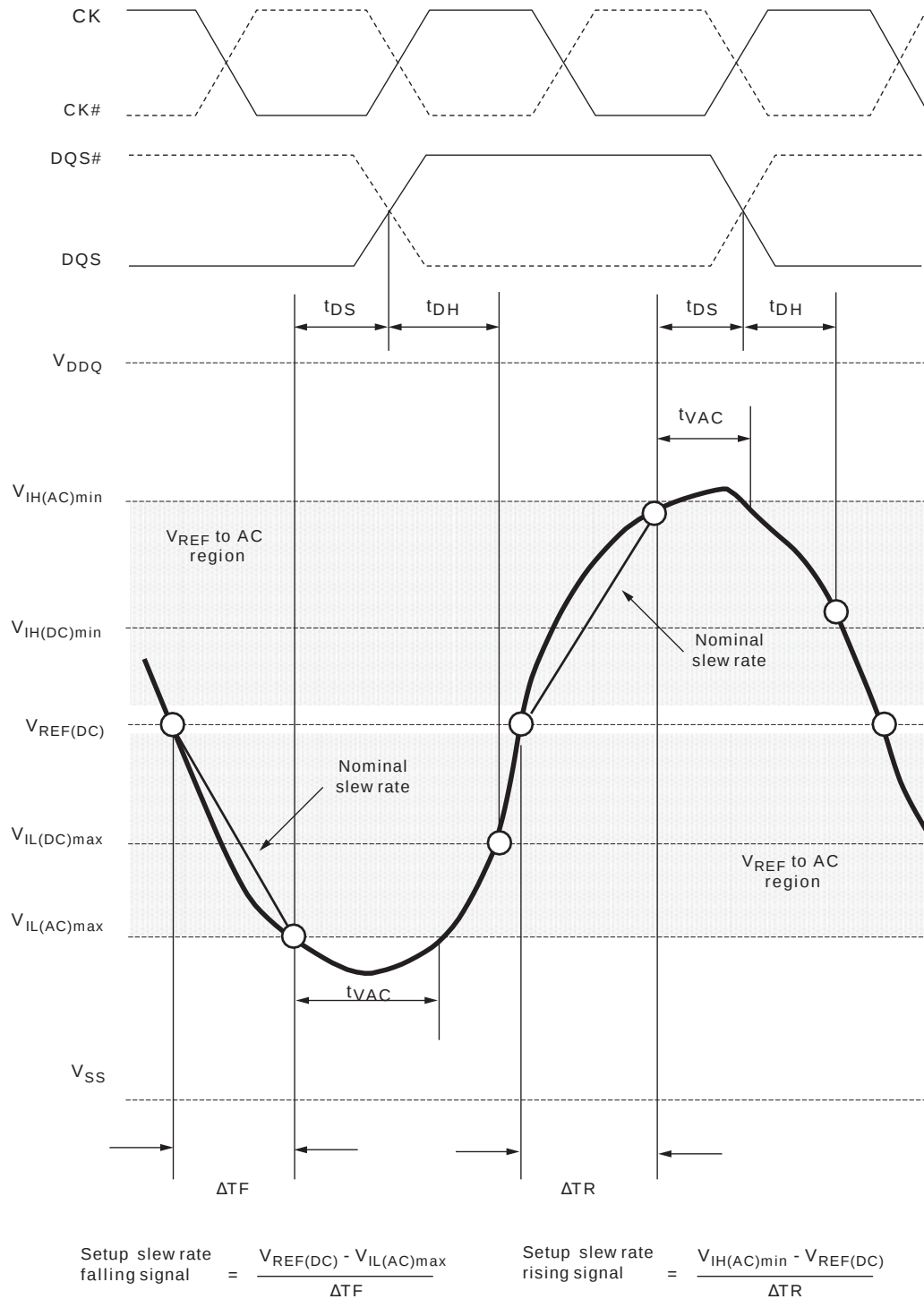
Δ^tDS, Δ^tDH Derating (ps) – AC/DC-Based																										
DQS, DQS# Differential Slew Rate																										
DQ Slew Rate V/ns		1.0 V/ns		1.2 V/ns		1.4 V/ns		1.6 V/ns		1.8 V/ns		2.0 V/ns		3.0 V/ns		4.0 V/ns		5.0 V/ns		6.0 V/ns		7.0 V/ns		8.0 V/ns		
		Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	Δ tDH	Δ tDS	
4.0																										
3.5																										
3.0																										
2.5																										
2.0																										
1.5																										
1.0																										
0.9																										
0.8																										
0.7		-8	-17	-24	-25	-34	-33	-42	-41	-50	-49															
0.6		-15	-13	-31	-21	-41	-29	-49	-37																	
0.5		-25	-15	-41	-23	-51	-31																			
0.4		-40	-20	-56	-28																					

Table 61 : DDR3L Required Minimum Time tVAC Above VIH(AC) (Below VIL(AC)) for Valid DQ Transition

Slew Rate (V/ns)	DDR3L-800/1066 160mV (ps) min	DDR3L-800/1066/1333 135mV (ps) min	DDR3L-1866 130mV (ps) min
>2.0	165	113	95
2.0	165	113	95
1.5	138	90	73
1.0	85	45	30
0.67	67	30	16
0.8	45	11	Note 1
0.7	16	Note 1	-
0.6	Note 1	Note 1	-
0.5	Note 1	Note 1	-
<0.5	Note 1	Note 1	-

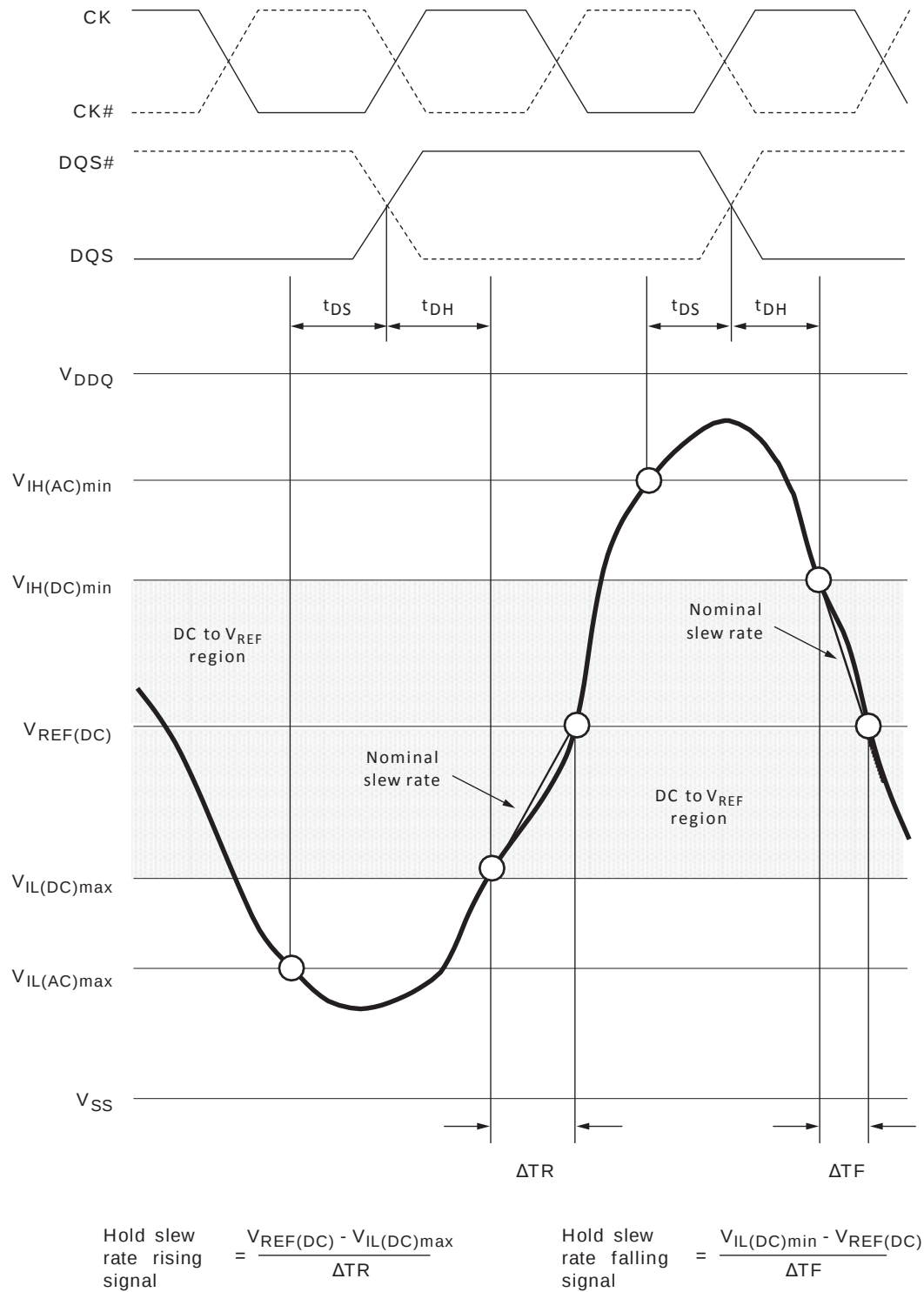
Note: 1. Rising input signal shall become equal to or greater than VIH(ac) level and Falling input signal shall become equal to or less than VIL(ac) level.

Figure 25 : Nominal Slew Rate and tVAC for tDS (DQ – Strobe)



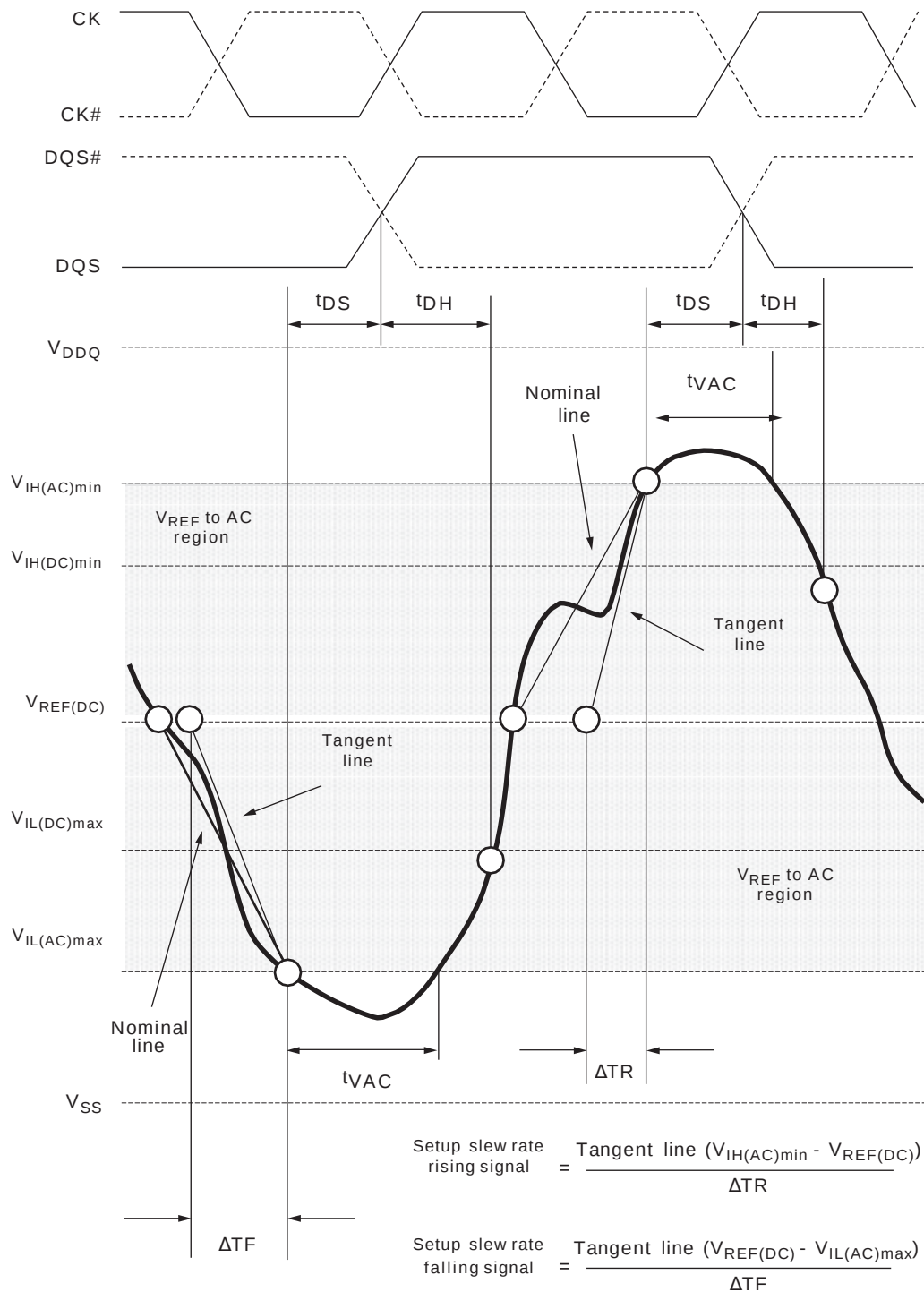
Note : 1. The clock and the strobe are drawn on different time scales.

Figure 26 : Nominal Slew Rate for t_{DH} (DQ – Strobe)



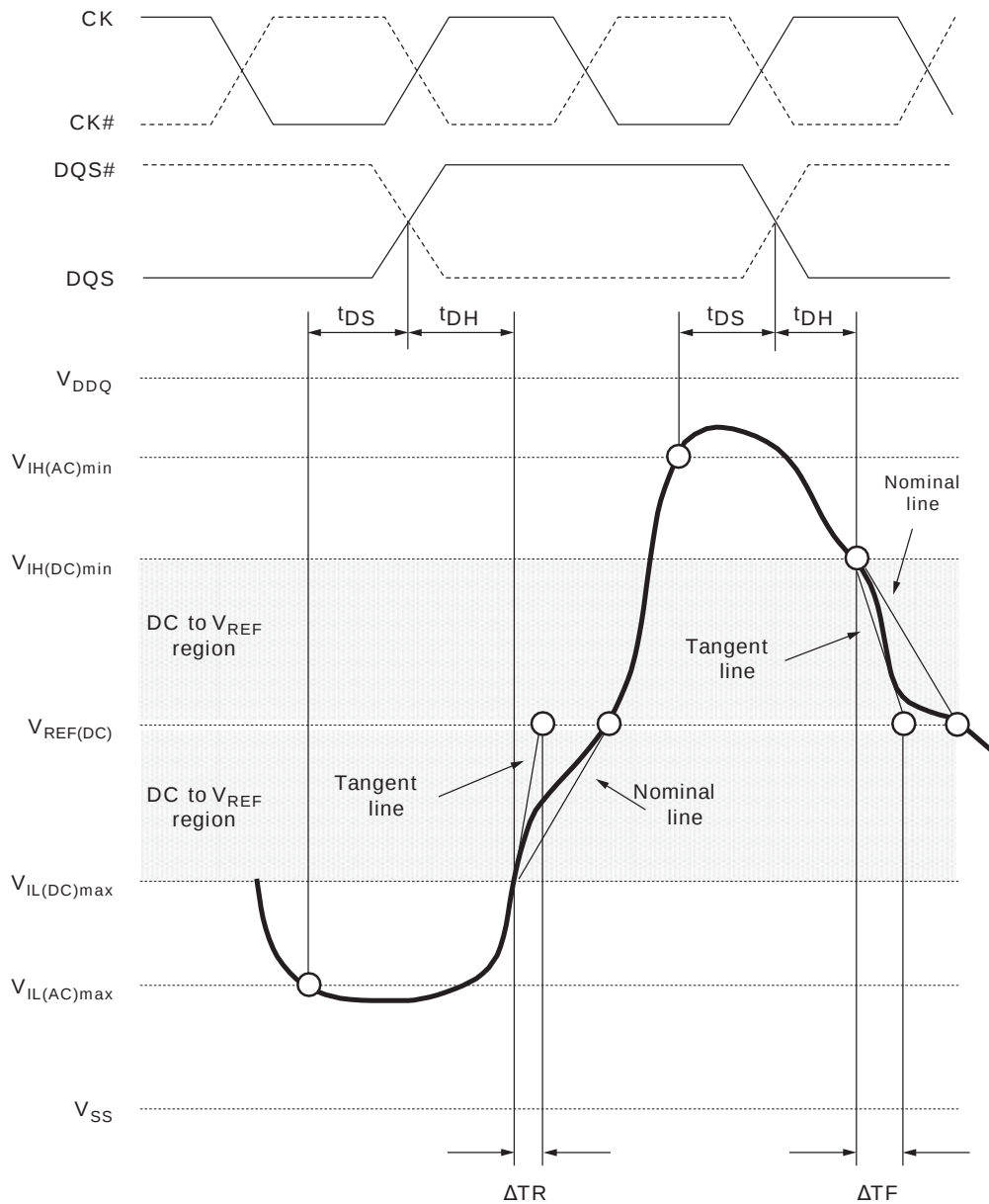
Note : 1. The clock and the strobe are drawn on different time scales.

Figure 27 : Tangent Line for tDS (DQ – Strobe)



Note : 1. The clock and the strobe are drawn on different time scales.

Figure 28 : Tangent Line for t_{DH} (DQ – Strobe)



$$\text{Hold slew rate rising signal} = \frac{\text{Tangent line } (V_{\text{REF(DC)}} - V_{\text{IL(DC)max}})}{\Delta \text{TR}}$$

$$\text{Hold slew rate falling signal} = \frac{\text{Tangent line } (V_{\text{IH(DC)min}} - V_{\text{REF(DC)}})}{\Delta \text{TF}}$$

Note: 1. The clock and the strobe are drawn on different time scales.

Commands – Truth Tables

Table 62 : Truth Table – Command

Notes 1–5 apply to the entire table

Function		Symbol	CKE		CS#	RAS#	CAS#	WE#	BA [2:0]	An	A12	A10	A[11, 9:0]	Notes
			Prev. Cycle	Next Cycle										
MODE REGISTER SET		MRS	H	H	L	L	L	L	BA	OP code				
REFRESH		REF	H	H	L	L	L	H	V	V	V	V	V	
Self refresh entry		SRE	H	L	L	L	L	H	V	V	V	V	V	6
Self refresh exit		SRX	L	H	H	V	V	V	V	V	V	V	V	6.7
					L	H	H	H						
Single-bank PRECHARGE		PRE	H	H	L	L	H	L	BA	V	V	L	V	
PRECHARGE all banks		PREA	H	H	L	L	H	L	V		V	H	V	
Bank ACTIVATE		ACT	H	H	L	L	H	H	BA	Row address (RA)				
WRITE	BL8MRS, BC4MRS	WR	H	H	L	H	L	L	BA	RFU	V	L	CA	8
	BC4OTF	WRS4	H	H	L	H	L	L	BA	RFU	L	L	CA	8
	BL8OTF	WRS8	H	H	L	H	L	L	BA	RFU	H	L	CA	8
WRITE with auto precharge	BL8MRS, BC4MRS	WRAP	H	H	L	H	L	L	BA	RFU	V	H	CA	8
	BC4OTF	WRAPS4	H	H	L	H	L	L	BA	RFU	L	H	CA	8
	BL8OTF	WRAPS8	H	H	L	H	L	L	BA	RFU	H	H	CA	8
READ	BL8MRS, BC4MRS	RD	H	H	L	H	L	H	BA	RFU	V	L	CA	8
	BC4OTF	RDS4	H	H	L	H	L	H	BA	RFU	L	L	CA	8
	BL8OTF	RDS8	H	H	L	H	L	H	BA	RFU	H	L	CA	8
READ with auto precharge	BL8MRS, BC4MRS	RDAP	H	H	L	H	L	H	BA	RFU	V	H	CA	8
	BC4OTF	RDAPS4	H	H	L	H	L	H	BA	RFU	L	H	CA	8
	BL8OTF	RDAPS8	H	H	L	H	L	H	BA	RFU	H	H	CA	8
NO OPERATION		NOP	H	H		H	H	H	V	V	V	V	V	9
Device DESELECTED		DES	H	H	H	X	X	X	X	X	X	X	X	10
Power-down entry		PDE	H	L	L	H	H	H	V	V	V	V	V	6
					H	V	V	V						
Power-down exit		PDX	L	H	L	H	H	H	V	V	V	V	V	6,11
					H	V	V	V						
ZQ CALIBRATION LONG		ZQCL	H	H	L	H	H	L	X	X	X	H	X	12
ZQ CALIBRATION SHORT		ZQCS	H	H	L	H	H	L	X	X	X	L	X	

- Notes :
1. Commands are defined by the states of CS#, RAS#, CAS#, WE#, and CKE at the rising edge of the clock. The MSB of BA, RA, and CA are device-, density-, and configuration dependent.
 2. RESET# is enabled LOW and used only for asynchronous reset. Thus, RESET# must be held HIGH during any normal operation.
 3. The state of ODT does not affect the states described in this table.
 4. Operations apply to the bank defined by the bank address. For MRS, BA selects one of four mode registers.
 5. "V" means "H" or "L" (a defined logic level), and "X" means "Don't Care."
 6. See Table 63 for additional information on CKE transition.
 7. Self refresh exit is asynchronous.
 8. Burst READs or WRITEs cannot be terminated or interrupted. MRS (fixed) and OTF BL/BC are defined in MR0.
 9. The purpose of the NOP command is to prevent the DRAM from registering any unwanted commands. A NOP will not terminate an operation that is executing.
 10. The DES and NOP commands perform similarly.
 11. The power-down mode does not perform any REFRESH operations.
 12. ZQ CALIBRATION LONG is used for either ZQinit (first ZQCL command during initialization) or ZQoper (ZQCL command after initialization).

Table 63 : Truth Table – CKE

Notes 1–2 apply to the entire table; see Table 62 for additional command details

Current State ³	CKE		Command ⁵ (RAS#, CAS#, WE#, CS#)	Action ⁵	Notes
	Previous Cycle ⁴ (<i>n</i> - 1)	Present Cycle ⁴ (<i>n</i>)			
Power-down	L	L	“Don’t Care”	Maintain power-down	
	L	H	DES or NOP	Power-down exit	
Self refresh	L	L	“Don’t Care”	Maintain self refresh	
	L	H	DES or NOP	Self refresh exit	
Bank(s) active	H	L	DES or NOP	Active power-down entry	
Reading	H	L	DES or NOP	Power-down entry	
Writing	H	L	DES or NOP	Power-down entry	
Precharging	H	L	DES or NOP	Power-down entry	
Refreshing	H	L	DES or NOP	Precharge power-down entry	
All banks idle	H	L	DES or NOP	Precharge power-down entry	6
	H	L	REFRESH	Self refresh	

- Notes :
1. All states and sequences not shown are illegal or reserved unless explicitly described elsewhere in this document.
 2. tCKE (MIN) means CKE must be registered at multiple consecutive positive clock edges. CKE must remain at the valid input level the entire time it takes to achieve the required number of registration clocks. Thus, after any CKE transition, CKE may not transition from its valid level during the time period of tIS + tCKE (MIN) + tIH.
 3. Current state = The state of the DRAM immediately prior to clock edge *n*.
 4. CKE (*n*) is the logic state of CKE at clock edge *n*; CKE (*n* - 1) was the state of CKE at the previous clock edge.
 5. COMMAND is the command registered at the clock edge (must be a legal command as defined in Table 62). Action is a result of COMMAND. ODT does not affect the states described in this table and is not listed.
 6. Idle state = All banks are closed, no data bursts are in progress, CKE is HIGH, and all timings from previous operations are satisfied. All self refresh exit and power-down exit parameters are also satisfied.

Commands

DESELECT

The Deselect (DES) command (CS# HIGH) prevents new commands from being executed by the DRAM. Operations already in progress are not affected.

NO OPERATION

The NO OPERATION (NOP) command (CS# LOW) prevents unwanted commands from being registered during idle or wait states. Operations already in progress are not affected.

ZQ CALIBRATION LONG

The ZQ CALIBRATION LONG (ZQCL) command is used to perform the initial calibration during a power-up initialization and reset sequence (see Figure 37). This command may be issued at any time by the controller, depending on the system environment. The ZQCL command triggers the calibration engine inside the DRAM. After calibration is achieved, the calibrated values are transferred from the calibration engine to the DRAM I/O, which are reflected as updated RON and ODT values. The DRAM is allowed a timing window defined by either tZQinit or tZQoper to perform a full calibration and transfer of values. When ZQCL is issued during the initialization sequence, the timing parameter tZQinit must be satisfied. When initialization is complete, subsequent ZQCL commands require the timing parameter tZQoper to be satisfied.

ZQ CALIBRATION SHORT

The ZQ CALIBRATION SHORT (ZQCS) command is used to perform periodic calibrations to account for small voltage and temperature variations. A shorter timing window is provided to perform the reduced calibration and transfer of values as defined by timing parameter tZQCS. A ZQCS command can effectively correct a minimum of 0.5% RON and RTT impedance error within 64 clock cycles, assuming the maximum sensitivities specified in DDR3L 34 Ohm Output Driver Sensitivity.

ACTIVATE

The ACTIVATE command is used to open (or activate) a row in a particular bank for a subsequent access. The value on the BA[2:0] inputs selects the bank, and the address provided on inputs A[n:0] selects the row. This row remains open (or active) for accesses until a PRECHARGE command is issued to that bank. A PRECHARGE command must be issued before opening a different row in the same bank.

READ

The READ command is used to initiate a burst read access to an active row. The address provided on inputs A[2:0] selects the starting column address, depending on the burst length and burst type selected (see Burst Order table for additional information). The value on input A10 determines whether auto precharge is used. If auto precharge is selected, the row being accessed will be precharged at the end of the READ burst. If auto precharge is not selected, the row will remain open for subsequent accesses. The value on input A12 (if enabled in the mode register) when the READ command is issued determines whether BC4 (chop) or BL8 is used. After a READ command is issued, the READ burst may not be interrupted.

Table 64 : READ Command Summary

Function		Symbol	CKE		CS#	RAS#	CAS#	WE#	BA [2:0]	An	A12	A10	A[11, 9:0]
			Prev. Cycle	Next Cycle									
READ	BL8MRS, BC4MRS	RD	H		L	H	L	H	BA	RFU	V	L	CA
	BC4OTF	RDS4	H		L	H	L	H	BA	RFU	L	L	CA
	BL8OTF	RDS8	H		L	H	L	H	BA	RFU	H	L	CA
READ with auto precharge	BL8MRS, BC4MRS	RDAP	H		L	H	L	H	BA	RFU	V	H	CA
	BC4OTF	RDAPS4	H		L	H	L	H	BA	RFU	L	H	CA
	BL8OTF	RDAPS8	H		L	H	L	H	BA	RFU	H	H	CA

WRITE

The WRITE command is used to initiate a burst write access to an active row. The value on the BA[2:0] inputs selects the bank. The value on input A10 determines whether auto precharge is used. The value on input A12 (if enabled in the MR) when the WRITE command is issued determines whether BC4 (chop) or BL8 is used. Input data appearing on the DQ is written to the memory array subject to the DM input logic level appearing coincident with the data. If a given DM signal is registered LOW, the corresponding data will be written to memory. If the DM signal is registered HIGH, the corresponding data inputs will be ignored and a WRITE will not be executed to that byte/column location..

Table 65 : WRITE Command Summary

Function		Symbol	CKE		CS#	RAS#	CAS#	WE#	BA [2:0]	An	A12	A10	A[11, 9:0]
			Prev. Cycle	Next Cycle									
WRITE	BL8MR BC4MR	WR	H		L	H	L	L	BA	RFU	V	L	CA
	BC4OTF	WRS4	H		L	H	L	L	BA	RFU	L	L	CA
	BL8OTF	WRS8	H		L	H	L	L	BA	RFU	H	L	CA
WRITE with auto precharge	BL8MRS BC4MRS	WRAP	H		L	H	L	L	BA	RFU	V	H	CA
	BC4OTF	WRAPS4	H		L	H	L	L	BA	RFU	L	H	CA
	BL8OTF	WRAPS8	H		L	H	L	L	BA	RFU	H	H	CA

PRECHARGE

The PRECHARGE command is used to de-activate the open row in a particular bank or in all banks. The bank(s) are available for a subsequent row access a specified time (tRP) after the PRECHARGE command is issued, except in the case of concurrent auto precharge.

A READ or WRITE command to a different bank is allowed during a concurrent auto precharge as long as it does not interrupt the data transfer in the current bank and does not violate any other timing parameters. Input A10 determines whether one or all banks are precharged. In the case where only one bank is precharged, inputs BA[2:0] select the bank; otherwise, BA[2:0] are treated as "Don't Care."

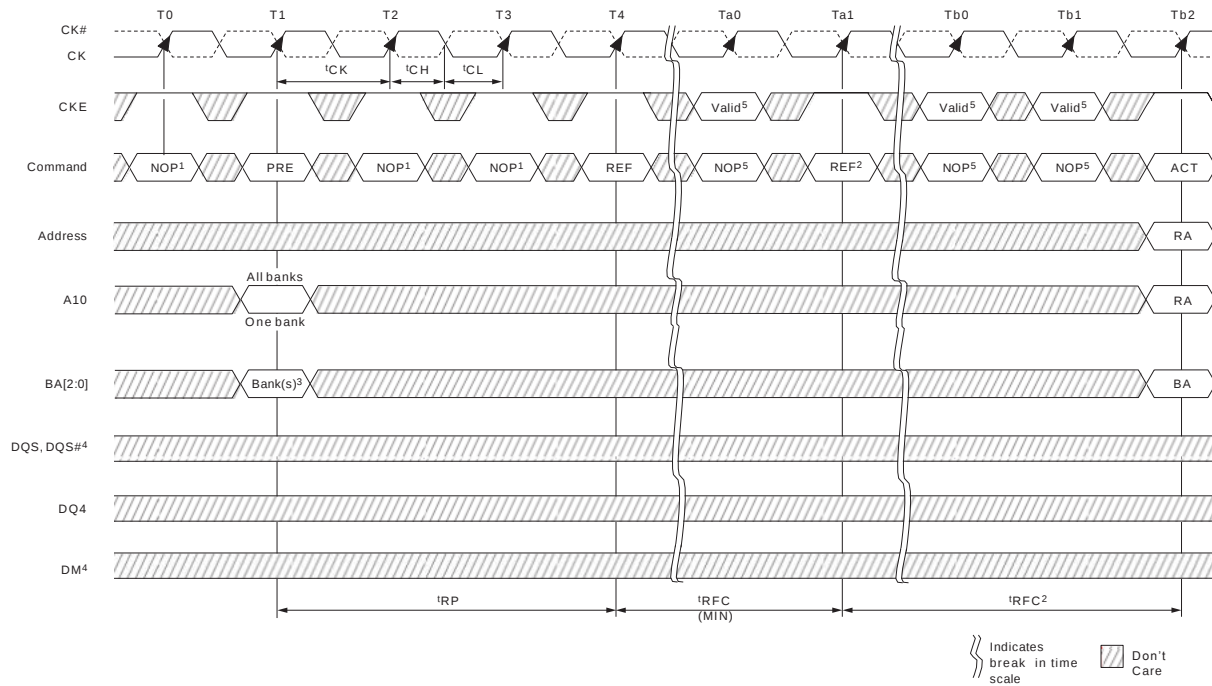
After a bank is precharged, it is in the idle state and must be activated prior to any READ or WRITE commands being issued to that bank. A PRECHARGE command is treated as a NOP if there is no open row in that bank (idle state) or if the previously open row is already in the process of precharging. However, the precharge period is determined by the last PRECHARGE command issued to the bank.

REFRESH

The REFRESH command is used during normal operation of the DRAM and is analogous to CAS#-before-RAS# (CBR) refresh or auto refresh. This command is nonpersistent, so it must be issued each time a refresh is required. The addressing is generated by the internal refresh controller. This makes the address bits a "Don't Care" during a REFRESH command.

The DRAM requires REFRESH cycles at an average interval of 7.8 μ s (maximum when TC $\leq$ 85°C or 3.9 μ s maximum when TC $\leq$ 95°C). The REFRESH period begins when the REFRESH command is registered and ends tRFC (MIN) later. To allow for improved efficiency in scheduling and switching between tasks, some flexibility in the absolute refresh interval is provided. A maximum of eight REFRESH commands can be posted to any given DRAM, meaning that the maximum absolute interval between any REFRESH command and the next REFRESH command is nine times the maximum average interval refresh rate. Self refresh may be entered with up to eight REFRESH commands being posted. After exiting self refresh (when entered with posted REFRESH commands), additional posting of REFRESH commands is allowed to the extent that the maximum number of cumulative posted REFRESH commands (both preand post-self refresh) does not exceed eight REFRESH commands. At any given time, a maximum of 16 REFRESH commands can be issued within 2 x tREFI.

Figure 29 : Refresh Mode



- Notes :
1. NOP commands are shown for ease of illustration; other valid commands may be possible at these times. CKE must be active during the PRECHARGE, ACTIVATE, and REFRESH commands, but may be inactive at other times (see Power-Down Mode).
 2. The second REFRESH is not required, but two back-to-back REFRESH commands are shown.
 3. "Don't Care" if A10 is HIGH at this point; however, A10 must be HIGH if more than one bank is active (must precharge all active banks).
 4. For operations shown, DM, DQ, and DQS signals are all "Don't Care"/High-Z.
 5. Only NOP and DES commands are allowed after a REFRESH command and until $t_{RFC} (MIN)$ is satisfied.

SELF REFRESH

The SELF REFRESH command is used to retain data in the DRAM, even if the rest of the system is powered down. When in self refresh mode, the DRAM retains data without external clocking. Self refresh mode is also a convenient method used to enable/disable the DLL as well as to change the clock frequency within the allowed synchronous operating range (see Input Clock Frequency Change). All power supply inputs (including VREFCA and VREFDQ) must be maintained at valid levels upon entry/exit and during self refresh mode operation. VREFDQ may float or not drive $VDDQ/2$ while in self refresh mode under the following conditions:

- $VSS < VREFDQ < VDD$ is maintained
- VREFDQ is valid and stable prior to CKE going back HIGH
- The first WRITE operation may not occur earlier than 512 clocks after VREFDQ is valid
- All other self refresh mode exit timing requirements are met

DLL Disable Mode

If the DLL is disabled by the mode register (MR1[0] can be switched during initialization or later), the DRAM is targeted, but not guaranteed, to operate similarly to the normal mode, with a few notable exceptions:

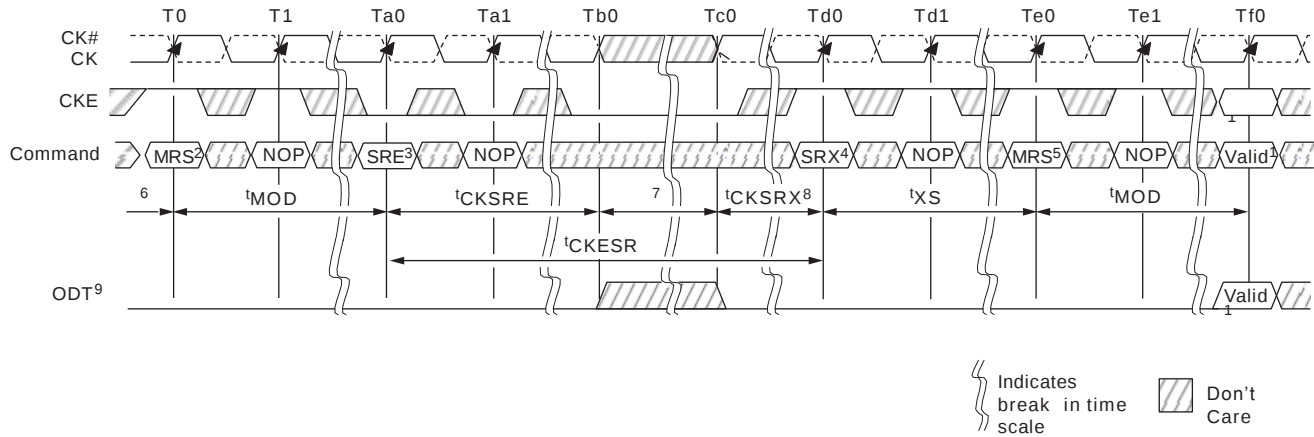
- The DRAM supports only one value of CAS latency (CL=6) and one value of CAS WRITE latency (CWL=6).
- DLL disable mode affects the read data clock-to-data strobe relationship (tDQSCK), but not the read data-to-data strobe relationship (tDQSQ, tQH). Special attention is required to line up the read data with the controller time domain when the DLL is disabled.
- In normal operation (DLL on), tDQSCK starts from the rising clock edge AL + CL cycles after the READ command. In DLL disable mode, tDQSCK starts AL + CL - 1 cycles after the READ command. Additionally, with the DLL disabled, the value of tDQSCK could be larger than tCK.

The ODT feature (including dynamic ODT) is not supported during DLL disable mode. The ODT resistors must be disabled by continuously registering the ODT ball LOW by programming RTT,nom MR1[9, 6, 2] and RTT (WR) MR2[10, 9] to 0 while in the DLL disable mode.

Specific steps must be followed to switch between the DLL enable and DLL disable modes due to a gap in the allowed clock rates between the two modes (tCK [AVG] MAX and tCK [DLL_DIS] MIN, respectively). The only time the clock is allowed to cross this clock rate gap is during self refresh mode. Thus, the required procedure for switching from the DLL enable mode to the DLL disable mode is to change frequency during self refresh:

1. Starting from the idle state (all banks are precharged, all timings are fulfilled, ODT is turned off, and $R_{TT,nom}$ and $R_{TT(WR)}$ are High-Z, set MR1[0] to 1 to disable the DLL.
2. Enter self refresh mode after tMOD has been satisfied.
3. After tCKSRE is satisfied, change the frequency to the desired clock rate.
4. Self refresh may be exited when the clock is stable with the new frequency for tCKSRX. After tXS is satisfied, update the mode registers with appropriate values.
5. The DRAM will be ready for its next command in the DLL disable mode after the greater of tMRD or tMOD has been satisfied. A ZQCL command should be issued with appropriate timings met.

Figure 30 : DLL Enable Mode to DLL Disable Mode

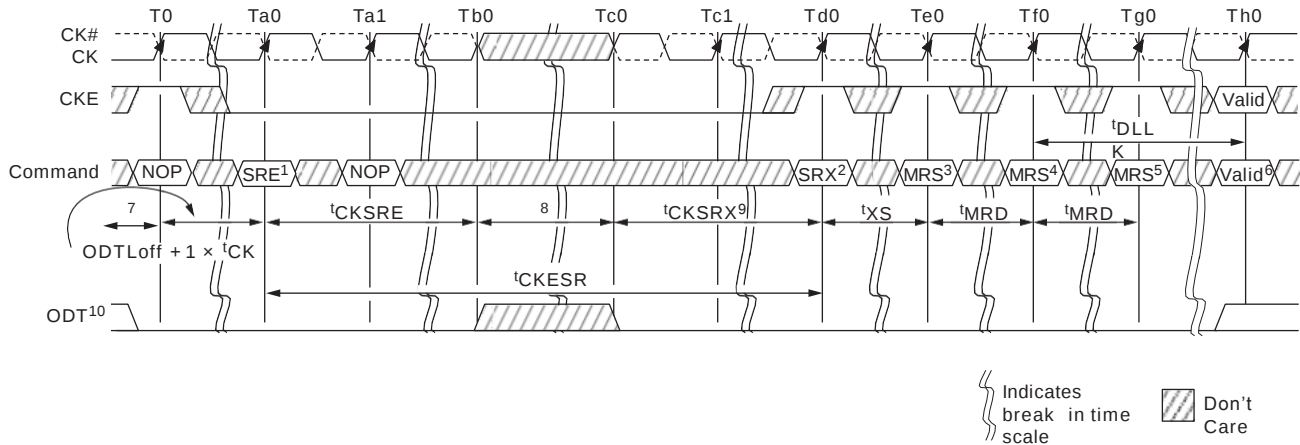


- Notes :
1. Any valid command.
 2. Disable DLL by setting MR1[0] to 1.
 3. Enter SELF REFRESH.
 4. Exit SELF REFRESH.
 5. Update the mode registers with the DLL disable parameters setting.
 6. Starting with the idle state, RTT is in the High-Z state.
 7. Change frequency.
 8. Clock must be stable tCKSRX.
 9. Static LOW in the case that RTT,nom or RTT(WR) is enabled; otherwise, static LOW or HIGH.

A similar procedure is required for switching from the DLL disable mode back to the DLL enable mode. This also requires changing the frequency during self refresh mode (see Figure 31).

1. Starting from the idle state (all banks are precharged, all timings are fulfilled, ODT is turned off, and RTT,nom and RTT(WR) are High-Z), enter self refresh mode.
2. After tCKSRE is satisfied, change the frequency to the new clock rate.
3. Self refresh may be exited when the clock is stable with the new frequency for tCKSRX. After tXS is satisfied, update the mode registers with the appropriate values. At a minimum, set MR1[0] to 0 to enable the DLL. Wait tMRD, then set MR0[8] to 1 to enable DLL RESET.
4. After another tMRD delay is satisfied, update the remaining mode registers with the appropriate values.
5. The DRAM will be ready for its next command in the DLL enable mode after the greater of tMRD or tMOD has been satisfied. However, before applying any command or function requiring a locked DLL, a delay of tDLLK after DLL RESET must be satisfied. A ZQCL command should be issued with the appropriate timings met.

Figure 31 : DLL Disable Mode to DLL Enable Mode



- Notes :
1. Enter SELF REFRESH.
 2. Exit SELF REFRESH.
 3. Wait t_{XS} , then set MR1[0] to 0 to enable DLL.
 4. Wait t_{MRD} , then set MR0[8] to 1 to begin DLL RESET.
 5. Wait t_{MRD} , update registers (CL, CWL, and write recovery may be necessary).
 6. Wait t_{MOD} , any valid command.
 7. Starting with the idle state.
 8. Change frequency.
 9. Clock must be stable at least t_{CKSRX} .
 10. Static LOW in the case that RTT,nom or RTT(WR) is enabled; otherwise, static LOW or HIGH.

The clock frequency range for the DLL disable mode is specified by the parameter t_{CK} (DLL_DIS). Due to latency counter and timing restrictions, only CL = 6 and CWL = 6 are supported.

DLL disable mode will affect the read data clock to data strobe relationship (t_{DQSCK}) but not the data strobe to data relationship (t_{DQSQ} , t_{QH}). Special attention is needed to line up read data to the controller time domain.

Compared to the DLL on mode where t_{DQSCK} starts from the rising clock edge AL + CL cycles after the READ command, the DLL disable mode t_{DQSCK} starts AL + CL - 1 cycles after the READ command.

WRITE operations function similarly between the DLL enable and DLL disable modes; however, ODT functionality is not allowed with DLL disable mode.

Figure 32 : DLL Disable tDQSCK

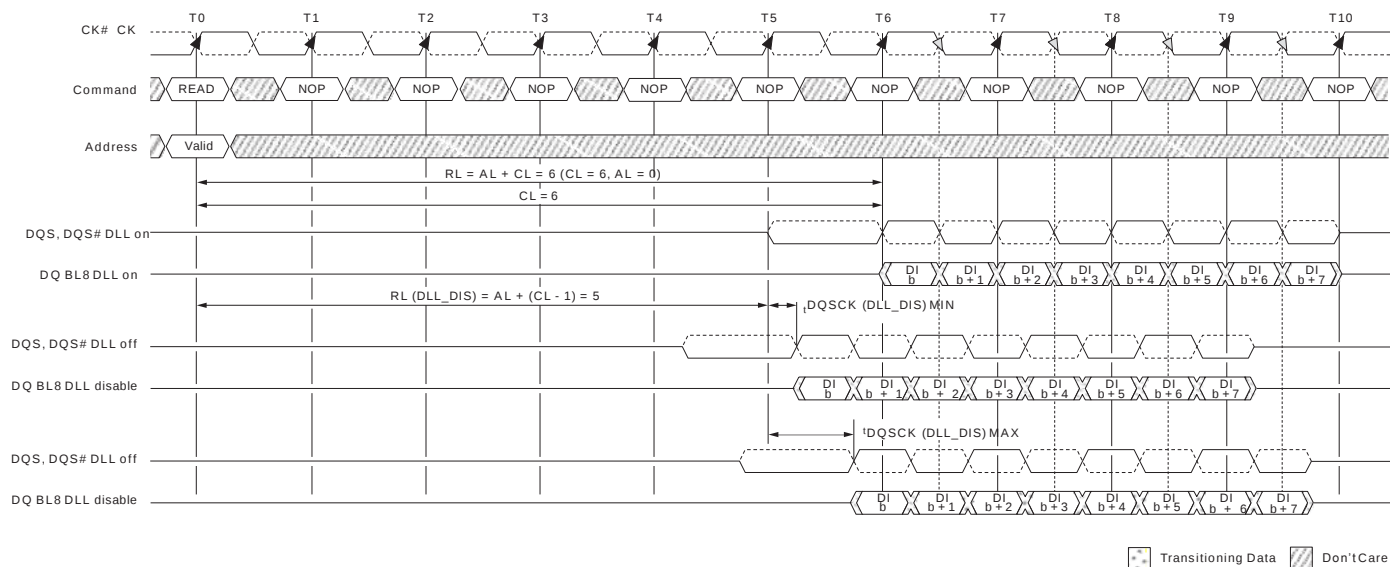


Table 66 : READ Electrical Characteristics, DLL Disable Mode

Parameter	Symbol	Min	Max	Unit
Access window of DQS from CK, CK#	$t_{DQSCK (DLL_DIS)}$	1	10	ns

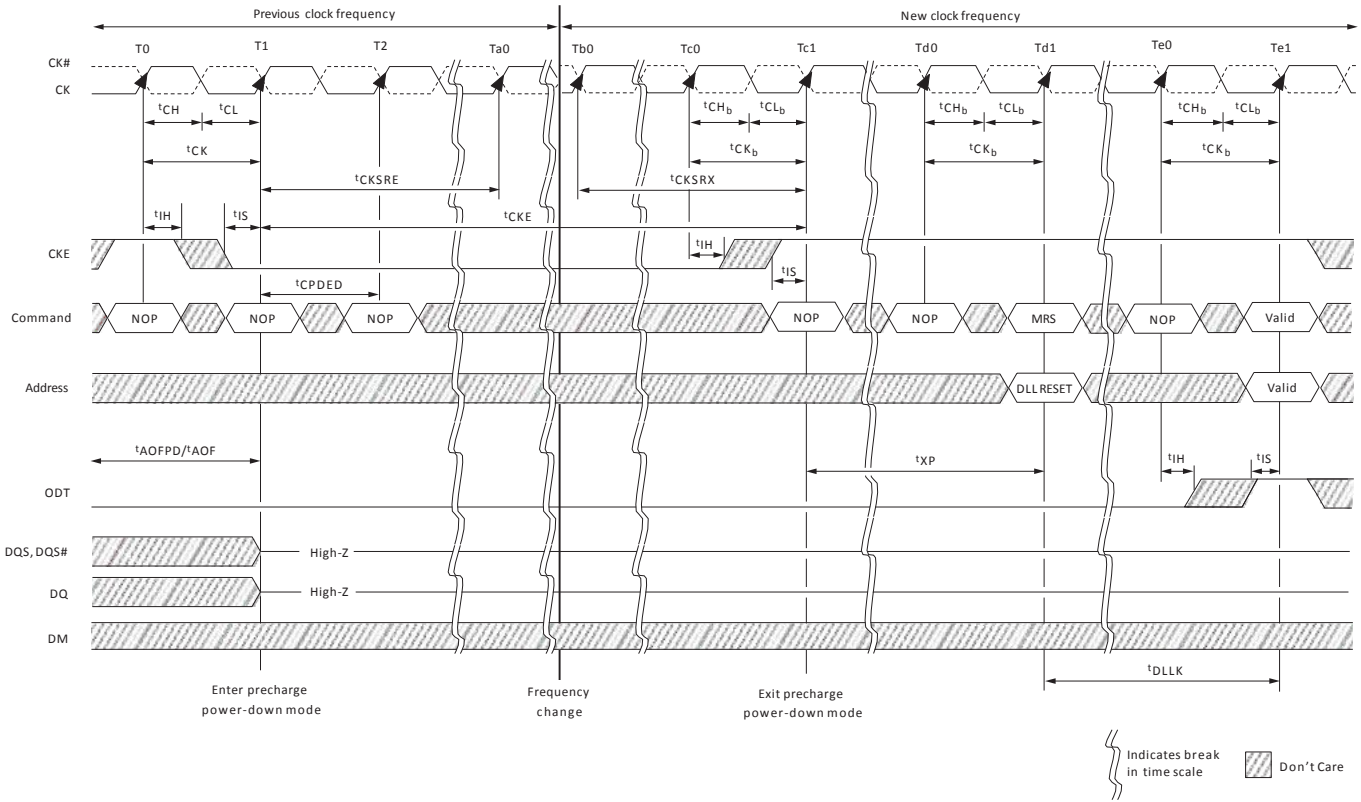
Input Clock Frequency Change

When the DDR3L SDRAM is initialized, the clock must be stable during most normal states of operation. This means that after the clock frequency has been set to the stable state, the clock period is not allowed to deviate, except for that is allowed by the clock jitter and spread spectrum clocking (SSC) specifications.

The input clock frequency can be changed from one stable clock rate to another under two conditions: self refresh mode and precharge power-down mode. It is illegal to change the clock frequency outside of those two modes. For the self refresh mode condition, when the DDR3L SDRAM has been successfully placed into self refresh mode and tCKSRE has been satisfied, the state of the clock becomes a "Don't Care." When the clock becomes a "Don't Care," changing the clock frequency is permissible if the new clock frequency is stable prior to tCKSRX. When entering and exiting self refresh mode for the sole purpose of changing the clock frequency, the self refresh entry and exit specifications must still be met.

The precharge power-down mode condition is when the DDR3L SDRAM is in precharge power-down mode (either fast exit mode or slow exit mode). Either ODT must be at a logic LOW or RTT,nom and RTT(WR) must be disabled via MR1 and MR2. This ensures RTT,nom and RTT(WR) are in an off state prior to entering precharge power-down mode, and CKE must be at a logic LOW. A minimum of tCKSRE must occur after CKE goes LOW before the clock frequency can change. The DDR3L SDRAM input clock frequency is allowed to change only within the minimum and maximum operating frequency specified for the particular speed grade (tCK [AVG] MIN to tCK [AVG] MAX). During the input clock frequency change, CKE must be held at a stable LOW level. When the input clock frequency is changed, a stable clock must be provided to the DRAM tCKSRX before precharge power-down may be exited. After precharge power-down is exited and tXP has been satisfied, the DLL must be reset via the MRS. Depending on the new clock frequency, additional MRS commands may need to be issued. During the DLL lock time, RTT,nom and RTT(WR) must remain in an off state. After the DLL lock time, the DRAM is ready to operate with a new clock frequency.

Figure 33 : Change Frequency During Precharge Power-Down



- Notes :
1. Applicable for both SLOW-EXIT and FAST-EXIT precharge power-down modes.
 2. tAOFPD and tAOF must be satisfied and outputs High-Z prior to T1 (see On-Die Termination (ODT)) for exact requirements).
 3. If the RTT,nom feature was enabled in the mode register prior to entering precharge power-down mode, the ODT signal must be continuously registered LOW, ensuring RTT is in an off state. If the RTT,nom feature was disabled in the mode register prior to entering precharge power-down mode, RTT will remain in the off state. The ODT signal can be registered LOW or HIGH in this case.

When write leveling is enabled, the rising edge of DQS samples CK, and the prime DQ outputs the sampled CK's status. The prime DQ for a x4 or x8 configuration is DQ0 with all other DQ (DQ[7:1]) driving LOW. The prime DQ for a x16 configuration is DQ0 for the lower byte and DQ8 for the upper byte. It outputs the status of CK sampled by LDQS and UDQS. All other DQ (DQ[7:1], DQ[15:9]) continue to drive LOW. Two prime DQ on a x16 enable each byte lane to be leveled independently.

The write leveling mode register interacts with other mode registers to correctly configure the write leveling functionality. Besides using MR1[7] to disable/enable write leveling, MR1[12] must be used to enable/disable the output buffers. The ODT value, burst length, and so forth need to be selected as well. This interaction is shown in Table 67. It should also be noted that when the outputs are enabled during write leveling mode, the DQS buffers are set as inputs, and the DQ are set as outputs. Additionally, during write leveling mode, only the DQS strobe terminations are activated and deactivated via the ODT ball. The DQ remain disabled and are not affected by the ODT ball.

Table 67 : Write Leveling Matrix

Note 1 applies to the entire table

MR1[7]	MR1[12]	MR1[2, 6, 9]	DRAM ODT Ball	DRAM R _{TT,nom}		DRAM State	Case	Notes
Write Leveling	Output Buffers	R _{TT,nom} Value		DQS	DQ			
Disabled	See normal operations					Write leveling not enabled	0	
Enabled (1)	Disabled (1)	n/a	Low	Off	Off	DQS not receiving: not terminated Prime DQ High-Z: not terminated Other DQ High-Z: not terminated	1	2
		20Ω,30Ω 40Ω, 60Ω, or 120Ω	High	On		DQS not receiving: terminated by R _{TT} Prime DQ High-Z: not terminated Other DQ High-Z: not terminated	2	
	Enabled (0)	n/a	Low	Off		DQS receiving: not terminated Prime DQ driving CK state: not terminated Other DQ driving LOW: not terminated	3	3
		40Ω,60Ω, or 120Ω	High	On		DQS receiving: terminated by R _{TT} Prime DQ driving CK state: not terminated Other DQ driving LOW: not terminated	4	

- Notes : 1. Expected usage if used during write leveling: Case 1 may be used when DRAM are on a dual-rank module and on the rank not being leveled or on any rank of a module not being leveled on a multislot system. Case 2 may be used when DRAM are on any rank of a module not being leveled on a multislot system. Case 3 is generally not used. Case 4 is generally used when DRAM are on the rank that is being leveled.
2. Since the DRAM DQS is not being driven (MR1[12] = 1), DQS ignores the input strobe, and all R_{TT,nom} values are allowed. This simulates a normal standby state to DQS.
3. Since the DRAM DQS is being driven (MR1[12] = 0), DQS captures the input strobe, and only some R_{TT,nom} values are allowed. This simulates a normal write state to DQS.

Write Leveling Mode Exit Procedure

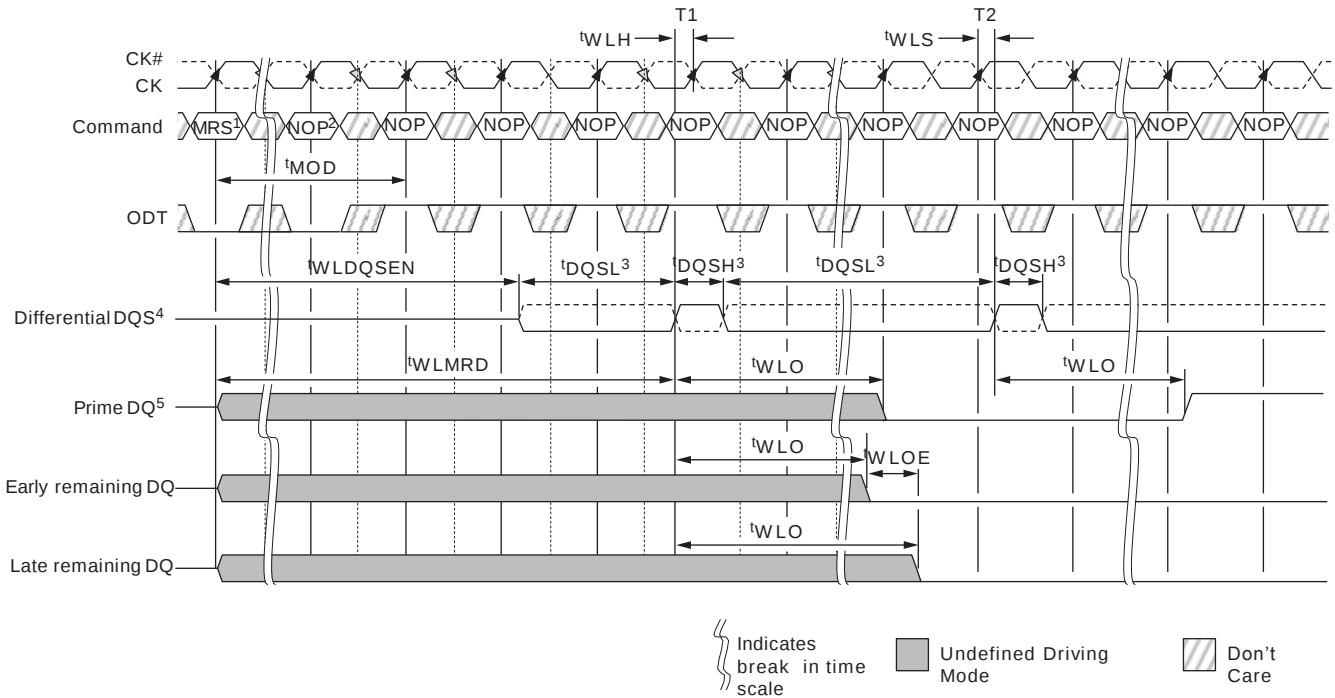
A memory controller initiates the DRAM write leveling mode by setting MR1[7] to 1, assuming the other programmable features (MR0, MR1, MR2, and MR3) are first set and the DLL is fully reset and locked. The DQ balls enter the write leveling mode going from a High-Z state to an undefined driving state, so the DQ bus should not be driven. During write leveling mode, only the NOP or DES commands are allowed. The memory controller should attempt to level only one rank at a time; thus, the outputs of other ranks should be disabled by setting MR1[12] to 1 in the other ranks. The memory controller may assert ODT after a t_{MOD} delay, as the DRAM will be ready to process the ODT transition. ODT should be turned on prior to DQS being driven LOW by at least $ODT_{Lon} - delay(WL-2 t_{CK})$, provided it does not violate the aforementioned t_{MOD} delay requirement.

The memory controller may drive DQS LOW and DQS# HIGH after $t_{WLDQSEN}$ has been satisfied. The controller may begin to toggle DQS after t_{WLMRD} (one DQS toggle is DQS transitioning from a LOW state to a HIGH state with DQS# transitioning from a HIGH state to a LOW state, then both transition back to their original states). At a minimum, ODT_{Lon} and t_{AON} must be satisfied at least one clock prior to DQS toggling.

After t_{WLMRD} and a DQS LOW preamble (t_{WPRE}) have been satisfied, the memory controller may provide either a single DQS toggle or multiple DQS toggles to sample CK for a given DQS-to-CK skew. Each DQS toggle must not violate $t_{DQSL} (MIN)$ and $t_{DQSH} (MIN)$ specifications. $t_{DQSL} (MAX)$ and $t_{DQSH} (MAX)$ specifications are not applicable during write leveling mode. The DQS must be able to distinguish the CK's rising edge within t_{WLS} and t_{WLH} . The prime DQ will output the CK's status asynchronously from the associated DQS rising edge CK capture within t_{WLO} . The remaining DQ that always drive LOW when DQS is toggling must be LOW within t_{WLOE} after the first t_{WLO} is satisfied (the prime DQ going LOW). As previously noted, DQS is an input and not an output during this process. Figure 35 depicts the basic timing parameters for the overall write leveling procedure.

The memory controller will most likely sample each applicable prime DQ state and determine whether to increment or decrement its DQS delay setting. After the memory controller performs enough DQS toggles to detect the CK's 0-to-1 transition, the memory controller should lock the DQS delay setting for that DRAM. After locking the DQS setting is locked, leveling for the rank will have been achieved, and the write leveling mode for the rank should be disabled or reprogrammed (if write leveling of another rank follows).

Figure 35 : Write Leveling Sequence



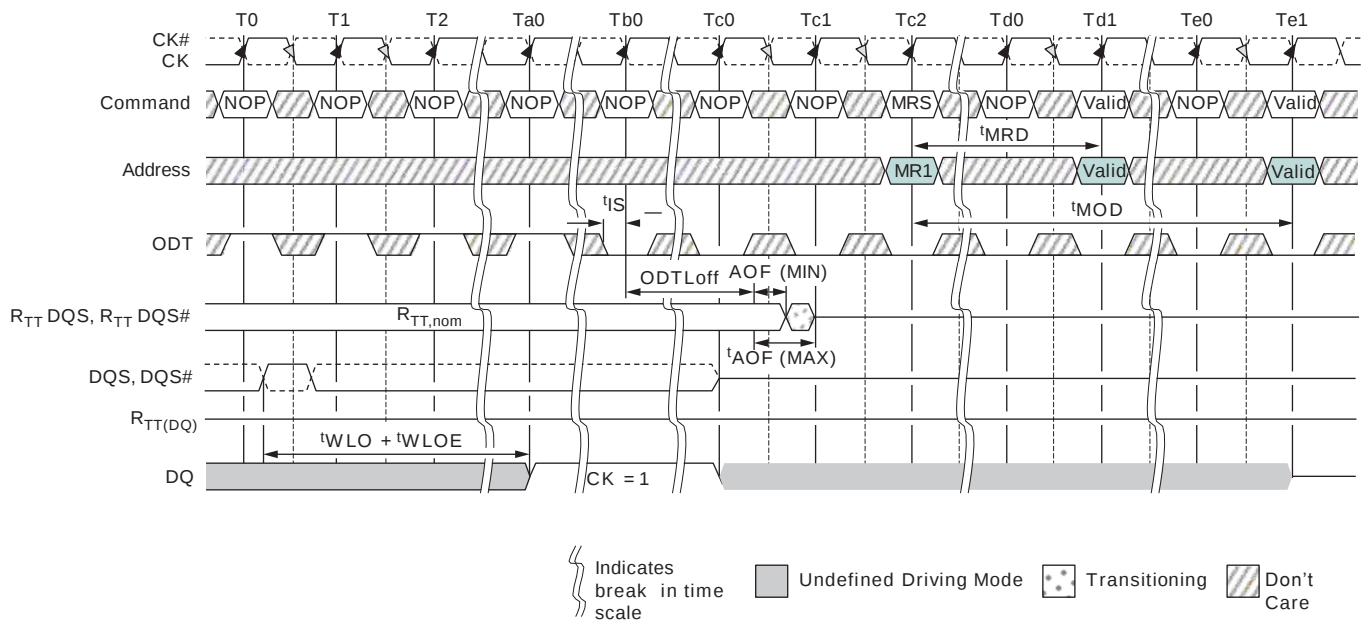
- Note :
1. MRS: Load MR1 to enter write leveling mode.
 2. NOP: NOP or DES.
 3. DQS, DQS# needs to fulfill minimum pulse width requirements t_{DQSH} (MIN) and t_{DQSL} (MIN) as defined for regular writes. The maximum pulse width is system-dependent.
 4. Differential DQS is the differential data strobe (DQS, DQS#). Timing reference points are the zero crossings. The solid line represents DQS; the dotted line represents DQS#.
 5. DRAM drives leveling feedback on a prime DQ (DQ0 for x4 and x8). The remaining DQ are driven LOW and remain in this state throughout the leveling procedure.

Write Leveling Mode Exit Procedure

After the DRAM are leveled, they must exit from write leveling mode before the normal mode can be used. Figure 36 depicts a general procedure for exiting write leveling mode. After the last rising DQS (capturing a 1 at T0), the memory controller should stop driving the DQS signals after t_{WLO} (MAX) delay plus enough delay to enable the memory controller to capture the applicable prime DQ state (at $\sim T_{b0}$). The DQ balls become undefined when DQS no longer remains LOW, and they remain undefined until t_{MOD} after the MRS command (at Te1).

The ODT input should be de-asserted LOW such that $ODTL_{off}$ (MIN) expires after the DQS is no longer driving LOW. When ODT LOW satisfies t_{IS} , ODT must be kept LOW (at $\sim T_{b0}$) until the DRAM is ready for either another rank to be leveled or until the normal mode can be used. After DQS termination is switched off, write level mode should be disabled via the MRS command (at Tc2). After t_{MOD} is satisfied (at Te1), any valid command may be registered by the DRAM. Some MRS commands may be issued after t_{MRD} (at Td1).

Figure 36 : Write Leveling Exit Procedure



Note : 1. The DQ result, = 1, between Ta0 and Tc0, is a result of the DQS, DQS# signals capturing CK HIGH just after the T0 state.

Initialization

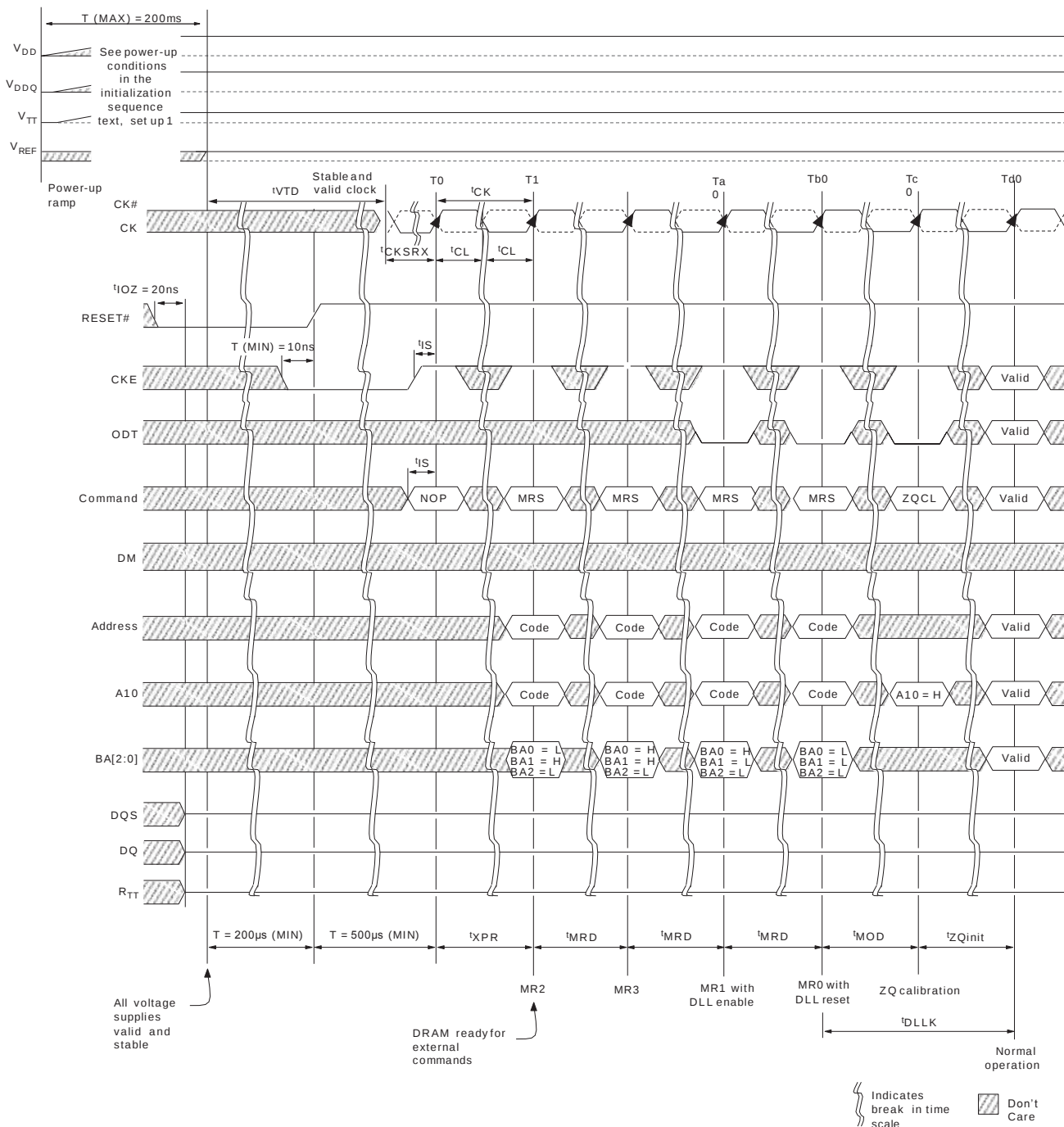
The following sequence is required for power-up and initialization, as shown in Figure 37.

1. Apply power. RESET# is recommended to be below $0.2 \times VDDQ$ during power ramp to ensure the outputs remain disabled (High-Z) and ODT off (RTT is also High-Z). All other inputs, including ODT, may be undefined.

During power-up, either of the following conditions may exist and must be met :

- Condition A:
 - VDD and VDDQ are driven from a single-power converter output and are ramped with a maximum delta voltage between them of $\Delta V \leq 300\text{mV}$. Slope reversal of any power supply signal is allowed. The voltage levels on all balls other than VDD, VDDQ, VSS, VSSQ must be less than or equal to VDDQ and VDD on one side, and must be greater than or equal to VSSQ and VSS on the other side.
 - Both VDD and VDDQ power supplies ramp to VDD,min and VDDQ,min within $tVDDPR = 200\text{ms}$.
 - VREFDQ tracks $VDD \times 0.5$, VREFCA tracks $VDD \times 0.5$.
 - VTT is limited to 0.95V when the power ramp is complete and is not applied directly to the device; however, $tVTD$ should be greater than or equal to 0 to avoid device latchup.
 - Condition B :
 - VDD may be applied before or at the same time as VDDQ.
 - VDDQ may be applied before or at the same time as VTT, VREFDQ, and VREFCA.
 - No slope reversals are allowed in the power supply ramp for this condition.
2. Until stable power, maintain RESET# LOW to ensure the outputs remain disabled (High-Z). After the power is stable, RESET# must be LOW for at least 200 μs to begin the initialization process. ODT will remain in the High-Z state while RESET# is LOW and until CKE is registered HIGH.
 3. CKE must be LOW 10ns prior to RESET# transitioning HIGH.
 4. After RESET# transitions HIGH, wait 500 μs (minus one clock) with CKE LOW.
 5. After the CKE LOW time, CKE may be brought HIGH (synchronously) and only NOP or DES commands may be issued. The clock must be present and valid for at least 10ns (and a minimum of five clocks) and ODT must be driven LOW at least tIS prior to CKE being registered HIGH. When CKE is registered HIGH, it must be continuously registered HIGH until the full initialization process is complete.
 6. After CKE is registered HIGH and after tXPR has been satisfied, MRS commands may be issued. Issue an MRS (LOAD MODE) command to MR2 with the applicable settings (provide LOW to BA2 and BA0 and HIGH to BA1).
 7. Issue an MRS command to MR3 with the applicable settings.
 8. Issue an MRS command to MR1 with the applicable settings, including enabling the DLL and configuring ODT.
 9. Issue an MRS command to MR0 with the applicable settings, including a DLL RESET command. $tDLLK$ (512) cycles of clock input are required to lock the DLL.
 10. Issue a ZQCL command to calibrate RTT and RON values for the process voltage temperature (PVT). Prior to normal operation, $tZQinit$ must be satisfied.
 11. When $tDLLK$ and $tZQinit$ have been satisfied, the DDR3L SDRAM will be ready for normal operation.

Figure 37 : Initialization Sequence



Voltage Initialization / Change

If the SDRAM is powered up and initialized for the 1.35V operating voltage range, voltage can be increased to the 1.5V operating range provided the following conditions are met (See Figure 38) :

- Just prior to increasing the 1.35V operating voltages, no further commands are issued, other than NOPs or COMMAND INHIBITs, and all banks are in the precharge state.
- The 1.5V operating voltages are stable prior to issuing new commands, other than NOPs or COMMAND INHIBITs.
- The DLL is reset and relocked after the 1.5V operating voltages are stable and prior to any READ command.
- The ZQ calibration is performed. t_{ZQinit} must be satisfied after the 1.5V operating voltages are stable and prior to any READ command.

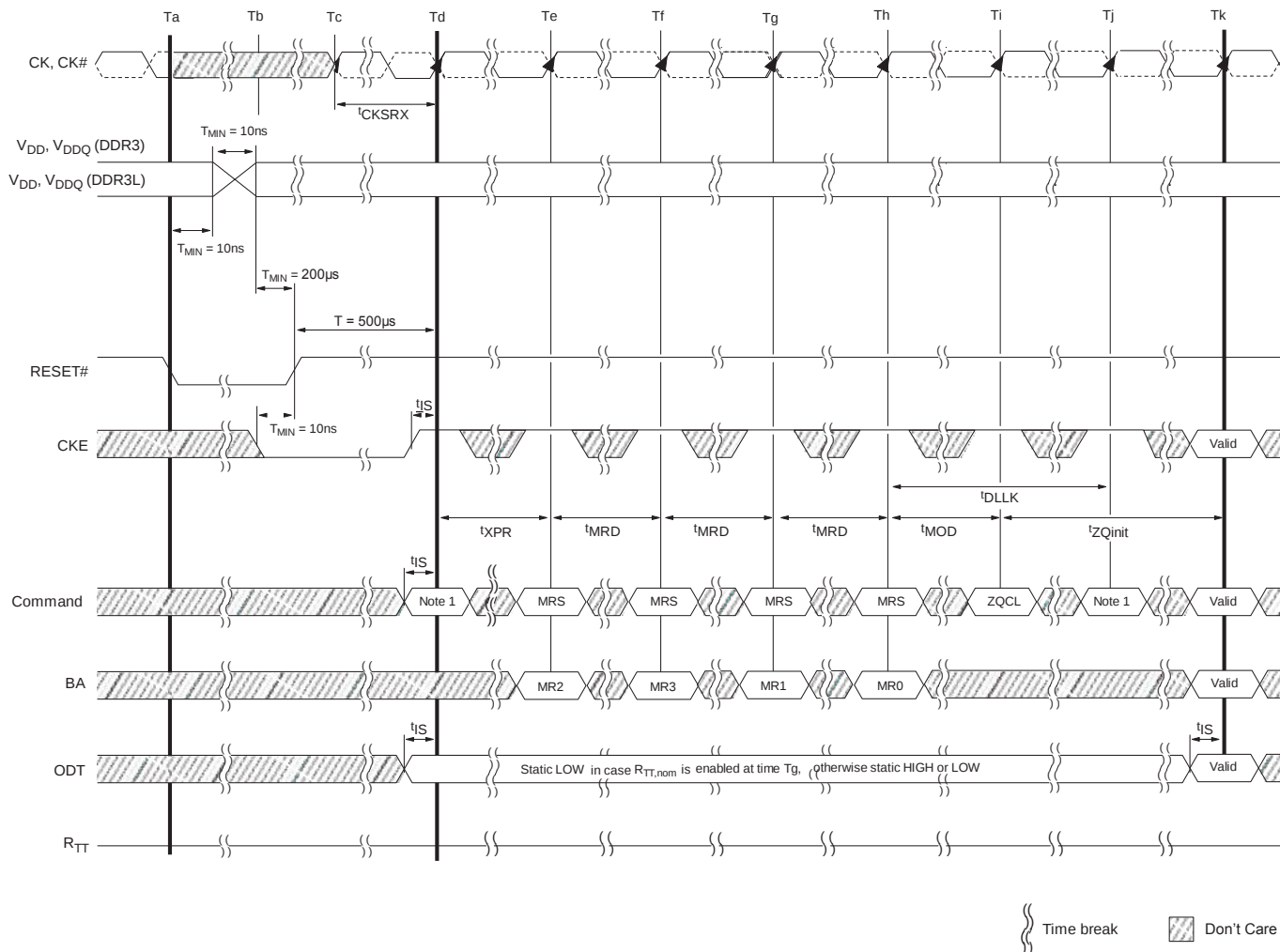
If the SDRAM is powered up and initialized for the 1.5V operating voltage range, voltage can be reduced to the 1.35V operation range provided the following conditions are met (See Figure 38) :

- Just prior to reducing the 1.5V operating voltages, no further commands are issued, other than NOPs or COMMAND INHIBITs, and all banks are in the precharge state.
- The 1.35V operating voltages are stable prior to issuing new commands, other than NOPs or COMMAND INHIBITs.
- The DLL is reset and relocked after the 1.35V operating voltages are stable and prior to any READ command.
- The ZQ calibration is performed. t_{ZQinit} must be satisfied after the 1.35V operating voltages are stable and prior to any READ command.

V_{DD} Voltage Switching

After the DDR3L DRAM is powered up and initialized, the power supply can be altered between the DDR3L and DDR3L levels, provided the sequence in Figure 38 is maintained.

Figure 38 : V_{DD} Voltage Switching



Note : 1. From time point Td until Tk, NOP or DES commands must be applied between MRS and ZQCL commands.

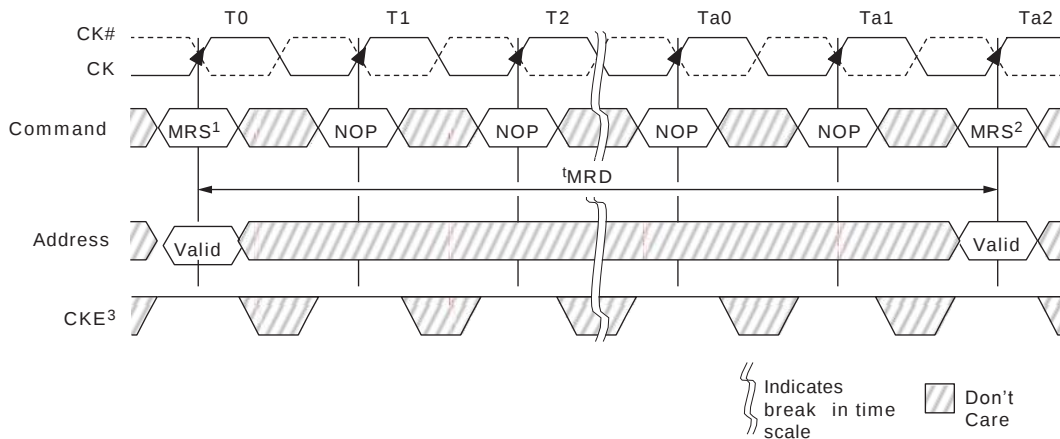
Mode Registers

Mode registers (MR0–MR3) are used to define various modes of programmable operations of the DDR3L SDRAM. A mode register is programmed via the mode register set (MRS) command during initialization, and it retains the stored information (except for MR0[8], which is self-clearing) until it is reprogrammed, RESET# goes LOW, the device loses power.

Contents of a mode register can be altered by re-executing the MRS command. Even if the user wants to modify only a subset of the mode register's variables, all variables must be programmed when the MRS command is issued. Reprogramming the mode register will not alter the contents of the memory array, provided it is performed correctly.

The MRS command can only be issued (or re-issued) when all banks are idle and in the precharged state (t_{RP} is satisfied and no data bursts are in progress). After an MRS command has been issued, two parameters must be satisfied: t_{MRD} and t_{MOD} . The controller must wait t_{MRD} before initiating any subsequent MRS commands.

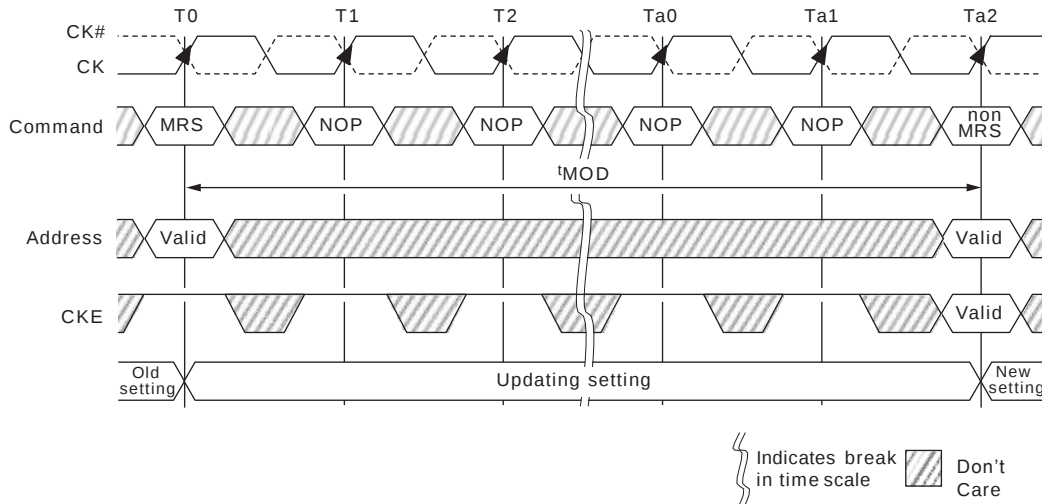
Figure 39 : MRS to MRS Command Timing (t_{MRD})



- Notes :
1. Prior to issuing the MRS command, all banks must be idle and precharged, t_{RP} (MIN) must be satisfied, and no data bursts can be in progress.
 2. t_{MRD} specifies the MRS to MRS command minimum cycle time.
 3. CKE must be registered HIGH from the MRS command until $t_{MRSPDEN}$ (MIN) (see Power-Down Mode).
 4. For a CAS latency change, t_{XPDLL} timing must be met before any non-MRS command.

The controller must also wait t_{MOD} before initiating any non-MRS commands (excluding NOP and DES). The DRAM requires t_{MOD} in order to update the requested features, with the exception of DLL RESET, which requires additional time. Until t_{MOD} has been satisfied, the updated features are to be assumed unavailable.

Figure 40 : MRS to nonMRS Command Timing (tMOD)



- Notes :
1. Prior to issuing the MRS command, all banks must be idle (they must be precharged, tRP must be satisfied, and no data bursts can be in progress).
 2. Prior to Ta2 when tMOD (MIN) is being satisfied, no commands (except NOP/DES) may be issued.
 3. If RTT was previously enabled, ODT must be registered LOW at T0 so that ODTL is satisfied prior to Ta1. ODT must also be registered LOW at each rising CK edge from T0 until tMODmin is satisfied at Ta2.
 4. CKE must be registered HIGH from the MRS command until tMRSPDEN (MIN), at which time power-down may occur (see Power-Down Mode).

Mode Register 0 (MR0)

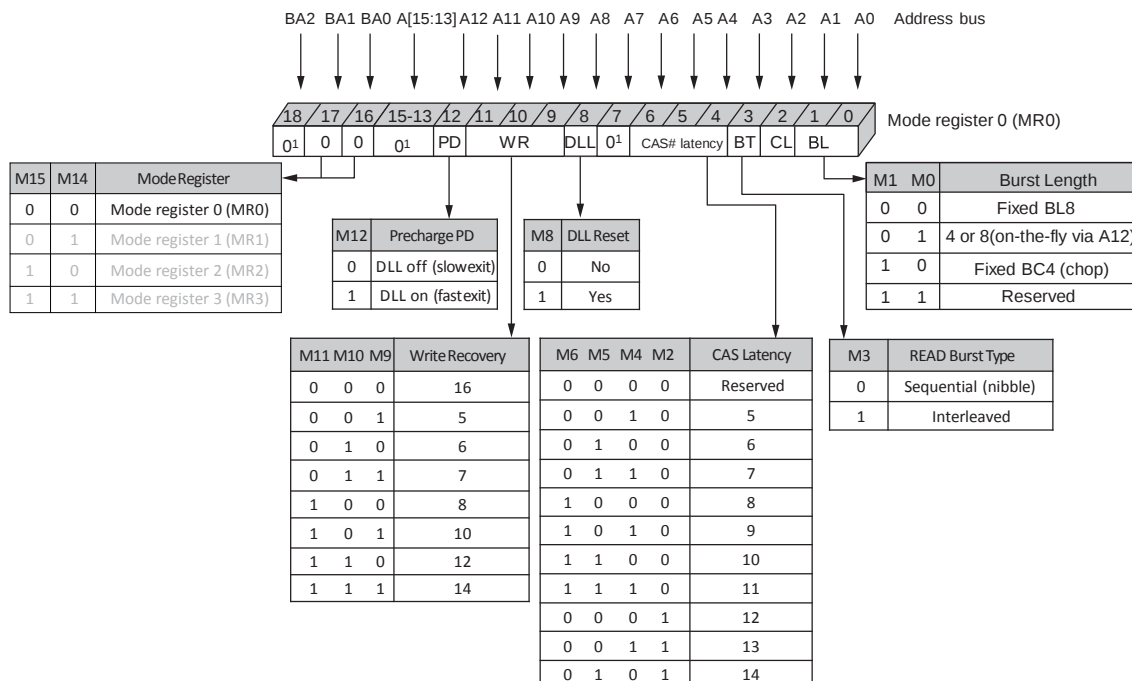
The base register, MR0, is used to define various DDR3L SDRAM modes of operation. These definitions include the selection of a burst length, burst type, CAS latency, operating mode, DLL RESET, write recovery, and precharge power-down mode, as shown in Figure 41.

Burst Length

Burst length is defined by MR0[1: 0]. Read and write accesses to the DDR3L SDRAM are burst-oriented, with the burst length being programmable to 4 (chop mode), 8 (fixed), or selectable using A12 during a READ/ WRITE command (on-the-fly). The burst length determines the maximum number of column locations that can be accessed for a given READ or WRITE command. When MR0[1:0] is set to 01 during a READ/WRITE command, if A12 = 0, then BC4 (chop) mode is selected. If A12 = 1, then BL8 mode is selected. Specific timing diagrams, and turnaround between READ/WRITE, are shown in the READ/WRITE sections of this document.

When a READ or WRITE command is issued, a block of columns equal to the burst length is effectively selected. All accesses for that burst take place within this block, meaning that the burst will wrap within the block if a boundary is reached. The block is uniquely selected by A[i:2] when the burst length is set to 4 and by A[i:3] when the burst length is set to 8 (where A_i is the most significant column address bit for a given configuration). The remaining (least significant) address bit(s) is (are) used to select the starting location within the block. The programmed burst length applies to both READ and WRITE bursts.

Figure 41 : Mode Register 0 (MR0) Definitions



Note : 1. MR0[18, 15:13, 7] are reserved for future use and must be programmed to 0.

Burst Type

Accesses within a given burst may be programmed to either a sequential or an interleaved order. The burst type is selected via MR0[3] (see Figure 41). The ordering of accesses within a burst is determined by the burst length, the burst type, and the starting column address. DDR3L only supports 4-bit burst chop and 8-bit burst access modes.

Full interleave address ordering is supported for READs, while WRITEs are restricted to nibble (BC4) or word (BL8) boundaries.

Table 68 : Burst Order

Burst Length	READ/ WRITE	Starting Column Address (A[2, 1, 0])	Burst Type = Sequential (Decimal)	Burst Type = Interleaved(Decimal)	Notes
4 (chop)	READ	0 0 0	0, 1, 2, 3, Z, Z, Z, Z	0, 1, 2, 3, Z, Z, Z, Z	1, 2
		0 0 1	1, 2, 3, 0, Z, Z, Z, Z	1, 0, 3, 2, Z, Z, Z, Z	1, 2
		0 1 0	2, 3, 0, 1, Z, Z, Z, Z	2, 3, 0, 1, Z, Z, Z, Z	1, 2
		0 1 1	3, 0, 1, 2, Z, Z, Z, Z	3, 2, 1, 0, Z, Z, Z, Z	1, 2
		1 0 0	4, 5, 6, 7, Z, Z, Z, Z	4, 5, 6, 7, Z, Z, Z, Z	1, 2
		1 0 1	5, 6, 7, 4, Z, Z, Z, Z	5, 4, 7, 6, Z, Z, Z, Z	1, 2
		1 1 0	6, 7, 4, 5, Z, Z, Z, Z	6, 7, 4, 5, Z, Z, Z, Z	1, 2
		1 1 1	7, 4, 5, 6, Z, Z, Z, Z	7, 6, 5, 4, Z, Z, Z, Z	1, 2
	WRITE	0 V V	0, 1, 2, 3, X, X, X, X	0, 1, 2, 3, X, X, X, X	1, 3,4
		1 V V	4, 5, 6, 7, X, X, X, X	4, 5, 6, 7, X, X, X, X	1, 3, 4
8 (fidexd)	READ	0 0 0	0, 1, 2, 3, 4, 5, 6, 7	0, 1, 2, 3, 4, 5, 6, 7	1
		0 0 1	1, 2, 3, 0, 5, 6, 7, 4	1, 0, 3, 2, 5, 4, 7, 6	1
		0 1 0	2, 3, 0, 1, 6, 7, 4, 5	2, 3, 0, 1, 6, 7, 4, 5	1
		0 1 1	3, 0, 1, 2, 7, 4, 5, 6	3, 2, 1, 0, 7, 6, 5, 4	1
		1 0 0	4, 5, 6, 7, 0, 1, 2, 3	4, 5, 6, 7, 0, 1, 2, 3	1
		1 0 1	5, 6, 7, 4, 1, 2, 3, 0	5, 4, 7, 6, 1, 0, 3, 2	1
		1 1 0	6, 7, 4, 5, 2, 3, 0, 1	6, 7, 4, 5, 2, 3, 0, 1	1
		1 1 1	7, 4, 5, 6, 3, 0, 1, 2	7, 6, 5, 4, 3, 2, 1, 0	1
	WRITE	V V V	0, 1, 2, 3, 4, 5, 6, 7	0, 1, 2, 3, 4, 5, 6, 7	1, 3

Notes : 1. Internal READ and WRITE operations start at the same point in time for BC4 as they do for BL8.

2. Z = Data and strobe output drivers are in tri-state.

3. V = A valid logic level (0 or 1), but the respective input buffer ignores level-on input pins.

4. X = "Don't Care."

DLL RESET

DLL RESET is defined by MR0[8] (see Figure 41). Programming MR0[8] to 1 activates the DLL RESET function. MR0[8] is self-clearing, meaning it returns to a value of 0 after the DLL RESET function has been initiated. Anytime the DLL RESET function is initiated, CKE must be HIGH and the clock held stable for 512 (tDLLK) clock cycles before a READ command can be issued. This is to allow time for the internal clock to be synchronized with the external clock. Failing to wait for synchronization to occur may result in invalid output timing specifications, such as tDQSCK timings.

Write Recovery

WRITE recovery time is defined by MR0[11:9] (see Figure 41). Write recovery values of 5, 6, 7, 8, 10, or 12 may be used by programming MR0[11:9]. The user is required to program the correct value of write recovery and is calculated by dividing tWR (ns) by tCK (ns) and rounding up a noninteger value to the next integer: WR (cycles) = roundup (tWR [ns]/tCK [ns]).

Precharge Power-Down (Precharge PD)

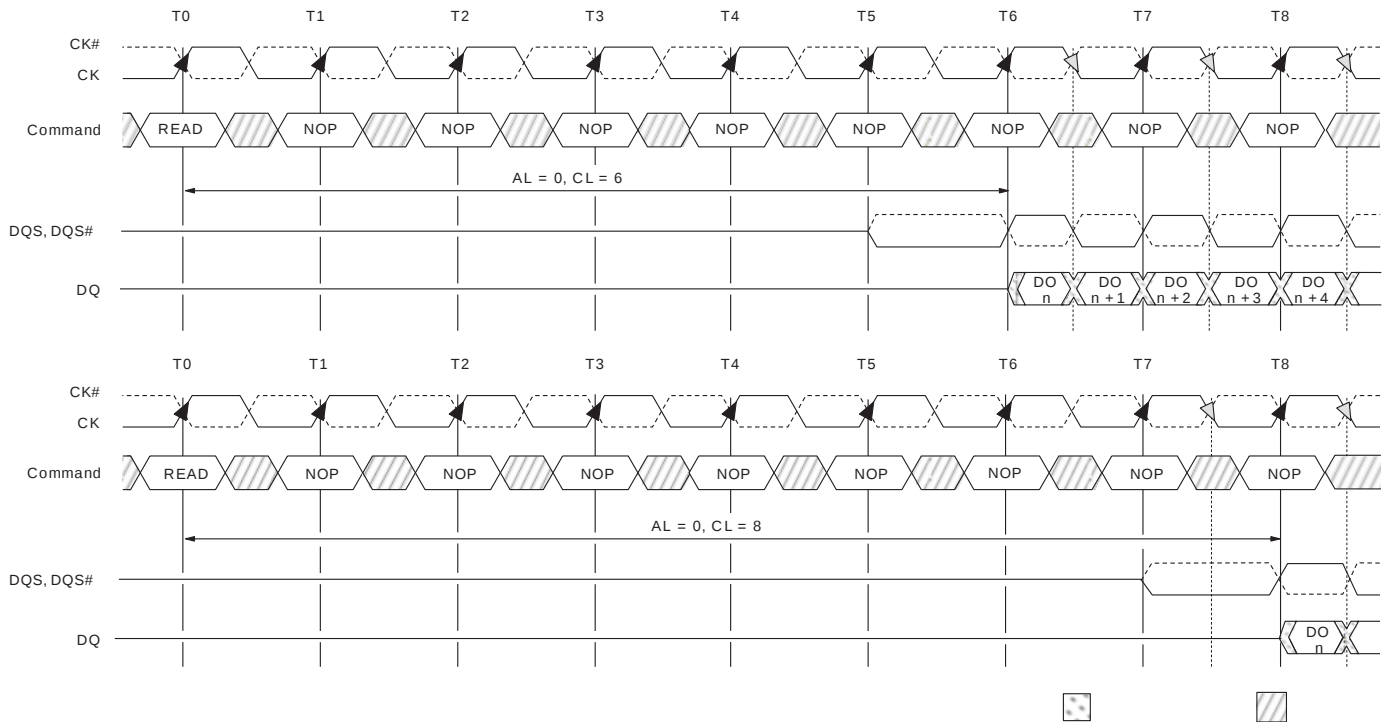
The precharge PD bit applies only when precharge power-down mode is being used. When MR0[12] is set to 0, the DLL is off during precharge power-down providing a lower standby current mode; however, tXPDLL must be satisfied when exiting. When MR0[12] is set to 1, the DLL continues to run during precharge power-down mode to enable a faster exit of precharge power-down mode; however, tXP must be satisfied when exiting (see Power-Down Mode).

CAS Latency (CL)

The CL is defined by MR0[6:4], as shown in Figure 41. CAS latency is the delay, in clock cycles, between the internal READ command and the availability of the first bit of output data. The CL can be set to 5, 6, 7, 8, 9, or 10. DDR3L SDRAM do not support half-clock latencies.

Examples of CL = 6 and CL = 8 are shown below. If an internal READ command is registered at clock edge n , and the CAS latency is m clocks, the data will be available nominally coincident with clock edge $n + m$. Speed Bin Tables for the CLs supported at various operating frequencies.

Figure 42 : READ Latency



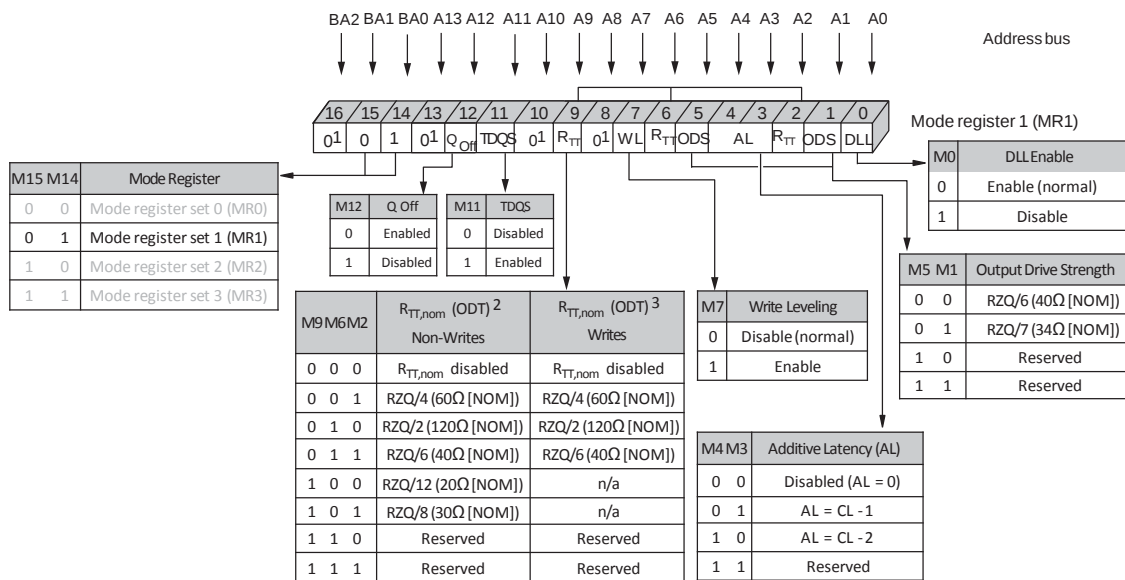
- Notes: 1. For illustration purposes, only CL = 6 and CL = 8 are shown. Other CL values are possible.
2. Shown with nominal tDQSCK and nominal tDSDQ.

Mode Register 1 (MR1)

The mode register 1 (MR1) controls additional functions and features not available in the other mode registers: Q OFF (OUTPUT DISABLE), TDQS (for the x8 configuration only), DLL ENABLE/DLL DISABLE, $R_{TT,nom}$ value (ODT), WRITE LEVELING, POSTED CAS ADDITIVE latency, and OUTPUT DRIVE STRENGTH. These functions are controlled via the bits shown in Figure 43. The MR1 register is programmed via the MRS command and retains the stored information until it is reprogrammed, until RESET# goes LOW, or until the device loses power. Reprogramming the MR1 register will not alter the contents of the memory array, provided it is performed correctly.

The MR1 register must be loaded when all banks are idle and no bursts are in progress. The controller must satisfy the specified timing parameters tMRD and tMOD before initiating a subsequent operation.

Figure 43 : Mode Register 1 (MR1) Definition



- Notes:
1. MR1[16, 13, 10, 8] are reserved for future use and must be programmed to 0.
 2. During write leveling, if MR1[7] and MR1[12] are 1, then all $R_{TT,nom}$ values are available for use.
 3. During write leveling, if MR1[7] is a 1, but MR1[12] is a 0, then only $R_{TT,nom}$ write values are available for use.

DLL Enable/DLL Disable

The DLL may be enabled or disabled by programming MR1[0] during the LOAD MODE command, as shown in Figure 43. The DLL must be enabled for normal operation. DLL enable is required during power-up initialization and upon returning to normal operation after having disabled the DLL for the purpose of debugging or evaluation. Enabling the DLL should always be followed by resetting the DLL using the appropriate LOAD MODE command.

If the DLL is enabled prior to entering self refresh mode, the DLL is automatically disabled when entering SELF REFRESH operation and is automatically re-enabled and reset upon exit of SELF REFRESH operation. If the DLL is disabled prior to entering self refresh mode, the DLL remains disabled even upon exit of SELF REFRESH operation until it is re-enabled and reset.

The DRAM is not tested to check—nor does Dosilicon warrant compliance with—normal mode timings or functionality when the DLL is disabled. An attempt has been made to have the DRAM operate in the normal mode where reasonably possible when the DLL has been disabled; however, by industry standard, a few known exceptions are defined:

- ODT is not allowed to be used
- The output data is no longer edge-aligned to the clock
- CL and CWL can only be six clocks

When the DLL is disabled, timing and functionality can vary from the normal operation specifications when the DLL is enabled (see DLL Disable Mode). Disabling the DLL also implies the need to change the clock frequency (see Input Clock Frequency Change).

Output Drive Strength

The DDR3L SDRAM uses a programmable impedance output buffer. The drive strength mode register setting is defined by MR1[5, 1]. RZQ/7 (34Ω [NOM]) is the primary output driver impedance setting for DDR3L SDRAM devices. To calibrate the output driver impedance, an external precision resistor (RZQ) is connected between the ZQ ball and VSSQ. The value of the resistor must be $240\Omega \pm 1\%$.

The output impedance is set during initialization. Additional impedance calibration updates do not affect device operation, and all data sheet timings and current specifications are met during an update.

To meet the 34Ω specification, the output drive strength must be set to 34Ω during initialization. To obtain a calibrated output driver impedance after power-up, the DDR3L SDRAM needs a calibration command that is part of the initialization and reset procedure.

OUTPUT ENABLE/DISABLE

The OUTPUT ENABLE function is defined by MR1[12], as shown in Figure 43. When enabled (MR1[12] = 0), all outputs (DQ, DQS, DQS#) function when in the normal mode of operation. When disabled (MR1[12] = 1), all DDR3L SDRAM outputs (DQ and DQS, DQS#) are tri-stated. The output disable feature is intended to be used during IDD characterization of the READ current and during tDQSS margining (write leveling) only.

TDQS Enable

Termination data strobe (TDQS) is a feature of the x8 DDR3L SDRAM configuration that provides termination resistance (RTT) and may be useful in some system configurations. TDQS is not supported in x4 or x16 configurations. When enabled via the mode register (MR1[11]), the RTT that is applied to DQS and DQS# is also applied to TDQS and TDQS#. In contrast to the RDQS function of DDR2 SDRAM, DDR3's TDQS provides the termination resistance RTT only. The OUTPUT DATA STROBE function of RDQS is not provided by TDQS; thus, RON does not apply to TDQS and TDQS#. The TDQS and DM functions share the same ball. When the TDQS function is enabled via the mode register, the DM function is not supported. When the TDQS function is disabled, the DM function is provided, and the TDQS# ball is not used. The TDQS function is available in the x8 DDR3L SDRAM configuration only and must be disabled via the mode register for the x4 and x16 configurations.

On-Die Termination

to ODT resistance RTT_{nom} is defined by MR1[9, 6, 2] (see Figure 43). The RTT termination value applies to the DQ, DM, DQS, DQS#, and TDQS, TDQS# balls. DDR3L supports multiple RTT termination values based on RZQ/*n* where *n* can be 2, 4, 6, 8, or 12 and RZQ is 240Ω. Unlike DDR2, DDR3L ODT must be turned off prior reading data out and must remain off during a READ burst. RTT_{nom} termination is allowed any time after the DRAM is initialized, calibrated, and not performing read access, or when it is not in self refresh mode. Additionally, write accesses with dynamic ODT enabled ($RTT(WR)$) temporarily replaces RTT_{nom} with $RTT(WR)$.

The actual effective termination, $RTT(EFF)$, may be different from the RTT targeted due to nonlinearity of the termination. For $RTT(EFF)$ values and calculations (see On-Die Termination (ODT)).

The ODT feature is designed to improve signal integrity of the memory channel by enabling the DDR3L SDRAM controller to independently turn on/off ODT for any or all devices. The ODT input control pin is used to determine when RTT is turned on (ODTL on) and off (ODTL off), assuming ODT has been enabled via MR1[9, 6, 2].

Timings for ODT are detailed in On-Die Termination (ODT).

WRITE LEVELING

The WRITE LEVELING function is enabled by MR1[7], as shown in Figure 43. Write leveling is used (during initialization) to deskew the DQS strobe to clock offset as a result of fly-by topology designs. For better signal integrity, DDR3L SDRAM memory modules adopted fly-by topology for the commands, addresses, control signals, and clocks.

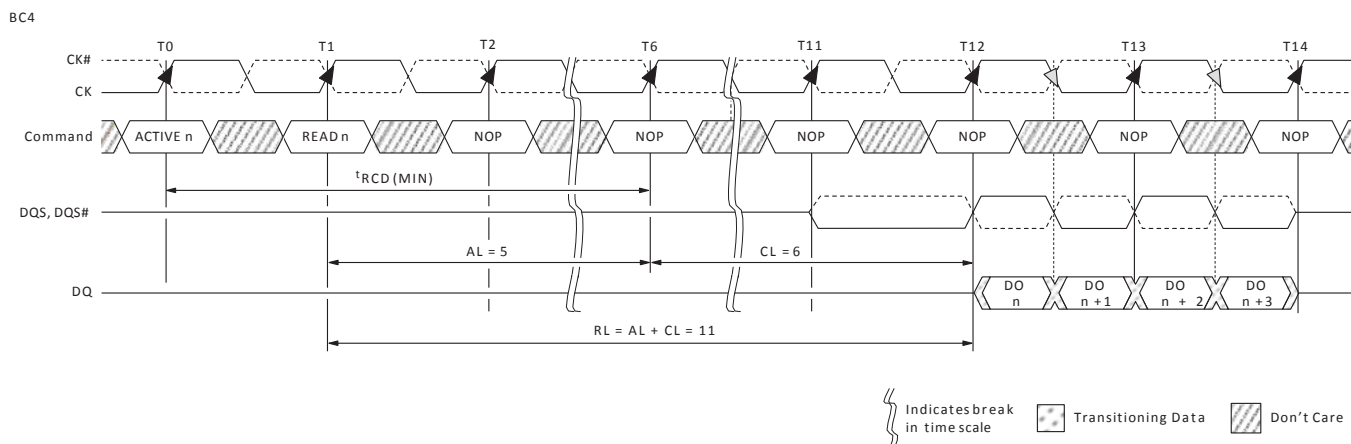
The fly-by topology benefits from a reduced number of stubs and their lengths. However, fly-by topology induces flight time skews between the clock and DQS strobe (and DQ) at each DRAM on the DIMM. Controllers will have a difficult time maintaining $tDQSS$, $tDSS$, and $tDSH$ specifications without supporting write leveling in systems which use fly-by topology-based modules. Write leveling timing and detailed operation information is provided in Write Leveling

POSTED CAS ADDITIVE Latency

POSTED CAS ADDITIVE latency (AL) is supported to make the command and data bus efficient for sustainable bandwidths in DDR3L SDRAM. MR1[4, 3] define the value of AL, as shown in Figure 44. MR1[4, 3] enable the user to program the DDR3L SDRAM with $AL = 0$, $CL - 1$, or $CL - 2$.

With this feature, the DDR3L SDRAM enables a READ or WRITE command to be issued after the ACTIVATE command for that bank prior to $tRCD$ (MIN). The only restriction is $ACTIVATE$ to READ or WRITE + $AL \geq tRCD$ (MIN) must be satisfied. Assuming $tRCD$ (MIN) = CL , a typical application using this feature sets $AL = CL - 1tCK = tRCD$ (MIN) - $1tCK$. The READ or WRITE command is held for the time of the AL before it is released internally to the DDR3L SDRAM device. READ latency (RL) is controlled by the sum of the AL and CAS latency (CL), $RL = AL + CL$. WRITE latency (WL) is the sum of CAS WRITE latency and AL, $WL = AL + CWL$ (see Mode Register 2 (MR2)). Examples of READ and WRITE latencies are shown in Figure 44 and Figure 46.)

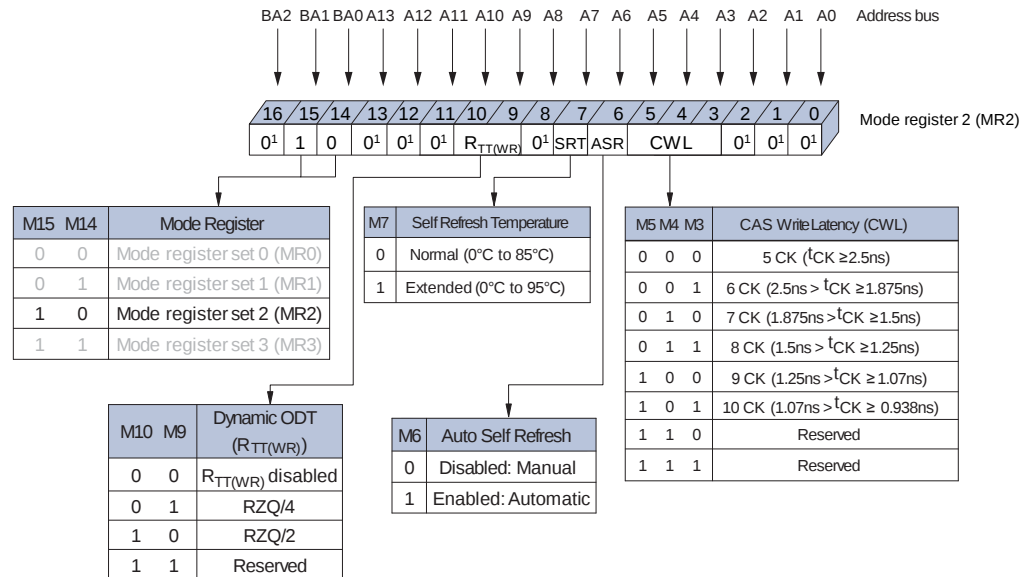
Figure 44 : READ Latency (AL = 5, CL = 6)



Mode Register 2 (MR2)

The mode register 2 (MR2) controls additional functions and features not available in the other mode registers. These additional functions are CAS WRITE latency (CWL), AUTO SELF REFRESH (ASR), SELF REFRESH TEMPERATURE (SRT), and DYNAMIC ODT (RTT(WR)). These functions are controlled via the bits shown in Figure 45. The MR2 is programmed via the MRS command and will retain the stored information until it is programmed again or until the device loses power. Reprogramming the MR2 register will not alter the contents of the memory array, provided it is performed correctly. The MR2 register must be loaded when all banks are idle and no data bursts are in progress, and the controller must wait the specified time tMRD and tMOD before initiating a subsequent operation.

Figure 45 : Mode Register 2 (MR2) Definition

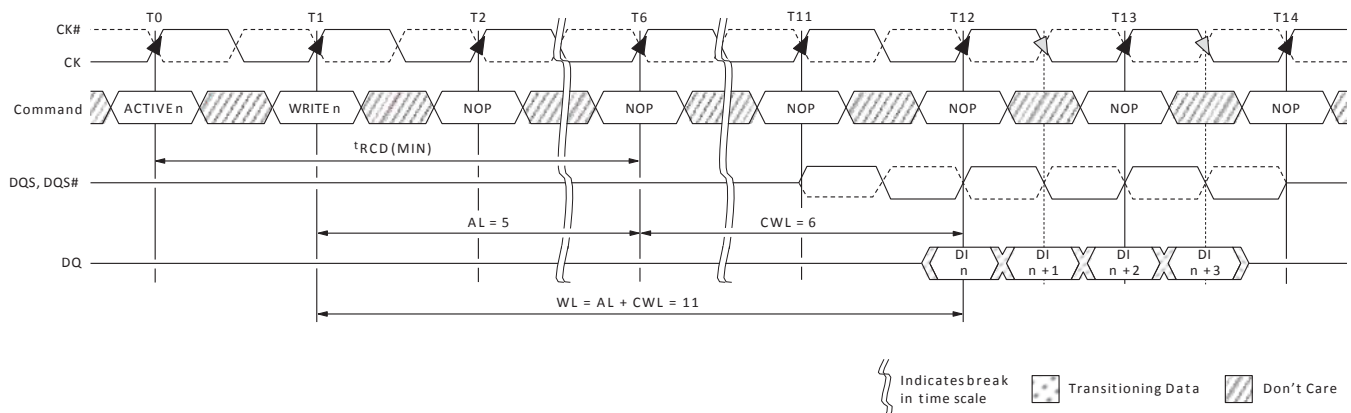


Note: 1. MR2[16, 13:11, 8, and 2:0] are reserved for future use and must all be programmed to 0.

CAS Write Latency (CWL)

CWL is defined by MR2[5:3] and is the delay, in clock cycles, from the releasing of the internal write to the latching of the first data in. CWL must be correctly set to the corresponding operating clock frequency (see Figure 45). The overall WRITE latency (WL) is equal to CWL + AL (Figure 43).

Figure 46 : CAS Write Latency



AUTO SELF REFRESH (ASR)

Mode register MR2[6] is used to disable/enable the ASR function. When ASR is disabled, the self refresh mode's refresh rate is assumed to be at the normal 85°C limit (sometimes referred to as 1x refresh rate). In the disabled mode, ASR requires the user to ensure the DRAM never exceeds a TC of 85°C while in self refresh unless the user enables the SRT feature listed below when the TC is between 85°C and 95°C.

Enabling ASR assumes the DRAM self refresh rate is changed automatically from 1x to 2x when the case temperature exceeds 85°C. This enables the user to operate the DRAM beyond the standard 85°C limit up to the optional extended temperature range of 95°C while in self refresh mode.

The standard self refresh current test specifies test conditions to normal case temperature (85°C) only, meaning if ASR is enabled, the standard self refresh current specifications do not apply (see Extended Temperature Usage).

SELF REFRESH TEMPERATURE (SRT)

Mode register MR2[7] is used to disable/enable the SRT function. When SRT is disabled, the self refresh mode's refresh rate is assumed to be at the normal 85°C limit (sometimes referred to as 1x refresh rate). In the disabled mode, SRT requires the user to ensure the DRAM never exceeds a TC of 85°C while in self refresh mode unless the user enables ASR.

When SRT is enabled, the DRAM self refresh is changed internally from 1x to 2x, regardless of the case temperature. This enables the user to operate the DRAM beyond the standard 85°C limit up to the optional extended temperature range of 95°C while in selfrefresh mode. The standard self refresh current test specifies test conditions to normal case temperature (85°C) only, meaning if SRT is enabled, the standard self refresh current specifications do not apply (see Extended Temperature Usage).

SRT vs. ASR

If the normal case temperature limit of 85°C is not exceeded, then neither SRT nor ASR is required, and both can be disabled throughout operation. However, if the extended temperature option of 95°C is needed, the user is required to provide a 2x refresh rate during (manual) refresh and to enable either the SRT or the ASR to ensure self refresh is performed at the 2x rate.

SRT forces the DRAM to switch the internal self refresh rate from 1x to 2x. Self refresh is performed at the 2x refresh rate regardless of the case temperature.

ASR automatically switches the DRAM's internal self refresh rate from 1x to 2x. However, while in self refresh mode, ASR enables the refresh rate to automatically adjust between 1x to 2x over the supported temperature range. One other disadvantage with ASR is the DRAM cannot always switch from a 1x to a 2x refresh rate at an exact case temperature of 85°C. Although the DRAM will support data integrity when it switches from a 1x to a 2x refresh rate, it may switch at a lower temperature than 85°C.

Since only one mode is necessary, SRT and ASR cannot be enabled at the same time.

DYNAMIC ODT

The dynamic ODT (RTT(WR)) feature is defined by MR2[10, 9]. Dynamic ODT is enabled when a value is selected. This new DDR3L SDRAM feature enables the ODT termination value to change without issuing an MRS command, essentially changing the ODT termination on-the-fly.

With dynamic ODT (RTT(WR)) enabled, the DRAM switches from normal ODT (RTT,nom) to dynamic ODT (RTT(WR)) when beginning a WRITE burst and subsequently switches back to ODT (RTT,nom) at the completion of the WRITE burst. If RTT,nom is disabled, the RTT,nom value will be High-Z. Special timing parameters must be adhered to when dynamic ODT (RTT(WR)) is enabled: ODTLcnw, ODTLcnw4, ODTLcnw8, ODTH4, ODTH8, and tADC.

Dynamic ODT is only applicable during WRITE cycles. If ODT (RTT,nom) is disabled, dynamic ODT (RTT(WR)) is still permitted. RTT,nom and RTT(WR) can be used independent of one other. Dynamic ODT is not available during write leveling mode, regardless of the state of ODT (RTT,nom). For details on dynamic ODT operation, refer to On-Die Termination (ODT).

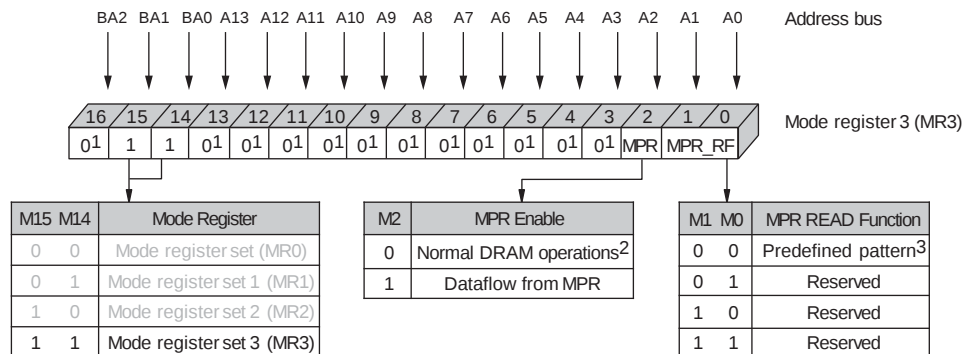
Enabling ASR assumes the DRAM self refresh rate is changed automatically from 1x to 2x when the case temperature exceeds 85°C. This enables the user to operate the DRAM beyond the standard 85°C limit up to the optional extended temperature range of 95°C while in self refresh mode.

The standard self refresh current test specifies test conditions to normal case temperature (85°C) only, meaning if ASR is enabled, the standard self refresh current specifications do not apply (see Extended Temperature Usage).

Mode Register 3 (MR3)

The mode register 3 (MR3) controls additional functions and features not available in the other mode registers. Currently defined is the MULTIPURPOSE REGISTER (MPR). This function is controlled via the bits shown in Figure 47. The MR3 is programmed via the LOAD MODE command and retains the stored information until it is programmed again or until the device loses power. Reprogramming the MR3 register will not alter the contents of the memory array, provided it is performed correctly. The MR3 register must be loaded when all banks are idle and no data bursts are in progress, and the controller must wait the specified time tMRD and tMOD before initiating a subsequent operation.

Figure 47 : Mode Register 3 (MR3) Definition



- Notes :
1. MR3[16 and 13:3] are reserved for future use and must all be programmed to 0.
 2. When MPR control is set for normal DRAM operation, MR3[1, 0] will be ignored.
 3. Intended to be used for READ synchronization

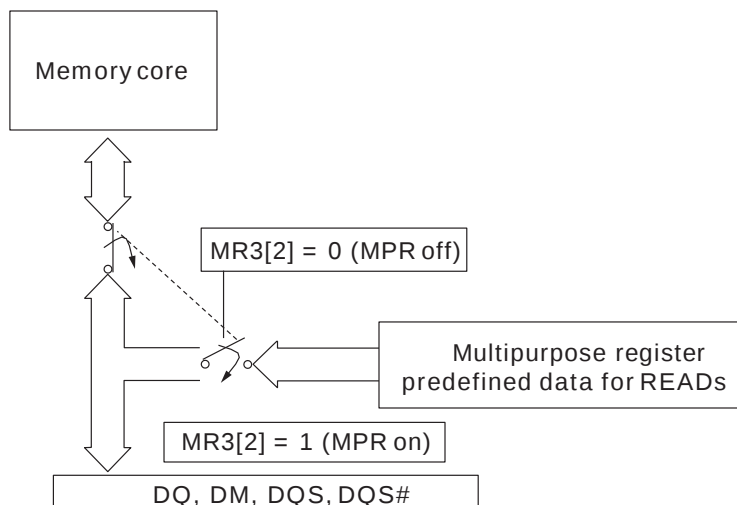
MULTIPURPOSE REGISTER (MPR)

The MULTIPURPOSE REGISTER function is used to output a predefined system timing calibration bit sequence. Bit 2 is the master bit that enables or disables access to the MPR register, and bits 1 and 0 determine which mode the MPR is placed in. The basic concept of the multipurpose register is shown in Figure 48.

If MR3[2] is a 0, then the MPR access is disabled, and the DRAM operates in normal mode. However, if MR3[2] is a 1, then the DRAM no longer outputs normal read data but outputs MPR data as defined by MR3[0, 1]. If MR3[0, 1] is equal to 00, then a predefined read pattern for system calibration is selected.

To enable the MPR, the MRS command is issued to MR3, and MR3[2] = 1. Prior to issuing the MRS command, all banks must be in the idle state (all banks are precharged, and tRP is met). When the MPR is enabled, any subsequent READ or RDAP commands are redirected to the multipurpose register. The resulting operation when either a READ or a RDAP command is issued, is defined by MR3[1:0] when the MPR is enabled (see Table 70). When the MPR is enabled, only READ or RDAP commands are allowed until a subsequent MRS command is issued with the MPR disabled (MR3[2] = 0). Power-down mode, self refresh, and any other non READ/RDAP commands are not allowed during MPR enable mode. The RESET function is supported during MPR enable mode.

Figure 48 : Multipurpose Register (MPR) Block Diagram



- Notes :
1. A predefined data pattern can be read out of the MPR with an external READ command.
 2. MR3[2] defines whether the data flow comes from the memory core or the MPR. When the data flow is defined, the MPR contents can be read out continuously with a regular READ or RDAP command.

Table 69 : MPR Functional Description of MR3 Bits

MR3[2]	MR3[1:0]	Function
MPR	MPR READ Function	
0	"Don't Care"	Normal operation, no MPR transaction All subsequent READs come from the DRAM memory array All subsequent WRITES go to the DRAM memory array
1	A[1:0] (see Table 70)	Enable MPR mode, subsequent READ/RDAP commands defined by bits1 and 2

MPR Functional Description

The MPR JEDEC definition enables either a prime DQ (DQ0 on a x4 and a x8; on a x16, DQ0 = lower byte and DQ8=upper byte) to output the MPR data with the remaining DQs driven LOW, or for all DQs to output the MPR data. The MPR readout supports fixed READ burst and READ burst chop (MRS and OTF via A12/BC#) with regular READ latencies and AC timings applicable, provided the DLL is locked as required.

MPR addressing for a valid MPR read is as follows :

- A[1:0] must be set to 00 as the burst order is fixed per nibble
- A2 selects the burst order:
 - BL8, A2 is set to 0, and the burst order is fixed to 0, 1, 2, 3, 4, 5, 6, 7
- For burst chop 4 cases, the burst order is switched on the nibble base along with the following:
 - A2 = 0; burst order = 0, 1, 2, 3
 - A2 = 1; burst order = 4, 5, 6, 7
- Burst order bit 0 (the first bit) is assigned to LSB, and burst order bit 7 (the last bit) is assigned to MSB
- A[9:3] are a "Don't Care"
- A10 is a "Don't Care"
- A11 is a "Don't Care"
- A12: Selects burst chop mode on-the-fly, if enabled within MRO
- A13 is a "Don't Care"
- BA[2:0] are a "Don't Care"

MPR Register Address Definitions and Bursting Order

The MPR currently supports a single data format. This data format is a predefined read pattern for system calibration. The predefined pattern is always a repeating 0–1 bit pattern.

Examples of the different types of predefined READ pattern bursts are shown in the following figures.

Table 70 : MPR Readouts and Burst Order Bit Mapping

MR3[2]	MR3[1:0]	Function	Burst Length	Read A[2:0]	Burst Order and Data Pattern
1	00	READ predefined pattern for system calibration	BL8	000	Burst order: 0, 1, 2, 3, 4, 5, 6, 7 Predefined pattern: 0, 1, 0, 1, 0, 1, 0, 1
			BC4	000	Burst order: 0, 1, 2, 3 Predefined pattern: 0, 1, 0, 1
			BC4	100	Burst order: 4, 5, 6, 7 Predefined pattern: 0, 1, 0, 1
1	01	RFU	n/a	N/A	N/A
			n/a	N/A	N/A
			n/a	N/A	N/A
1	10	RFU	n/a	N/A	N/A
			n/a	N/A	N/A
			n/a	N/A	N/A
1	11	RFU	n/a	N/A	N/A
			n/a	N/A	N/A
			n/a	N/A	N/A

Note: 1. Burst order bit 0 is assigned to LSB, and burst order bit 7 is assigned to MSB of the selected MPR agent.

Notes: 1. READ with BL8 either by MRS or OTF.
2. Memory controller must drive 0 on A[2:0].

The diagram illustrates the timing relationships for a memory device. The horizontal axis represents time, with key points marked as T0, Ta, Tb, Tc0, Tc1, Tc2, Tc3, Tc4, Tc5, Tc6, Tc7, Tc8, Tc9, Tc10, and Td. The vertical axis lists the signals: CK#, CK, Command, Bank address, A[1:0], A[2], A[9:3], A[10/AP], A[11], A[12/BC#], A[15:13], DQS, DQS#, and DQ.

Command Sequence: The Command signal starts with PREA at T0, followed by MRS at Ta, READ at Tb, and a series of NOP commands from Tc0 to Tc9. The final command is Valid at Td.

Bank address and Data Signals: The Bank address signal is Valid from Ta to Td. The data signals (A[1:0], A[2], A[9:3], A[10/AP], A[11], A[12/BC#], A[15:13]) are Valid from Ta to Td. The data values are: A[1:0] = 02, A[2] = 12, A[9:3] = 00, A[10/AP] = 0, A[11] = 0, A[12/BC#] = 0, A[15:13] = 0.

Timing Parameters:

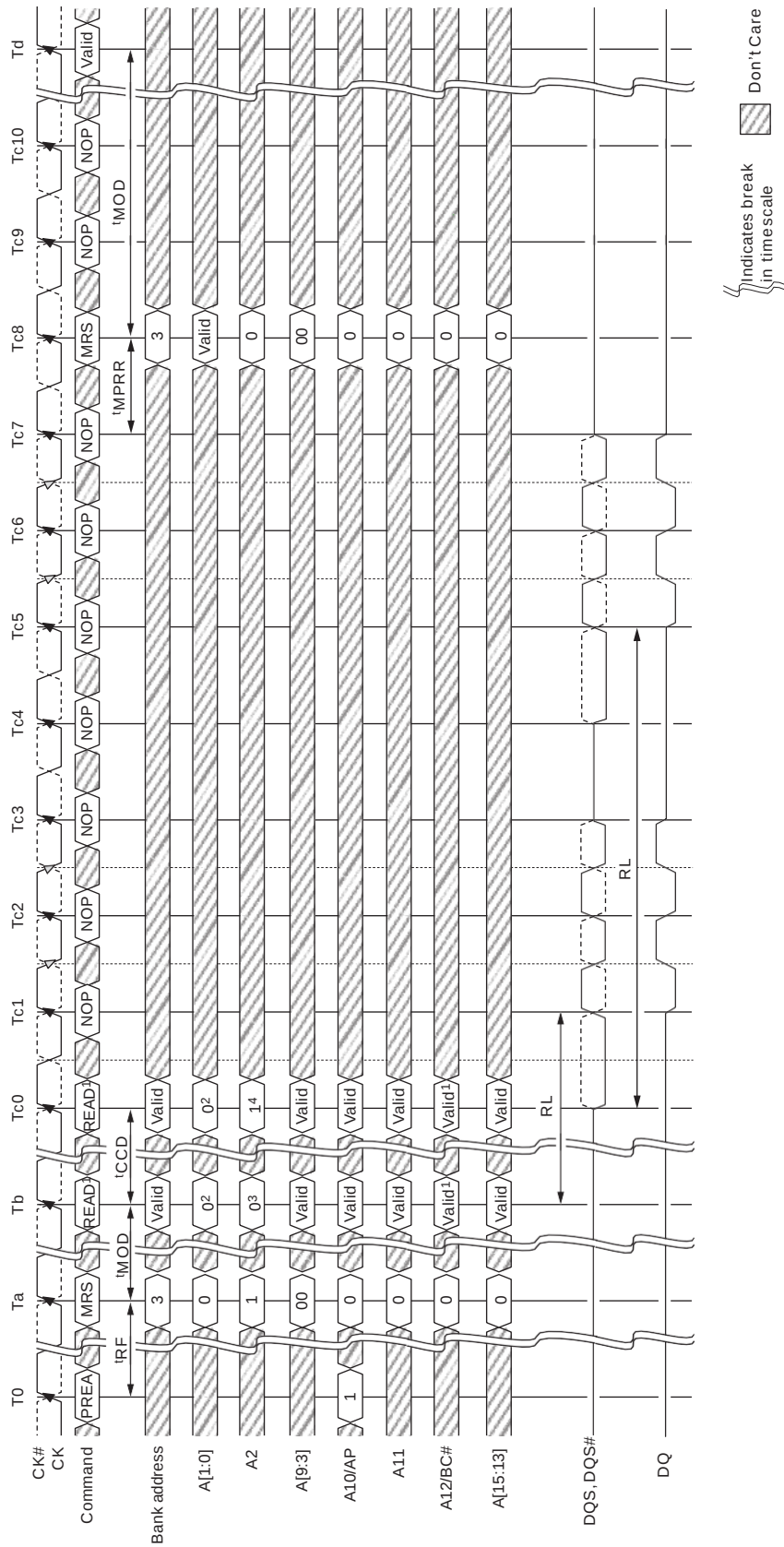
- t_{RP} : Read Precharge time (from T0 to Ta).
- t_{MOD} : Mode Register Set time (from Ta to Tb).
- t_{MRR} : Memory Refresh time (from Tb to Tc0).
- t_{CCD} : Command to Data Delay time (from Tb to Tc0).
- t_{MOD} : Mode Register Set time (from Tc0 to Tc1).
- t_{MOD} : Mode Register Set time (from Tc1 to Tc2).
- t_{MOD} : Mode Register Set time (from Tc2 to Tc3).
- t_{MOD} : Mode Register Set time (from Tc3 to Tc4).
- t_{MOD} : Mode Register Set time (from Tc4 to Tc5).
- t_{MOD} : Mode Register Set time (from Tc5 to Tc6).
- t_{MOD} : Mode Register Set time (from Tc6 to Tc7).
- t_{MOD} : Mode Register Set time (from Tc7 to Tc8).
- t_{MOD} : Mode Register Set time (from Tc8 to Tc9).
- t_{MOD} : Mode Register Set time (from Tc9 to Tc10).
- t_{MOD} : Mode Register Set time (from Tc10 to Td).

Legend:

- Hatched area: Don't Care
- Break symbol: Indicates break in time scale

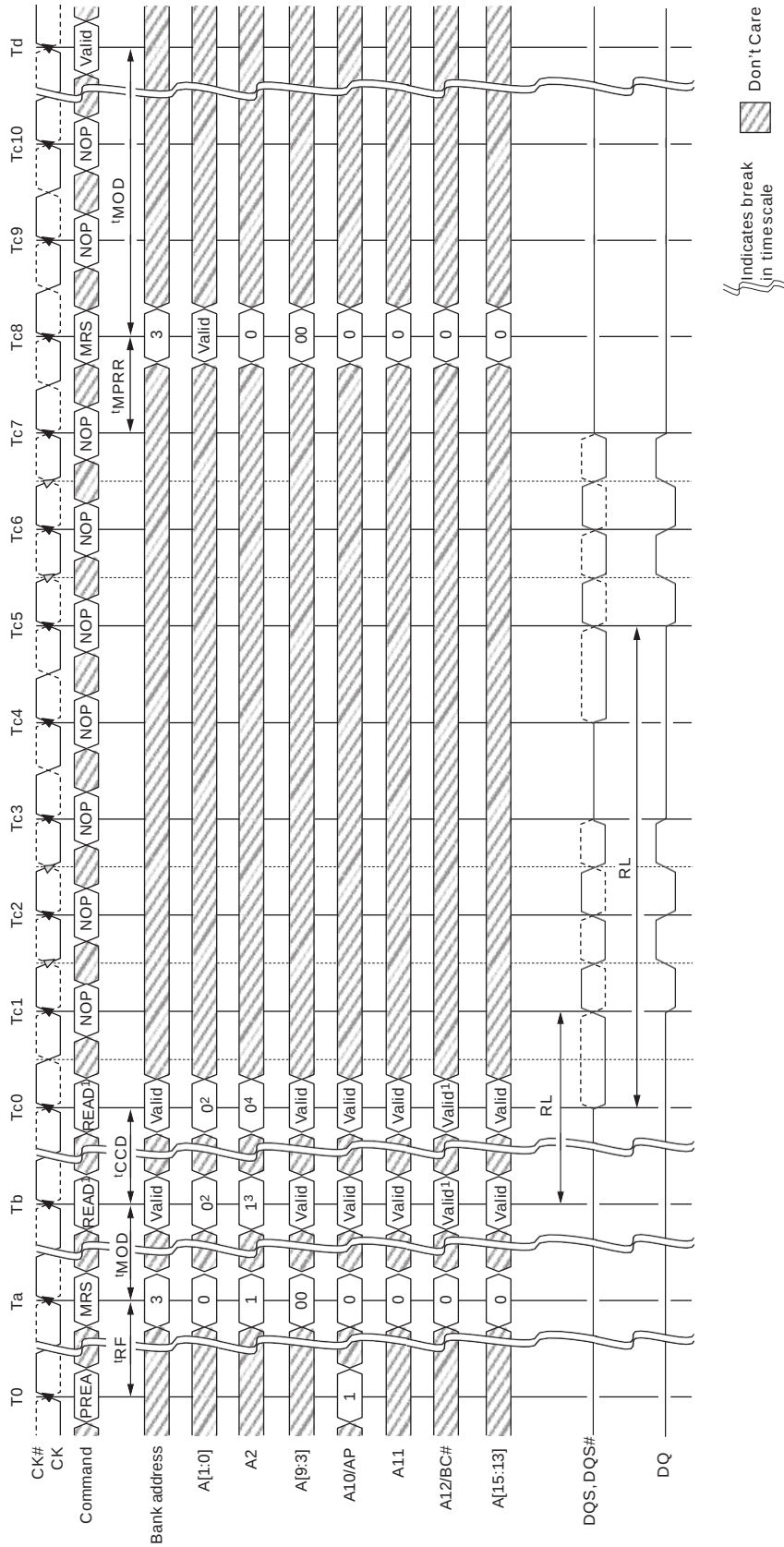
Notes: 1. READ with BL8 either by MRS or OTF.
2. Memory controller must drive 0 on A[2:0].

Figure 51 : MPR System Read Calibration with BC4: Lower Nibble, Then Upper Nibble



- Notes:
1. READ with BC4 either by MRS or OTF.
 2. Memory controller must drive 0 on A[1:0].
 3. A2 = 0 selects lower 4 nibble bits 0 . . . 3.
 4. A2 = 1 selects upper 4 nibble bits 4 . . . 7.

Figure 52 : MPR System Read Calibration with BC4: Upper Nibble, Then Lower Nibble



- Notes:
1. READ with BC4 either by MRS or OTF.
 2. Memory controller must drive 0 on A[1:0].
 3. A2 = 1 selects upper 4 nibble bits 4 . . . 7.
 4. A2 = 0 selects lower 4 nibble bits 0 . . . 3.

MPR Read Predefined Pattern

The predetermined read calibration pattern is a fixed pattern of 0, 1, 0, 1, 0, 1, 0, 1. The following is an example of using the read out predetermined read calibration pattern. The example is to perform multiple reads from the multipurpose register to do system level read timing calibration based on the predetermined and standardized pattern.

The following protocol outlines the steps used to perform the read calibration :

1. Precharge all banks
2. After tRP is satisfied, set MRS, MR3[2] = 1 and MR3[1:0] = 00. This redirects all subsequent reads and loads the predefined pattern into the MPR. As soon as tMRD and tMOD are satisfied, the MPR is available
3. Data WRITE operations are not allowed until the MPR returns to the normal DRAM state
4. Issue a read with burst order information (all other address pins are "Don't Care"):
 - A[1:0] = 00 (data burst order is fixed starting at nibble)
 - A2 = 0 (for BL8, burst order is fixed as 0, 1, 2, 3, 4, 5, 6, 7)
 - A12 = 1 (use BL8)
5. After RL = AL + CL, the DRAM bursts out the predefined read calibration pattern (0, 1, 0, 1, 0, 1, 0, 1)
6. The memory controller repeats the calibration reads until read data capture at memory controller is optimized
7. After the last MPR READ burst and after tMPRR has been satisfied, issue MRS, MR3[2] = 0, and MR3[1:0] = "Don't Care" to the normal DRAM state. All subsequent read and write accesses will be regular reads and writes from/to the DRAM array
8. When tMRD and tMOD are satisfied from the last MRS, the regular DRAM commands (such as activate a memory bank for regular read or write access) are permitted

MODE REGISTER SET (MRS) Command

The mode registers are loaded via inputs BA[2:0], A[13:0]. BA[2:0] determine which mode register is programmed:

- BA2 = 0, BA1 = 0, BA0 = 0 for MR0
- BA2 = 0, BA1 = 0, BA0 = 1 for MR1
- BA2 = 0, BA1 = 1, BA0 = 0 for MR2
- BA2 = 0, BA1 = 1, BA0 = 1 for MR3

The MRS command can only be issued (or re-issued) when all banks are idle and in the precharged state (tRP is satisfied and no data bursts are in progress). The controller must wait the specified time tMRD before initiating a subsequent operation such as an ACTIVATE command (see Figure 39). There is also a restriction after issuing an MRS command with regard to when the updated functions become available. This parameter is specified by tMOD. Both tMRD and tMOD parameters are shown in Figure 39 and Figure 40. Violating either of these requirements will result in unspecified operation.

ZQ CALIBRATION Operation

The ZQ CALIBRATION command is used to calibrate the DRAM output drivers (RON) and ODT values (RTT) over process, voltage, and temperature, provided a dedicated 240Ω ($\pm 1\%$) external resistor is connected from the DRAM's ZQ ball to VSSQ.

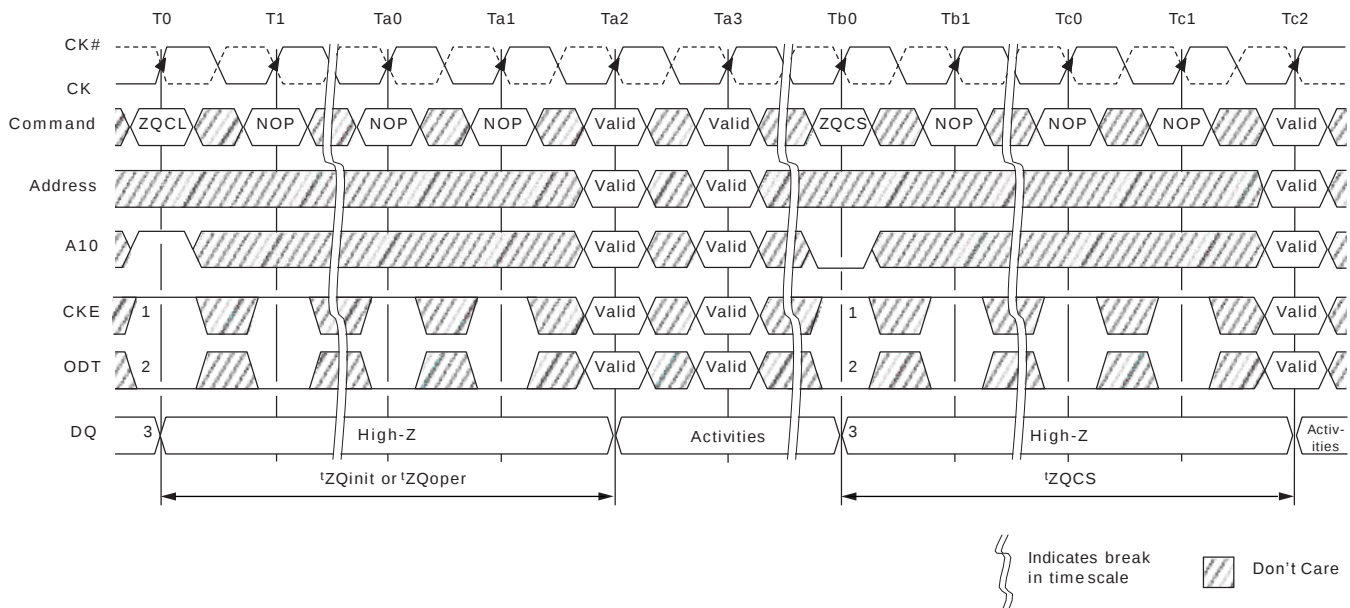
DDR3L SDRAM require a longer time to calibrate RON and ODT at power-up initialization and self refresh exit, and a relatively shorter time to perform periodic calibrations. DDR3L SDRAM defines two ZQ CALIBRATION commands : ZQCL and ZQCS. An example of ZQ calibration timing is shown below.

All banks must be precharged and tRP must be met before ZQCL or ZQCS commands can be issued to the DRAM. No other activities (other than issuing another ZQCL or ZQCS command) can be performed on the DRAM channel by the controller for the duration of tZQinit or tZQoper. The quiet time on the DRAM channel helps accurately calibrate RON and ODT. After DRAM calibration is achieved, the DRAM should disable the ZQ ball's current consumption path to reduce power.

ZQ CALIBRATION commands can be issued in parallel to DLL RESET and locking time. Upon self refresh exit, an explicit ZQCL is required if ZQ calibration is desired.

In dual-rank systems that share the ZQ resistor between devices, the controller must not enable overlap of tZQinit, tZQoper, or tZQCS between ranks.

Figure 53 : ZQ CALIBRATION Timing (ZQCL and ZQCS)



- Notes :
1. CKE must be continuously registered HIGH during the calibration procedure.
 2. ODT must be disabled via the ODT signal or the MRS during the calibration procedure.
 3. All devices connected to the DQ bus should be High-Z during calibration.

ACTIVATE Operation

Before any READ or WRITE commands can be issued to a bank within the DRAM, a row in that bank must be opened (activated). This is accomplished via the ACTIVATE command, which selects both the bank and the row to be activated.

After a row is opened with an ACTIVATE command, a READ or WRITE command may be issued to that row, subject to the t_{RCD} specification. However, if the additive latency is programmed correctly, a READ or WRITE command may be issued prior to t_{RCD} (MIN). In this operation, the DRAM enables a READ or WRITE command to be issued after the ACTIVATE command for that bank, but prior to t_{RCD} (MIN) with the requirement that $(\text{ACTIVATE-to-READ/WRITE}) + \text{AL} \geq t_{RCD}$ (MIN) (see Posted CAS Additive Latency). t_{RCD} (MIN) should be divided by the clock period and rounded up to the next whole number to determine the earliest clock edge after the ACTIVATE command on which a READ or WRITE command can be entered. The same procedure is used to convert other specification limits from time units to clock cycles.

When at least one bank is open, any READ-to-READ command delay or WRITE-to-WRITE command delay is restricted to t_{CCD} (MIN). A subsequent ACTIVATE command to a different row in the same bank can only be issued after the previous active row has been closed (precharged). The minimum time interval between successive ACTIVATE commands to the same bank is defined by t_{RC} .

A subsequent ACTIVATE command to another bank can be issued while the first bank is being accessed, which results in a reduction of total row-access overhead. The minimum time interval between successive ACTIVATE commands to different banks is defined by t_{RRD} . No more than four bank ACTIVATE commands may be issued in a given t_{FAW} (MIN) period, and the t_{RRD} (MIN) restriction still applies. The t_{FAW} (MIN) parameter applies, regardless of the number of banks already opened or closed.

Figure 54 : Example: Meeting t_{RRD} (MIN) and t_{RCD} (MIN)

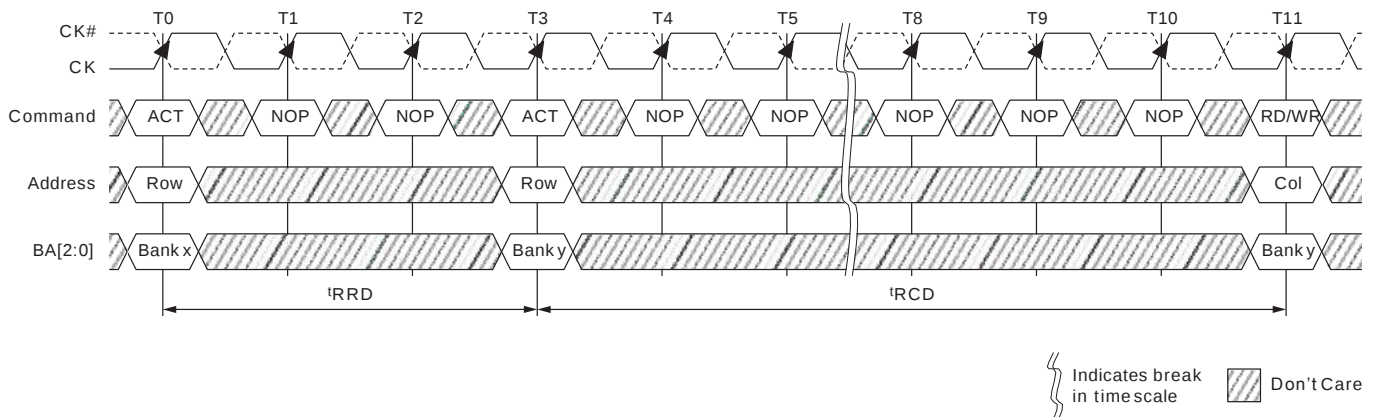
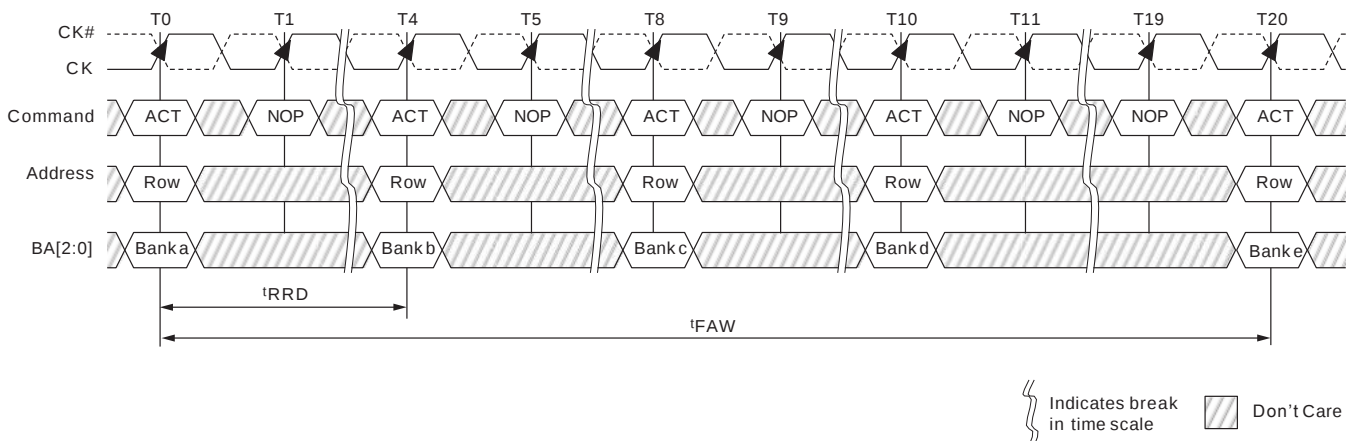


Figure 55 : Example: t_{FAW}

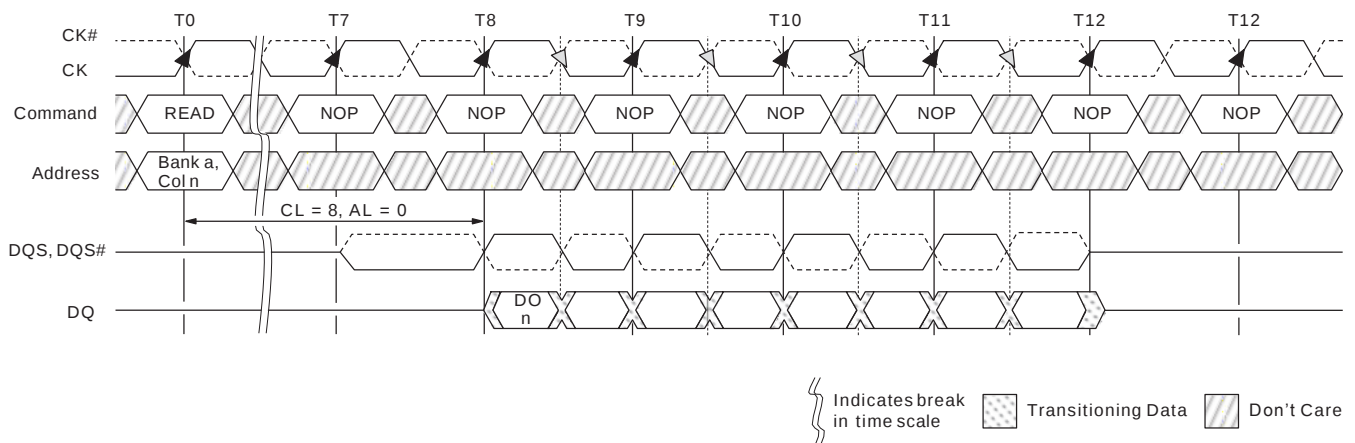


READ Operation

READ bursts are initiated with a READ command. The starting column and bank addresses are provided with the READ command and auto precharge is either enabled or disabled for that burst access. If auto precharge is enabled, the row being accessed is automatically precharged at the completion of the burst. If auto precharge is disabled, the row will be left open after the completion of the burst.

During READ bursts, the valid data-out element from the starting column address is available READ latency (RL) clocks later. RL is defined as the sum of posted CAS additive latency (AL) and CAS latency (CL) ($RL = AL + CL$). The value of AL and CL is programmable in the mode register via the MRS command. Each subsequent data-out element is valid nominally at the next positive or negative clock edge (that is, at the next crossing of CK and CK#). Figure 56 shows an example of RL based on a CL setting of 8 and an AL setting of 0.

Figure 56 : READ Latency



- Notes :
1. DO n = data-out from column n .
 2. Subsequent elements of data-out appear in the programmed order following DO n .

DQS, DQS# is driven by the DRAM along with the output data. The initial LOW state on DQS and HIGH state on DQS# is known as the READ preamble (tRPRE). The LOW state on DQS and the HIGH state on DQS#, coincident with the last data-out element, is known as the READ postamble (tRPST). Upon completion of a burst, assuming no other commands have been initiated, the DQ goes High-Z. A detailed explanation of tDQSQ (valid data-out skew), tQH (data-out window hold), and the valid data window are depicted in Figure 67. A detailed explanation of tDQSCK (DQS transition skew to CK) is also depicted in Figure 67.

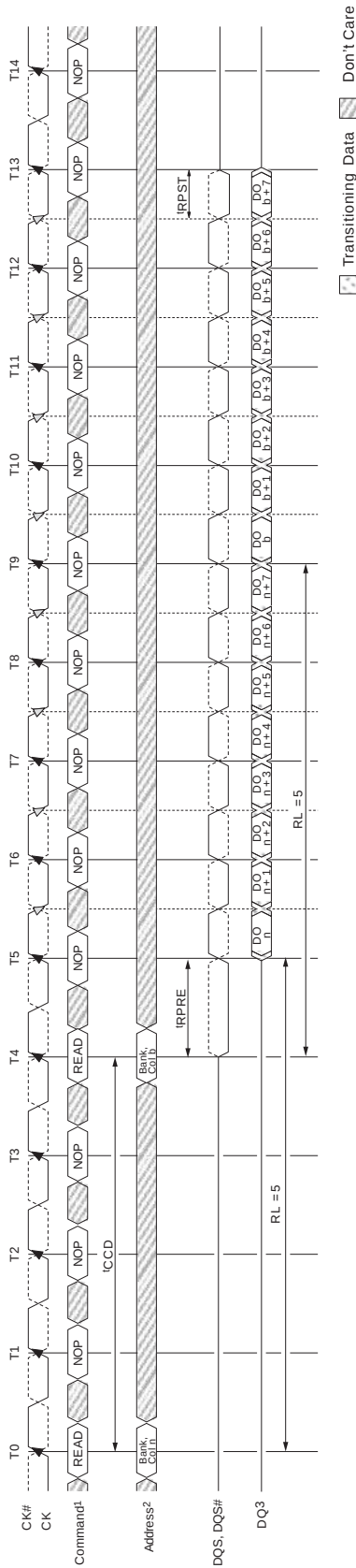
Data from any READ burst may be concatenated with data from a subsequent READ command to provide a continuous flow of data. The first data element from the new burst follows the last element of a completed burst. The new READ command should be issued tCCD cycles after the first READ command. This is shown for BL8 in Figure 57. If BC4 is enabled, tCCD must still be met, which will cause a gap in the data output, as shown in Figure 58. Nonconsecutive READ data is reflected in Figure 59. DDR3L SDRAM does not allow interrupting or truncating any READ burst.

Data from any READ burst must be completed before a subsequent WRITE burst is allowed. An example of a READ burst followed by a WRITE burst for BL8 is shown in Figure 60 (BC4 is shown in Figure 61). To ensure the READ data is completed before the WRITE data is on the bus, the minimum READ-to-WRITE timing is $RL + tCCD - WL + 2tCK$.

A READ burst may be followed by a PRECHARGE command to the same bank, provided auto precharge is not activated. The minimum READ-to-PRECHARGE command spacing to the same bank is four clocks and must also satisfy a minimum analog time from the READ command. This time is called tRTP (READ-to-RECHARGE). tRTP starts AL cycles later than the READ command. Examples for BL8 are shown in Figure 62 and BC4 in Figure 63. Following the PRECHARGE command, a subsequent command to the same bank cannot be issued until tRP is met. The PRECHARGE command followed by another PRECHARGE command to the same bank is allowed. However, the precharge period will be determined by the last PRECHARGE command issued to the bank.

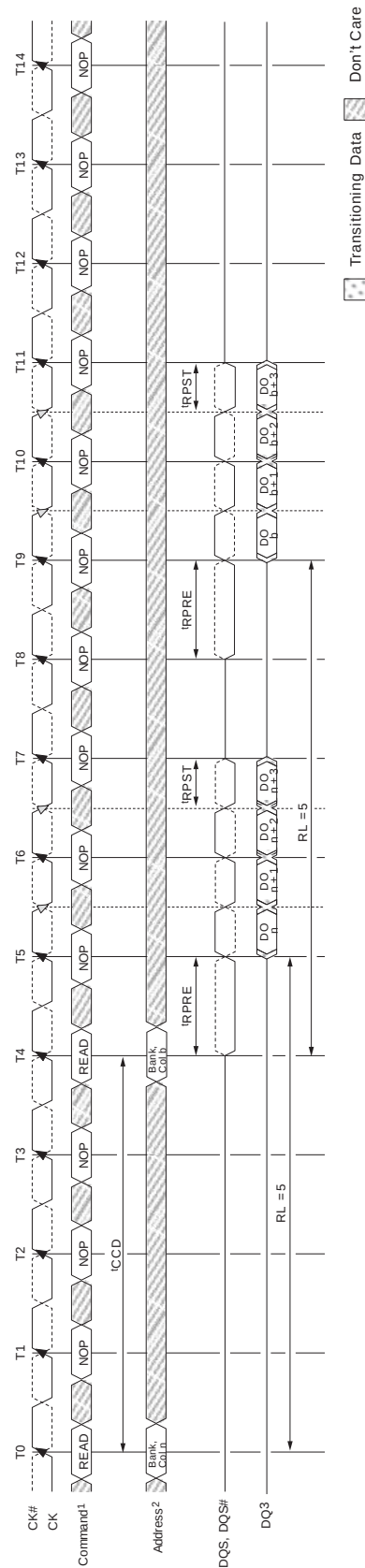
If A10 is HIGH when a READ command is issued, the READ with auto precharge function is engaged. The DRAM starts an auto precharge operation on the rising edge, which is $AL + tRTP$ cycles after the READ command. DRAM support a tRAS lockout feature (see Figure 65). If tRAS (MIN) is not satisfied at the edge, the starting point of the auto precharge operation will be delayed until tRAS (MIN) is satisfied. If tRTP (MIN) is not satisfied at the edge, the starting point of the auto precharge operation is delayed until tRTP (MIN) is satisfied. In case the internal precharge is pushed out by tRTP, tRP starts at the point at which the internal precharge happens (not at the next rising clock edge after this event). The time from READ with auto precharge to the next ACTIVATE command to the same bank is $AL + (tRTP + tRP)^*$, where * means rounded up to the next integer. In any event, internal precharge does not start earlier than four clocks after the last 8n-bit prefetch.

Figure 57 : Consecutive READ Bursts (BL8)



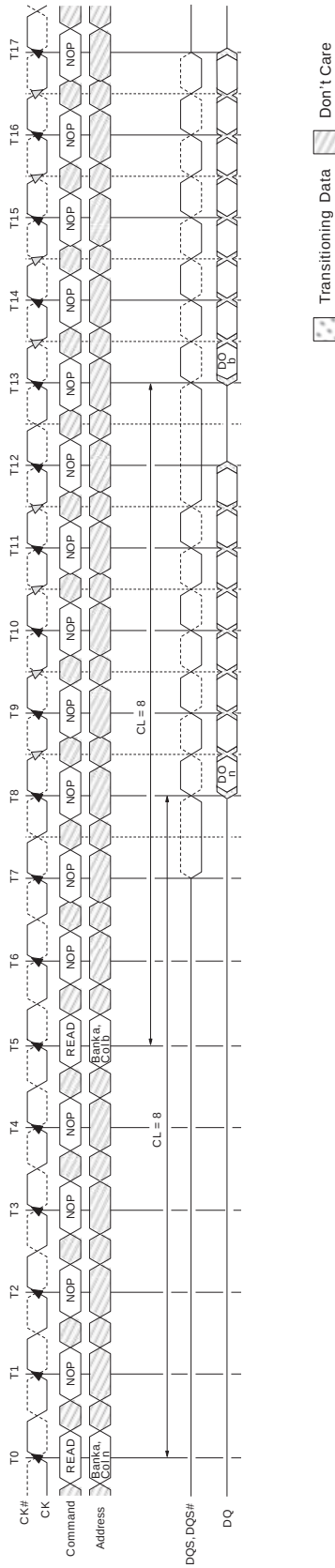
- Notes :
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The BL8 setting is activated by either MR0[1:0] = 00 or MR0[1:0] = 01 and A12 = 1 during READ command at T0 and T4.
 3. DO n (or b) = data-out from column n (or column b).
 4. BL8, RL = 5 (CL = 5, AL = 0).

Figure 58 : Consecutive READ Bursts (BC4)



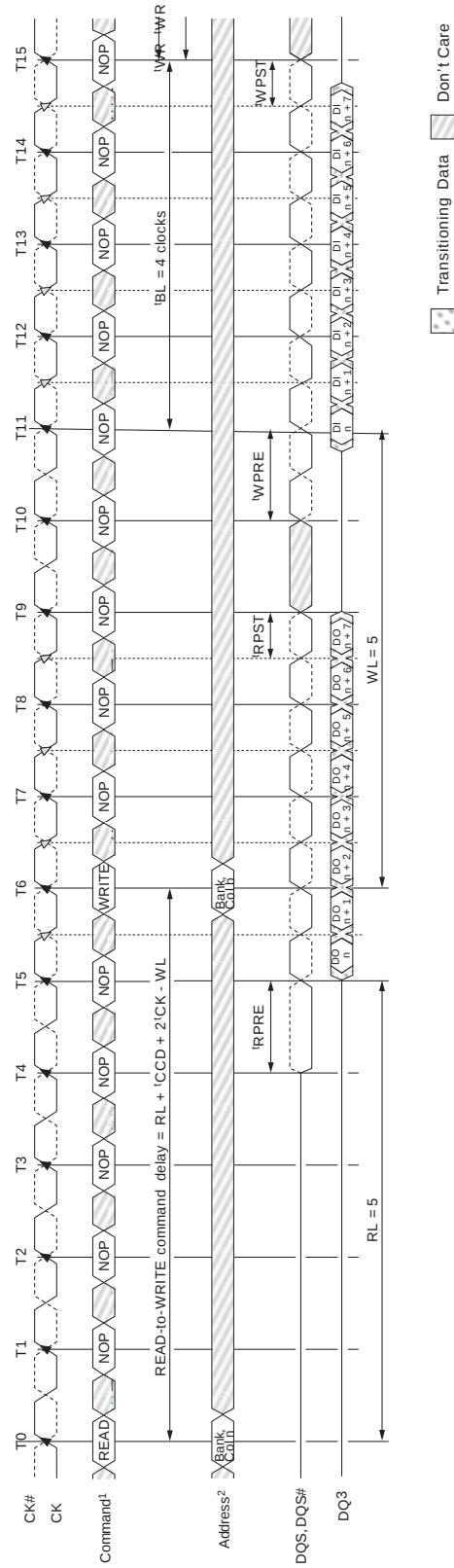
- Notes :
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The BC4 setting is activated by either MR0[1:0] = 10 or MR0[1:0] = 01 and A12 = 0 during READ command at T0 and T4.
 3. DO n (or b) = data-out from column n (or column b).
 4. BC4, RL = 5 (CL = 5, AL = 0).

Figure 59 : Nonconsecutive READ Bursts



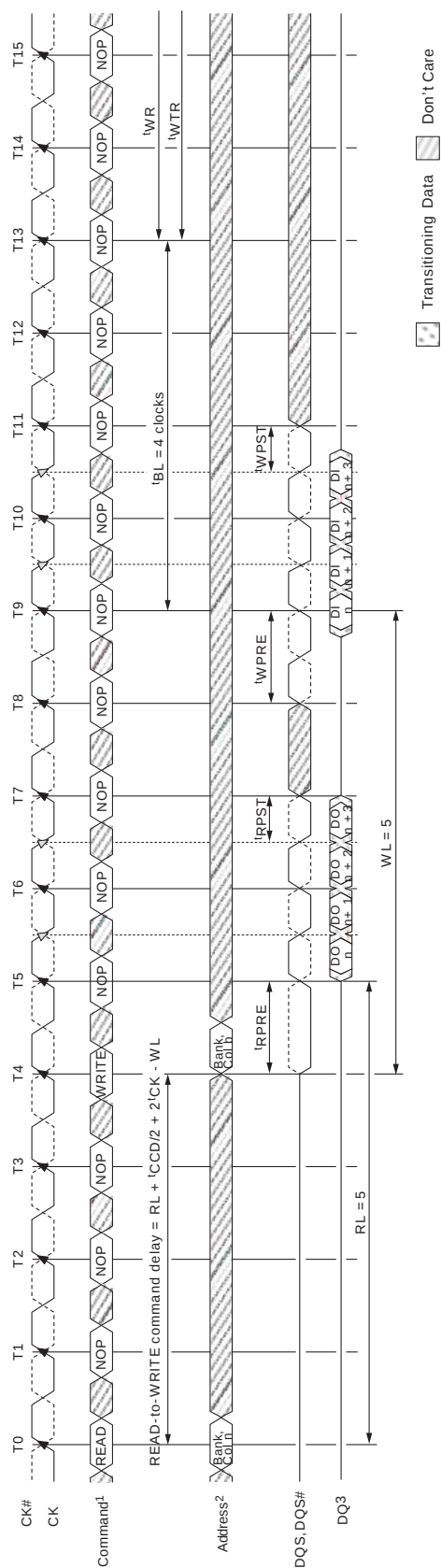
- Notes:
1. AL = 0, RL = 8.
 2. DO n (or b) = data-out from column n (or column b).
 3. Seven subsequent elements of data-out appear in the programmed order following DO n .
 4. Seven subsequent elements of data-out appear in the programmed order following DO b .

Figure 60 : READ (BL8) to WRITE (BL8)



- Notes :
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The BL8 setting is activated by either MR0[1:0] = 00 or MR0[1:0] = 01 and A12 = 1 during the READ command at T0, and the WRITE command at T6.
 3. DO n = data-out from column, DI b = data-in for column b .
 4. BL8, RL = 5 (AL = 0, CL = 5), WL = 5 (AL = 0, CWL = 5).

Figure 61 : READ (BC4) to WRITE (BC4) OTF



- Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The BC4 OTF setting is activated by MR0[1:0] and A12 = 0 during READ command at T0 and WRITE command at T4.
 3. DO n = data-out from column n ; DI n = data-in from column n .
 4. BC4, RL = 5 (AL = 0, CL = 5), WL = 5 (AL = 0, CWL = 5).

Figure 62 : READ to PRECHARGE (BL8)

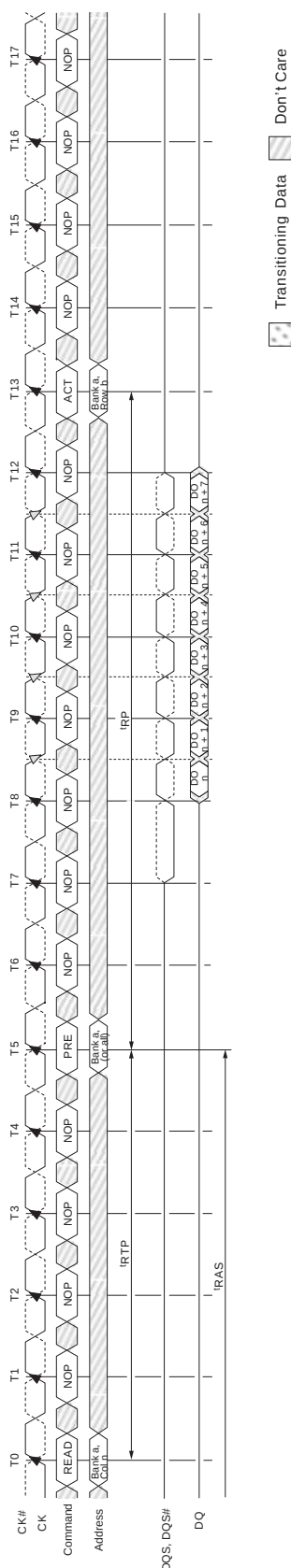


Figure 63 : READ to PRECHARGE (BC4)

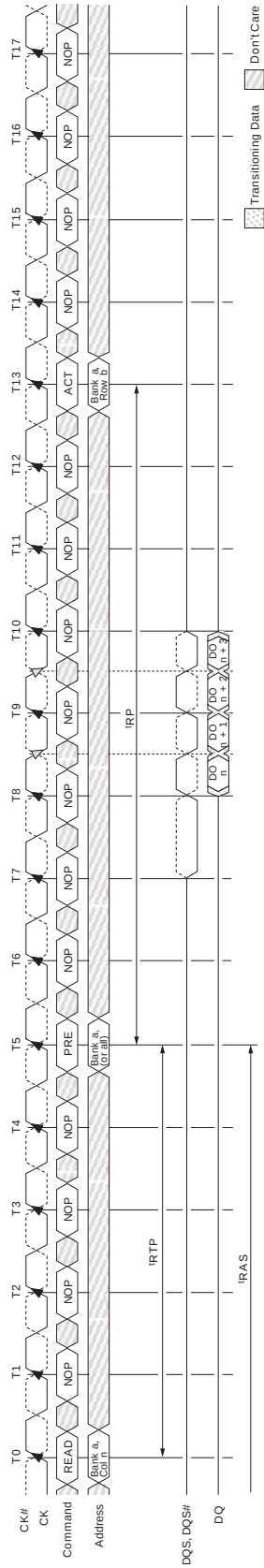


Figure 64 : READ to PRECHARGE (AL = 5, CL = 6)

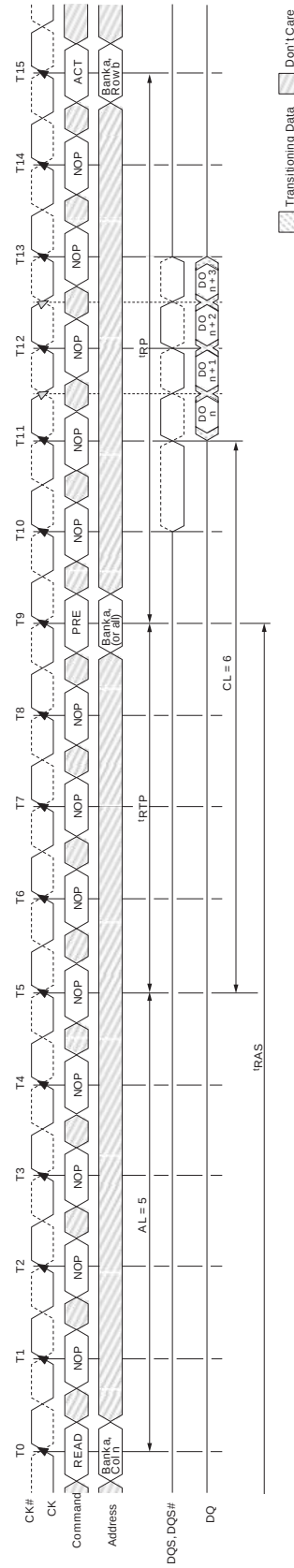
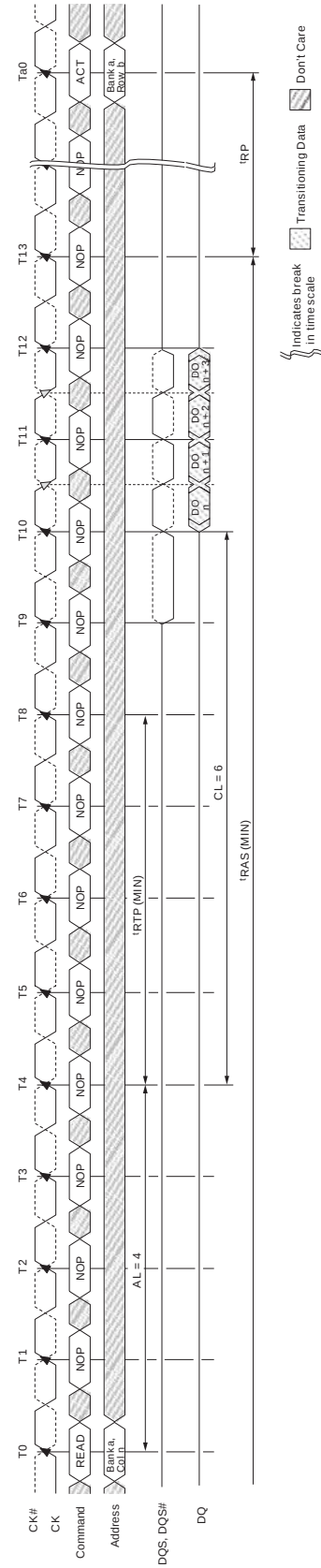


Figure 65 : READ with Auto Precharge (AL = 4, CL = 6)



DQS to DQ output timing is shown in Figure 66. The DQ transitions between valid data outputs must be within t_{DQSQ} of the crossing point of DQS, DQS#. DQS must also maintain a minimum HIGH and LOW time of t_{QSH} and t_{QSL} . Prior to the READ preamble, the DQ balls will either be floating or terminated, depending on the status of the ODT signal.

Figure 67 shows the strobe-to-clock timing during a READ. The crossing point DQS, DQS# must transition within $\pm t_{DQSCK}$ of the clock crossing point. The data out has no timing relationship to CK, only to DQS, as shown in Figure 67.

Figure 67 also shows the READ preamble and postamble. Typically, both DQS and DQS# are High-Z to save power (VDDQ). Prior to data output from the DRAM, DQS is driven LOW and DQS# is HIGH for t_{RPRE} . This is known as the READ preamble.

The READ postamble, t_{RPST} , is one half clock from the last DQS, DQS# transition. During the READ postamble, DQS is driven LOW and DQS# is HIGH. When complete, the DQ is disabled or continues terminating, depending on the state of the ODT signal. Figure 70 demonstrates how to measure t_{RPST} .

The diagram illustrates the timing for a Read Command with a 2T delay. The sequence of signals is as follows:

- T0:** CK# and CK are sampled. Command1 (READ) is issued. Address2 (Bank, Col) is provided.
- T1 to T10:** The command is executed. The delay from the command to the first data is $RL = AL + CL$.
- DQS and DQS#:** Strobe signals that are active for a duration of $DQSQ (MAX)$ and $DQSQ (MIN)$.
- Data:** Data words DO_n to DO_{n+7} are output. The first data word is valid for a duration of $RPST$ after the DQS# signal. The last data word is valid for a duration of $HZDQ (MAX)$ after the DQS signal.
- Don't Care:** Indicated by a hatched pattern in the original image.

- 152

tHZ and tLZ transitions occur in the same access time as valid data transitions. These parameters are referenced to a specific voltage level that specifies when the device output is no longer driving tHZDQS and tHZDQ, or begins driving tLZDQS, tLZDQ. Figure 68 shows a method of calculating the point when the device is no longer driving tHZDQS and tHZDQ, or begins driving tLZDQS, tLZDQ, by measuring the signal at two different voltages. The actual voltage measurement points are not critical as long as the calculation is consistent. The parameters tLZDQS, tLZDQ, tHZDQS, and tHZDQ are defined as single-ended.

Figure 67 : Data Strobe Timing – READs

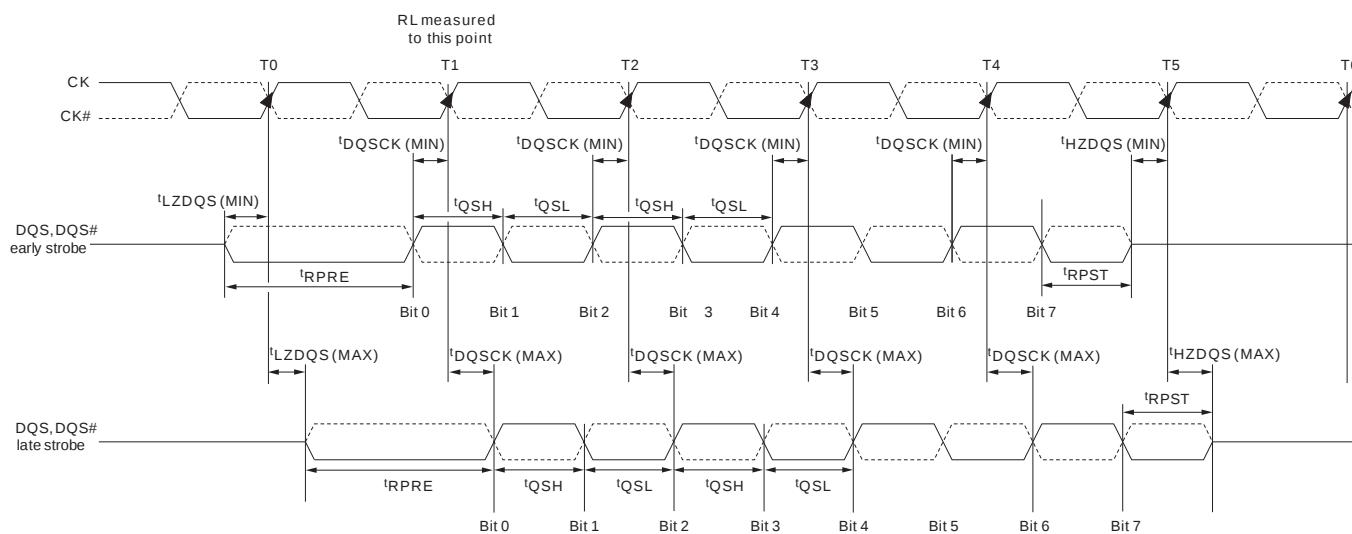
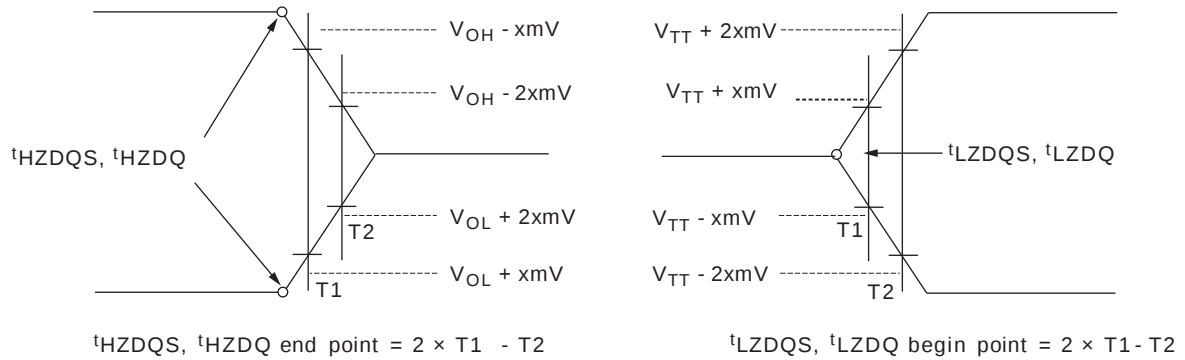


Figure 68 : Method for Calculating tLZ and tHZ



- Notes :
1. Within a burst, the rising strobe edge is not necessarily fixed at tDQSCK (MIN) or tDQSCK (MAX). Instead, the rising strobe edge can vary between tDQSCK (MIN) and tDQSCK (MAX).
 2. The DQS HIGH pulse width is defined by tQSH, and the DQS LOW pulse width is defined by tQSL. Likewise, tLZDQS (MIN) and tHZDQS (MIN) are not tied to tDQSCK (MIN) (early strobe case), and tLZDQS (MAX) and tHZDQS (MAX) are not tied to tDQSCK (MAX) (late strobe case); however, they tend to track one another.
 3. The minimum pulse width of the READ preamble is defined by tRPRE (MIN). The minimum pulse width of the READ postamble is defined by tRPST (MIN).

Figure 69 : tRPRE Timing

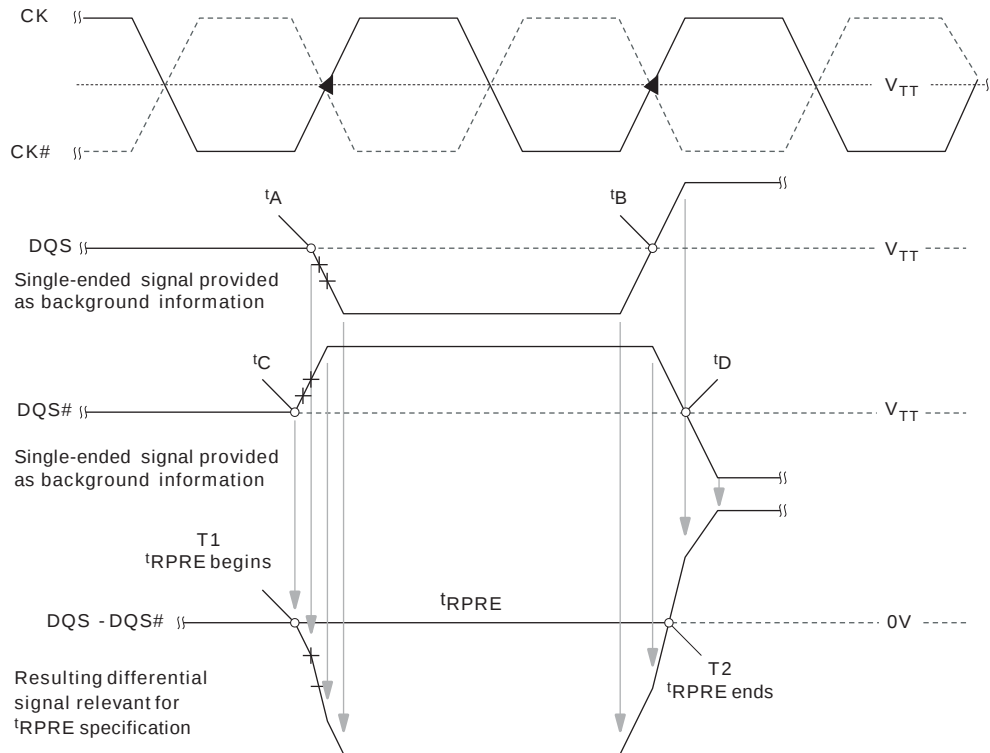
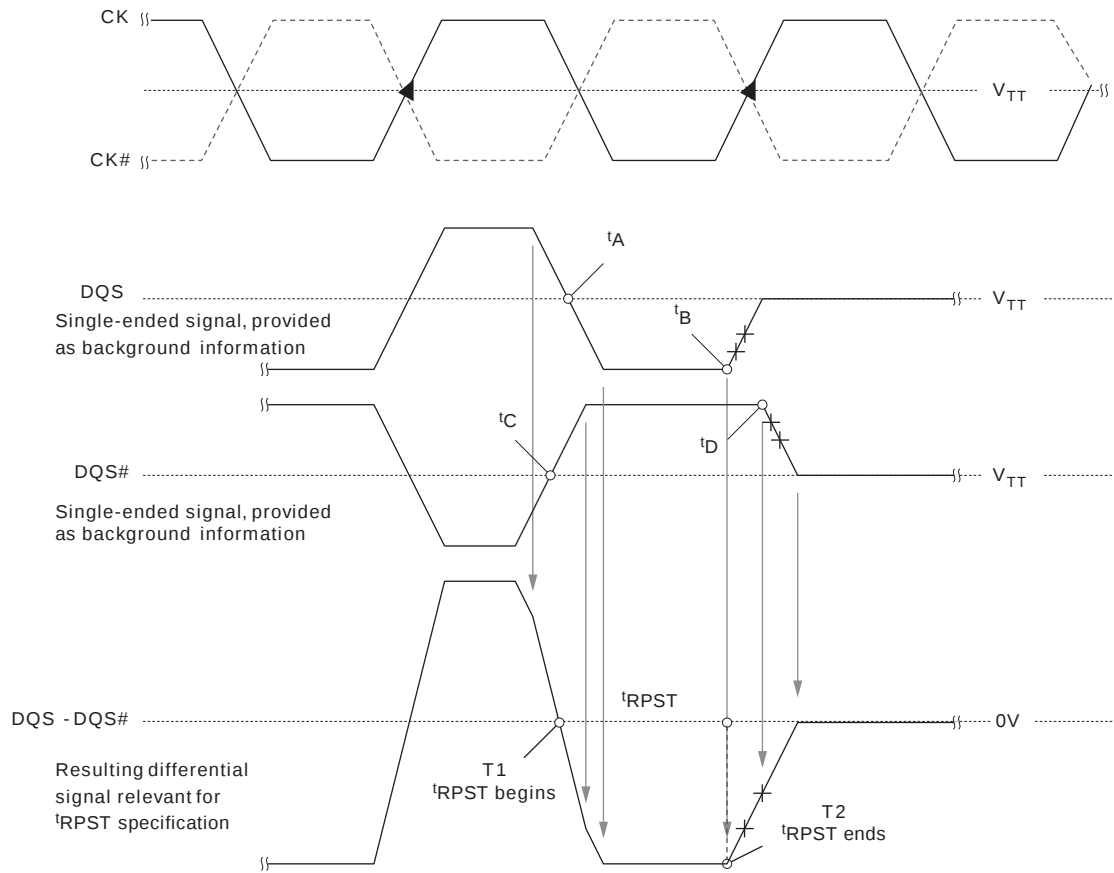


Figure 70 : tRPST Timing



WRITE Operation

WRITE bursts are initiated with a WRITE command. The starting column and bank addresses are provided with the WRITE command, and auto precharge is either enabled or disabled for that access. If auto precharge is selected, the row being accessed is precharged at the end of the WRITE burst. If auto precharge is not selected, the row will remain open for subsequent accesses. After a WRITE command has been issued, the WRITE burst may not be interrupted. For the generic WRITE commands used in Figure 73 through Figure 81, auto precharge is disabled.

During WRITE bursts, the first valid data-in element is registered on a rising edge of DQS following the WRITE latency (WL) clocks later and subsequent data elements will be registered on successive edges of DQS. WRITE latency (WL) is defined as the sum of posted CAS additive latency (AL) and CAS WRITE latency (CWL): $WL=AL+CWL$. The values of AL and CWL are programmed in the MR0 and MR2 registers, respectively. Prior to the first valid DQS edge, a full cycle is needed (including a dummy crossover of DQS(#)) and specified as the WRITE preamble shown in Figure 72. The half cycle on DQS following the last data-in element is known as the WRITE postamble.

The time between the WRITE command and the first valid edge of DQS is WL clocks $\pm tDQSS$. Figure 74 through Figure 81 show the nominal case where $tDQSS = 0ns$; however, Figure 73 includes $tDQSS (MIN)$ and $tDQSS (MAX)$ cases.

Data may be masked from completing a WRITE using data mask. The data mask occurs on the DM ball aligned to the WRITE data. If DM is LOW, the WRITE completes normally. If DM is HIGH, that bit of data is masked.

Upon completion of a burst, assuming no other commands have been initiated, the DQ will remain High-Z, and any additional input data will be ignored.

Data for any WRITE burst may be concatenated with a subsequent WRITE command to provide a continuous flow of input data. The new WRITE command can be $tCCD$ clocks following the previous WRITE command. The first data element from the new burst is applied after the last element of a completed burst. Figure 74 and Figure 75 show concatenated bursts. An example of nonconsecutive WRITES is shown in Figure 76.

Data for any WRITE burst may be followed by a subsequent READ command after $tWTR$ has been met (see Figure 77, Figure 78, and Figure 79).

Data for any WRITE burst may be followed by a subsequent PRECHARGE command, providing tWR has been met, as shown in Figure 80 and Figure 81.

Both $tWTR$ and tWR starting time may vary, depending on the mode register settings (fixed BC4, BL8 versus OTF).

Figure 71 : tWPRE Timing

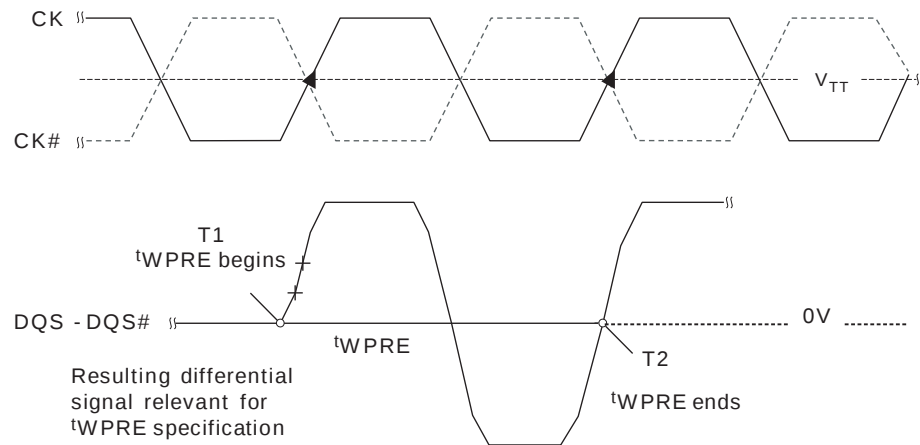


Figure 72 : tWPST Timing

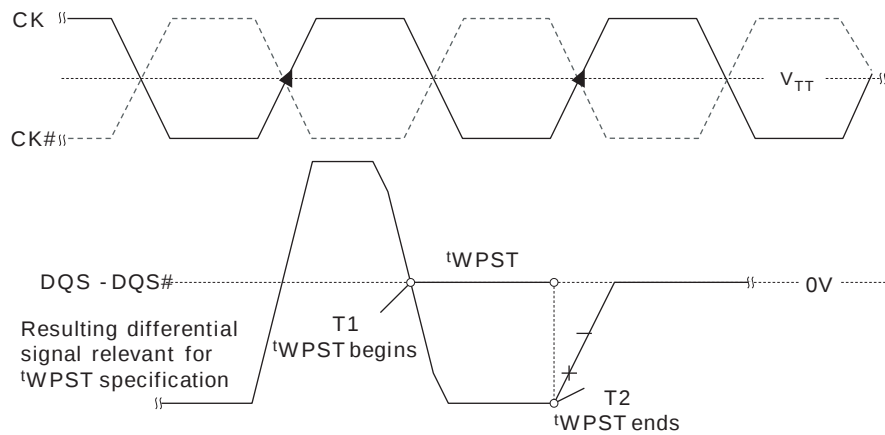
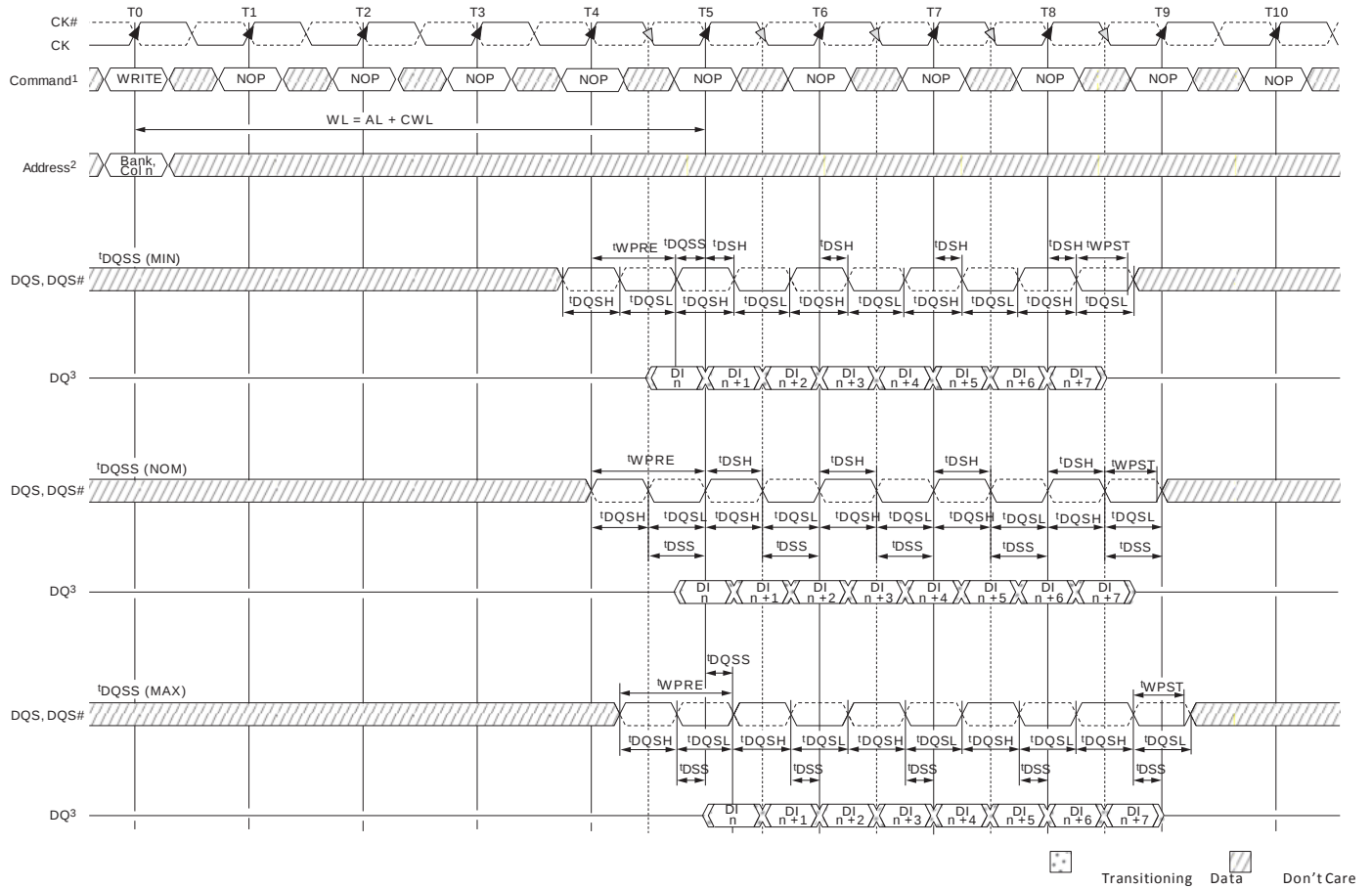
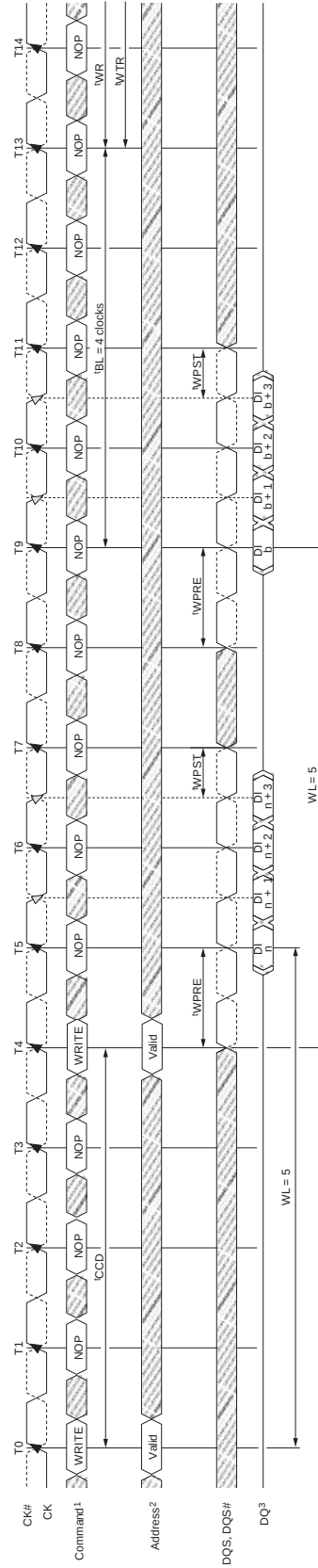


Figure 73 : WRITE Burst



- Notes :
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The BL8 setting is activated by either $MR0[1:0] = 00$ or $MR0[1:0] = 01$ and $A12 = 1$ during the WRITE command at T0.
 3. DI_n = data-in for column n .
 4. BL8, $WL = 5$ ($AL = 0$, $CWL = 5$).
 5. t_{DQSS} must be met at each rising clock edge.
 6. t_{WPST} is usually depicted as ending at the crossing of DQS, DQS#; however, t_{WPST} actually ends when DQS no longer drives LOW and DQS# no longer drives HIGH.

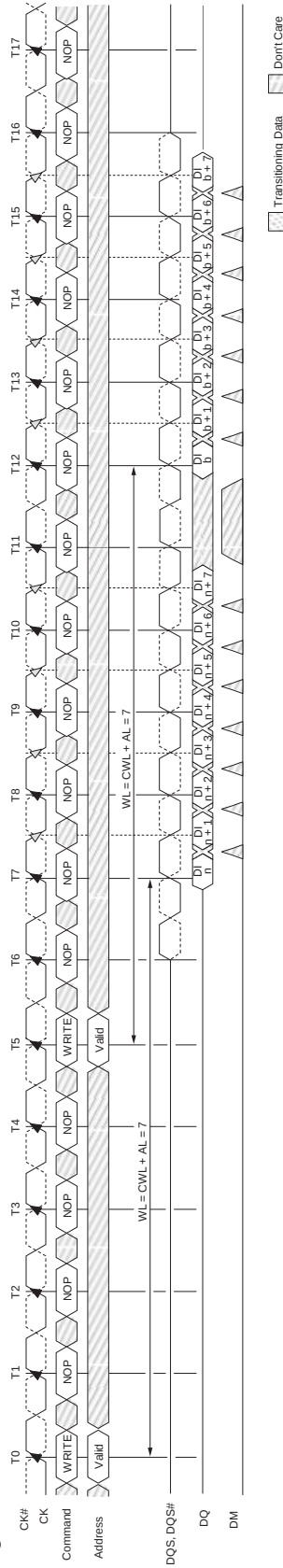
Figure 75 : Consecutive WRITE (BC4) to WRITE (BC4) via OTF



5. If set via MRS (fixed) t^w WR and t^w WTR would start T11 (2 cycles earlier).

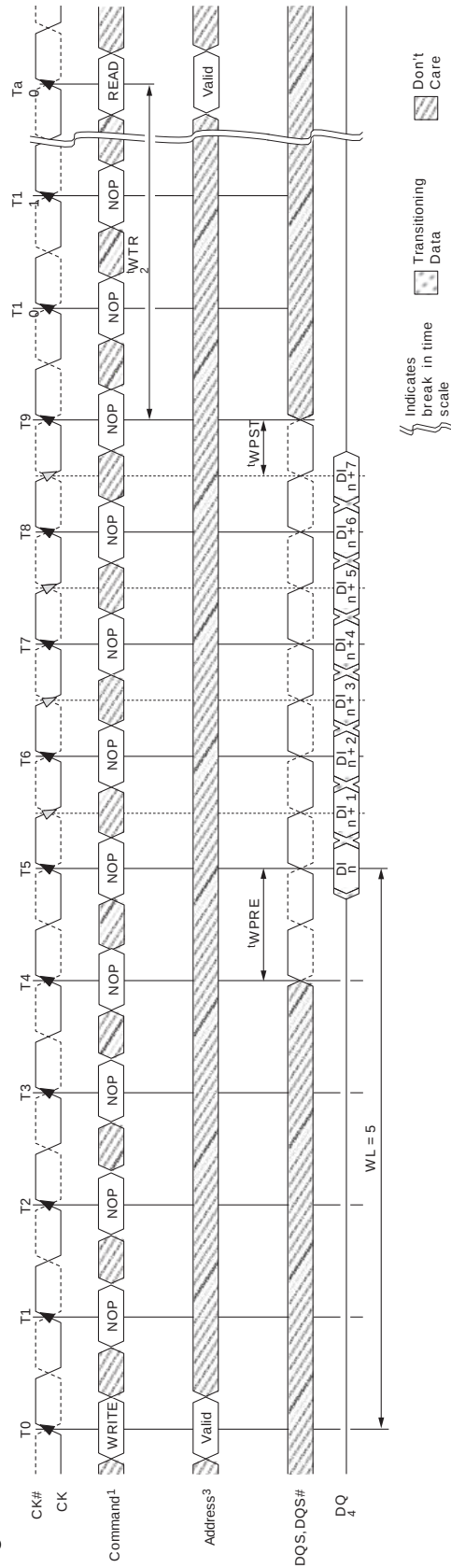
4. BL8, WL = 5 (AL = 0, CWL = 5).

Figure 76 : Nonconsecutive WRITE to WRITE



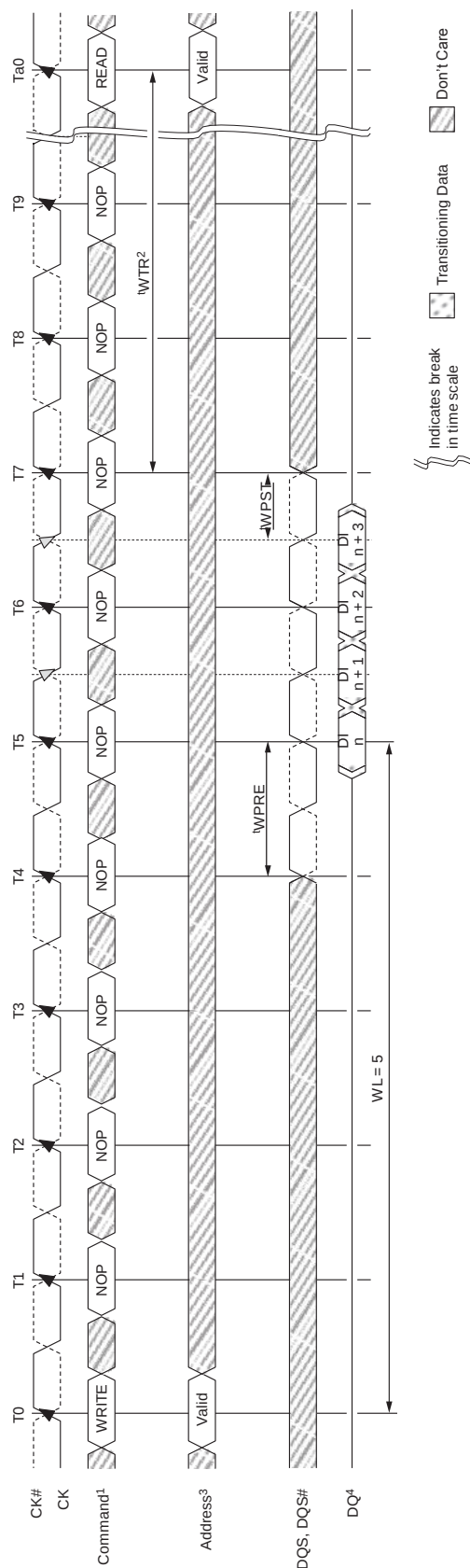
- Notes:
1. DI n (or b) = data-in for column n (or column b).
 2. Seven subsequent elements of data-in are applied in the programmed order following DO n .
 3. Each WRITE command may be to any bank.
 4. Shown for WL = 7 (CWL = 7, AL = 0).

Figure 77 : Nonconsecutive WRITE to WRITE



- Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. tWTR controls the WRITE-to-READ delay to the same device and starts with the first rising clock edge after the last write data shown at T9.
 3. The BL8 setting is activated by either MR0[1:0] = 00 or MR0[1:0] = 01 and MR0[12] = 1 during the WRITE command at T0. The READ command at Ta0 can be either BC4 or BL8, depending on MR0[1:0] and the A12 status at Ta0.
 4. DI n = data-in for column n .
 5. RL = 5 (AL = 0, CL = 5), WL = 5 (AL = 0, CWL = 5).

Figure 78 : WRITE to READ (BC4 Mode Register Setting)



Notes: 1. NOP commands are shown for ease of illustration; other commands may be valid at these times.

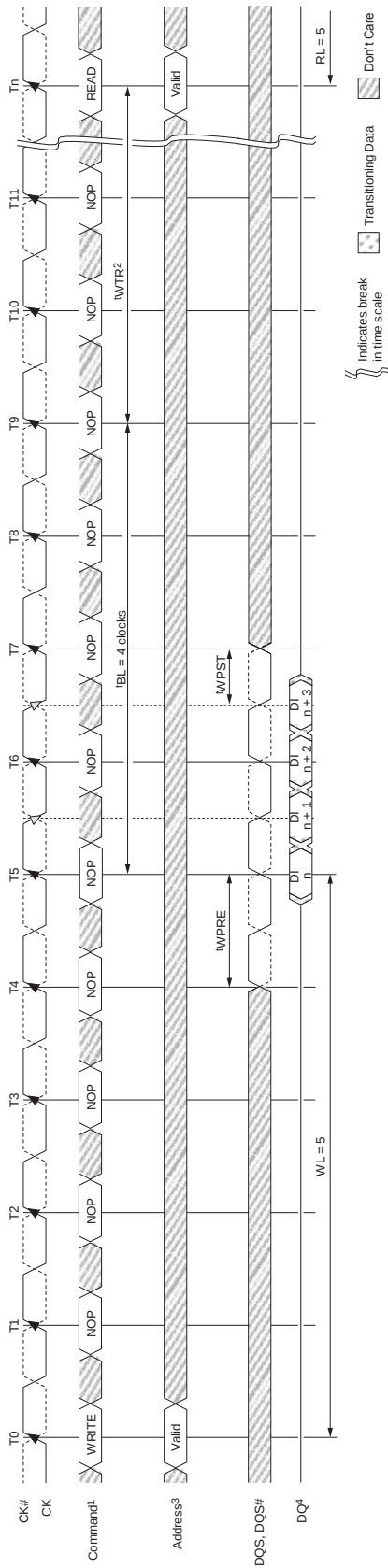
2. tWTR controls the WRITE-to-READ delay to the same device and starts with the first rising clock edge after the last write data shown at T7.

3. The fixed BC4 setting is activated by MR0[1:0] = 10 during the WRITE command at T0 and the READ command at Ta0.

4. DI n = data-in for column n.

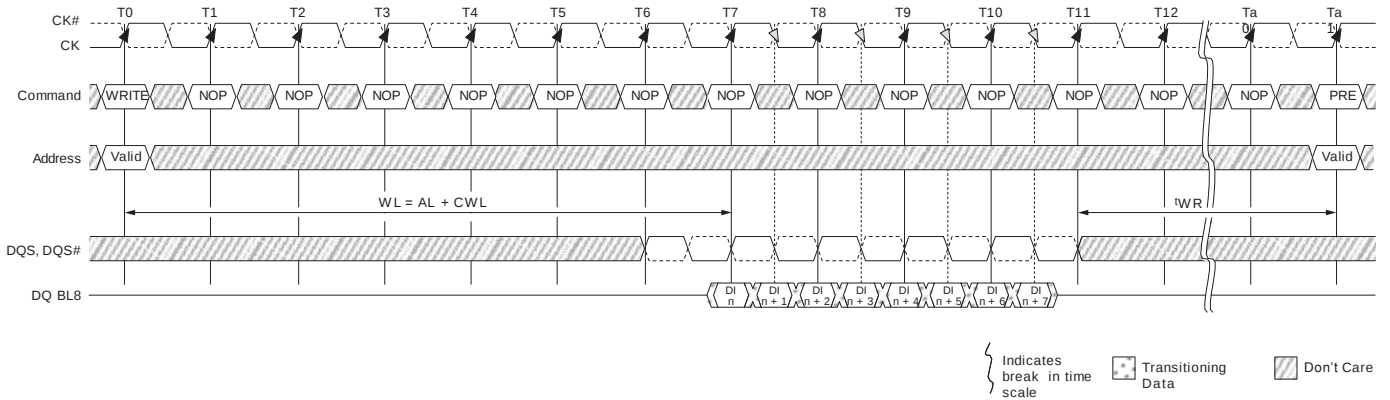
5. BC4 (fixed), WL = 5 (AL = 0, CWL = 5), RL = 5 (AL = 0, CL = 5).

Figure 79 : WRITE (BC4 OTF) to READ (BC4 OTF)



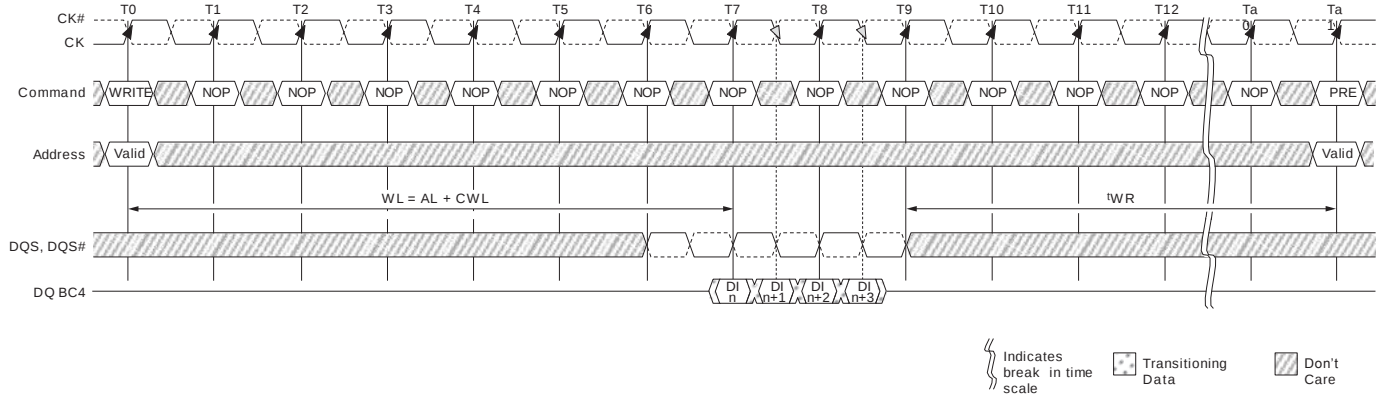
- Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. $tWTR$ controls the WRITE-to-READ delay to the same device and starts after tBL .
 3. The BC4 OTF setting is activated by $MRO[1:0] = 01$ and $A12 = 0$ during the WRITE command at T_0 and the READ command at T_n .
 4. DI_n = data-in for column n .
 5. BC4, $RL = 5$ ($AL = 0$, $CL = 5$), $WL = 5$ ($AL = 0$, $CWL = 5$).

Figure 80 : WRITE (BL8) to PRECHARGE



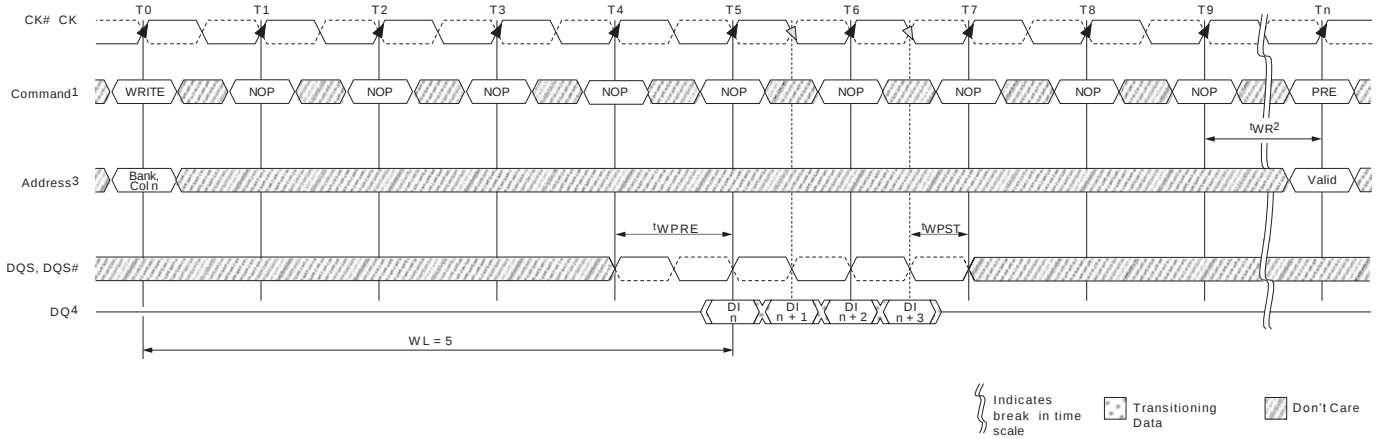
- Notes:
1. DI n = data-in from column n .
 2. Seven subsequent elements of data-in are applied in the programmed order following DO n .
 3. Shown for WL = 7 (AL = 0, CWL = 7).

Figure 81 : WRITE (BC4 Mode Register Setting) to PRECHARGE



- Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The write recovery time (t_{WR}) is referenced from the first rising clock edge after the last write data is shown at T7. t_{WR} specifies the last burst WRITE cycle until the PRECHARGE command can be issued to the same bank.
 3. The fixed BC4 setting is activated by MR0[1:0] = 10 during the WRITE command at T0.
 4. DI n = data-in for column n .
 5. BC4 (fixed), WL = 5, RL = 5.

Figure 82 : WRITE (BC4 OTF) to PRECHARGE



- Notes:
1. NOP commands are shown for ease of illustration; other commands may be valid at these times.
 2. The write recovery time (t_{WR}) is referenced from the rising clock edge at T9. t_{WR} specifies the last burst WRITE cycle until the PRECHARGE command can be issued to the same bank.
 3. The BC4 setting is activated by $MR0[1:0] = 01$ and $A12 = 0$ during the WRITE command at T0.
 4. DI_n = data-in for column n .
 5. BC4 (OTF), $WL = 5$, $RL = 5$.

DQ Input Timing

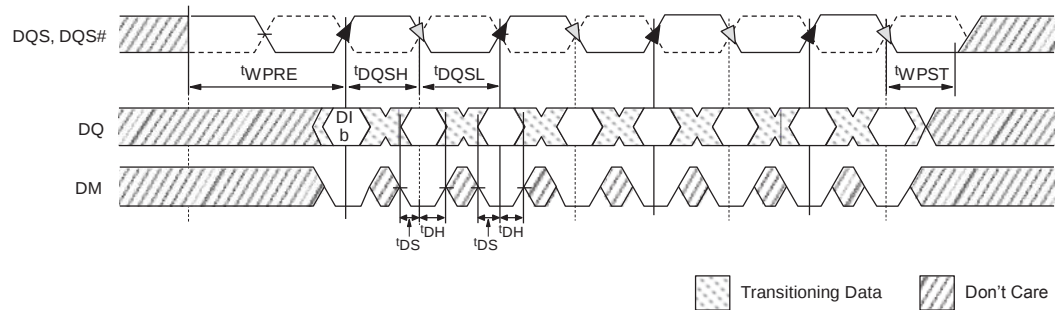
Figure 73 shows the strobe-to-clock timing during a WRITE burst. DQS, DQS# must transition within $0.25t_{CK}$ of the clock transitions, as limited by t_{DQSS} . All data and data mask setup and hold timings are measured relative to the DQS, DQS# crossing, not the clock crossing.

The WRITE preamble and postamble are also shown in Figure 73. One clock prior to data input to the DRAM, DQS must be HIGH and DQS# must be LOW. Then for a half clock, DQS is driven LOW (DQS# is driven HIGH) during the WRITE preamble, t_{WPRE} . Likewise, DQS must be kept LOW by the controller after the last data is written to the DRAM during the WRITE postamble, t_{WPST} .

Data setup and hold times are also shown in Figure 73. All setup and hold times are measured from the crossing points of DQS and DQS#. These setup and hold values pertain to data input and data mask input.

Additionally, the half period of the data input strobe is specified by t_{DQSH} and t_{DQSL} .

Figure 83 : Data Input Timing



PRECHARGE Operation

Input A10 determines whether one bank or all banks are to be precharged and, in the case where only one bank is to be precharged, inputs BA[2:0] select the bank.

When all banks are to be precharged, inputs BA[2:0] are treated as “Don’t Care.” After a bank is precharged, it is in the idle state and must be activated prior to any READ or WRITE commands being issued.

SELF REFRESH Operation

The SELF REFRESH operation is initiated like a REFRESH command except CKE is LOW. The DLL is automatically disabled upon entering SELF REFRESH and is automatically enabled and reset upon exiting SELFREFRESH.

All power supply inputs (including VREFCA and VREFDQ) must be maintained at valid levels upon entry/exit and during self refresh mode operation. VREFDQ may float or not drive VDDQ/2 while in self refresh mode under certain conditions :

- $VSS < VREFDQ < VDD$ is maintained.
- VREFDQ is valid and stable prior to CKE going back HIGH.
- The first WRITE operation may not occur earlier than 512 clocks after VREFDQ is valid.
- All other self refresh mode exit timing requirements are met.

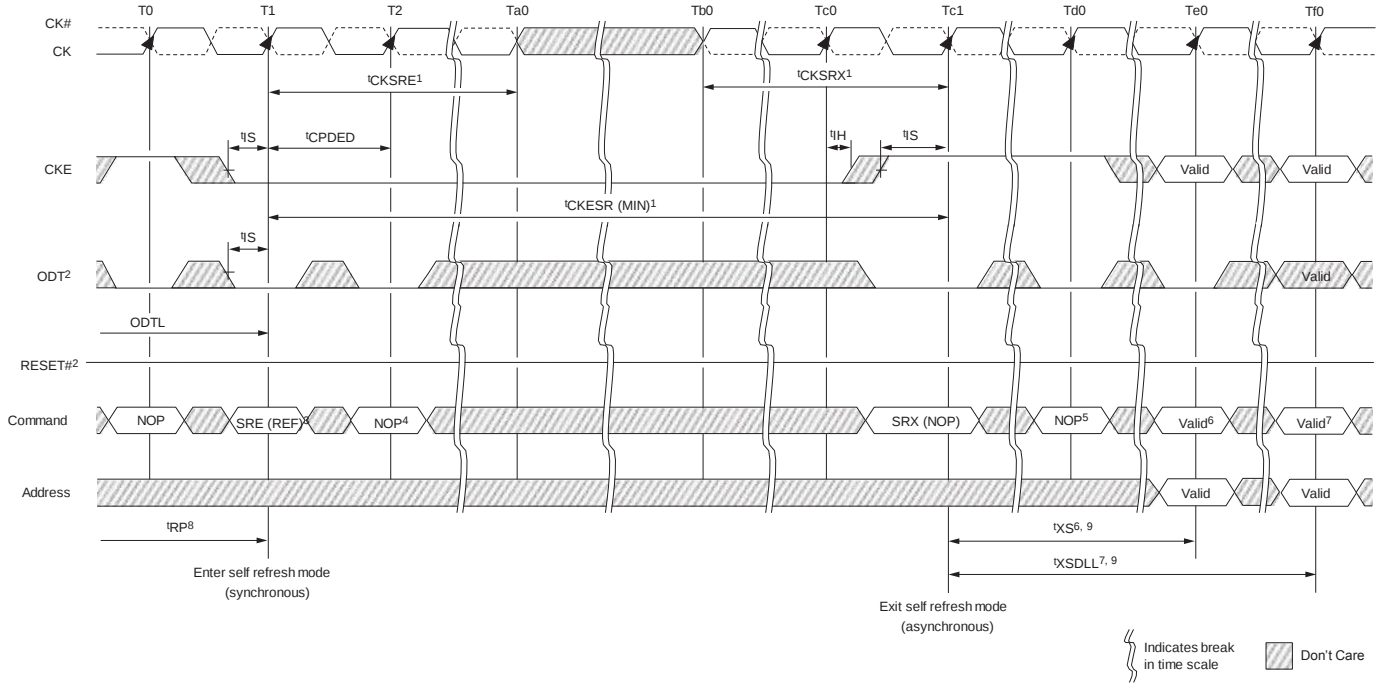
The DRAM must be idle with all banks in the precharge state (tRP is satisfied and no bursts are in progress) before a self refresh entry command can be issued. ODT must also be turned off before self refresh entry by registering the ODT ball LOW prior to the self refresh entry command (see On-Die Termination (ODT) for timing requirements). If RTT,nom and RTT(WR) are disabled in the mode registers, ODT can be a “Don’t Care.” After the self refresh entry command is registered, CKE must be held LOW to keep the DRAM in self refresh mode.

After the DRAM has entered self refresh mode, all external control signals, except CKE and RESET#, are “Don’t Care.” The DRAM initiates a minimum of one REFRESH command internally within the tCKE period when it enters self refresh mode.

The requirements for entering and exiting self refresh mode depend on the state of the clock during self refresh mode. First and foremost, the clock must be stable (meeting tCK specifications) when self refresh mode is entered. If the clock remains stable and the frequency is not altered while in self refresh mode, then the DRAM is allowed to exit self refresh mode after tCKESR is satisfied (CKE is allowed to transition HIGH tCKESR later than when CKE was registered LOW). Since the clock remains stable in self refresh mode (no frequency change), tCKSRE and tCKSRX are not required. However, if the clock is altered during self refresh mode (if it is turned-off or its frequency changes), then tCKSRE and tCKSRX must be satisfied. When entering self refresh mode, tCKSRE must be satisfied prior to altering the clock's frequency. Prior to exiting self refresh mode, tCKSRX must be satisfied prior to registering CKE HIGH.

When CKE is HIGH during self refresh exit, NOP or DES must be issued for tXS time. tXS is required for the completion of any internal refresh already in progress and must be satisfied before a valid command not requiring a locked DLL can be issued to the device. tXS is also the earliest time self refresh re-entry may occur. Before a command requiring a locked DLL can be applied, a ZQCL command must be issued, tZQOPER timing must be met, and tXSDLL must be satisfied. ODT must be off during tXSDLL.

Figure 84 : Self Refresh Entry/Exit Timing



- Notes:
1. The clock must be valid and stable, meeting tCK specifications at least tCKSRE after entering self refresh mode, and at least tCKSRX prior to exiting self refresh mode, if the clock is stopped or altered between states Ta0 and Tb0. If the clock remains valid and unchanged from entry and during self refresh mode, then tCKSRE and tCKSRX do not apply; however, tCKESR must be satisfied prior to exiting at SRX.
 2. ODT must be disabled and RTT off prior to entering self refresh at state T1. If both RTT,nom and RTT(WR) are disabled in the mode registers, ODT can be a "Don't Care."
 3. Self refresh entry (SRE) is synchronous via a REFRESH command with CKE LOW.
 4. A NOP or DES command is required at T2 after the SRE command is issued prior to the inputs becoming "Don't Care."
 5. NOP or DES commands are required prior to exiting self refresh mode until state Te0.
 6. tXS is required before any commands not requiring a locked DLL.
 7. tXSDLL is required before any commands requiring a locked DLL.
 8. The device must be in the all banks idle state prior to entering self refresh mode. For example, all banks must be precharged, tRP must be met, and no data bursts can be in progress.
 9. Self refresh exit is asynchronous; however, tXS and tXSDLL timings start at the first rising clock edge where CKE HIGH satisfies tISXR at Tc1. tCKSRX timing is also measured so that tISXR is satisfied at Tc1.

Extended Temperature Usage

Dosilicon's DDR3L SDRAM support the optional extended case temperature (TC) range of 0°C to 95°C. Thus, the SRT and ASR options must be used at a minimum.

The extended temperature range DRAM must be refreshed externally at 2x (double refresh) anytime the case temperature is above 85°C (and does not exceed 95°C). The external refresh requirement is accomplished by reducing the refresh period from 64ms to 32ms. However, self refresh mode requires either ASR or SRT to support the extended temperature. Thus, either ASR or SRT must be enabled when TC is above 85°C or self refresh cannot be used until TC is at or below 85°C. Table 71 summarizes the two extended temperature options and Table 72 summarizes how the two extended temperature options relate to one another.

Table 71 : Self Refresh Temperature and Auto Self Refresh Description

Field	MR2 Bits	Description
Self Refresh Temperature (SRT)		
SRT	7	If ASR is disabled (MR2[6] = 0), SRT must be programmed to indicate T _{OPER} during self refresh: *MR2[7] = 0: Normal operating temperature range (0°C to 85°C) *MR2[7] = 1: Extended operating temperature range (0°C to 95°C) If ASR is enabled (MR2[7] = 1), SRT must be set to 0, even if the extended temperature range is supported *MR2[7] = 0: SRT is disabled
Auto Self Refresh (ASR)		
ASR	6	When ASR is enabled, the DRAM automatically provides SELF REFRESH power management functions, (refresh rate for all supported operating temperature values) * MR2[6] = 1: ASR is enabled (M7 must = 0) When ASR is not enabled, the SRT bit must be programmed to indicate T _{OPER} during SELF REFRESH operation * MR2[6] = 0: ASR is disabled; must use manual self refresh temperature (SRT)

Table 72 : Self Refresh Mode Summary

MR2[6] (ASR)	MR2[7] (SRT)	SELF REFRESH Operation	Permitted Operating Temperature Range for Self Refresh Mode
0	0	Self refresh mode is supported in the normal temperature range	Normal (0°C to 85°C)
0	1	Self refresh mode is supported in normal and extended temperature ranges; When SRT is enabled, it increases self refresh power consumption	Normal and extended (0°C to 95°C)
1	0	Self refresh mode is supported in normal and extended temperature ranges; Self refresh power consumption may be temperature-dependent	Normal and extended (0°C to 95°C)
1	1	Illegal	

Power-Down Mode

Power-down is synchronously entered when CKE is registered LOW coincident with a NOP or DES command. CKE is not allowed to go LOW while an MRS, MPR, ZQCAL, READ, or WRITE operation is in progress. CKE is allowed to go LOW while any of the other legal operations (such as ROW ACTIVATION, PRECHARGE, auto precharge, or REFRESH) are in progress. However, the power-down IDD specifications are not applicable until such operations have completed. Depending on the previous DRAM state and the command issued prior to CKE going LOW, certain timing constraints must be satisfied (as noted in Table 73). Timing diagrams detailing the different power-down mode entry and exits are shown in Figure 85 through Figure 94.

Table 73 : Command to Power-Down Entry Parameters

DRAM Status	Last Command Prior to CKE LOW ¹	Parameter (Min)	Parameter Value	Figure
Idle or active	ACTIVATE	tACTPDEN	1tCK	92
Idle or active	PRECHARGE	tPRPDEN	1tCK	93
Active	READ or READAP	tRDPDEN	RL + 4tCK + 1tCK	88
Active	WRITE: BL8OTF, BL8MRS, BC4OTF	tWRPDEN	WL + 4tCK + tWR/tCK	89
Active	WRITE: BC4MRS		WL + 2tCK + tWR/tCK	89
Active	WRITEAP: BL8OTF, BL8MRS, BC4OTF	tWRAPDEN	WL + 4tCK + WR + 1tCK	90
Active	WRITEAP: BC4MRS		WL + 2tCK + WR + 1tCK	90
Idle	REFRESH	tREFPDEN	1tCK	91
Power-down	REFRESH	tXPDLL	Greater of 10tCK or 24ns	95
Idle	MODE REGISTER SET	tMRSPDEN	tMOD	94

Note : 1. If slow-exit mode precharge power-down is enabled and entered, ODT becomes asynchronous tANPD prior to CKE going LOW and remains asynchronous until tANPD + tXPDLL after CKE goes HIGH.

Entering power-down disables the input and output buffers, excluding CK, CK#, ODT, CKE, and RESET#. NOP or DES commands are required until tCPDED has been satisfied, at which time all specified input/output buffers are disabled. The DLL should be in a locked state when power-down is entered for the fastest power-down exit timing. If the DLL is not locked during power-down entry, the DLL must be reset after exiting power-down mode for proper READ operation as well as synchronous ODT operation.

During power-down entry, if any bank remains open after all in-progress commands are complete, the DRAM will be in active power-down mode. If all banks are closed after all in-progress commands are complete, the DRAM will be in precharge power-down mode. Precharge power-down mode must be programmed to exit with either a slow exit mode or a fast exit mode. When entering precharge power-down mode, the DLL is turned off in slow exit mode or kept on in fast exit mode.

The DLL also remains on when entering active power-down. ODT has special timing constraints when slow exit mode precharge power-down is enabled and entered. Refer to Asynchronous ODT Mode for detailed ODT usage requirements in slow exit mode precharge power-down. A summary of the two power-down modes is listed in Table 74.

While in either power-down state, CKE is held LOW, RESET# is held HIGH, and a stable clock signal must be maintained. ODT must be in a valid state but all other input signals are “Don’t Care.” If RESET# goes LOW during power-down, the DRAM will switch out of power-down mode and go into the reset state. After CKE is registered LOW, CKE must remain LOW until tPD (MIN) has been satisfied. The maximum time allowed for powerdown duration is tPD (MAX) ($9 \times tREFI$).

The power-down states are synchronously exited when CKE is registered HIGH (with a required NOP or DES command). CKE must be maintained HIGH until tCKE has been satisfied. A valid, executable command may be applied after power-down exit latency, tXP, and tXPDLL have been satisfied. A summary of the power-down modes is listed below.

For specific CKE-intensive operations, such as repeating a power-down-exit-to-refresh-to-power-down-entry sequence, the number of clock cycles between power-down exit and power-down entry may not be sufficient to keep the DLL properly updated. In addition to meeting tPD when the REFRESH command is used between power-down exit and power-down entry, two other conditions must be met. First, tXP must be satisfied before issuing the REFRESH command. Second, tXPDLL must be satisfied before the next power-down may be entered. An example is shown in Figure 95.

Table 74 : Power-Down Modes

DRAM State	MR0[12]	DLL State	Power-Down Exit	Relevant Parameters
Active (any bank open)	“Don’t Care”	On	Fast	^t XP to any other valid command
Precharged (all banks precharged)	1	On	Fast	^t XP to any other valid command
	0	Off	Slow	^t XPDLL to commands that require the DLL to be locked (READ, RDAP, or ODT on); ^t XP to any other valid command

Figure 85 : Active Power-Down Entry and Exit

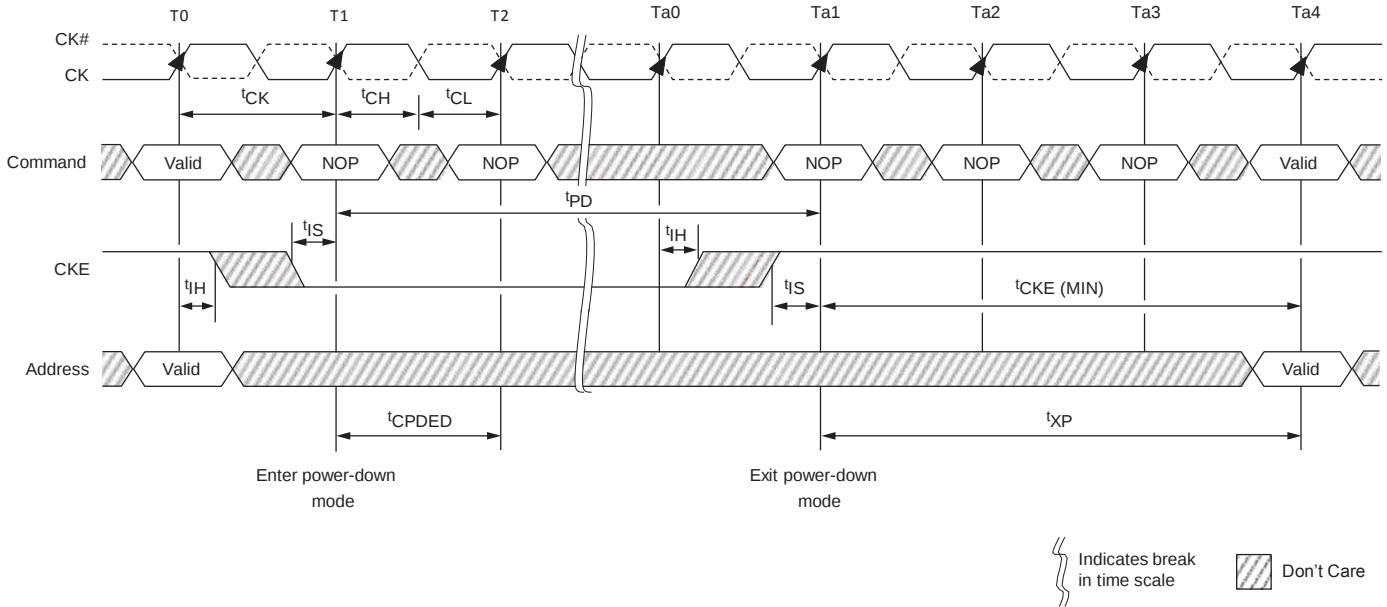


Figure 86 : Precharge Power-Down (Fast-Exit Mode) Entry and Exit

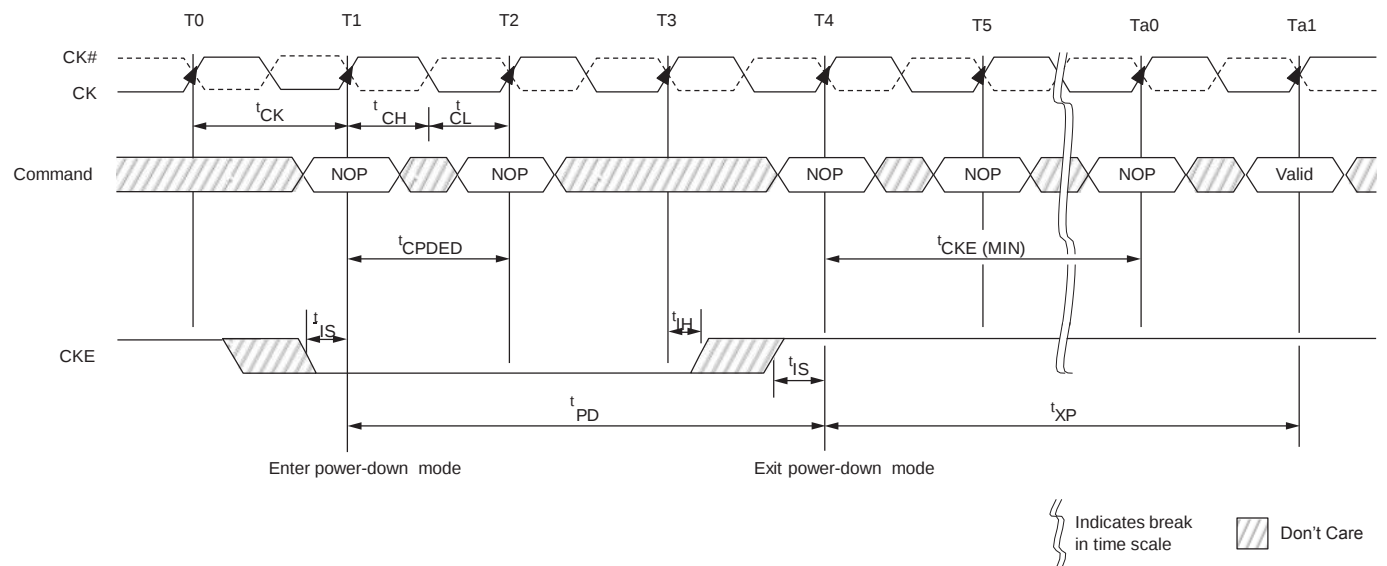
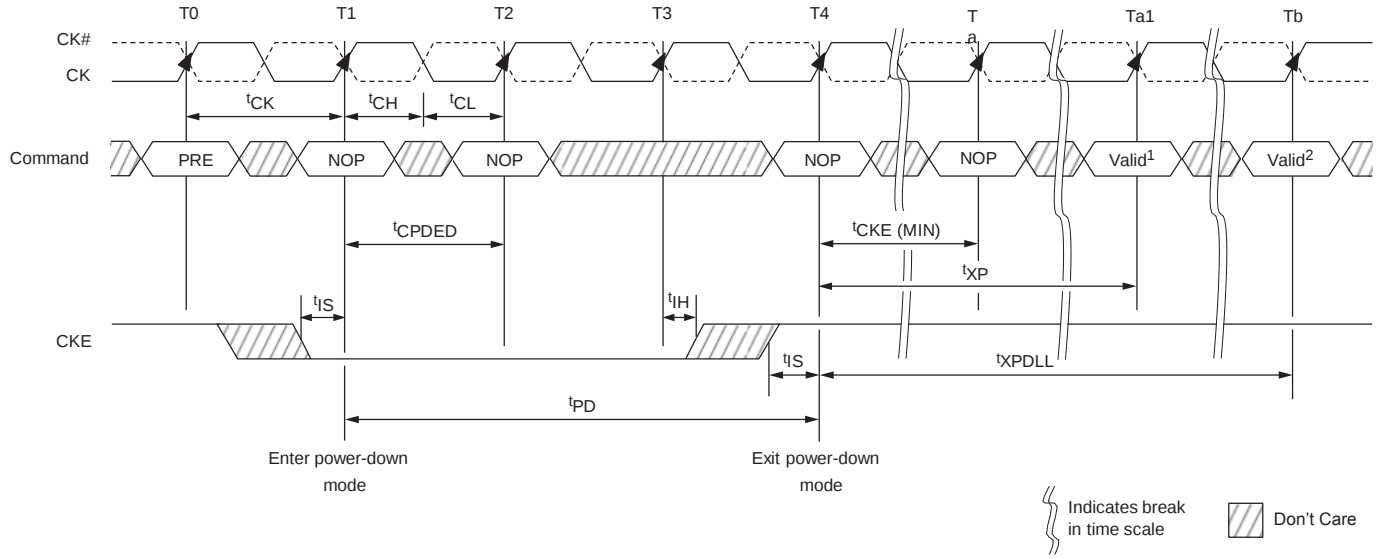


Figure 87 : Precharge Power-Down (Slow-Exit Mode) Entry and Exit



Notes: 1. Any valid command not requiring a locked DLL.
2. Any valid command requiring a locked DLL.

Figure 88 : Power-Down Entry After READ or READ with Auto Precharge (RDAP)

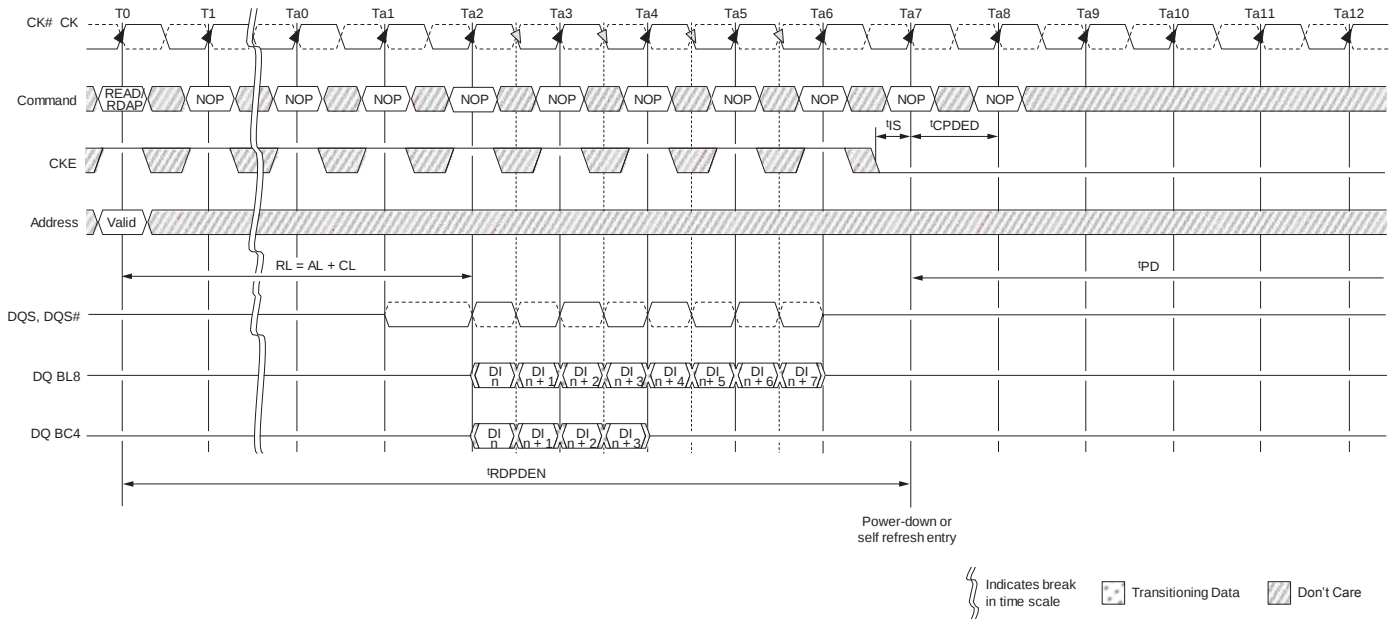
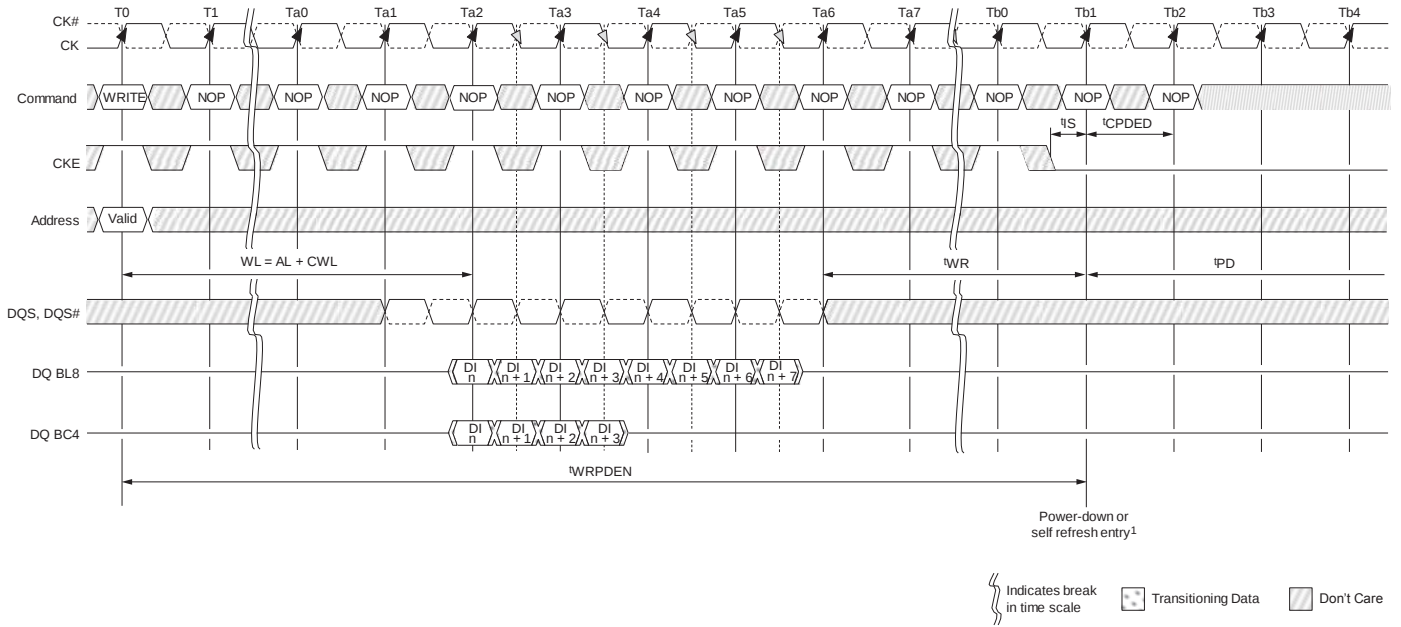
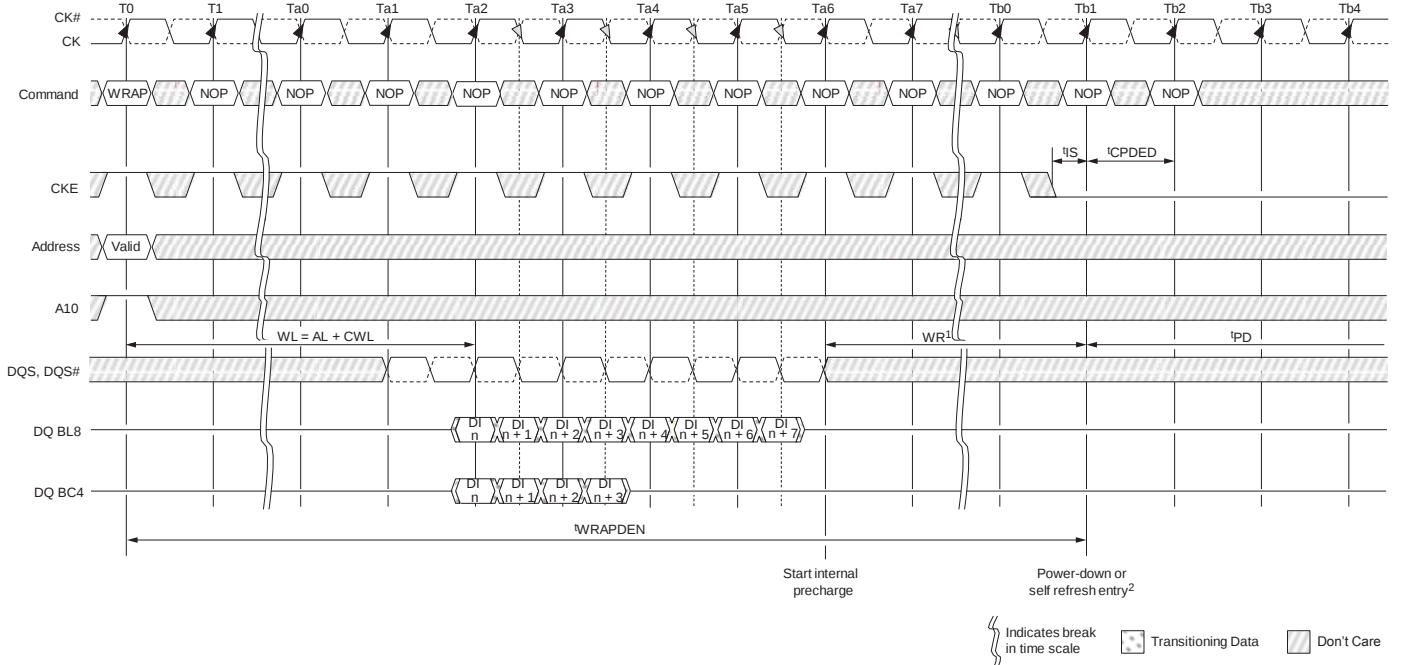


Figure 89 : Power-Down Entry After WRITE



Note: 1. CKE can go LOW 2tCK earlier if BC4MRS.

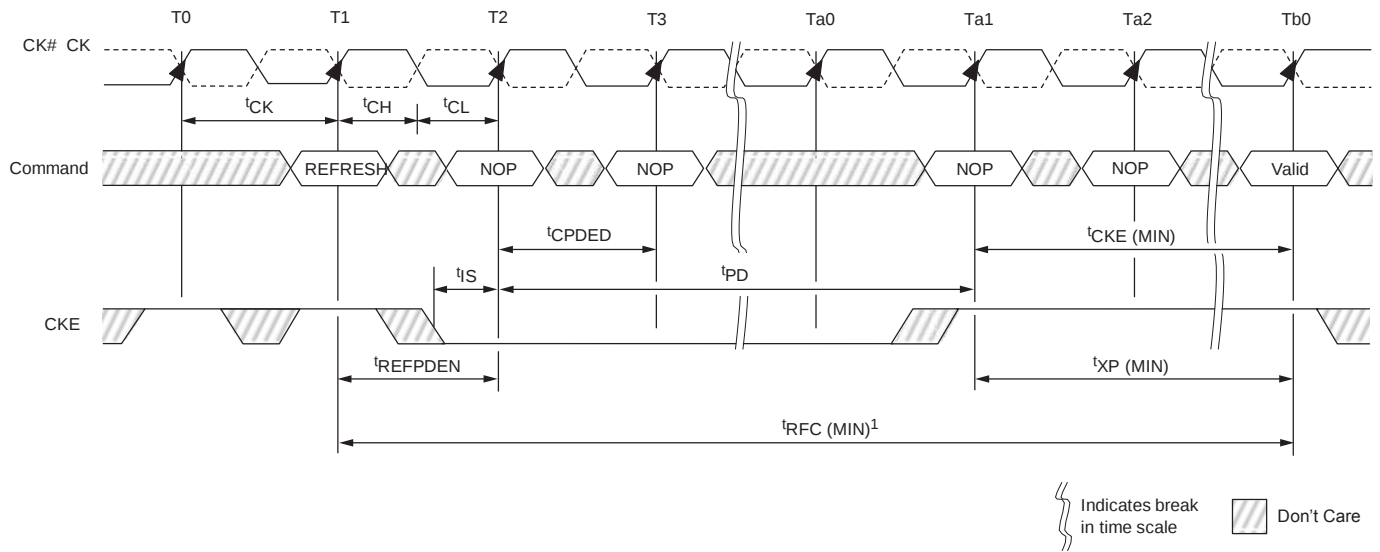
Figure 90 : Power-Down Entry After WRITE with Auto Precharge (WRAP)



Notes: 1. tWR is programmed through MR0[11:9] and represents tWRmin (ns)/tCK rounded up to the next integer tCK.

2. CKE can go LOW 2tCK earlier if BC4MRS.

Figure 91 : REFRESH to Power-Down Entry



Note: 1. After CKE goes HIGH during t_{RFC} , CKE must remain HIGH until t_{RFC} is satisfied.

Figure 92 : ACTIVATE to Power-Down Entry

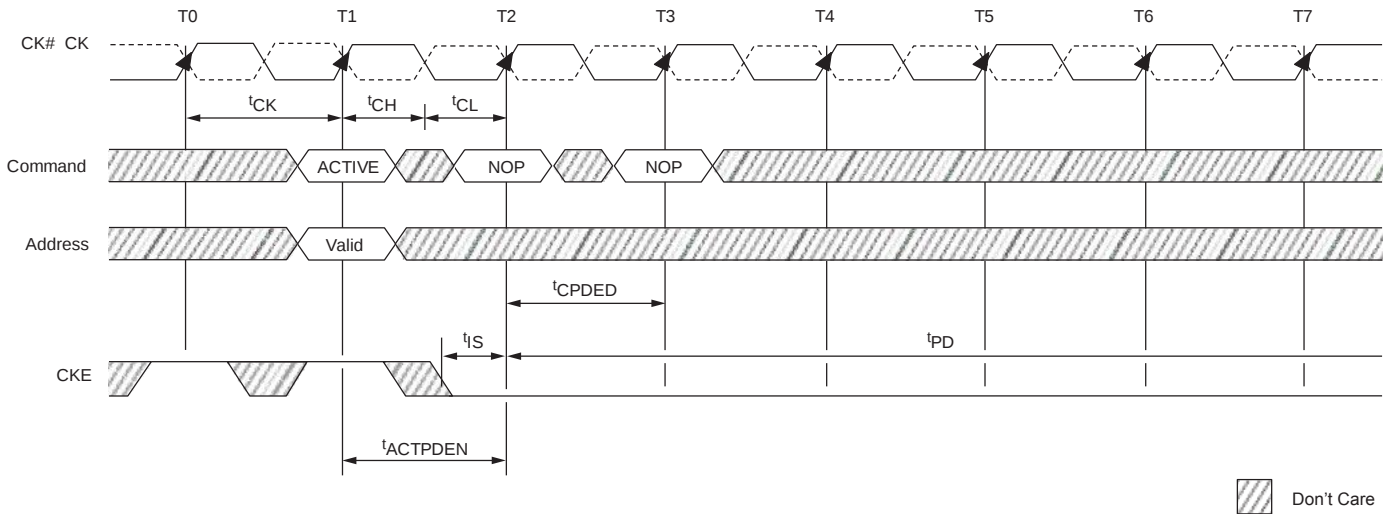


Figure 93 : PRECHARGE to Power-Down Entry

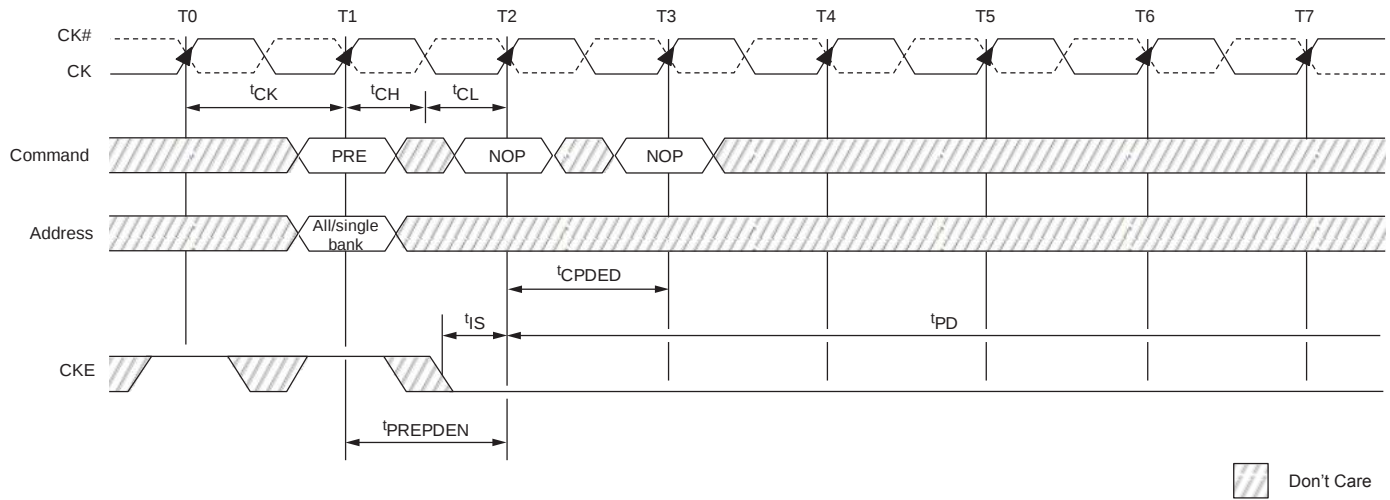


Figure 94 : MRS Command to Power-Down Entry

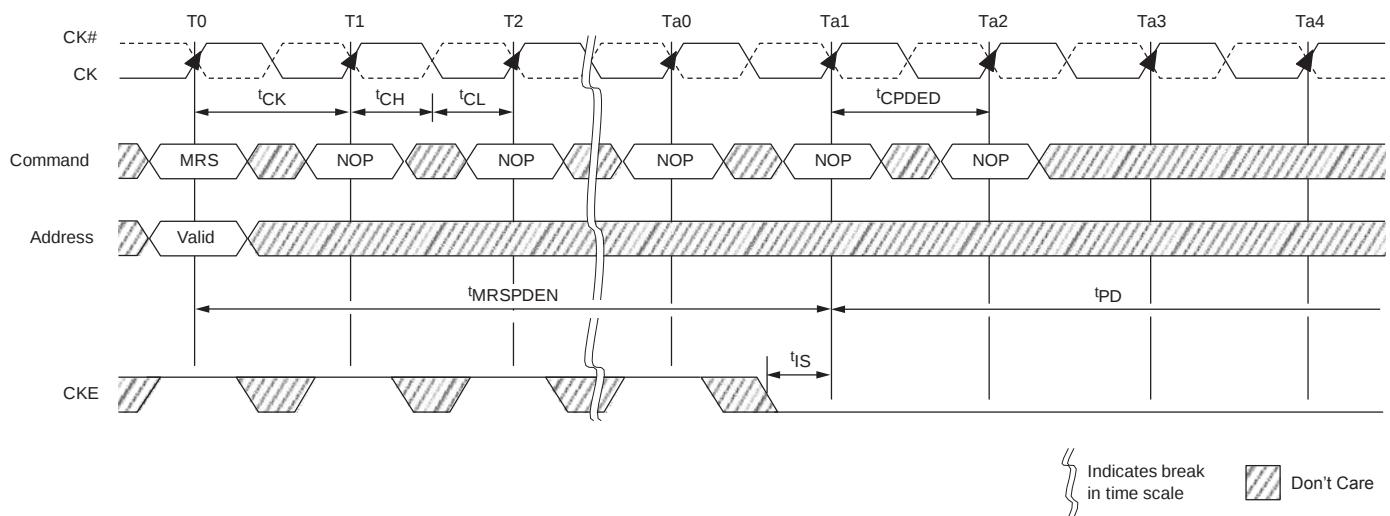
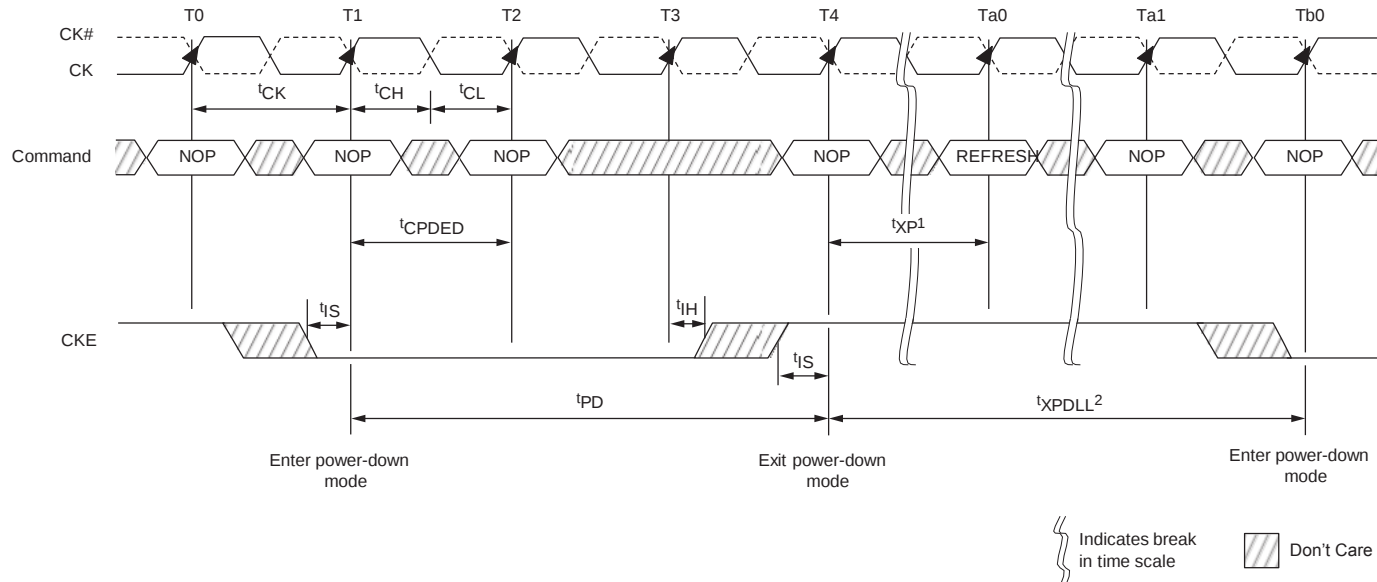


Figure 95 : Power-Down Exit to Refresh to Power-Down Entry



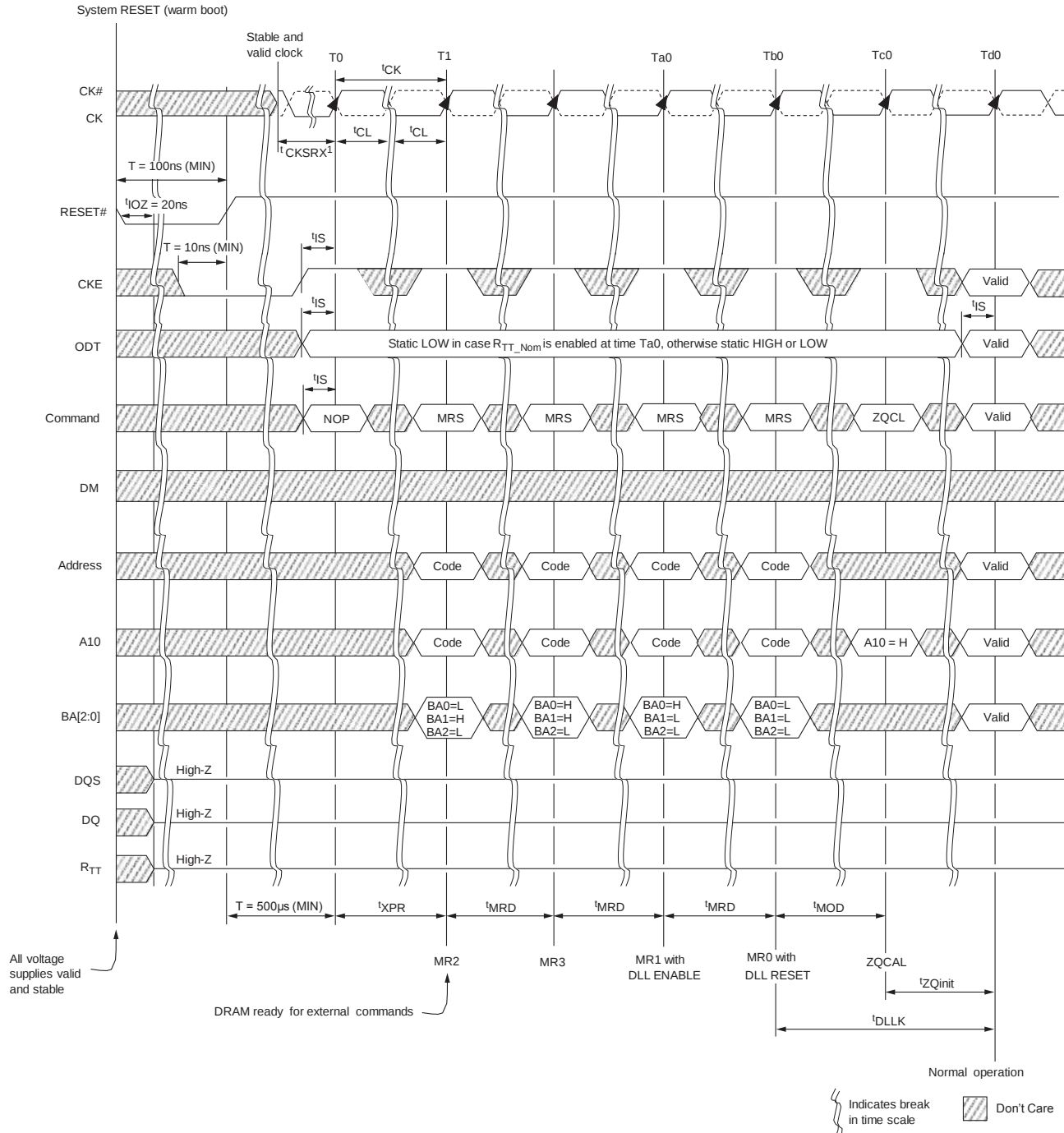
Notes: 1. t_{XP} must be satisfied before issuing the command.

2. t_{XPDLL2} must be satisfied (referenced to the registration of power-down exit) before the next power-down can be entered.

RESET Operation

The RESET signal (RESET#) is an asynchronous reset signal that triggers any time it drops LOW, and there are no restrictions about when it can go LOW. After RESET# goes LOW, it must remain LOW for 100ns. During this time, the outputs are disabled, ODT (RTT) turns off (High-Z), and the DRAM resets itself. CKE should be driven LOW prior to RESET# being driven HIGH. After RESET# goes HIGH, the DRAM must be re-initialized as though a normal power-up was executed. All refresh counters on the DRAM are reset, and data stored in the DRAM is assumed unknown after RESET# has gone LOW.

Figure 96 : RESET Sequence



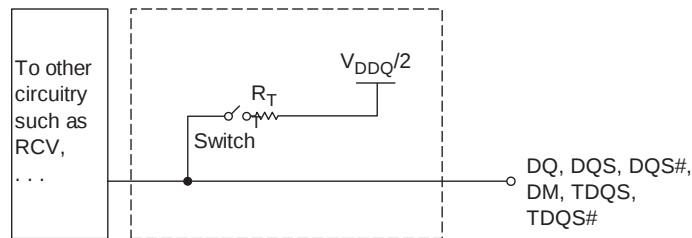
Note: 1. The minimum time required is the longer of 10ns or 5 clocks.

On-Die Termination (ODT)

On-die termination (ODT) is a feature that enables the DRAM to enable/disable and turn on/off termination resistance for each DQ, DQS, DQS#, and DM for the x4 and x8 configurations (and TDQS, TDQS# for the x8 configuration, when enabled). ODT is applied to each DQ, UDQS, UDQS#, LDQS, LDQS#, UDM, and LDM signal for the x16 configuration.

ODT is designed to improve signal integrity of the memory channel by enabling the DRAM controller to independently turn on/off the DRAM's internal termination resistance for any grouping of DRAM devices. ODT is not supported during DLL disable mode (simple functional representation shown below). The switch is enabled by the internal ODT control logic, which uses the external ODT ball and other control information.

Figure 97 : On-Die Termination



Functional Representation of ODT

The value of R_{TT} (ODT termination resistance value) is determined by the settings of several mode register bits (see Table 80). The ODT ball is ignored while in self refresh mode (must be turned off prior to self refresh entry) or if mode registers MR1 and MR2 are programmed to disable ODT. ODT is comprised of nominal ODT and dynamic ODT modes and either of these can function in synchronous or asynchronous mode (when the DLL is off during precharge power-down or when the DLL is synchronizing). Nominal ODT is the base termination and is used in any allowable ODT state. Dynamic ODT is applied only during writes and provides OTF switching from no R_{TT} or $R_{TT,nom}$ to $R_{TT}(WR)$.

The actual effective termination, $R_{TT}(EFF)$, may be different from R_{TT} targeted due to nonlinearity of the termination. For $R_{TT}(EFF)$ values and calculations, see ODT Characteristics.

Nominal ODT

ODT (NOM) is the base termination resistance for each applicable ball; it is enabled or disabled via MR1[9, 6, 2] (see Mode Register 1 (MR1) Definition), and it is turned on or off via the ODT ball.

Table 75 : Truth Table – ODT (Nominal)

Note 1 applies to the entire table

MR1[9, 6, 2]	ODT Pin	DRAM Termination State	DRAM State	Notes
000	0	$R_{TT,nom}$ disabled, ODT off	Any valid	2
000	1	$R_{TT,nom}$ disabled, ODT on	Any valid except self refresh, read	3
000–101	0	$R_{TT,nom}$ enabled, ODT off	Any valid	2
000–101	1	$R_{TT,nom}$ enabled, ODT on	Any valid except self refresh, read	3
110 and 111	X	$R_{TT,nom}$ reserved, ODT on or off	Illegal	

Notes: 1. Assumes dynamic ODT is disabled (see Dynamic ODT) when enabled).

2. ODT is enabled and active during most writes for proper termination, but it is not illegal for it to be off during writes.
3. ODT must be disabled during reads. The $R_{TT,nom}$ value is restricted during writes. Dynamic ODT is applicable if enabled.

Nominal ODT resistance $R_{TT,nom}$ is defined by MR1[9, 6, 2], as shown in Mode Register 1 (MR1) Definition. The $R_{TT,nom}$ termination value applies to the output pins previously mentioned. DDR3L SDRAM supports multiple $R_{TT,nom}$ values based on RZQ/n where n can be 2, 4, 6, 8, or 12 and RZQ is 240Ω. $R_{TT,nom}$ termination is allowed any time after the DRAM is initialized, calibrated, and not performing read access, or when it is not in self refresh mode.

Write accesses use $R_{TT,nom}$ if dynamic ODT ($R_{TT}(WR)$) is disabled. If $R_{TT,nom}$ is used during writes, only $RZQ/2$, $RZQ/4$, and $RZQ/6$ are allowed(see Table 79). ODT timings are summarized in Table 76, as well as listed in the Electrical Characteristics and AC Operating Conditions table..

Examples of nominal ODT timing are shown in conjunction with the synchronous mode of operation in Synchronous ODT Mode.

Table 76 : ODT Parameters

Symbol	Description	Begins at	Defined to	Definition for All DDR3L Speed Bins	Unit
ODTLon	ODT synchronous turn-on delay	ODT registered HIGH	$R_{TT(ON)} \pm t_{AON}$	CWL + AL - 2	t'CK
ODTLoff	ODT synchronous turn-off delay	ODT registered HIGH	$R_{TT(OFF)} \pm t_{AOF}$	CWL + AL - 2	t'CK
t'AONPD	ODT asynchronous turn-on delay	ODT registered HIGH	$R_{TT(ON)}$	2–8.5	ns
t'AOFPD	ODT asynchronous turn-off delay	ODT registered HIGH	$R_{TT(OFF)}$	2–8.5	ns
ODTH4	ODT minimum HIGH time after ODT assertion or write (BC4)	ODT registered HIGH or write registration with ODT HIGH	ODT registered LOW	4t'CK	t'CK
ODTH8	ODT minimum HIGH time after write (BL8)	Write registration with ODT HIGH	ODT registered LOW	6t'CK	t'CK
t'AON	ODT turn-on relative to ODTLon completion	Completion of ODTLon	$R_{TT(ON)}$	See Electrical Characteristics and AC Operating Conditions table	ps
t'AOF	ODT turn-off relative to ODTLoff completion	Completion of ODTLoff	$R_{TT(OFF)}$	$0.5t'CK \pm 0.2t'CK$	t'CK

Dynamic ODT

In certain application cases, and to further enhance signal integrity on the data bus, it is desirable that the termination strength of the DDR3L SDRAM can be changed without issuing an MRS command, essentially changing the ODT termination on the fly. With dynamic ODT RTT(WR)) enabled, the DRAM switches from nominal ODT RTT,nom) to dynamic ODT RTT(WR)) when beginning a WRITE burst and subsequently switches back to nominal ODT RTT,nom) at the completion of the WRITE burst. This requirement is supported by the dynamic ODT feature, as described below.

Dynamic ODT Special Use Case

When DDR3L devices are architect as a single rank memory array, dynamic ODT offers a special use case: the ODT ball can be wired high (via a current limiting resistor preferred) by having RTT,nom disabled via MR1 and RTT(WR) enabled via MR2. This will allow the ODT signal not to have to be routed yet the DRAM can provide ODT coverage during write accesses.

When enabling this special use case, some standard ODT spec conditions may be violated : ODT is sometimes suppose to be held low. Such ODT spec violation (ODT not LOW) is allowed under this special use case. Most notably, if Write Leveling is used, this would appear to be a problem since RTT(WR) can not be used (should be disabled) and RTT(NOM) should be used. For Write leveling during this special use case, with the DLL locked, then RTT(NOM) maybe enabled when entering Write Leveling mode and disabled when exiting Write Leveling mode. More so, RTT(NOM) must be enabled when enabling Write Leveling, via same MR1 load, and disabled when disabling Write Leveling, via same MR1 load if RTT(NOM) is to be used.

ODT will turn-on within a delay of $ODTLon + tAON + tMOD + 1CK$ (enabling via MR1) or turn-off within a delay of $ODTLoFF + tAOFF + tMOD + 1CK$. As seen in the table below, between the Load Mode of MR1 and the previously specified delay, the value of ODT is uncertain. this means the DQ ODT termination could turn-on and then turn-off again during the period of stated uncertainty.

Table 77 : Write Leveling with Dynamic ODT Special Case

Begin $R_{TT,nom}$ Uncertainty	End $R_{TT,nom}$ Uncertainty	I/Os	$R_{TT,nom}$ Final State
MR1 load mode command: Enable Write Leveling and $R_{TT(NOM)}$	$ODTLon + tAON + tMOD + 1CK$	DQS, DQS#	Drive $R_{TT,nom}$ value
		DQs	No $R_{TT,nom}$
MR1 load mode command: Disable Write Leveling and $R_{TT(NOM)}$	$ODTLoFF + tAOFF + tMOD + 1CK$	DQS, DQS#	No $R_{TT,nom}$
		DQs	No $R_{TT,nom}$

Functional Description

The dynamic ODT mode is enabled if either MR2[9] or MR2[10] is set to 1. Dynamic ODT is not supported during DLL disable mode so RTT(WR) must be disabled. The dynamic ODT function is described below:

- Two RTT values are available—RTT,nom and RTT(WR).
 - The value for RTT,nom is preselected via MR1[9, 6, 2].
 - The value for RTT(WR) is preselected via MR2[10, 9].
- During DRAM operation without READ or WRITE commands, the termination is controlled.
 - Nominal termination strength RTT,nom is used.
 - Termination on/off timing is controlled via the ODT ball and latencies ODTLon and ODTLoFF.
- When a WRITE command (WR, WRAP, WRS4, WRS8, WRAPS4, WRAPS8) is registered, and if dynamic ODT is enabled, the ODT termination is controlled.
 - A latency of ODTLcnw after the WRITE command: termination strength RTT,nom switches to RTT(WR)
 - A latency of ODTLcwn8 (for BL8, fixed or OTF) or ODTLcwn4 (for BC4, fixed or OTF) after the WRITE command : termination strength RTT(WR) switches back to RTT,nom.

- On/off termination timing is controlled via the ODT ball and determined by ODTLon, ODTLoff, ODTL4, and ODTL8.
- During the tADC transition window, the value of RTT is undefined.

ODT is constrained during writes and when dynamic ODT is enabled (see the table below, Dynamic ODT Specific Parameters). ODT timings listed in the ODT Parameters table in On-Die Termination (ODT) also apply to dynamic ODT mode.

Table 78 : Dynamic ODT Specific Parameters

Symbol	Description	Begins at	Defined to	Definition for All DDR3L Speed Bins	Unit
ODTLcnw	Change from $R_{TT,nom}$ to $R_{TT(WR)}$	Write registration	R_{TT} switched from $R_{TT,nom}$ to $R_{TT(WR)}$	WL - 2	tCK
ODTLcwn4	Change from $R_{TT(WR)}$ to $R_{TT,nom}$ (BC4)	Write registration	R_{TT} switched from $R_{TT(WR)}$ to $R_{TT,nom}$	4tCK + ODTL off	tCK
ODTLcwn8	Change from $R_{TT(WR)}$ to $R_{TT,nom}$ (BL8)	Write registration	R_{TT} switched from $R_{TT(WR)}$ to $R_{TT,nom}$	6tCK + ODTL off	tCK
tADC	R_{TT} change skew	ODTLcnw completed	R_{TT} transition complete	$0.5tCK \pm 0.2tCK$	tCK

Table 79 : Mode Registers for $R_{TT,nom}$

MR1 ($R_{TT,nom}$)			$R_{TT,nom}$ (RZQ)	$R_{TT,nom}$ (Ohm)	$R_{TT,nom}$ Mode Restriction
M9	M6	M2			
0	0	0	Off	Off	n/a
0	0	1	RZQ/4	60	Self refresh
0	1	0	RZQ/2	120	
0	1	1	RZQ/6	40	
1	0	0	RZQ/12	20	Self refresh, write
1	0	1	RZQ/8	30	
1	1	0	Reserved	Reserved	n/a
1	1	1	Reserved	Reserved	n/a

Note: 1. RZQ = 240Ω. If $R_{TT,nom}$ is used during WRITES, only RZQ/2, RZQ/4, RZQ/6 are allowed.

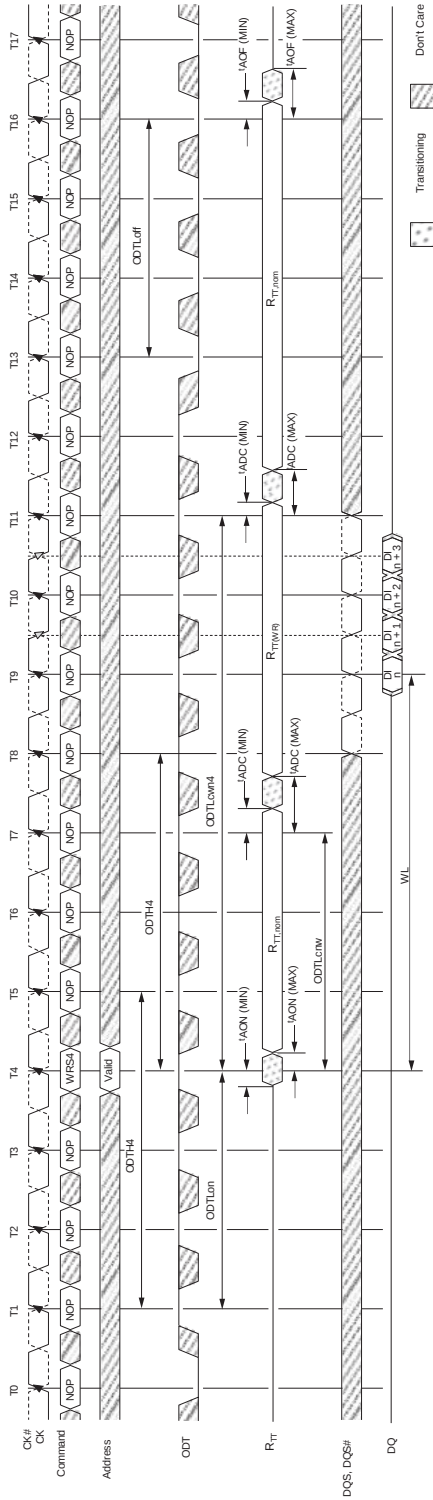
Table 80 : Mode Registers for RTT(WR)

MR2 (R _{TT(WR)})		R _{TT(WR)} (RZQ)	R _{TT(WR)} (Ohm)
M10	M9		
0	0	Dynamic ODT off: WRITE does not affect R _{TT,nom}	
0	1	RZQ/4	60
1	0	RZQ/2	120
1	1	Reserved	Reserved

Table 81 : Timing Diagrams for Dynamic ODT

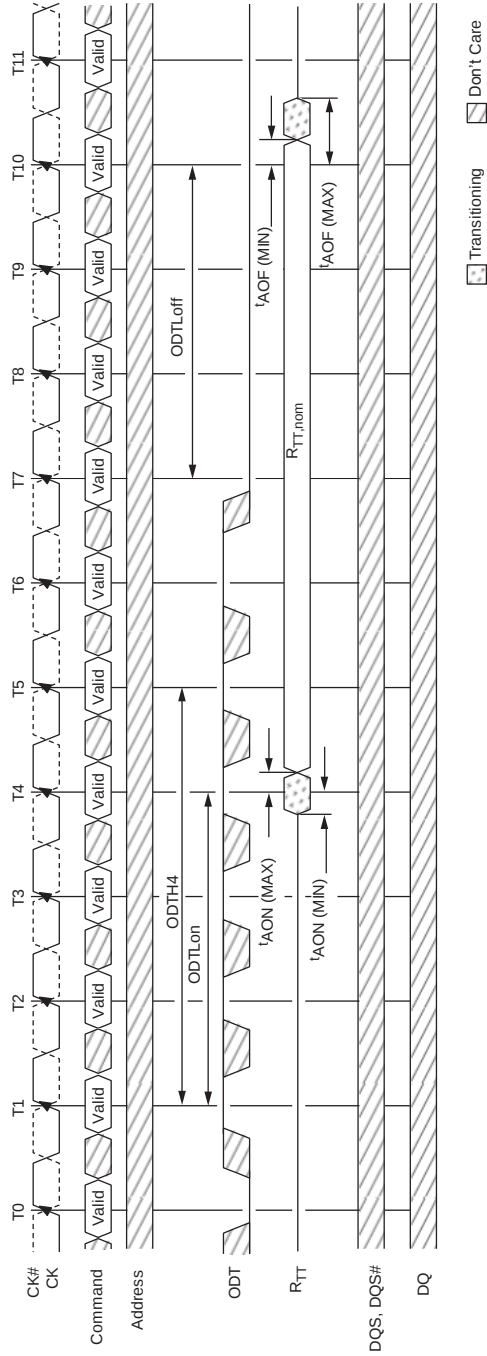
Figure and Page	Title
Figure 98	Dynamic ODT: ODT Asserted Before and After the WRITE, BC4
Figure 99	Dynamic ODT: Without WRITE Command
Figure 100	Dynamic ODT: ODT Pin Asserted Together with WRITE Command for 6 Clock Cycles, BL8
Figure 101	Dynamic ODT: ODT Pin Asserted with WRITE Command for 6 Clock Cycles, BC4
Figure 102	Dynamic ODT: ODT Pin Asserted with WRITE Command for 4 Clock Cycles, BC4

Figure 98 : Dynamic ODT: ODT Asserted Before and After the WRITE, BC4



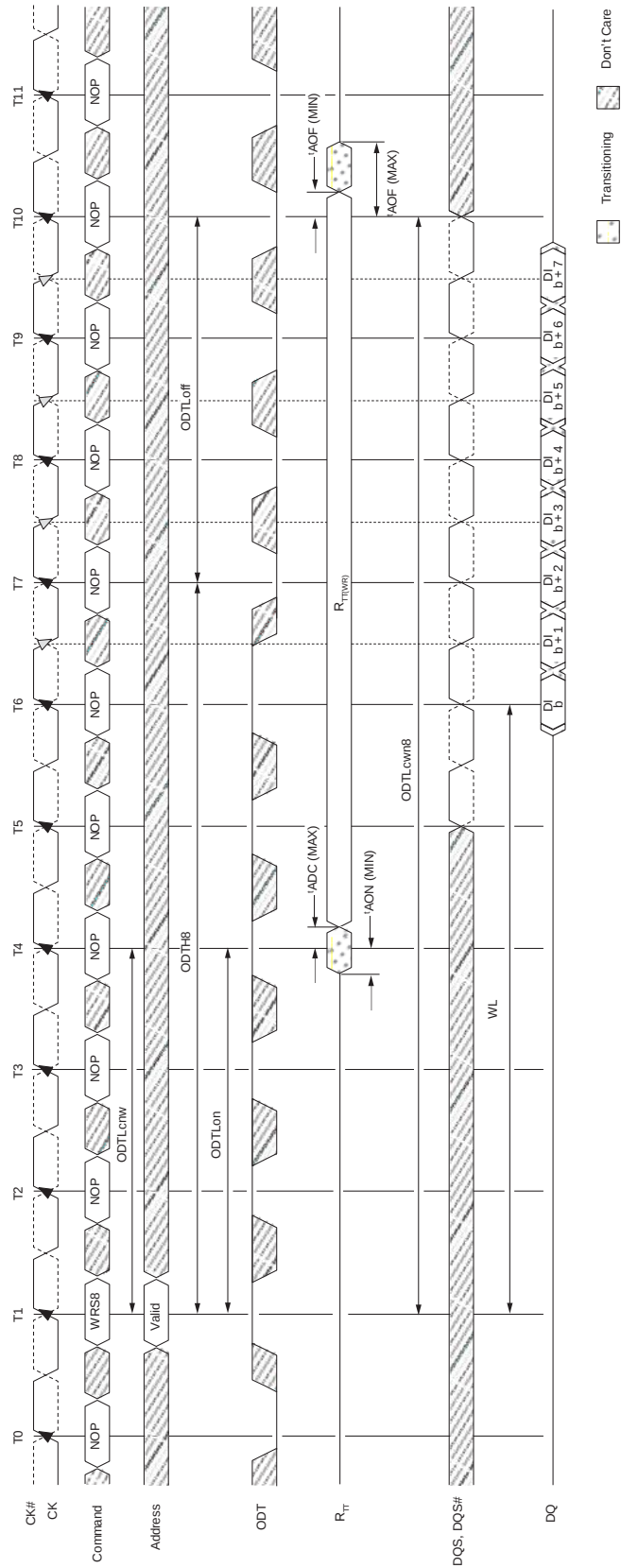
- Notes:
1. Via MRS or OTF. AL = 0, CWL = 5, RTT_{nom} and RTT(WR) are enabled.
 2. ODT44 applies to first registering ODT HIGH and then to the registration of the WRITE command. In this example, ODT44 is satisfied if ODT goes LOW at T8 (four clocks after the WRITE command).

Figure 99 : Dynamic ODT: Without WRITE Command



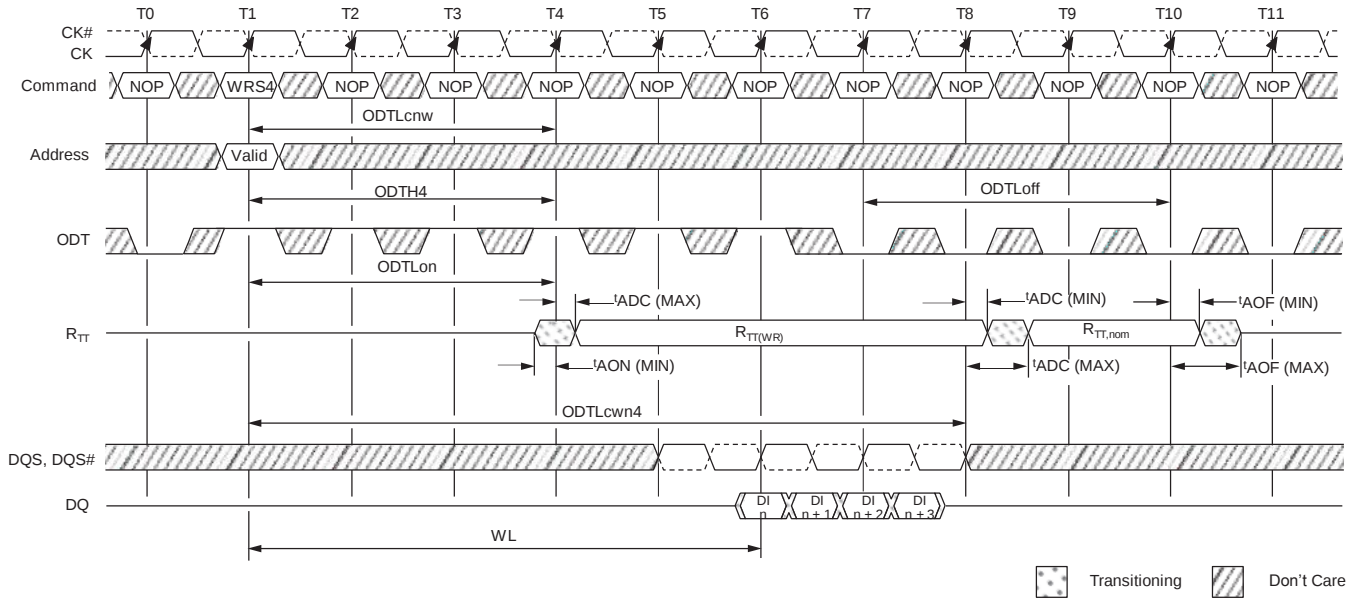
- Notes:
1. AL = 0, CWL = 5, RTT_{nom} is enabled and RTT(WR) is either enabled or disabled.
 2. ODT44 is defined from ODT registered HIGH to ODT registered LOW; in this example, ODT44 is satisfied. ODT registered LOW at T5 is also legal.

Figure 100 : Dynamic ODT: ODT Pin Asserted Together with WRITE Command for 6 Clock Cycles, BL8



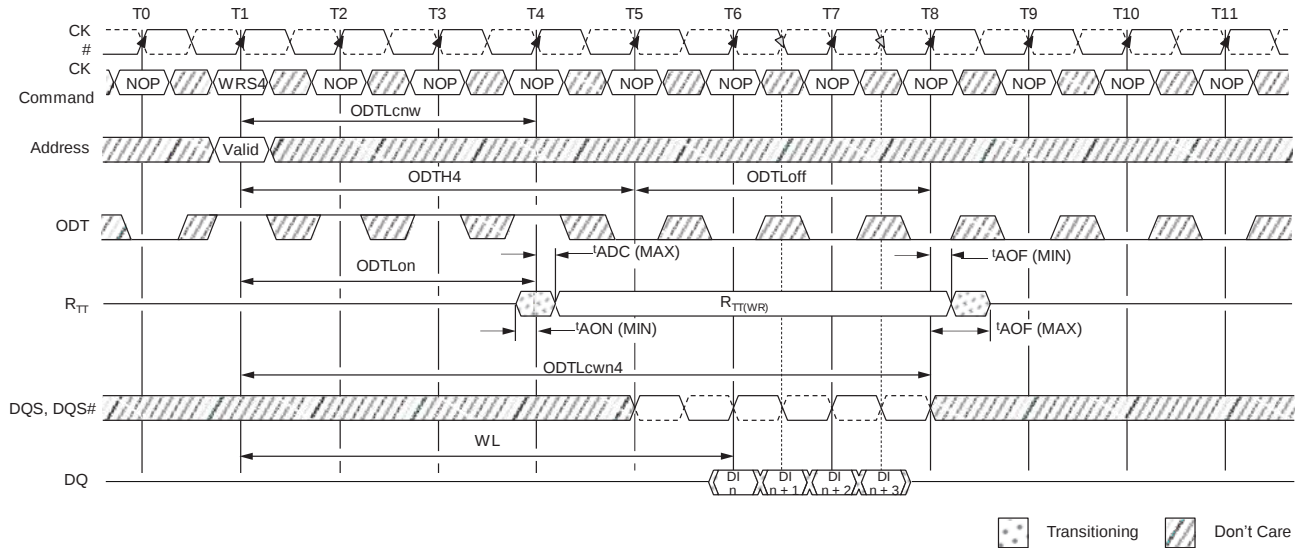
Notes: 1. Via MRS or OTF; AL = 0, CWL = 5. If RTT_{nom} can be either enabled or disabled, ODT can be HIGH. RTT(WR) is enabled.
2. In this example, ODT_{H8} = 6 is satisfied exactly.

Figure 101 : Dynamic ODT: ODT Pin Asserted with WRITE Command for 6 Clock Cycles, BC4



- Notes: 1. Via MRS or OTF. AL = 0, CWL = 5. RTT,nom and RTT(WR) are enabled.
 2. ODLH4 is defined from ODT registered HIGH to ODT registered LOW, so in this example, ODLH4 is satisfied. ODT registered LOW at T5 is also legal.

Figure 102 : Dynamic ODT: ODT Pin Asserted with WRITE Command for 4 Clock Cycles, BC4



- Notes: 1. Via MRS or OTF. AL = 0, CWL = 5. RTT,nom can be either enabled or disabled. If disabled, ODT can remain HIGH. RTT(WR) is enabled.
 2. In this example ODLH4 = 4 is satisfied exactly.

Synchronous ODT Mode

Synchronous ODT mode is selected whenever the DLL is turned on and locked and when either RTT,nom or RTT(WR) is enabled. Based on the power-down definition, these modes are:

- Any bank active with CKE HIGH
- Refresh mode with CKE HIGH
- Idle mode with CKE HIGH
- Active power-down mode (regardless of MR0[12])
- Precharge power-down mode if DLL is enabled by MR0[12] during precharge powerdown

ODT Latency and Posted ODT

In synchronous ODT mode, RTT turns on ODTLon clock cycles after ODT is sampled HIGH by a rising clock edge and turns off ODTLoff clock cycles after ODT is registered LOW by a rising clock edge. The actual on/off times varies by tAON and tAOF around each clock edge (see Table 82). The ODT latency is tied to the WRITE latency (WL) by $ODTLon = WL - 2$ and $ODTLoff = WL - 2$.

Since write latency is made up of CAS WRITE latency (CWL) and additive latency (AL), the AL programmed into the mode register (MR1[4, 3]) also applies to the ODT signal. The device's internal ODT signal is delayed a number of clock cycles defined by the AL relative to the external ODT signal. Thus, $ODTLon = CWL + AL - 2$ and $ODTLoff = CWL + AL - 2$.

Timing Parameters

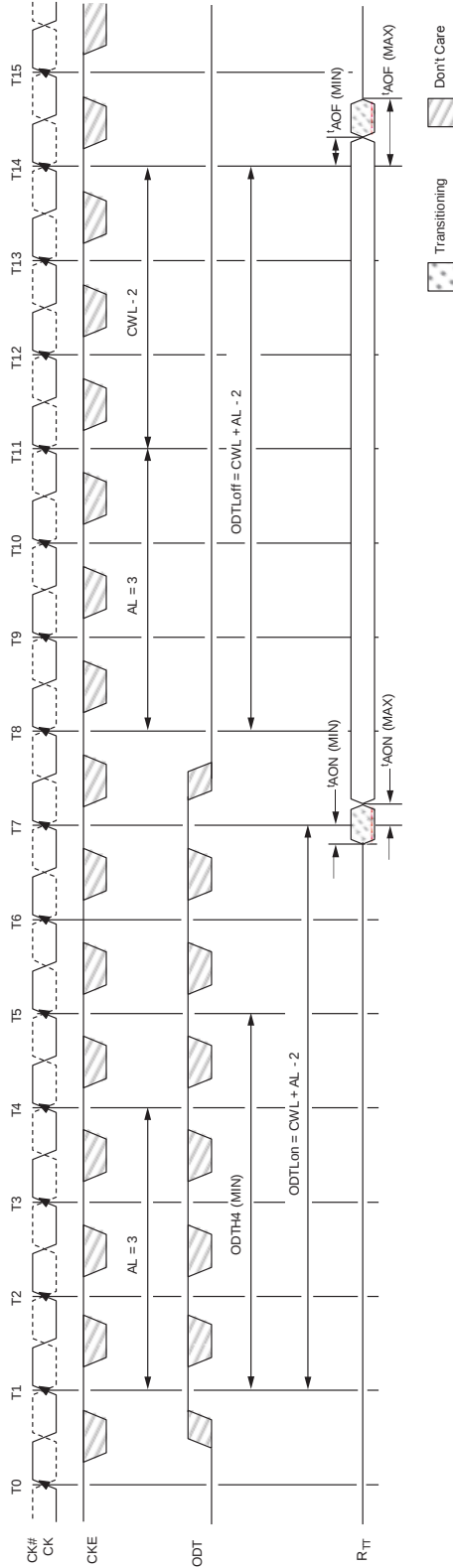
Synchronous ODT mode uses the following timing parameters: ODTLon, ODTLoff, ODTH4, ODTH8, tAON, and tAOF. The minimum RTT turn-on time (tAON [MIN]) is the point at which the device leaves High-Z and ODT resistance begins to turn on. Maximum RTT turn-on time (tAON [MAX]) is the point at which ODT resistance is fully on. Both are measured relative to ODTLon. The minimum RTT turn-off time (tAOF [MIN]) is the point at which the device starts to turn off ODT resistance. The maximum RTT turn off time (tAOF [MAX]) is the point at which ODT has reached High-Z. Both are measured from ODTLoff.

When ODT is asserted, it must remain HIGH until ODTH4 is satisfied. If a WRITE command is registered by the DRAM with ODT HIGH, then ODT must remain HIGH until ODTH4 (BC4) or ODTH8 (BL8) after the WRITE command (see Figure 104). ODTH4 and ODTH8 are measured from ODT registered HIGH to ODT registered LOW or from the registration of a WRITE command until ODT is registered LOW.

Table 82 : Synchronous ODT Parameters

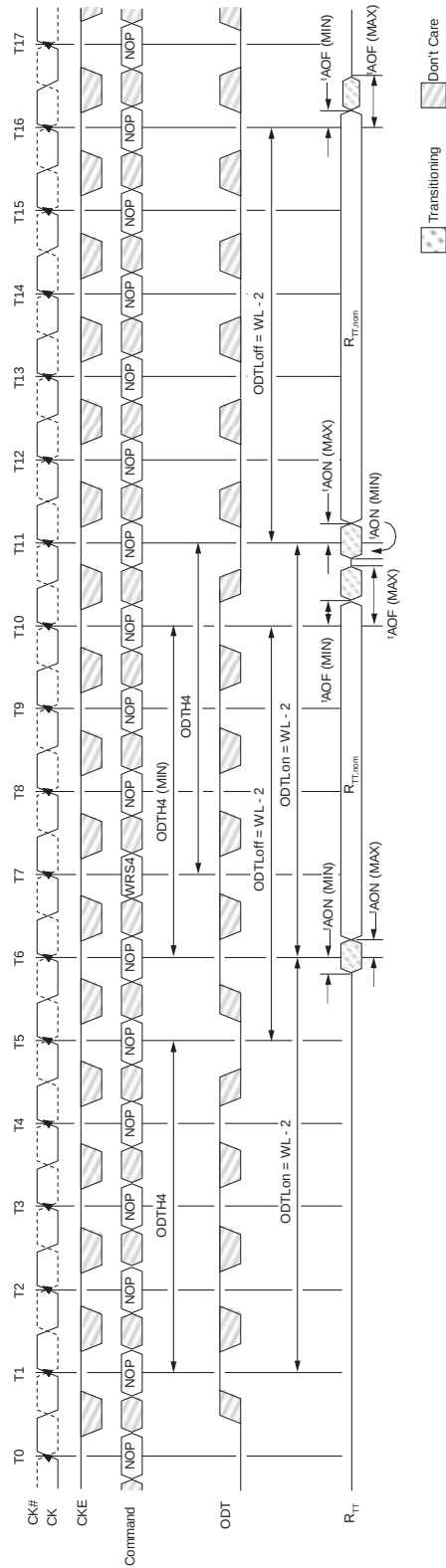
Symbol	Description	Begins at	Defined to	Definition for All DDR3L Speed Bins	Unit
ODTLon	ODT synchronous turn-on delay	ODT registered HIGH	$R_{TT(ON)} \pm t_{AON}$	$CWL + AL - 2$	t'CK
ODTLoff	ODT synchronous turn-off delay	ODT registered HIGH	$R_{TT(OFF)} \pm t_{AOF}$	$CWL + AL - 2$	t'CK
ODTH4	ODT minimum HIGH time after ODT assertion or WRITE (BC4)	ODT registered HIGH or write registration with ODT HIGH	ODT registered LOW	4t'CK	t'CK
ODTH8	ODT minimum HIGH time after WRITE (BL8)	Write registration with ODT HIGH	ODT registered LOW	6t'CK	t'CK
t'AON	ODT turn-on relative to ODTLon completion	Completion of ODTLon	$R_{TT(ON)}$	See Electrical Characteristics and AC Operating Conditions table	ps
t'AOF	ODT turn-off relative to ODTLoff completion	Completion of ODTLoff	$R_{TT(OFF)}$	$0.5t'CK \pm 0.2t'CK$	t'CK

Figure 103 : Synchronous ODT



Note: 1. AL = 3; CWL = 5; ODTLon = WL = 6.0; ODTLoff = WL - 2 = 6. R_{TT,nom} is enabled.

Figure 104 : Synchronous ODT (BC4)



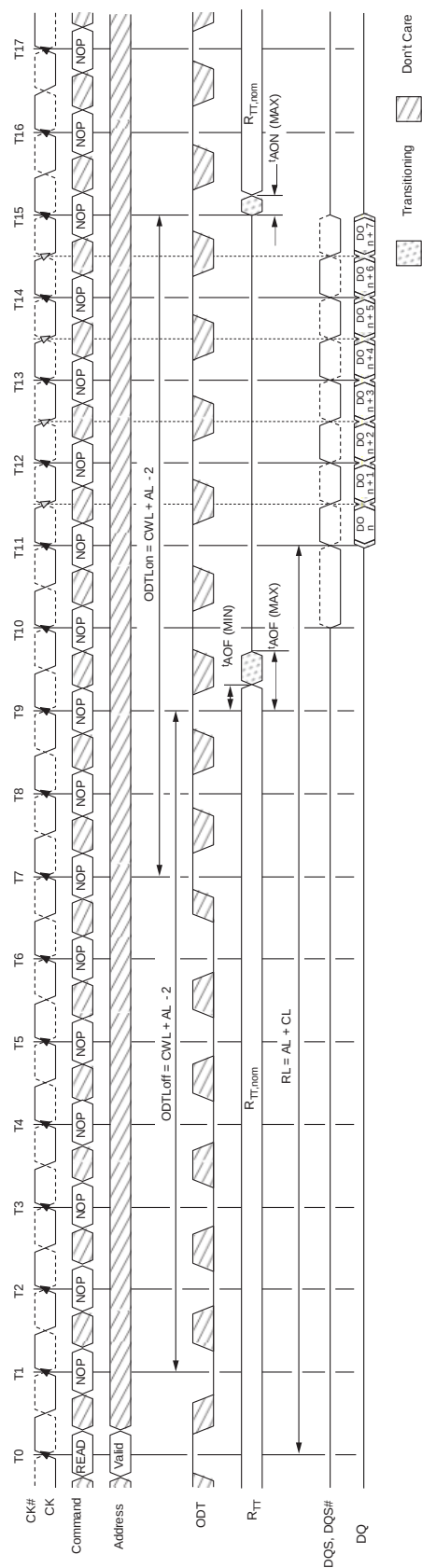
- Notes:
1. WL = 7. RTT_{nom} is enabled. RTT(WR) is disabled.
 2. ODT must be held HIGH for at least ODT_{H4} after assertion (T1).
 3. ODT must be kept HIGH ODT_{H4} (BC4) or ODT_{H8} (BL8) after the WRITE command (T7).
 4. ODT_H is measured from ODT first registered HIGH to ODT first registered LOW or from the registration of the WRITE command with ODT HIGH to ODT registered LOW.
 5. Although ODT_{H4} is satisfied from ODT registered HIGH at T6, ODT must not go LOW before T11 as ODT_{H4} must also be satisfied from the registration of the WRITE command at T7.

ODT Off During READs

Because the device cannot terminate and drive at the same time, RTT must be disabled at least one-half clock cycle before the READ preamble by driving the ODT ball LOW (if either RTT_{nom} or RTT(WR) is enabled). RTT may not be enabled until the end of the postamble, as shown in the following example.

Note : ODT may be disabled earlier and enabled later than shown in Figure 105.

Figure 105 : ODT During READs



Note: 1. ODT must be disabled externally during READs by driving ODT LOW. For example, $CL = 6$; $AL = CL - 1 = 5$; $RL = AL + CL = 11$; $CWL = 5$; $ODT_{Loff} = CWL + AL - 2 = 8$; $ODT_{Lon} = CWL + AL - 2 = 8$. $R_{TT, nom}$ is enabled. $R_{TT} (WR)$ is a "Don't Care."

Asynchronous ODT Mode

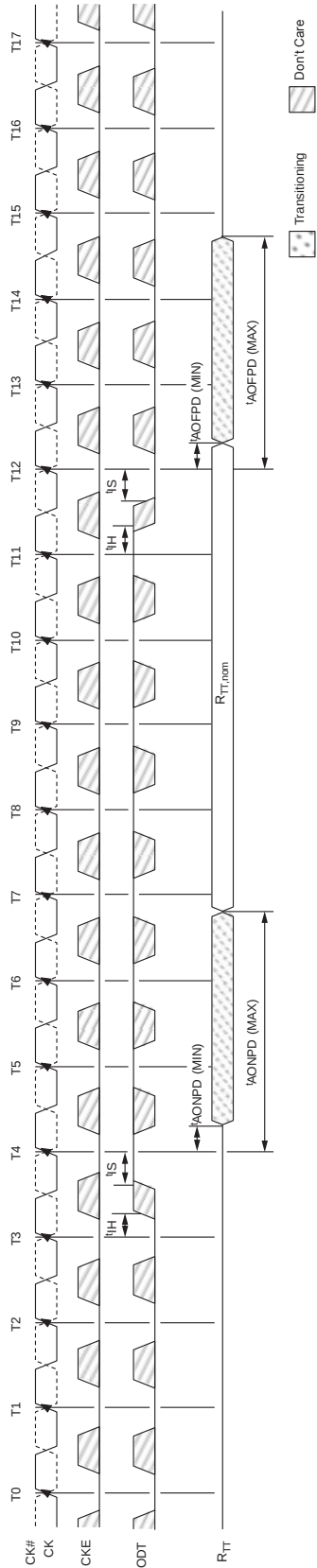
Asynchronous ODT mode is available when the DRAM runs in DLL on mode and when either $R_{TT,nom}$ or $R_{TT(WR)}$ is enabled; however, the DLL is temporarily turned off in pre-charged power-down standby (via MR0[12]). Additionally, ODT operates asynchronously when the DLL is synchronizing after being reset. See Power-Down Mode for definition and guidance over power-down details.

In asynchronous ODT timing mode, the internal ODT command is not delayed by AL relative to the external ODT command. In asynchronous ODT mode, ODT controls R_{TT} by analog time. The timing parameters t_{AONPD} and t_{AOFPD} replace $ODTLon/t_{AON}$ and $ODTLoft/t_{AOF}$, respectively, when ODT operates asynchronously.

The minimum R_{TT} turn-on time (t_{AONPD} [MIN]) is the point at which the device termination circuit leaves High-Z and ODT resistance begins to turn on. Maximum R_{TT} turn-on time (t_{AONPD} [MAX]) is the point at which ODT resistance is fully on. t_{AONPD} (MIN) and t_{AONPD} (MAX) are measured from ODT being sampled HIGH.

The minimum R_{TT} turn-off time (t_{AOFPD} [MIN]) is the point at which the device termination circuit starts to turn off ODT resistance. Maximum R_{TT} turn-off time (t_{AOFPD} [MAX]) is the point at which ODT has reached High-Z. t_{AOFPD} (MIN) and t_{AOFPD} (MAX) are measured from ODT being sampled LOW.

Figure 106 : Asynchronous ODT Timing with Fast ODT Transition



Note: 1. AL is ignored.

Table 83 : Asynchronous ODT Timing Parameters for All Speed Bins

Symbol	Description	Min	Max	Unit
tAONPD	Asynchronous R _{TT} turn-on delay (power-down with DLL off)	2	8.5	ns
tAOFPD	Asynchronous R _{TT} turn-off delay (power-down with DLL off)	2	8.5	ns

Synchronous to Asynchronous ODT Mode Transition (Power-Down Entry)

There is a transition period around power-down entry (PDE) where the DRAM's ODT may exhibit either synchronous or asynchronous behavior. This transition period occurs if the DLL is selected to be off when in precharge power-down mode by the setting MR0[12] = 0. Power-down entry begins tANPD prior to CKE first being registered LOW, and ends when CKE is first registered LOW. tANPD is equal to the greater of ODTLoff + 1tCK or ODTLon + 1tCK. If a REFRESH command has been issued, and it is in progress when CKE goes LOW, power-down entry ends tRFC after the REFRESH command, rather than when CKE is first registered LOW. Power-down entry then becomes the greater of tANPD and tRFC - REFRESH command to CKE registered LOW.

ODT assertion during power-down entry results in an RTT change as early as the lesser of tAONPD (MIN) and ODTLon × tCK + tAON (MIN), or as late as the greater of tAONPD (MAX) and ODTLon × tCK + tAON (MAX). ODT de-assertion during power-down entry can result in an RTT change as early as the lesser of tAOFPD (MIN) and ODTLoff × tCK + tAOF (MIN), or as late as the greater of tAOFPD (MAX) and ODTLoff × tCK + tAOF (MAX). Table 84 summarizes these parameters.

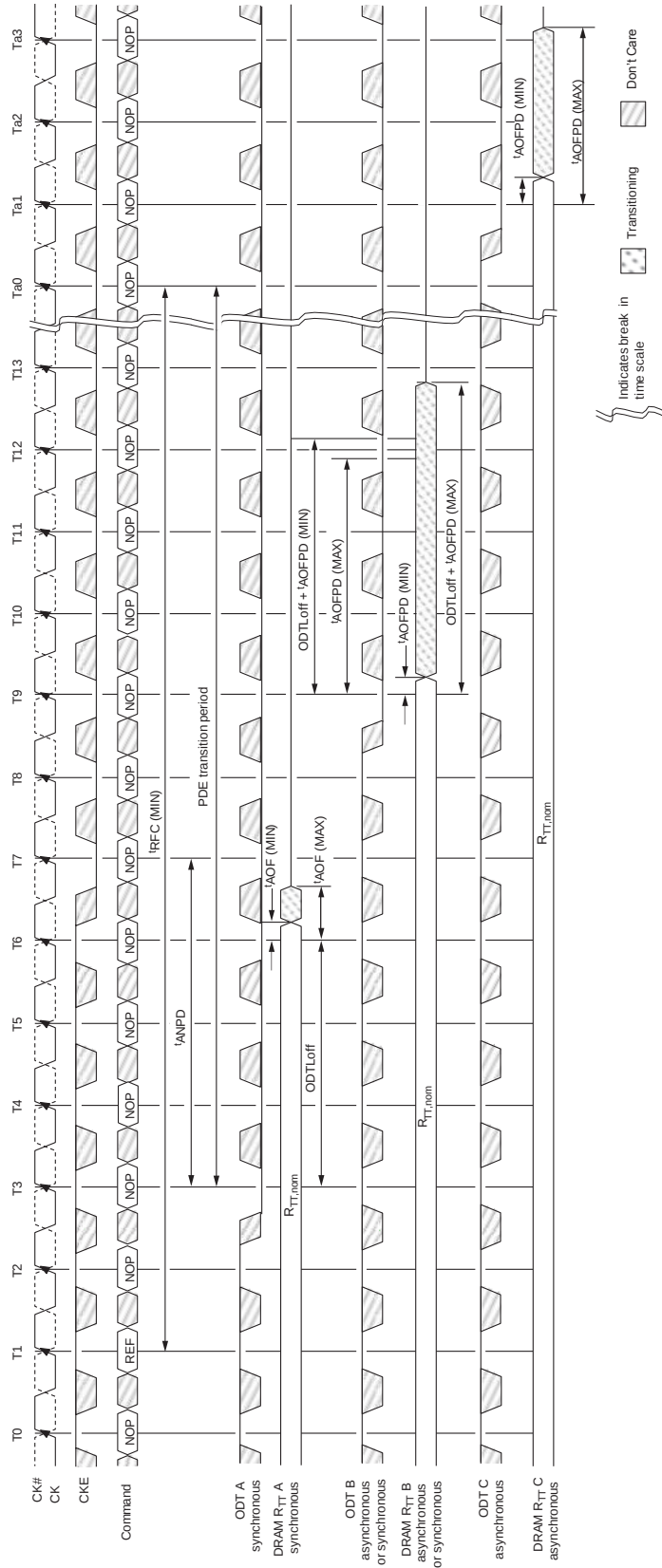
If AL has a large value, the uncertainty of the state of RTT becomes quite large. This is because ODTLon and ODTLoff are derived from the WL; and WL is equal to CWL + AL. Figure 107 shows three different cases:

- ODT_A: Synchronous behavior before tANPD.
- ODT_B: ODT state changes during the transition period with tAONPD (MIN) < ODTLon × tCK + tAON (MIN) and tAONPD (MAX) > ODTLon × tCK + tAON (MAX).
- ODT_C: ODT state changes after the transition period with asynchronous behavior.

Table 84 : ODT Parameters for Power-Down (DLL Off) Entry and Exit Transition Period

Description	Min	Max
Power-down entry transition period (power-down entry)	Greater of: t_{ANPD} or t_{RFC} - refresh to CKE LOW	
Power-down exit transition period (power-down exit)	$t_{ANPD} + t_{XPDLL}$	
ODT to R_{TT} turn-on delay ($ODT_{Lon} = WL - 2$)	Lesser of: t_{AONPD} (MIN) (2ns) or $ODT_{Lon} \times t_{CK} + t_{AON}$ (MIN)	Greater of: t_{AONPD} (MAX) (8.5ns) or $ODT_{Lon} \times t_{CK} + t_{AON}$ (MAX)
ODT to R_{TT} turn-off delay ($ODT_{Loff} = WL - 2$)	Lesser of: t_{AOFPD} (MIN) (2ns) or $ODT_{Loff} \times t_{CK} + t_{AOF}$ (MIN)	Greater of: t_{AOFPD} (MAX) (8.5ns) or $ODT_{Loff} \times t_{CK} + t_{AOF}$ (MAX)
t_{ANPD}	$WL - 1$ (greater of $ODT_{Loff} + 1$ or $ODT_{Lon} + 1$)	

Figure 107 : Synchronous to Asynchronous Transition During Precharge Power-Down (DLL Off) Entry



Note: 1. $AL = 0$; $CWL = 5$; $ODTL(off) = WL - 2 = 3$.

Asynchronous to Synchronous ODT Mode Transition (Power-Down Exit)

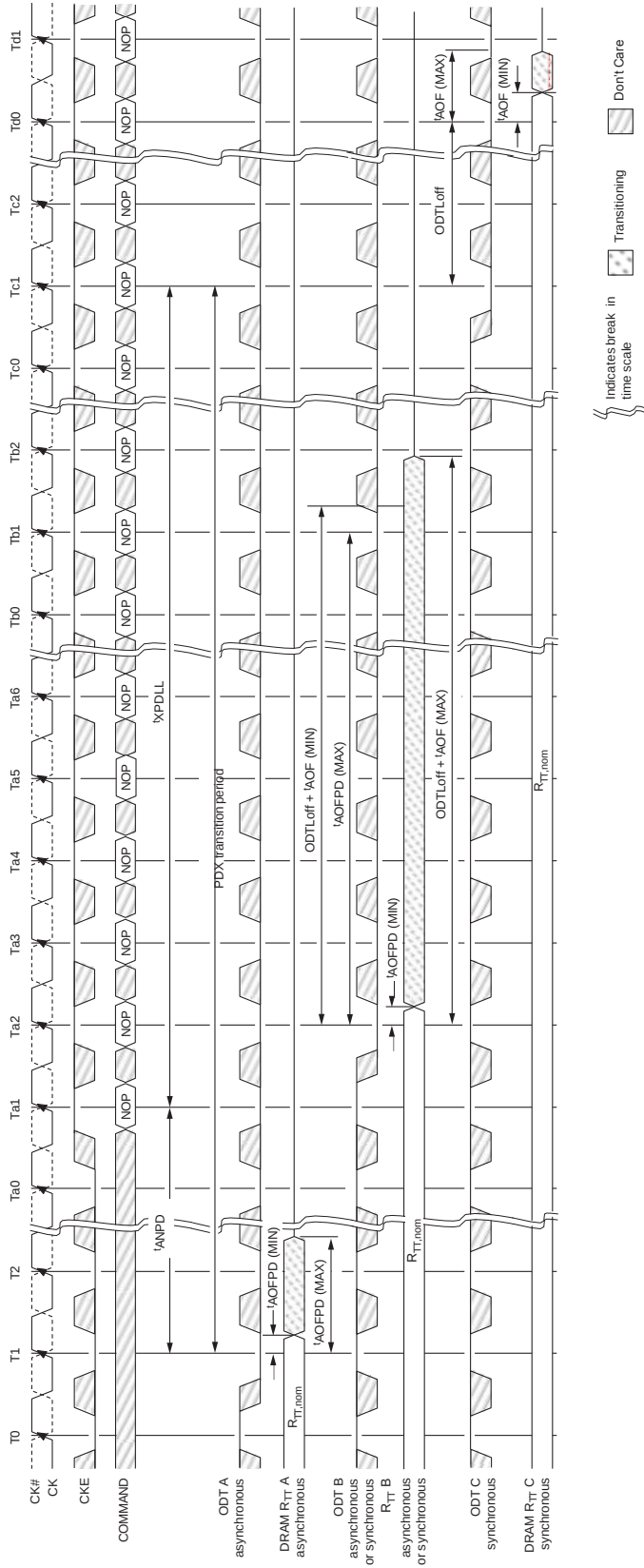
The DRAM's ODT can exhibit either asynchronous or synchronous behavior during power-down exit (PDX). This transition period occurs if the DLL is selected to be off when in precharge power-down mode by setting MR0[12] to 0. Power-down exit begins tANPD prior to CKE first being registered HIGH, and ends tXPDLL after CKE is first registered HIGH. tANPD is equal to the greater of ODTLoff + 1tCK or ODTLon + 1tCK. The transition period is tANPD + tXPDLL.

ODT assertion during power-down exit results in an RTT change as early as the lesser of tAONPD (MIN) and ODTLon × tCK + tAON (MIN), or as late as the greater of tAONPD (MAX) and ODTLon × tCK + tAON (MAX). ODT de-assertion during power-down exit may result in an RTT change as early as the lesser of tAOFPD (MIN) and ODTLoff × tCK + tAOF (MIN), or as late as the greater of tAOFPD (MAX) and ODTLoff × tCK + tAOF (MAX). Table 84 summarizes these parameters.

If AL has a large value, the uncertainty of the RTT state becomes quite large. This is because ODTLon and ODTLoff are derived from WL, and WL is equal to CWL + AL. Figure 108 shows three different cases :

- ODT C: Asynchronous behavior before tANPD.
- ODT B: ODT state changes during the transition period, with tAOFPD (MIN) < ODTLoff × tCK + tAOF (MIN), and ODTLoff × tCK + tAOF (MAX) > tAOFPD (MAX).
- ODT A: ODT state changes after the transition period with synchronous response.

Figure 108 : Asynchronous to Synchronous Transition During Precharge Power-Down (DLL Off) Exit



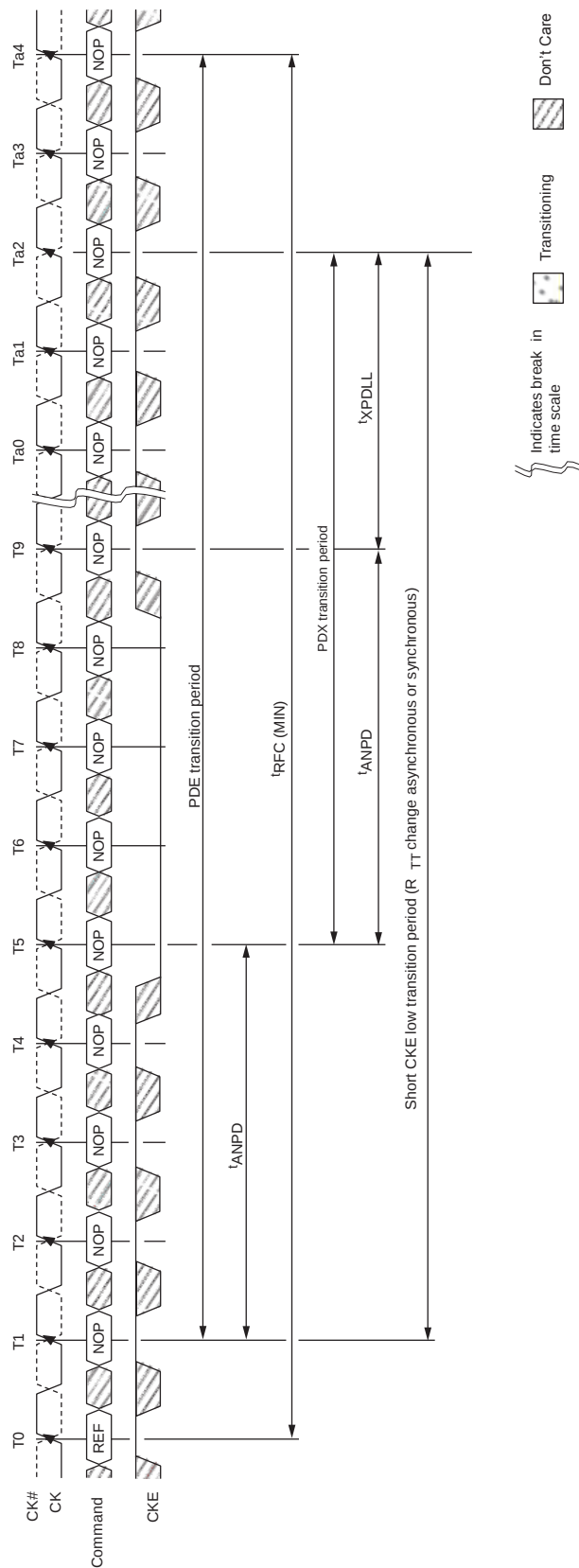
Note: 1. CL = 6; AL = CL - 1; CWL = 5; ODTLoff = WL - 2 = 8.

Asynchronous to Synchronous ODT Mode Transition (Short CKE Pulse)

If the time in the precharge power-down or idle states is very short (short CKE LOW pulse), the power-down entry and power-down exit transition periods overlap. When overlap occurs, the response of the DRAM's RTT to a change in the ODT state can be synchronous or asynchronous from the start of the power-down entry transition period to the end of the power-down exit transition period, even if the entry period ends later than the exit period.

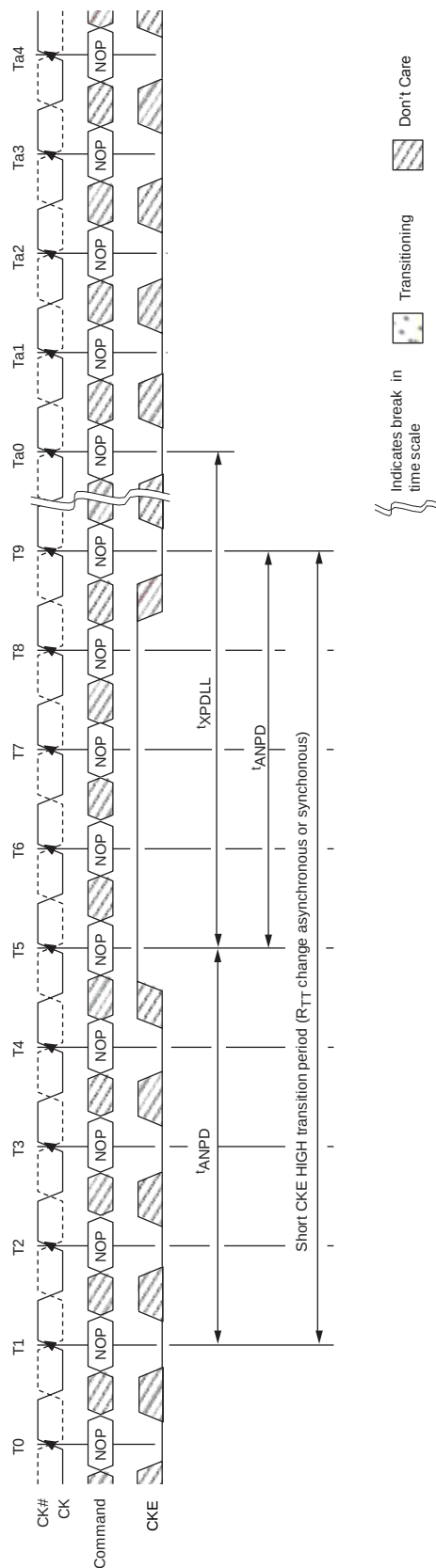
If the time in the idle state is very short (short CKE HIGH pulse), the power-down exit and power-down entry transition periods overlap. When this overlap occurs, the response of the DRAM's RTT to a change in the ODT state may be synchronous or asynchronous from the start of power-down exit transition period to the end of the powerdown entry transition period.

Figure 109 : Transition Period for Short CKE LOW Cycles with Entry and Exit Period Overlapping



Note: 1. AL = 0, WL = 5, tANPD = 4.

Figure 110 : Transition Period for Short CKE HIGH Cycles with Entry and Exit Period Overlapping



Note: 1. AL = 0, WL = 5, tANPD = 4.

Selection Guide

Part Number	VDD/VDDQ	I/O Width	Frequency	Data Rate	PKG TYPE
FM38D04SAA-5FGx	1.35V	X4	533Mhz	1066	78Ball FBGA
FM38D04SAA-6HGx	1.35V	X4	667Mhz	1333	78Ball FBGA
FM38D04SAA-8KGx	1.35V	X4	800Mhz	1600	78Ball FBGA
FM38D04SAA-9MGx	1.35V	X4	933Mhz	1866	78Ball FBGA
FM38D08SAA-5FGx	1.35V	X8	533Mhz	1066	78Ball FBGA
FM38D08SAA-6HGx	1.35V	X8	667Mhz	1333	78Ball FBGA
FM38D08SAA-8KGx	1.35V	X8	800Mhz	1600	78Ball FBGA
FM38D08SAA-9MGx	1.35V	X8	933Mhz	1866	78Ball FBGA
FM38D16SAB-5FGx	1.35V	X16	533Mhz	1066	96Ball FBGA
FM38D16SAB-6HGx	1.35V	X16	667Mhz	1333	96Ball FBGA
FM38D16SAB-8KGx	1.35V	X16	800Mhz	1600	96Ball FBGA
FM38D16SAB-9MGx	1.35V	X16	933Mhz	1866	96Ball FBGA

Part Numbering System

